

S3A7 Microcontroller Group

Datasheet

Renesas Synergy™ Platform

Synergy Microcontrollers

S3 Series

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High efficiency 48-MHz Arm® Cortex®-M4 microcontroller, up to 1-MB code flash memory, 192-KB SRAM, Segment LCD Controller, Capacitive Touch Sensing Unit, USB 2.0 Full-Speed Module, 14-bit A/D Converter, 12-bit D/A Converter, security and safety features

Features

■ Arm Cortex-M4 Core with Floating Point Unit (FPU)

- Armv7E-M architecture with DSP instruction set
- Maximum operating frequency: 48 MHz
- Support for 4-GB address space
- Arm Memory Protection Unit (Arm MPU) with 8 regions
- Debug and Trace: ITM, DWT, FPB, TPIU, ETB
- CoreSight™ Debug Port: JTAG-DP and SW-DP

■ Memory

- Up to 1-MB code flash memory
- 16-KB data flash memory (100,000 program/erase (P/E) cycles)
- Up to 192-KB SRAM
- Flash Cache (FCACHE)
- Memory Protection Unit (MPU)
- Memory Mirror Function (MMF)
- 128-bit unique ID

■ Connectivity

- USB 2.0 Full-Speed Module (USBFS)
 - On-chip transceiver with voltage regulator
 - Compliant with USB Battery Charging Specification 1.2
- Serial Communications Interface (SCI) × 6
 - UART
 - Simple IIC
 - Simple SPI
- Serial Peripheral Interface (SPI) × 2
- I²C bus interface (IIC) × 3
- Controller Area Network (CAN) module
- Serial Sound Interface (SSI) × 2
- SD/MMC Host Interface (SDHI)
- Quad Serial Peripheral Interface (QSPI)
- IrDA interface
- External address space
 - 8- or 16-bit bus space selectable per area

■ Analog

- 14-Bit A/D Converter (ADC14)
- 12-Bit D/A Converter (DAC12) × 2
- High-Speed Analog Comparator (ACMPHS) × 2
- Low-Power Analog Comparator (ACMPLP) × 2
- Operational Amplifier (OPAMP) × 4
- Temperature Sensor (TSN)

■ Timers

- General PWM Timer 32-bit (GPT32) × 10
- Asynchronous General-Purpose Timer (AGT) × 2
 - VBATT support
- Watchdog Timer (WDT)

■ Safety

- Error Correction Code (ECC) in SRAM
- SRAM parity error check
- Flash area protection
- ADC self-diagnosis function
- Clock Frequency Accuracy Measurement Circuit (CAC)
- Cyclic Redundancy Check (CRC) calculator
- Data Operation Circuit (DOC)
- Port Output Enable for GPT (POEG)
- Independent Watchdog Timer (IWDT)
- GPIO readback level detection
- Register write protection
- Main oscillator stop detection
- Illegal memory access

■ System and Power Management

- Low power modes
- Realtime Clock (RTC) with calendar and Battery Backup support
- Event Link Controller (ELC)
- DMA Controller (DMAC) × 4
- Data Transfer Controller (DTC)
- Key Interrupt Function (KINT)
- Power-on reset
- Low Voltage Detection (LVD) with voltage settings

■ Security and Encryption

- AES128/256
- GHASH
- True Random Number Generator (TRNG)

■ Human Machine Interface (HMI)

- Segment LCD Controller (SLCDC)
 - Up to 52 segments × 4 commons
 - Up to 48 segments × 8 commons
- Capacitive Touch Sensing Unit (CTSUS)

■ Multiple Clock Sources

- Main clock oscillator (MOSC)
 - (1 to 20 MHz when VCC = 2.4 to 5.5 V)
 - (1 to 8 MHz when VCC = 1.8 to 2.4 V)
 - (1 to 4 MHz when VCC = 1.6 to 1.8 V)
- Sub-clock oscillator (SOSC) (32.768 kHz)
- High-speed on-chip oscillator (HOCO)
 - (24, 32, 48, 64 MHz when VCC = 2.4 to 5.5 V)
 - (24, 32, 48 MHz when VCC = 1.8 to 5.5 V)
 - (24, 32 MHz when VCC = 1.6 to 5.5 V)
- Middle-speed on-chip oscillator (MOCO) (8 MHz)
- Low-speed on-chip oscillator (LOCO) (32.768 kHz)
- IWDT-dedicated on-chip oscillator (15 kHz)
- Clock trim function for HOCO/MOCO/LOCO
- Clock out support

■ General Purpose I/O Ports

- Up to 124 input/output pins
 - Up to 3 CMOS input
 - Up to 121 CMOS input/output
 - Up to 10 input/output 5-V tolerant
 - Up to 2 high current (20 mA)

■ Operating Voltage

- VCC: 1.6 to 5.5 V

■ Operating Temperature and Packages

- Ta = -40°C to +85°C
 - 145-pin LGA (7 mm × 7 mm, 0.5 mm pitch)
 - 121-pin BGA (8 mm × 8 mm, 0.65 mm pitch)
 - 100-pin LGA (7 mm × 7 mm, 0.65 mm pitch)
- Ta = -40°C to +105°C
 - 144-pin LQFP (20 mm × 20 mm, 0.5 mm pitch)
 - 100-pin LQFP (14 mm × 14 mm, 0.5 mm pitch)
 - 64-pin LQFP (10 mm × 10 mm, 0.5 mm pitch)
 - 64-pin QFN (8 mm × 8 mm, 0.4 mm pitch)

1. Overview

The MCU integrates multiple series of software- and pin-compatible Arm[®]-based 32-bit MCUs that share a common set of Renesas peripherals to facilitate design scalability and efficient platform-based product development.

The MCU provides an optimal combination of low power, high performance Arm Cortex[®]-M4 core running up to 48 MHz with the following features:

- Up to 1-MB code flash memory
- 192-KB SRAM
- Segment LCD Controller (SLCDC)
- Capacitive Touch Sensing Unit (CTSU)
- USB 2.0 Full-Speed Module (USBFS)
- 14-bit A/D Converter (ADC14)
- 12-bit D/A Converter (DAC12)
- Security features.

1.1 Function Outline

Table 1.1 Arm core

Feature	Functional description
Arm Cortex-M4	<ul style="list-style-type: none"> • Maximum operating frequency: up to 48 MHz • Arm Cortex-M4 <ul style="list-style-type: none"> - Revision: r0p1-01rel0 - Armv7E-M architecture profile - Single precision floating-point unit compliant with the ANSI/IEEE Std 754-2008. • Arm Memory Protection Unit (Arm MPU) <ul style="list-style-type: none"> - Armv7 Protected Memory System Architecture - 8 protected regions. • SysTick timer <ul style="list-style-type: none"> - Driven by SYSTICCLK (LOCO) or ICLK.

Table 1.2 Memory

Feature	Functional description
Code flash memory	Maximum 1-MB code flash memory. See section 48, Flash Memory in User's Manual.
Data flash memory	16-KB data flash memory. See section 48, Flash Memory in User's Manual.
Option-setting memory	The option-setting memory determines the state of the MCU after a reset. See section 7, Option-Setting Memory in User's Manual.
Memory Mirror Function (MMF)	The Memory Mirror Function (MMF) can be configured to mirror the desired application image load address in code flash memory to the application image link address in the 23-bit unused memory space (memory mirror space addresses). Your application code is developed and linked to run from this MMF destination address. The application code does not need to know the load location where it is stored in code flash memory. See section 5, Memory Mirror Function (MMF) in User's Manual.
SRAM	On-chip high-speed SRAM with either parity-bit or Error Correction Code (ECC). An area in SRAM0 provides error correction capability using ECC. See section 47, SRAM in User's Manual.

Table 1.3 System (1 of 2)

Feature	Functional description
Operating modes	Two operating modes: <ul style="list-style-type: none"> • Single-chip mode • SCI/USB boot mode. See section 3, Operating Modes in User's Manual.
Resets	14 resets: <ul style="list-style-type: none"> • RES pin reset • Power-on reset • VBATT-selected voltage power-on reset • Independent watchdog timer reset • Watchdog timer reset • Voltage monitor 0 reset • Voltage monitor 1 reset • Voltage monitor 2 reset • SRAM parity error reset • SRAM ECC error reset • Bus master MPU error reset • Bus slave MPU error reset • CPU stack pointer error reset • Software reset. See section 6, Resets in User's Manual.
Low Voltage Detection (LVD)	The Low Voltage Detection (LVD) function monitors the voltage level input to the VCC pin, and the detection level can be selected using a software program. See section 8, Low Voltage Detection (LVD) in User's Manual.
Clocks	<ul style="list-style-type: none"> • Main clock oscillator (MOSC) • Sub-clock oscillator (SOSC) • High-speed on-chip oscillator (HOCO) • Middle-speed on-chip oscillator (MOCO) • Low-speed on-chip oscillator (LOCO) • PLL frequency synthesizer • IWDT-dedicated on-chip oscillator • Clock out support. See section 9, Clock Generation Circuit in User's Manual.
Clock Frequency Accuracy Measurement Circuit (CAC)	The Clock Frequency Accuracy Measurement Circuit (CAC) counts pulses of the clock to be measured (measurement target clock) within the time generated by the clock to be used as a measurement reference (measurement reference clock), and determines the accuracy depending on whether the number of pulses is within the allowable range. When measurement is complete or the number of pulses within the time generated by the measurement reference clock is not within the allowable range, an interrupt request is generated. See section 10, Clock Frequency Accuracy Measurement Circuit (CAC) in User's Manual.
Interrupt Controller Unit (ICU)	The Interrupt Controller Unit (ICU) controls which event signals are linked to the NVIC/DTC module and DMAC module. The ICU also controls NMI interrupts. See section 14, Interrupt Controller Unit (ICU) in User's Manual.
Key Interrupt Function (KINT)	A key interrupt can be generated by setting the Key Return Mode Register (KRM) and inputting a rising or falling edge to the key interrupt input pins. See section 21, Key Interrupt Function (KINT) in User's Manual.
Low power modes	Power consumption can be reduced in multiple ways, such as by setting clock dividers, controlling EBCLK output, stopping modules, selecting power control mode in normal operation, and transitioning to low power modes. See section 11, Low Power Modes in User's Manual.
Battery backup function	A battery backup function is provided for partial powering by a battery. The battery-powered area includes RTC, AGT, SOSC, LOCO, Wakeup Control, Backup Memory, VBATT_R Low Voltage Detection, and switches between VCC and VBATT. During normal operation, the battery powered area is powered by the main power supply, the VCC pin. When a VCC voltage drop is detected, the power source is switched to the dedicated battery backup power pin, the VBATT pin. When the voltage rises again, the power source is switched from the VBATT pin to the VCC pin. See section 12, Battery Backup Function in User's Manual.
Register write protection	The register write protection function protects important registers from being overwritten due to software errors. See section 13, Register Write Protection in User's Manual.

Table 1.3 System (2 of 2)

Feature	Functional description
Memory Protection Unit (MPU)	Four MPUs and a CPU stack pointer monitor function are provided for memory protection. See section 16, Memory Protection Unit (MPU) in User's Manual.
Watchdog Timer (WDT)	The WDT is a 14-bit down-counter. It can be used to reset the MCU when the counter underflows because the system has run out of control and is unable to refresh the WDT. In addition, a non-maskable interrupt or interrupt can be generated by an underflow. A refresh-permitted period can be set to refresh the counter and be used as the condition for detecting when the system runs out of control. See section 26, Watchdog Timer (WDT) in User's Manual.
Independent Watchdog Timer (IWDT)	The IWDT consists of a 14-bit down-counter that must be serviced periodically to prevent counter underflow. The IWDT provides functionality to reset the MCU or to generate a non-maskable interrupt/interrupt for a timer underflow. Because the timer operates with an independent, dedicated clock source, it is particularly useful in returning the MCU to a known state as a fail safe mechanism when the system runs out of control. The IWDT can be triggered automatically on a reset, underflow, or refresh error, or by a refresh of the count value in the registers. See section 27, Independent Watchdog Timer (IWDT) in User's Manual.

Table 1.4 Event link

Feature	Functional description
Event Link Controller (ELC)	The ELC uses the interrupt requests generated by various peripheral modules as event signals to connect them to different modules, enabling direct interaction between the modules without CPU intervention. See section 19, Event Link Controller (ELC) in User's Manual.

Table 1.5 Direct memory access

Feature	Functional description
Data Transfer Controller (DTC)	A DTC module is provided for transferring data when activated by an interrupt request. See section 18, Data Transfer Controller (DTC) in User's Manual.
DMA Controller (DMAC)	A 4-channel DMAC module is provided for transferring data without the CPU. When a DMA transfer request is generated, the DMAC transfers data stored at the transfer source address to the transfer destination address. See section 17, DMA Controller (DMAC) in User's Manual.

Table 1.6 External bus interface

Feature	Functional description
External bus	<ul style="list-style-type: none"> • CS area: Connected to the external devices (external memory interface) • QSPI area: Connected to the QSPI (external device interface).

Table 1.7 Timers

Feature	Functional description
General PWM Timer (GPT)	The GPT is a 32-bit timer with 10 channels. PWM waveforms can be generated by controlling the up-counter, down-counter, or the up- and down-counter. In addition, PWM waveforms can be generated for controlling brushless DC motors. The GPT can also be used as a general-purpose timer. See section 23, General PWM Timer (GPT) in User's Manual.
Port Output Enable for GPT (POEG)	Use the POEG function to place the General PWM Timer (GPT) output pins in the output disable state. See section 22, Port Output Enable for GPT (POEG) in User's Manual.
Asynchronous General Purpose Timer (AGT)	The AGT is a 16-bit timer that can be used for pulse output, external pulse width or period measurement, and counting of external events. This 16-bit timer consists of a reload register and a down-counter. The reload register and the down-counter are allocated to the same address, and they can be accessed with the AGT register. See section 24, Asynchronous General Purpose Timer (AGT) in User's Manual.
Realtime Clock (RTC)	The RTC has two counting modes, calendar count mode and binary count mode, that are controlled by the register settings. For calendar count mode, the RTC has a 100-year calendar from 2000 to 2099 and automatically adjusts dates for leap years. For binary count mode, the RTC counts seconds and retains the information as a serial value. Binary count mode can be used for calendars other than the Gregorian (Western) calendar. See section 25, Realtime Clock (RTC) in User's Manual.

Table 1.8 Communication interfaces (1 of 2)

Feature	Functional description
Serial Communications Interface (SCI)	The SCI is configurable to five asynchronous and synchronous serial interfaces: <ul style="list-style-type: none"> • Asynchronous interfaces (UART and asynchronous communications interface adapter (ACIA)) • 8-bit clock synchronous interface • Simple IIC (master-only) • Simple SPI • Smart card interface. The smart card interface complies with the ISO/IEC 7816-3 standard for electronic signals and transmission protocol. Each SCI has FIFO buffers to enable continuous and full-duplex communication, and the data transfer speed can be configured individually using an on-chip baud rate generator. See section 29, Serial Communications Interface (SCI) in User's Manual.
IrDA Interface (IrDA)	The IrDA interface sends and receives IrDA data communication waveforms in cooperation with the SCI1 based on the IrDA (Infrared Data Association) standard 1.0. See section 30, IrDA Interface in User's Manual.
I ² C Bus Interface (IIC)	The 3-channel IIC module conforms with and provides a subset of the NXP I ² C bus (Inter-Integrated Circuit bus) interface functions. See section 31, I2C Bus Interface (IIC) in User's Manual.
Serial Peripheral Interface (SPI)	Two independent SPI channels are capable of high-speed, full-duplex synchronous serial communications with multiple processors and peripheral devices. See section 33, Serial Peripheral Interface (SPI) in User's Manual.
Serial Sound Interface (SSI)	The SSI peripheral provides functionality to interface with digital audio devices for transmitting PCM audio data over a serial bus with the MCU. The SSI supports an audio clock frequency of up to 50 MHz, and can be operated as a slave or master receiver, transmitter, or transceiver to suit various applications. The SSI includes 8-stage FIFO buffers in the receiver and transmitter, and supports interrupts and DMA-driven data reception and transmission. See section 36, Serial Sound Interface (SSI) in User's Manual.
Quad Serial Peripheral Interface (QSPI)	The QSPI is a memory controller for connecting a serial ROM (nonvolatile memory such as a serial flash memory, serial EEPROM, or serial FeRAM) that has an SPI-compatible interface. See section 34, Quad Serial Peripheral Interface (QSPI) in User's Manual.
Controller Area Network (CAN) Module	The CAN module provides functionality to receive and transmit data using a message-based protocol between multiple slaves and masters in electromagnetically noisy applications. The CAN module complies with the ISO 11898-1 (CAN 2.0A/CAN 2.0B) standard and supports up to 32 mailboxes, which can be configured for transmission or reception in normal mailbox and FIFO modes. Both standard (11-bit) and extended (29-bit) messaging formats are supported. See section 32, Controller Area Network (CAN) Module in User's Manual.

Table 1.8 Communication interfaces (2 of 2)

Feature	Functional description
USB 2.0 Full-Speed Module (USBFS)	<p>The full-speed USB controller can operate as a host controller or device controller. The module supports full-speed and low-speed (host controller only) transfer as defined in the Universal Serial Bus Specification 2.0. The module has an internal USB transceiver and supports all of the transfer types defined in the Universal Serial Bus Specification 2.0. The USB has buffer memory for data transfer, providing a maximum of 10 pipes. Pipes 1 to 9 can be assigned any endpoint number based on the peripheral devices used for communication or based on the user system.</p> <p>The MCU supports revision 1.2 of the battery charging specification. Because the MCU can be powered at 5 V, the USB LDO regulator provides the internal USB transceiver power supply 3.3 V. See section 28, USB 2.0 Full-Speed Module (USBFS) in User's Manual.</p>
SD/MMC Host Interface (SDHI)	<p>The SDHI provides the functionality needed to connect a variety of external memory cards to the MCU. The SDHI supports both 1-bit and 4-bit buses for connecting memory cards that support SD, SDHC, and SDXC formats. When developing host devices that are compliant with the SD specifications, you must comply with the SD Host/Ancillary Product License Agreement (SD HALA).</p> <p>The MMC interface supports 1-bit, 4-bit, and 8-bit MMC buses that provide eMMC 4.51 (JEDEC Standard JESD 84-B451) device access. This interface also provides backward compatibility and supports high-speed SDR transfer modes. See section 37, SD/MMC Host Interface (SDHI) in User's Manual.</p>

Table 1.9 Analog

Feature	Functional description
14-bit A/D Converter (ADC14)	A 14-bit successive approximation A/D converter is provided. Up to 28 analog input channels are selectable. Temperature sensor output and internal reference voltage are selectable for conversion. The A/D conversion accuracy is selectable from 12-bit and 14-bit conversion making it possible to optimize the tradeoff between speed and resolution in generating a digital value. See section 39, 14-Bit A/D Converter (ADC14) in User's Manual.
12-bit D/A Converter (DAC12)	The 12-bit D/A converts data and includes an output amplifier. See section 40, 12-Bit D/A Converter (DAC12) in User's Manual.
Temperature Sensor (TSN)	The on-chip temperature sensor determines and monitors the die temperature for reliable operation of the device. The sensor outputs a voltage directly proportional to the die temperature, and the relationship between the die temperature and the output voltage is linear. The output voltage is provided to the ADC14 for conversion and can be further used by the end application. See section 41, Temperature Sensor (TSN) in User's Manual.
High-Speed Analog Comparator (ACMPHS)	ACMPHS compares the test voltage with a reference voltage and to provide a digital output based on the result of conversion. Both the test and reference voltages can be provided to the comparator from internal sources such as the DAC12 output and internal reference voltage, and an external source. Such flexibility is useful in applications that require go/no-go comparisons to be performed between analog signals without necessarily requiring A/D conversion. See section 43, High-Speed Analog Comparator (ACMPHS) in User's Manual.
Low-Power Analog Comparator (ACMPLP)	ACMPLP compares a reference input voltage and analog input voltage. The comparison result can be read by software and also be output externally. The reference input voltage can be selected from either an input to the CMPREFi (i = 0, 1) pin or from the internal reference voltage (Vref) generated internally in the MCU. The ACMPLP response speed can be set before starting an operation. Setting the high-speed mode decreases the response delay time, but increases current consumption. Setting the low-speed mode increases the response delay time, but decreases current consumption. See section 44, Low Power Analog Comparator (ACMPLP) in User's Manual.
Operational Amplifier (OPAMP)	OPAMP amplifies small analog input voltages and outputs the amplified voltages. A total of four differential operational amplifier units with two input pins and one output pin are provided. See section 42, Operational Amplifier (OPAMP) in User's Manual.

Table 1.10 Human machine interfaces

Feature	Functional description
Segment LCD Controller (SLCDC)	<p>The SLCDC provides the following functions:</p> <ul style="list-style-type: none"> • Waveform A or B selectable • The LCD driver voltage generator can switch between an internal voltage boosting method, a capacitor split method, and an external resistance division method • Automatic output of segment and common signals based on automatic display data register read • The reference voltage generated when operating the voltage boost circuit can be selected in 16 steps (contrast adjustment) • The LCD can be made to blink. <p>See section 49, Segment LCD Controller/Driver (SLCDC) in User's Manual.</p>
Capacitive Touch Sensing Unit (CTSU)	<p>The Capacitive Touch Sensing Unit (CTSU) measures the electrostatic capacitance of the touch sensor. Changes in the electrostatic capacitance are determined by software, which enables the CTSU to detect whether a finger is in contact with the touch sensor. The electrode surface of the touch sensor is usually enclosed with an electrical insulator so that a finger does not come into direct contact with the electrodes. See section 45, Capacitive Touch Sensing Unit (CTSU) in User's Manual.</p>

Table 1.11 Data processing

Feature	Functional description
Cyclic Redundancy Check (CRC) Calculator	<p>The CRC calculator generates CRC codes to detect errors in the data. The bit order of CRC calculation results can be switched for LSB-first or MSB-first communication. Additionally, various CRC generation polynomials are available. The snoop function allows monitoring reads from and writes to specific addresses. This function is useful in applications that require CRC code to be generated automatically in certain events, such as monitoring writes to the serial transmit buffer and reads from the serial receive buffer. See section 35, Cyclic Redundancy Check (CRC) Calculator in User's Manual.</p>
Data Operation Circuit (DOC)	<p>The Data Operation Circuit (DOC) compares, adds, and subtracts 16-bit data. See section 46, Data Operation Circuit (DOC) in User's Manual.</p>

Table 1.12 Security

Feature	Functional description
Secure Crypto Engine 5 (SCE5)	<ul style="list-style-type: none"> • Security algorithm: <ul style="list-style-type: none"> - Symmetric algorithm: AES. • Other support features: <ul style="list-style-type: none"> - TRNG (True Random Number Generator) - Hash-value generation: GHASH.

1.2 Block Diagram

Figure 1.1 shows the block diagram of the MCU superset. Some individual devices within the group have a subset of the features.

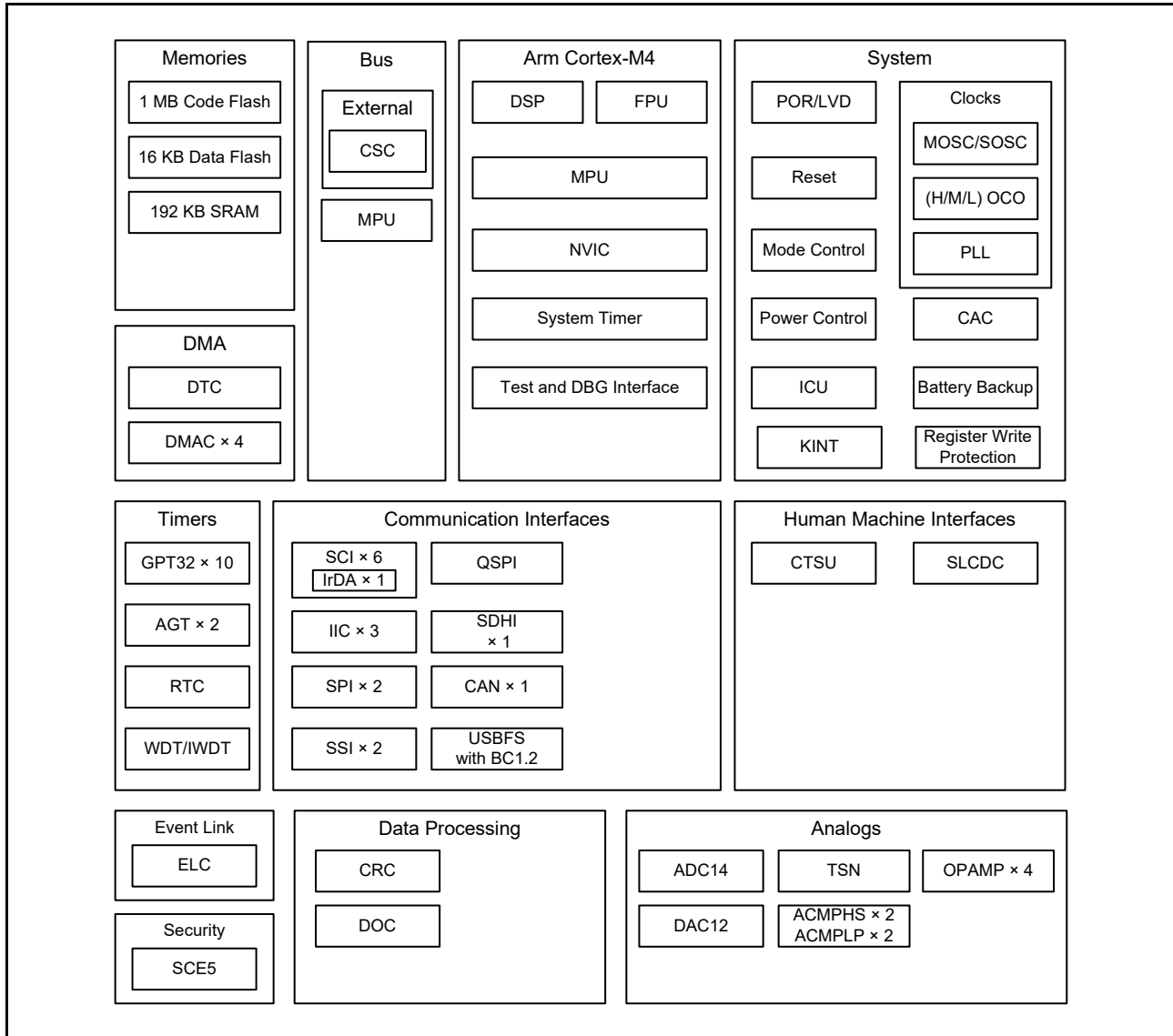


Figure 1.1 Block diagram

1.3 Part Numbering

Figure 1.2 shows the product part number information, including memory capacity, and package type. Table 1.13 shows a product list.

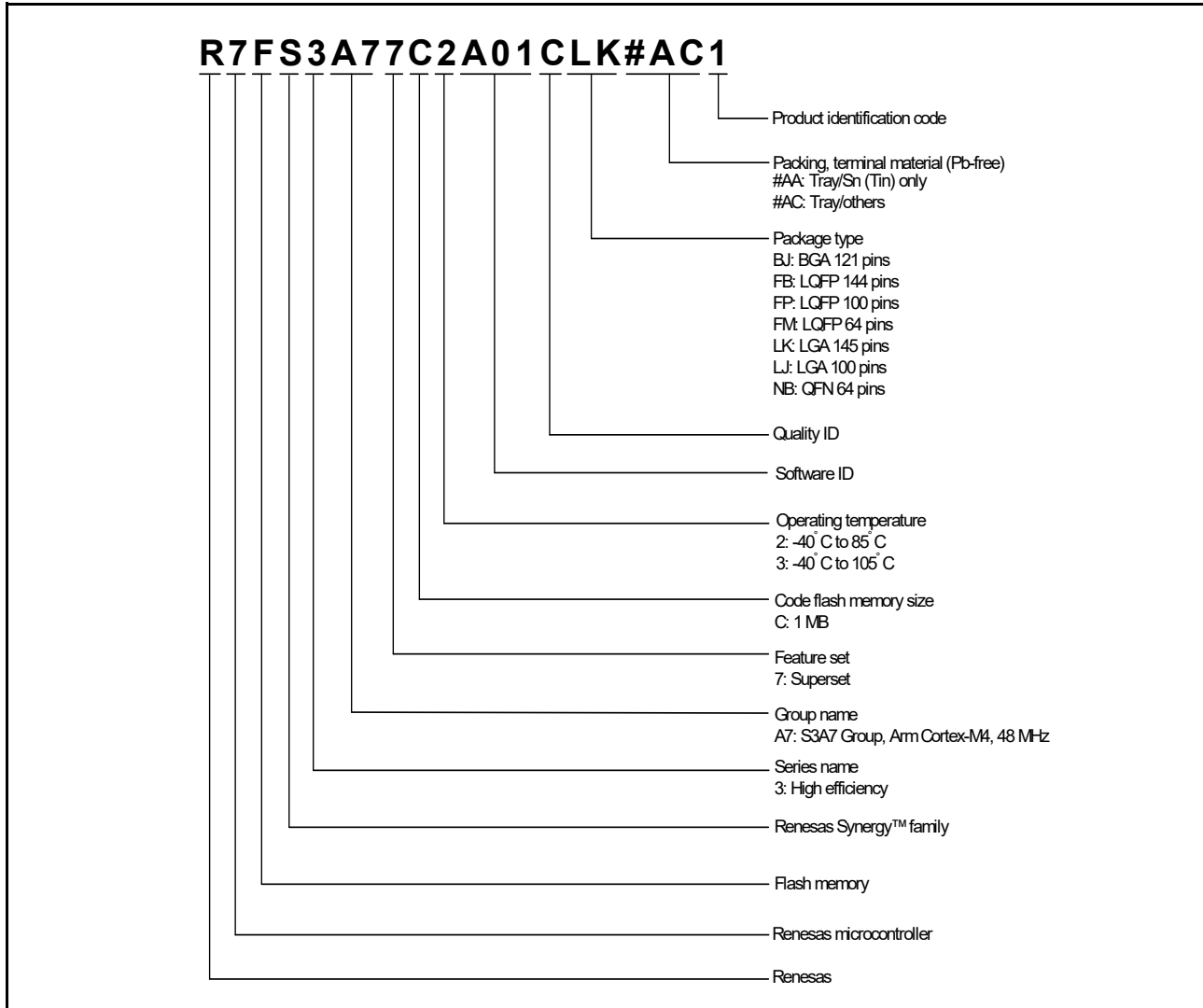


Figure 1.2 Part numbering scheme

Table 1.13 Product list

Part number	Ordering part number	Package	Code flash	Data flash	SRAM	Operating temperature
R7FS3A77C2A01CLK	R7FS3A77C2A01CLK#AC1	PTLG0145KA-A	1 MB	16 KB	192 KB	-40 to +85°C
R7FS3A77C3A01CFB	R7FS3A77C3A01CFB#AA1	PLQP0144KA-B	1 MB	16 KB	192 KB	-40 to +105°C
R7FS3A77C2A01CBJ	R7FS3A77C2A01CBJ#AC1	PLBG0121JA-A	1 MB	16 KB	192 KB	-40 to +85°C
R7FS3A77C3A01CFP	R7FS3A77C3A01CFP#AA1	PLQP0100KB-B	1 MB	16 KB	192 KB	-40 to +105°C
R7FS3A77C2A01CLJ	R7FS3A77C2A01CLJ#AC1	PTLG0100JA-A	1 MB	16 KB	192 KB	-40 to +85°C
R7FS3A77C3A01CFM	R7FS3A77C3A01CFM#AA1	PLQP0064KB-C	1 MB	16 KB	192 KB	-40 to +105°C
R7FS3A77C3A01CNB	R7FS3A77C3A01CNB#AC1	PWQN0064LA-A	1 MB	16 KB	192 KB	-40 to +105°C

1.4 Function Comparison

Table 1.14 Function comparison

Parts number	R7FS3A77C2A01CLK	R7FS3A77C3A01CFB	R7FS3A77C2A01CBJ	R7FS3A77C3A01CFP	R7FS3A77C2A01CLJ	R7FS3A77C3A01CFM R7FS3A77C3A01CNB	
Pin count	145	144	121	100	100	64	
Package	LGA	LQFP	BGA	LQFP	LGA	LQFP/QFN	
Code flash memory	1 MB						
Data flash memory	16 KB						
SRAM	192 KB						
	Parity	176 KB					
	ECC	16 KB					
System	CPU clock	48 MHz					
	Backup registers	512 bytes					
	ICU	Yes					
	KINT	8					
Event control	ELC	Yes					
DMA	DTC	Yes					
	DMAC	4					
BUS	External bus	16-bit bus		8-bit bus		No	
Timers	GPT32	10	10	10	10	10	9
	AGT	2	2	2	2	2	2
	RTC	Yes					
	WDT/IWDT	Yes					
Communication	SCI	6					
	IIC	3		2			
	SPI	2					
	SSI	2					1
	QSPI	1					No
	SDHI	1					No
	CAN	1					
	USBFS	Yes					
Analog	ADC14	28		26	25	25	18
	DAC12	2					
	ACMPHS	2					
	ACMPLP	2					
	OPAMP	4	4	4	4	4	3
	TSN	Yes					
HMI	SLCDC	4 com × 52 seg or 8 com × 48 seg		4 com × 38 seg or 8 com × 34 seg	4 com × 26 seg or 8 com × 22 seg	4 com × 26 seg or 8 com × 22 seg	No
	CTSU	31			26		14
Data processing	CRC	Yes					
	DOC	Yes					
Security	SCE5						

1.5 Pin Functions

Function	Signal	I/O	Description
Power supply	VCC	Input	Power supply pin. Connect to the system power supply. Connect this pin to VSS through a 0.1- μ F capacitor. Place the capacitor close to the pin.
	VCL	Input	Connect this pin to the VSS pin through the smoothing capacitor used to stabilize the internal power supply. Place the capacitor close to the pin.
	VSS	Input	Ground pin. Connect it to the system power supply (0 V).
	VBATT	Input	Backup power supply pin
Clock	XTAL	Output	Pins for a crystal resonator. An external clock signal can be input through the EXTAL pin.
	EXTAL	Input	
	XCIN	Input	Input/output pins for the sub-clock oscillator. Connect a crystal resonator between XCOU and XCIN.
	XCOU	Output	
	EBCLK	Output	Outputs the external bus clock for external devices
	CLKOUT	Output	Clock output pin
Operating mode control	MD	Input	Pin for setting the operating mode. The signal level on this pin must not be changed during operation mode transition on release from the reset state.
System control	RES	Input	Reset signal input pin. The MCU enters the reset state when this signal goes low.
CAC	CACREF	Input	Measurement reference clock input pin
Interrupt	NMI	Input	Non-maskable interrupt request pin
	IRQ0 to IRQ15	Input	Maskable interrupt request pins
KINT	KR00 to KR07	Input	A key interrupt (KINT) can be generated by inputting a falling edge to the key interrupt input pins
On-chip debug	TMS	I/O	On-chip emulator or boundary scan pins
	TDI	Input	
	TCK	Input	
	TDO	Output	
	SWDIO	I/O	Serial wire debug data Input/output pin
	SWCLK	Input	Serial wire clock pin
	SWO	Output	Serial wire trace output pin
External bus interface	RD	Output	Strobe signal indicating that reading from the external bus interface space is in progress, active-low
	WR	Output	Strobe signal indicating that writing to the external bus interface space is in progress, in 1-write strobe mode, active-low
	WR0, WR1	Output	Strobe signals indicating that either group of data bus pins (D07 to D00, D15 to D08) is valid in writing to the external bus interface space, in byte strobe mode, active-low
	BC0, BC1	Output	Strobe signals indicating that either group of data bus pins (D07 to D00, D15 to D08) is valid in access to the external bus interface space, in 1-write strobe mode, active-low
	WAIT	Input	Input pin for wait request signals in access to the external space, active-low
	CS0 to CS3	Output	Select signals for CS areas, active-low
	A00 to A16	Output	Address bus
	D00 to D15	I/O	Data bus
Battery Backup	VBATWIO0 to VBATWIO2	I/O	Output wakeup signal for the VBATT wakeup control function. External event input for the VBATT wakeup control function.

Function	Signal	I/O	Description
GPT	GTETRGA, GTETRGB, GTETRGC, GTETRGD	Input	External trigger input pins
	GTIOC0A to GTIOC9A, GTIOC0B to GTIOC9B	I/O	Input capture, output capture, or PWM output pins
	GTIU	Input	Hall sensor input pin U
	GTIV	Input	Hall sensor input pin V
	GTIW	Input	Hall sensor input pin W
	GTOUUP	Output	3-phase PWM output for BLDC motor control (positive U phase)
	GTOULO	Output	3-phase PWM output for BLDC motor control (negative U phase)
	GTOVUP	Output	3-phase PWM output for BLDC motor control (positive V phase)
	GTOVLO	Output	3-phase PWM output for BLDC motor control (negative V phase)
	GTOWUP	Output	3-phase PWM output for BLDC motor control (positive W phase)
	GTOVLO	Output	3-phase PWM output for BLDC motor control (negative W phase)
	AGT	AGTEE0, AGTEE1	Input
AGTIO0, AGTIO1		I/O	External event input and pulse output pins
AGTO0, AGTO1		Output	Pulse output pins
AGTOA0, AGTOA1		Output	Output compare match A output pins
AGTOB0, AGTOB1		Output	Output compare match B output pins
RTC	RTCOUT	Output	Output pin for 1-Hz/64-Hz clock
	RTCIC0 to RTCIC2	Input	Time capture event input pins
SCI	SCK0 to SCK4, SCK9	I/O	Input/output pins for the clock (clock synchronous mode)
	RXD0 to RXD4, RXD9	Input	Input pins for received data (asynchronous mode/clock synchronous mode)
	TXD0 to TXD4, TXD9	Output	Output pins for transmitted data (asynchronous mode/clock synchronous mode)
	CTS0_RTS0 to CTS4_RTS4, CTS9_RTS9	I/O	Input/output pins for controlling the start of transmission and reception (asynchronous mode/clock synchronous mode), active-low
	SCL0 to SCL4, SCL9	I/O	Input/output pins for the I ² C clock (simple IIC)
	SDA0 to SDA4, SDA9	I/O	Input/output pins for the I ² C data (simple IIC)
	SCK0 to SCK4, SCK9	I/O	Input/output pins for the clock (simple SPI)
	MISO0 to MISO4, MISO9	I/O	Input/output pins for slave transmission of data (simple SPI)
	MOSI0 to MOSI4, MOSI9	I/O	Input/output pins for master transmission of data (simple SPI)
	SS0 to SS4, SS9	Input	Chip-select input pins (simple SPI), active-low
IIC	SCL0 to SCL2	I/O	Input/output pins for the clock
	SDA0 to SDA2	I/O	Input/output pins for the data
SSI	SSISCK0	I/O	SSI serial bit clock pins
	SSISCK1		
	SSIWS0	I/O	Word select pins
	SSIWS1		
	SSITXD0	Output	Serial data output pin
	SSIRXD0	Input	Serial data input pin
	SSIDATA1	I/O	Serial data input/output pin
	AUDIO_CLK	Input	External clock pin for audio (input oversampling clock)

Function	Signal	I/O	Description
SPI	RSPCKA, RSPCKB	I/O	Clock input/output pin
	MOSIA, MOSIB	I/O	Input or output pins for data output from the master
	MISOA, MISOB	I/O	Input or output pins for data output from the slave
	SSLA0, SSLB0	I/O	Input or output pins for slave selection
	SSLA1, SSLA2, SSLA3, SSLB1, SSLB2, SSLB3	Output	Output pins for slave selection
QSPI	QSPCLK	Output	QSPI clock output pin
	QSSL	Output	QSPI slave output pin
	QIO0	I/O	Master transmit data/Data 0
	QIO1	I/O	Master input data/Data 1
	QIO2, QIO3	I/O	Data 2, Data 3
CAN	CRX0	Input	Receive data
	CTX0	Output	Transmit data
USBFS	VSS_USB	Input	Ground pins
	VCC_USB_LDO	Input	Power supply pin for USB LDO regulator
	VCC_USB	I/O	Input: Power supply pin for USB transceiver. Output: USB LDO regulator output pin. This pin should be connected to an external capacitor.
	USB_DP	I/O	D+ I/O pin of the USB on-chip transceiver. Connect this pin to the D+ pin of the USB bus.
	USB_DM	I/O	D- I/O pin of the USB on-chip transceiver. Connect this pin to the D- pin of the USB bus.
	USB_VBUS	Input	USB cable connection monitor pin. Connect this pin to VBUS of the USB bus. The VBUS pin status (connected or disconnected) can be detected when the USB module is operating as a device controller.
	USB_EXICEN	Output	Low power control signal for external power supply (OTG) chip
	USB_VBUSEN	Output	VBUS (5 V) supply enable signal for external power supply chip
	USB_OVRCURA, USB_OVRCURB	Input	Connect the external overcurrent detection signals to these pins. Connect the VBUS comparator signals to these pins when the OTG power supply chip is connected.
USB_ID	USB_ID	Input	Connect the MicroAB connector ID input signal to this pin during operation in OTG mode
SDHI	SD0CLK	Output	SD clock output pin
	SD0CMD	I/O	Command output pin and response input signal pin
	SD0DAT0 to SD0DAT7	I/O	SD and MMC data bus pins
	SD0WP	Input	SD write-protect signal
Analog power supply	AVCC0	Input	Analog voltage supply pin
	AVSS0	Input	Analog voltage supply ground pin
	VREFH0	Input	Analog reference voltage supply pin
	VREFL0	Input	Reference power supply ground pin
	VREFH	Input	Analog reference voltage supply pin for DAC12
VREFL	Input	Analog reference ground pin for DAC12	
ADC14	AN000 to AN027	Input	Input pins for the analog signals to be processed by the ADC14
	ADTRG0	Input	Input pins for the external trigger signals that start the A/D conversion, active-low
DAC12	DA0, DA1	Output	Output pins for the analog signals to be processed by the D/A converter
Comparator output	VCOUT	Output	Comparator output pin
ACMPHS	IVREF0 to IVREF5	Input	Reference voltage input pin
	IVCMP0 to IVCMP5	Input	Analog voltage input pins
ACMPLP	COMPREF0, COMPREF1	Input	Reference voltage input pins
	COMPIN0, COMPIN1	Input	Analog voltage input pins
OPAMP	AMP0+ to AMP3+	Input	Analog voltage input pins
	AMP0- to AMP3-	Input	Analog voltage input pins
	AMP00 to AMP30	Output	Analog voltage output pins

Function	Signal	I/O	Description
CTSU	TS00, TS01, TS03 to TS22, TS26 to TS27, TS29 to TS35	Input	Capacitive touch detection pins (touch pins)
	TSCAP	-	Secondary power supply pin for the touch driver
I/O ports	P000 to P015	I/O	General-purpose input/output pins
	P100 to P115	I/O	General-purpose input/output pins
	P200	Input	General-purpose input pin
	P201 to P206, P212, P213	I/O	General-purpose input/output pins
	P214, P215	Input	General-purpose input pins
	P300 to P315	I/O	General-purpose input/output pins
	P400 to P415	I/O	General-purpose input/output pins
	P500 to P507, P511, P512	I/O	General-purpose input/output pins
	P600 to P606, P608 to P614	I/O	General-purpose input/output pins
	P700 to P705, P708 to P713	I/O	General-purpose input/output pins
	P800 to P809	I/O	General-purpose input/output pins
	P900 to P902	I/O	General-purpose input/output pins
SLCDC	VL1, VL2, VL3, VL4	I/O	Voltage pin for driving the LCD
	CAPH, CAPL	I/O	Capacitor connection pin for the LCD controller/driver
	COM0 to COM7	Output	Common signal output pins for the LCD controller/driver
	SEG00 to SEG51	Output	Segment signal output pins for the LCD controller/driver

1.6 Pin Assignments

Figure 1.3 to Figure 1.9 show the pin assignments.

R7FS3A77C2A01CLK															
	A	B	C	D	E	F	G	H	J	K	L	M	N		
13	P407	P409	P412	P708	P711	VCC	P212 /EXTAL	P215 /XCIN	VCL	P702	P405	P402	P400	13	
12	USB_DM	USB_DP	P410	P414	P710	VSS	P213 /XTAL	P214 /XCOUT	VBATT	P701	P404	P511	VCC	12	
11	VCC_USB	VSS_USB	VCC_USB_LDO	P411	P415	P712	P705	P704	P703	P403	P401	P512	VSS	11	
10	P205	P206	P204	P408	P413	P709	P713	P700	P406	P003	P000	P002	P001	10	
9	P203	P313	P202	P314						P004	P006	P009	P008	9	
8	P900	P901	P200	P315						P005	AVSS0	P011 /VREFL0	P010 /VREFH0	8	
7	VSS	P902	RES	P310						P007	AVCC0	P013 /VREFL	P012 /VREFH	7	
6	VCC	P201/MD	P312	P305						P505	P506	P015	P014	6	
5	P309	P311	P308	P303	NC						P503	P504	VSS	VCC	5
4	P307	P306	P304	P109/TDO /SWO	P114	P608	P604	P600	P105	P500	P502	P501	P507	4	
3	P808	P809	P301	P112	P115	P610	P614	P603	P107	P106	P104	P803	P802	3	
2	P302	P300/TCK /SWCLK	P111	P806	P609	P612	VSS	P605	P601	P805	P800	P101	P801	2	
1	P108/TMS /SWDIO	P110/TDI	P113	P807	P611	P613	VCC	P606	P602	P804	P103	P102	P100	1	
	A	B	C	D	E	F	G	H	J	K	L	M	N		

Figure 1.3 Pin assignment for 145-pin LGA (top view)

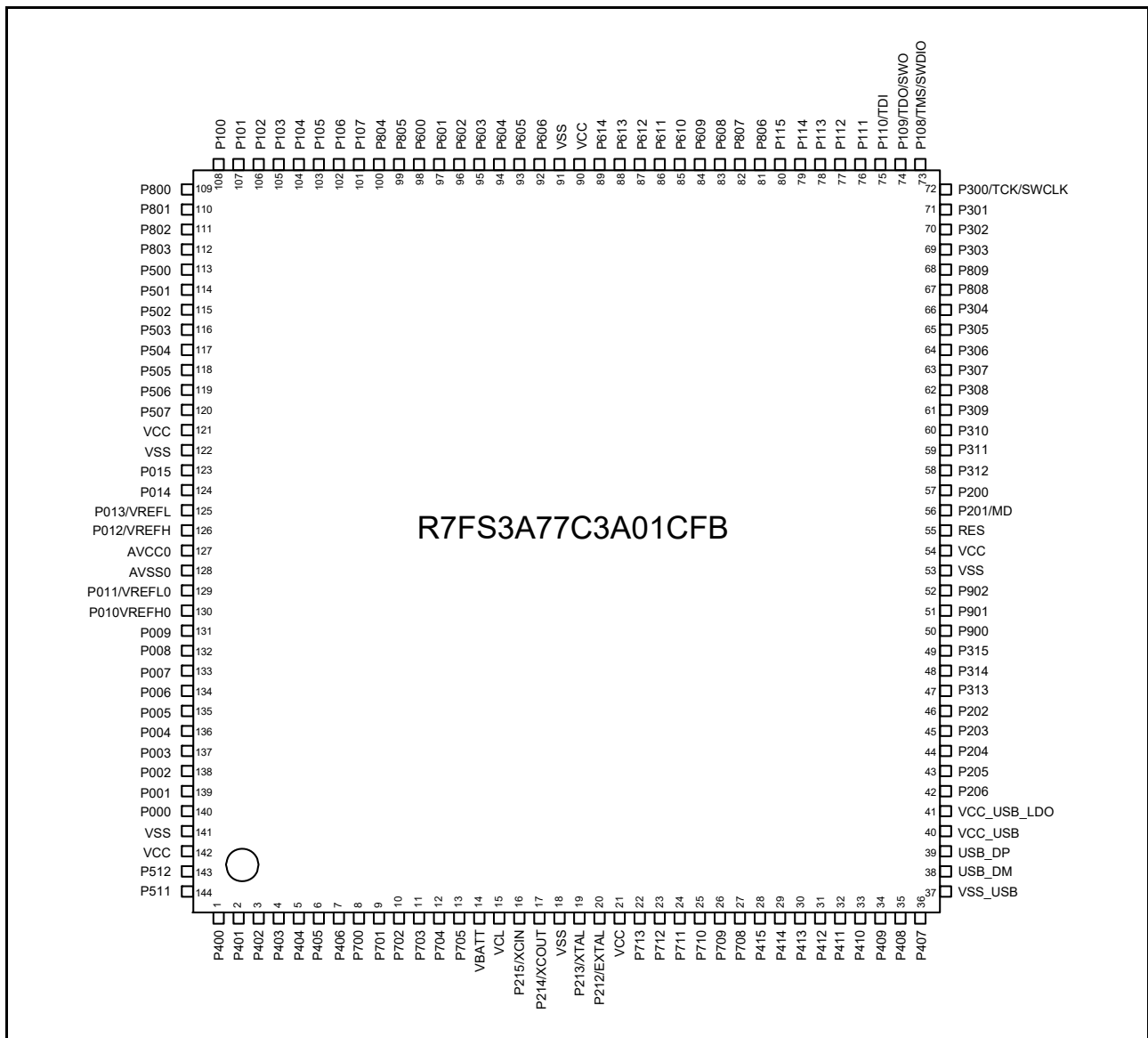


Figure 1.4 Pin assignment for 144-pin LQFP (top view)

R7FS3A77C2A01CBJ

	A	B	C	D	E	F	G	H	J	K	L	
11	P407	P408	P411	P414	P212/ EXTAL	P215/ XCIN	VCL	P406	P403	P401	P400	11
10	USB_DM	USB_DP	P410	P415	P213/ XTAL	P214/ XCOUT	VBATT	P405	P402	P511	P512	10
9	VCC_ USB	VSS_ USB	P409	P412	P708	VCC	VSS	P404	P002	P001	P000	9
8	P205	VCC_ USB_ LDO	P206	P204	P413	P710	P702	P006	P004	P003	P005	8
7	P203	P202	P313	P314	P315	P709	P701	P007	AVSS0	P011/ VREFL0	P010/ VREFH0	7
6	VSS	VCC	RES	P201/MD	P200	NC	P700	P008	AVCC0	P013/ VREFL	P012/ VREFH	6
5	P308	P309	P307	P302	P304	P612	P601	P506	P505	P015	P014	5
4	P305	P306	P808	P114	P611	P603	P600	P504	P503	VSS	VCC	4
3	P809	P303	P110/TDI	P111	P609	P604	P106	P104	P502	P500	P501	3
2	P301	P108/ TMS/ SWDIO	P113	P608	P613	P605	P602	P105	P102	P801	P800	2
1	P300/ TCK/ SWCLK	P109/ TDO/ SWO	P112	P115	P610	VCC	VSS	P107	P103	P101	P100	1
	A	B	C	D	E	F	G	H	J	K	L	

Figure 1.5 Pin assignment for 121-pin BGA (top view)

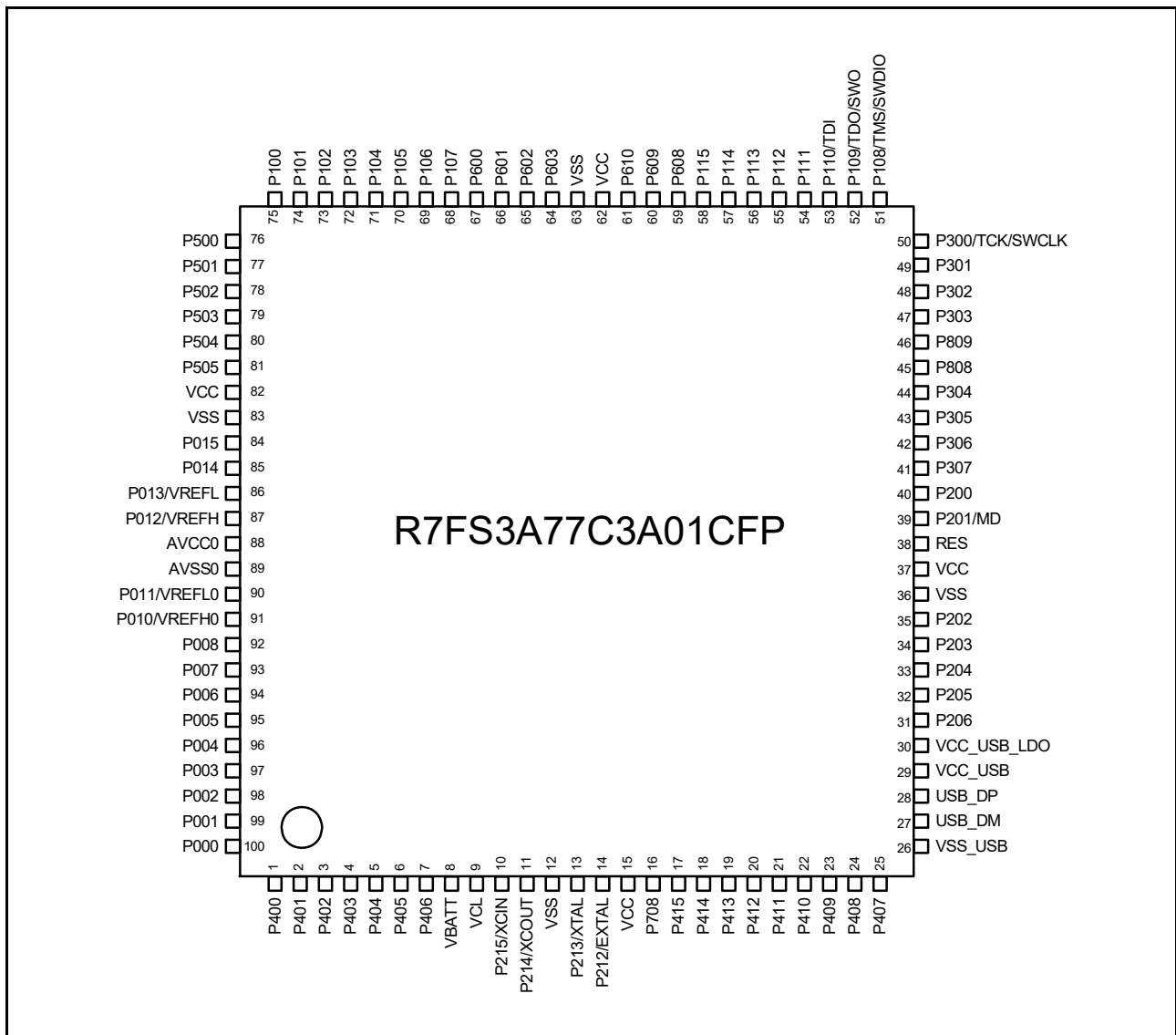


Figure 1.6 Pin assignment for 100-pin LQFP (top view)

R7FS3A77C2A01CLJ

	A	B	C	D	E	F	G	H	J	K	
10	P407	P409	P412	VCC	P212/ EXTAL	P215/ XCIN	VCL	P403	P400	P000	10
9	USB_DM	USB_DP	P413	VSS	P213/ XTAL	P214/ XCOUT	VBATT	P405	P401	P001	9
8	VCC_USB	VSS_USB	VCC_USB B_LDO	P411	P415	P708	P404	P003	P004	P002	8
7	P205	P204	P206	P408	P414	P406	P006	P007	P008	P005	7
6	VSS	VCC	P202	P203	P410	P402	P505	AVSS0	P011/ VREFL0	P010/ VREFH0	6
5	P200	P201/MD	P307	RES	P113	P600	P504	AVCC0	P013/ VREFL	P012/ VREFH	5
4	P305	P304	P808	P306	P115	P601	P503	P100	P015	P014	4
3	P809	P303	P110/TDI	P111	P609	P602	P107	P103	VSS	VCC	3
2	P300/ TCK/ SWCLK	P302	P301	P114	P610	P603	P106	P101	P501	P502	2
1	P108/ TMS/ SWDIO	P109/ TDO/ SWO	P112	P608	VCC	VSS	P105	P104	P102	P500	1
	A	B	C	D	E	F	G	H	J	K	

Figure 1.7 Pin assignment for 100-pin LGA (top view)

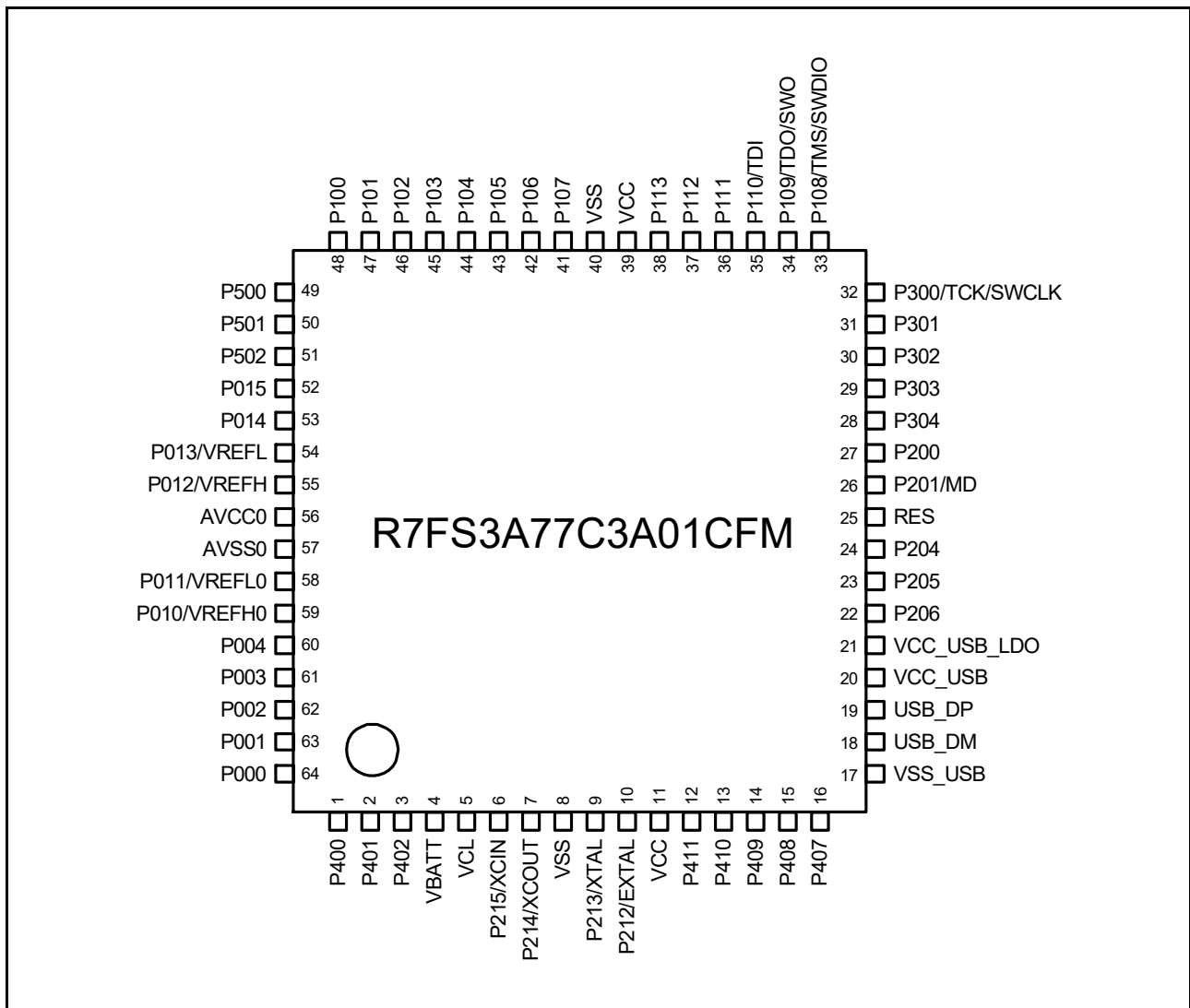


Figure 1.8 Pin assignment for 64-pin LQFP (top view)

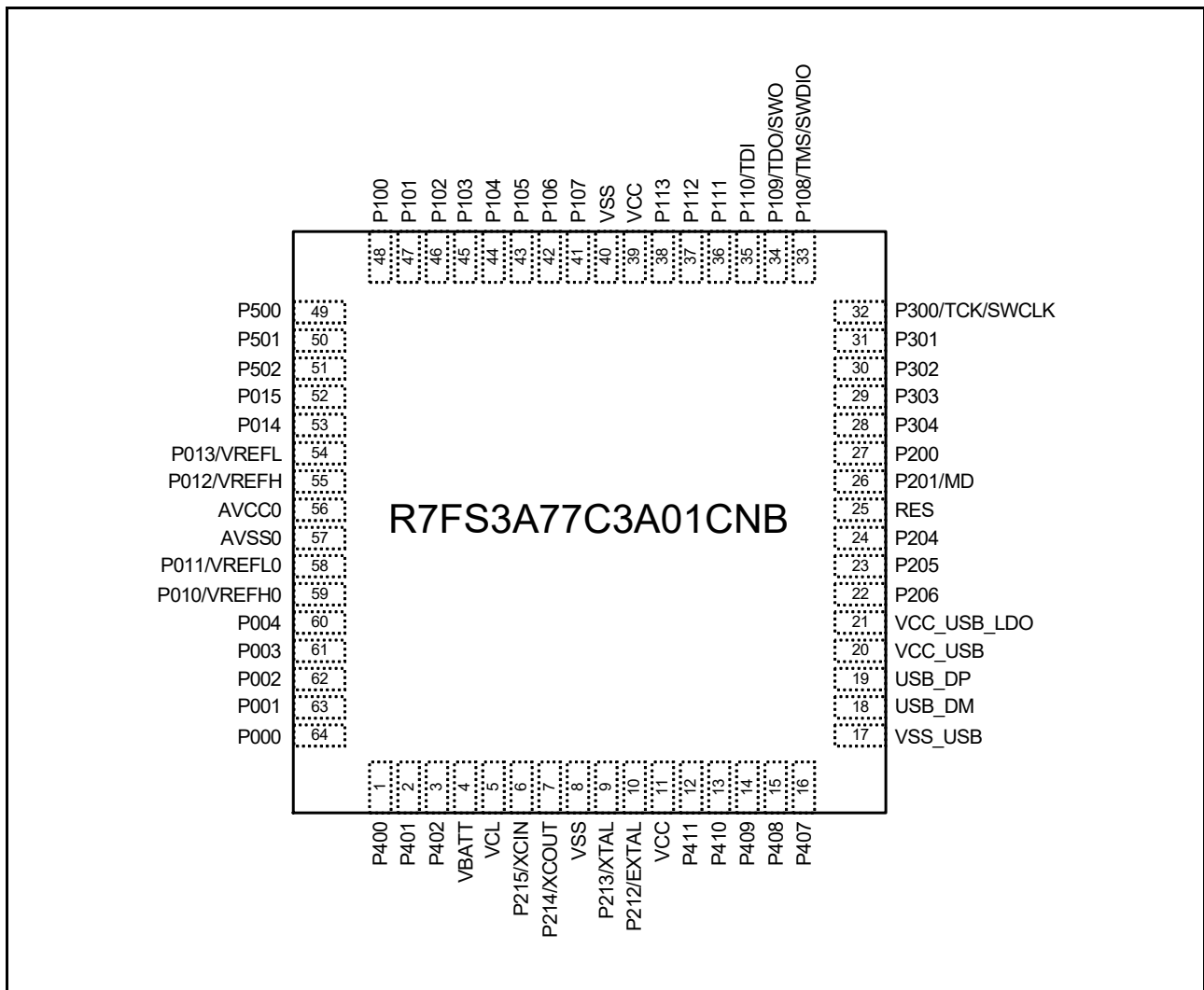


Figure 1.9 Pin assignment for 64-pin QFN (top view)

Pin number	Pin number						Power, System, Clock, Debug, CAC, VBATT	Interrupt	I/O ports	External bus	Timers				Communication interfaces					Analog			HMI	
	LGA145	LQFP144	BGA121	LQFP100	LGA100	LQFP64					QFN64	AGT	GPT_OPS, POEG	GPT	RTC	USBFS,CAN	SCI	IIC	SPI/QSPI	SSI	SDHI	ADC14	DAC12, OPAMP	ACMPHS, ACMPLP
K10	137	K8	97	H8	61	61				P003								AN003	AMP1 O	IVREF 3/ IVCMP 3				
M10	138	J9	98	K8	62	62		IRQ8		P002								AN002	AMP0 O	IVREF 2/ IVCMP 2				
N10	139	K9	99	K9	63	63		IRQ7		P001								AN001	AMP0-	IVREF 1/ IVCMP 1		TS22		
L10	140	L9	100	K10	64	64		IRQ6		P000								AN000	AMP0+	IVREF 0/ IVCMP 0		TS21		
N11	141						VSS																	
N12	142						VCC																	
M11	143	L10						IRQ14		P512			GTIOC 0A_B		TXD4_ B/ MOSI4 B/ SDA4_ B	SCL2								
M12	144	K10						IRQ15		P511			GTIOC 0B_B		RXD4_ B/ MISO4 B/ SCL4_ B	SDA2								
E5		F6					NC																	

Note: Some pin names have the added suffix of _A, _B, and _C. The suffix can be ignored when assigning functionality.

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

$VCC^{*1} = AVCC0 = VCC_USB^{*2} = VCC_USB_LDO^{*2} = 1.6$ to $5.5V$, $VREFH = VREFH0 = 1.6$ to $AVCC0$, $VBATT = 1.6$ to $3.6V$, $VSS = AVSS0 = VREFL = VREFL0 = VSS_USB = 0V$, $T_a = T_{opr}$

Note 1. The typical condition is set to $VCC = 3.3V$.

Note 2. When USBFS is not used.

Figure 2.1 shows the timing conditions.

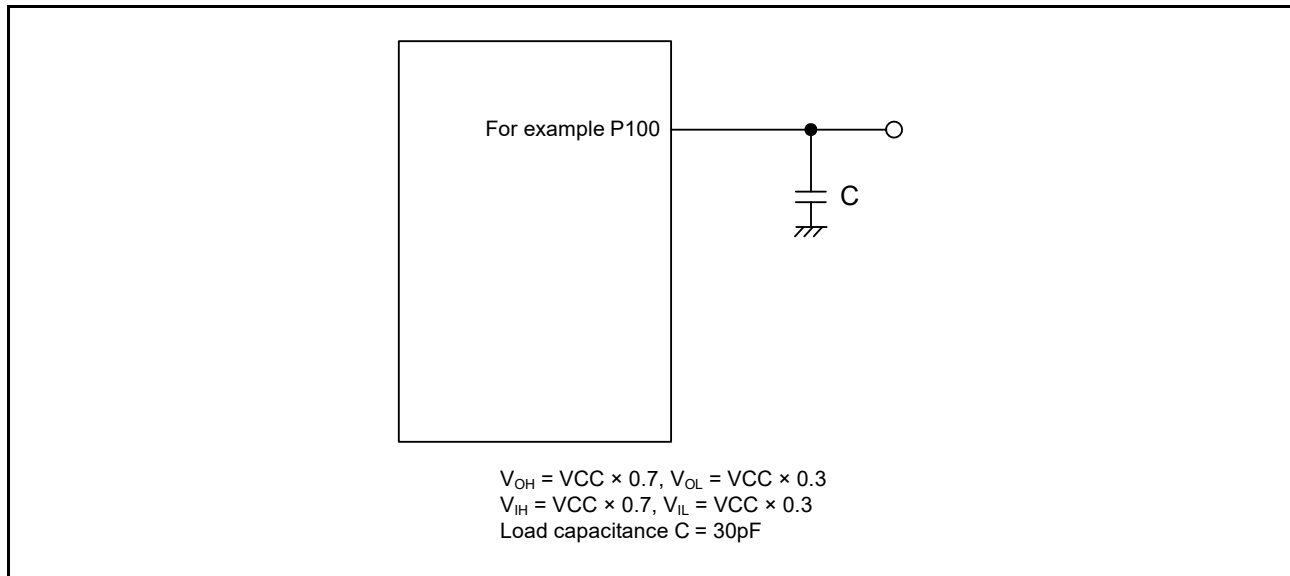


Figure 2.1 Input or output timing measurement conditions

The measurement conditions of timing specification in each peripherals are recommended for the best peripheral operation. However, make sure to adjust driving abilities of each pin to meet your conditions.

Each function pin used for the same function must select the same drive ability. If the I/O drive ability of each function pin is mixed, the AC specification of each function is not guaranteed.

2.1 Absolute Maximum Ratings

Table 2.1 Absolute maximum ratings

Parameter	Symbol	Value	Unit
Power supply voltage	VCC	-0.5 to +6.5	V
Input voltage	5V-tolerant ports*1	V_{in}	-0.3 to +6.5
	P000 to P015	V_{in}	-0.3 to AVCC0 + 0.3
	Others	V_{in}	-0.3 to VCC + 0.3
Reference power supply voltage	VREFH0	-0.3 to +6.5	V
	VREFH		V
VBATT power supply voltage	VBATT	-0.5 to +6.5	V
Analog power supply voltage	AVCC0	-0.5 to +6.5	V
USB power supply voltage	VCC_USB	-0.5 to +6.5	V
	VCC_USB_LDO	-0.5 to +6.5	V
Analog input voltage	When AN000 to AN015 are used	V_{AN}	-0.3 to AVCC0 + 0.3
	When AN016 to AN027 are used		-0.3 to VCC + 0.3
LCD voltage	VL1 voltage	V_{L1}	-0.3 to +2.8
	VL2 voltage	V_{L2}	-0.3 to +6.5
	VL3 voltage	V_{L3}	-0.3 to +6.5
	VL4 voltage	V_{L4}	-0.3 to +6.5
Operating temperature*2 *3 *4	T_{opr}	-40 to +85	°C
		-40 to +105	°C
Storage temperature	T_{stg}	-55 to +125	°C

Note 1. Ports P205, P206, P400 to P404, P407, P511, P512 are 5V-tolerant.

Note 2. See [section 2.2.1, Tj/Ta Definition](#).

Note 3. Contact Renesas Electronics sales office for information on derating operation under $T_a = +85^\circ\text{C}$ to $+105^\circ\text{C}$. Derating is the systematic reduction of load for improved reliability.

Note 4. The upper limit of operating temperature is 85°C or 105°C , depending on the product. For details, refer to [section 1.3, Part Numbering](#).

Caution: Permanent damage to the MCU may result if absolute maximum ratings are exceeded.

To preclude any malfunctions due to noise interference, insert capacitors of high frequency characteristics between the VCC and VSS pins, between the AVCC0 and AVSS0 pins, between the VCC_USB and VSS_USB pins, between the VREFH0 and VREFL0 pins, and between the VREFH and VREFL pins. Place capacitors of about 0.1 μF as close as possible to every power supply pin and use the shortest and heaviest possible traces. Also, connect capacitors as stabilization capacitance.

Connect the VCL pin to a VSS pin by a 4.7 μF capacitor. The capacitor must be placed close to the pin.

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up might cause malfunction and the abnormal current that passes in the device at this time might cause degradation of internal elements.

Table 2.2 Recommended operating conditions

Parameter	Symbol	Value	Min	Typ	Max	Unit
Power supply voltages	VCC*1, *2	When USBFS is not used	1.6	-	5.5	V
		When USBFS is used USB Regulator Disable	VCC_USB	-	3.6	V
		When USBFS is used USB Regulator Enable	VCC_USB _LDO	-	5.5	V
	VSS	-	0	-	V	
USB power supply voltages	VCC_USB	When USBFS is not used	-	VCC	-	V
		When USBFS is used USB Regulator Disable (Input)	3.0	3.3	3.6	V
	VCC_USB_LDO	When USBFS is not used	-	VCC	-	V
		When USBFS is used USB Regulator Disable	-	VCC	-	V
		When USBFS is used USB Regulator Enable	3.8	-	5.5	V
	VSS_USB	-	0	-	V	
VBATT power supply voltage	VBATT	When the battery backup function is not used	-	VCC	-	V
		When the battery backup function is used	1.6	-	3.6	V
Analog power supply voltages	AVCC0*1, *2		1.6	-	5.5	V
	AVSS0		-	0	-	V
	VREFH0	When used as ADC14 Reference	1.6	-	AVCC0	V
	VREFL0		-	0	-	V
	VREFH	When used as DAC12 Reference	1.6	-	AVCC0	V
	VREFL		-	0	-	V

Note 1. Use AVCC0 and VCC under the following conditions:

AVCC0 and VCC can be set individually within the operating range when $VCC \geq 2.2\text{ V}$ and $AVCC0 \geq 2.2\text{ V}$
 $AVCC0 = VCC$ when $VCC < 2.2\text{ V}$ or $AVCC0 < 2.2\text{ V}$

Note 2. When powering on the VCC and AVCC0 pins, power them on at the same time or the VCC pin first and then the AVCC0 pin.

2.2 DC Characteristics

2.2.1 Tj/Ta Definition

Table 2.3 DC Characteristics

Conditions: Products with operating temperature (T_a) –40 to +105°C

Parameter	Symbol	Typ	Max	Unit	Test conditions
Permissible junction temperature	Tj	-	125	°C	High-speed mode Middle-speed mode Low-voltage mode Low-speed mode Subosc-speed mode
			105*1		

Note: Make sure that $T_j = T_a + \theta_{ja} \times \text{total power consumption (W)}$, where total power consumption = $(V_{CC} - V_{OH}) \times \Sigma I_{OH} + V_{OL} \times \Sigma I_{OL} + I_{CCmax} \times V_{CC}$.

Note 1. The upper limit of operating temperature is 85°C or 105°C, depending on the product. For details, see [section 1.3, Part Numbering](#). If the part number shows the operation temperature as 85°C, then Tj max is 105°C, otherwise it is 125°C.

2.2.2 I/O V_{IH}, V_{IL}

Table 2.4 I/O V_{IH}, V_{IL} (1)

Conditions: VCC = 2.7 to 5.5 V, AVCC0 = 2.7 to 5.5 V, VBATT = 1.6 to 3.6 V, VSS = AVSS0 = 0 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
Schmitt trigger input voltage	IIC*1 (except for SMBus)	V _{IH}	VCC × 0.7	-	5.8	V	-
		V _{IL}	-	-	VCC × 0.3		
		ΔV _T	VCC × 0.05	-	-		
	RES, NMI Other peripheral input pins excluding IIC	V _{IH}	VCC × 0.8	-	-		
		V _{IL}	-	-	VCC × 0.2		
		ΔV _T	VCC × 0.1	-	-		
Input voltage (except for Schmitt trigger input pin)	IIC (SMBus)*2	V _{IH}	2.2	-	-	V	VCC = 3.6 to 5.5 V
		V _{IH}	2.0	-	-		VCC = 2.7 to 3.6 V
		V _{IL}	-	-	0.8		-
		5V-tolerant ports*3	V _{IH}	VCC × 0.8	-		5.8
			V _{IL}	-	-		VCC × 0.2
		P000 to P015	V _{IH}	AVCC0 × 0.8	-		-
	V _{IL}		-	-	AVCC0 × 0.2		
	EXTAL D00 to D15 Input ports pins except for P000 to P015	V _{IH}	VCC × 0.8	-	-		
		V _{IL}	-	-	VCC × 0.2		
	When V _{BATT} power supply is selected	P402, P403, P404	V _{IH}	V _{BATT} × 0.8	-		V _{BATT} + 0.3
			V _{IL}	-	-		V _{BATT} × 0.2
			ΔV _T	V _{BATT} × 0.05	-		-

Note 1. SCL0_A, SDA0_A, SCL1_A, SDA1_A, SCL2, SDA2, SDA0_B (total 7 pins).

Note 2. SCL0_A, SDA0_A, SCL0_B, SDA0_B, SCL1_A, SDA1_A, SCL1_B, SDA1_B, SCL2, SDA2 (total 10 pins).

Note 3. P205, P206, P400 to P404, P407, P511, P512 (total 10 pins).

Table 2.5 I/O V_{IH} , V_{IL} (2)Conditions: $V_{CC} = 1.6$ to 2.7 V, $AV_{CC0} = 1.6$ to 2.7 V, $V_{BATT} = 1.6$ to 3.6 V, $V_{SS} = AV_{SS0} = 0$ V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Schmitt trigger input voltage	RES, NMI Peripheral input pins	V_{IH}	$V_{CC} \times 0.8$	-	-	V	-
		V_{IL}	-	-	$V_{CC} \times 0.2$		
		ΔV_T	$V_{CC} \times 0.01$	-	-		
Input voltage (except for Schmitt trigger input pin)	5V-tolerant ports*1	V_{IH}	$V_{CC} \times 0.8$	-	5.8		
		V_{IL}	-	-	$V_{CC} \times 0.2$		
	P000 to P015	V_{IH}	$AV_{CC0} \times 0.8$	-	-		
		V_{IL}	-	-	$AV_{CC0} \times 0.2$		
	EXTAL D0 to D15 Input ports pins except for P000 to P015	V_{IH}	$V_{CC} \times 0.8$	-	-		
		V_{IL}	-	-	$V_{CC} \times 0.2$		
When V_{BATT} power supply is selected	P402, P403, P404	V_{IH}	$V_{BATT} \times 0.8$	-	$V_{BATT} + 0.3$		
		V_{IL}	-	-	$V_{BATT} \times 0.2$		
		ΔV_T	$V_{BATT} \times 0.01$	-	-		

Note 1. P205, P206, P400 to P404, P407, P511, P512 (total 10 pins)

2.2.3 I/O I_{OH} , I_{OL} **Table 2.6** I/O I_{OH} , I_{OL} Conditions: $V_{CC} = AV_{CC0} = 1.6$ to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	
Permissible output current (average value per pin)	Ports P000 to P015, Ports P212, P213	-	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	4.0	mA
	Ports P408, P409	Low drive*1	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2 $V_{CC} = 2.7$ to 3.0 V	I_{OH}	-	-	-8.0	mA
			I_{OL}	-	-	8.0	mA
		Middle drive*2 $V_{CC} = 3.0$ to 5.5 V	I_{OH}	-	-	-20.0	mA
			I_{OL}	-	-	20.0	mA
	Ports P100 to P115, P201 to P204, P300 to P315, P500 to P503, P600 to P606, P608 to P614, P800 to P809, P900 to P902 (total 67 pins)	Low drive*1	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	8.0	mA
	Other output pin*3	Low drive*1	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2	I_{OH}	-	-	-8.0	mA
			I_{OL}	-	-	8.0	mA
Permissible output current (Max value per pin)	Ports P000 to P015, Ports P212, P213	-	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	4.0	mA
	Ports P408, P409	Low drive*1	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2 $V_{CC} = 2.7$ to 3.0 V	I_{OH}	-	-	-8.0	mA
			I_{OL}	-	-	8.0	mA
		Middle drive*2 $V_{CC} = 3.0$ to 5.5 V	I_{OH}	-	-	-20.0	mA
			I_{OL}	-	-	20.0	mA
	Ports P100 to P115, P201 to P204, P300 to P315, P500 to P503, P600 to P606, P608 to P614, P800 to P809, P900 to P902 (total 67 pins)	Low drive*1	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	8.0	mA
	Other output pin*3	Low drive*1	I_{OH}	-	-	-4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2	I_{OH}	-	-	-8.0	mA
			I_{OL}	-	-	8.0	mA
Permissible output current (max value total pins)	Total of ports P000 to P015	$\Sigma I_{OH}(\max)$	-	-	-30	mA	
		$\Sigma I_{OL}(\max)$	-	-	30	mA	
	Total of all output pin	$\Sigma I_{OH}(\max)$	-	-	-60	mA	
		$\Sigma I_{OL}(\max)$	-	-	60	mA	

Caution: To protect the reliability of the MCU, the output current values should not exceed the values in this table. The average output current indicates the average value of current measured during 100 μ s.

Note 1. This is the value when low driving ability is selected with the Port Drive Capability bit in PmnPFS register.

Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in PmnPFS register.

Note 3. Except for ports P200, P214, P215, which are input ports.

2.2.4 I/O V_{OH} , V_{OL} , and Other Characteristics**Table 2.7** I/O V_{OH} , V_{OL} (1)Conditions: $V_{CC} = AV_{CC0} = 4.0$ to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions	
Output voltage	IIC*1, *2	V_{OL}	-	-	0.4	V	$I_{OL} = 3.0$ mA	
		V_{OL}	-	-	0.6		$I_{OL} = 6.0$ mA	
	Ports P408, P409*2, *3	V_{OH}	$V_{CC} - 1.0$	-	-		$I_{OH} = -20$ mA	
		V_{OL}	-	-	1.0		$I_{OL} = 20$ mA	
	Ports P000 to P015	Low drive	V_{OH}	$AV_{CC0} - 0.8$	-		-	$I_{OH} = -2.0$ mA
			V_{OL}	-	-		0.8	$I_{OL} = 2.0$ mA
		Middle drive	V_{OH}	$AV_{CC0} - 0.8$	-		-	$I_{OH} = -4.0$ mA
			V_{OL}	-	-		0.8	$I_{OL} = 4.0$ mA
	Other output pins*4	Low drive	V_{OH}	$V_{CC} - 0.8$	-		-	$I_{OH} = -2.0$ mA
			V_{OL}	-	-		0.8	$I_{OL} = 2.0$ mA
		Middle drive*5	V_{OH}	$V_{CC} - 0.8$	-		-	$I_{OH} = -4.0$ mA
			V_{OL}	-	-		0.8	$I_{OL} = 4.0$ mA

Note 1. SCL0_A, SDA0_A, SCL0_B, SDA0_B, SCL1_A, SDA1_A, SCL1_B, SDA1_B, SCL2, SDA2 (total 10 pins).

Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in PmnPFS register.

Note 3. Based on characterization data, not tested in production.

Note 4. Except for ports P200, P214, P215, which are input ports.

Note 5. Except for P212, P213.

Table 2.8 I/O V_{OH} , V_{OL} (2)Conditions: $V_{CC} = AV_{CC0} = 2.7$ to 4.0 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions	
Output voltage	IIC*1, *2	V_{OL}	-	-	0.4	V	$I_{OL} = 3.0$ mA	
		V_{OL}	-	-	0.6		$I_{OL} = 6.0$ mA	
	Ports P408, P409*2, *3	V_{OH}	$V_{CC} - 1.0$	-	-		$I_{OH} = -20$ mA $V_{CC} = 3.3$ V	
		V_{OL}	-	-	1.0		$I_{OL} = 20$ mA $V_{CC} = 3.3$ V	
	Ports P000 to P015	Low drive	V_{OH}	$AV_{CC0} - 0.5$	-		-	$I_{OH} = -1.0$ mA
			V_{OL}	-	-		0.5	$I_{OL} = 1.0$ mA
		Middle drive	V_{OH}	$AV_{CC0} - 0.5$	-		-	$I_{OH} = -2.0$ mA
			V_{OL}	-	-		0.5	$I_{OL} = 2.0$ mA
	Other output pins*4	Low drive	V_{OH}	$V_{CC} - 0.5$	-		-	$I_{OH} = -1.0$ mA
			V_{OL}	-	-		0.5	$I_{OL} = 1.0$ mA
		Middle drive*5	V_{OH}	$V_{CC} - 0.5$	-		-	$I_{OH} = -2.0$ mA
			V_{OL}	-	-		0.5	$I_{OL} = 2.0$ mA

Note 1. SCL0_A, SDA0_A, SCL0_B, SDA0_B, SCL1_A, SDA1_A, SCL1_B, SDA1_B, SCL2, SDA2 (total 10 pins).

Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in PmnPFS register.

Note 3. Based on characterization data, not tested in production.

Note 4. Except for ports P200, P214, P215, which are input ports.

Note 5. Except for P212, P213.

Table 2.9 I/O V_{OH} , V_{OL} (3)Conditions: $V_{CC} = AV_{CC0} = 1.6$ to 2.7 V

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
Output voltage	Ports P000 to P015	Low drive	V_{OH}	$AV_{CC0} - 0.3$	-	-	V	$I_{OH} = -0.5$ mA
			V_{OL}	-	-	0.3		$I_{OL} = 0.5$ mA
		Middle drive	V_{OH}	$AV_{CC0} - 0.3$	-	-		$I_{OH} = -1.0$ mA
			V_{OL}	-	-	0.3		$I_{OL} = 1.0$ mA
	Other output pins*1	Low drive	V_{OH}	$V_{CC} - 0.3$	-	-		$I_{OH} = -0.5$ mA
			V_{OL}	-	-	0.3		$I_{OL} = 0.5$ mA
		Middle drive*2	V_{OH}	$V_{CC} - 0.3$	-	-		$I_{OH} = -1.0$ mA
			V_{OL}	-	-	0.3		$I_{OL} = 1.0$ mA

Note 1. Except for ports P200, P214, P215, which are input ports.

Note 2. Except for P212, P213.

Table 2.10 I/O Other CharacteristicsConditions: $V_{CC} = AV_{CC0} = 1.6$ to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Input leakage current	RES, P200, P214, P215	$ I_{in} $	-	-	1.0	μ A	$V_{in} = 0$ V $V_{in} = V_{CC}$
Three-state leakage current (off state)	5V-tolerant ports	$ I_{TSI} $	-	-	1.0	μ A	$V_{in} = 0$ V $V_{in} = 5.8$ V
	Other ports (except for ports P200, P214, P215 and 5 V tolerant)		-	-	1.0		$V_{in} = 0$ V $V_{in} = V_{CC}$
Input pull-up resistor	All Ports (except for ports P200, P214, P215)	R_U	10	20	50	k Ω	$V_{in} = 0$ V
Input capacitance	USB_DP, USB_DM, P100 to P103, P111, P112, P200	C_{in}	-	-	30	pF	$V_{in} = 0$ V $f = 1$ MHz $T_a = 25^\circ$ C
	Other input pins		-	-	15		

2.2.5 I/O Pin Output Characteristics of Low Drive Capacity

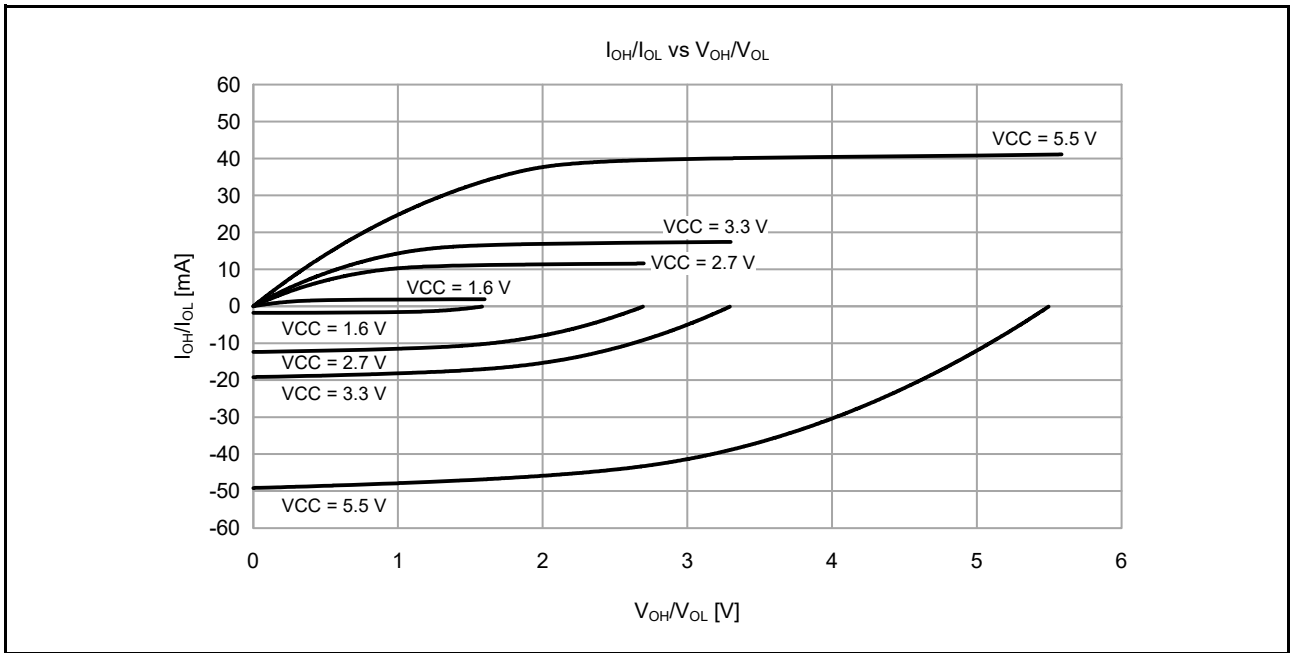


Figure 2.2 VOH/VOL and IOH/IOL voltage characteristics at Ta = 25°C when low drive output is selected (reference data)

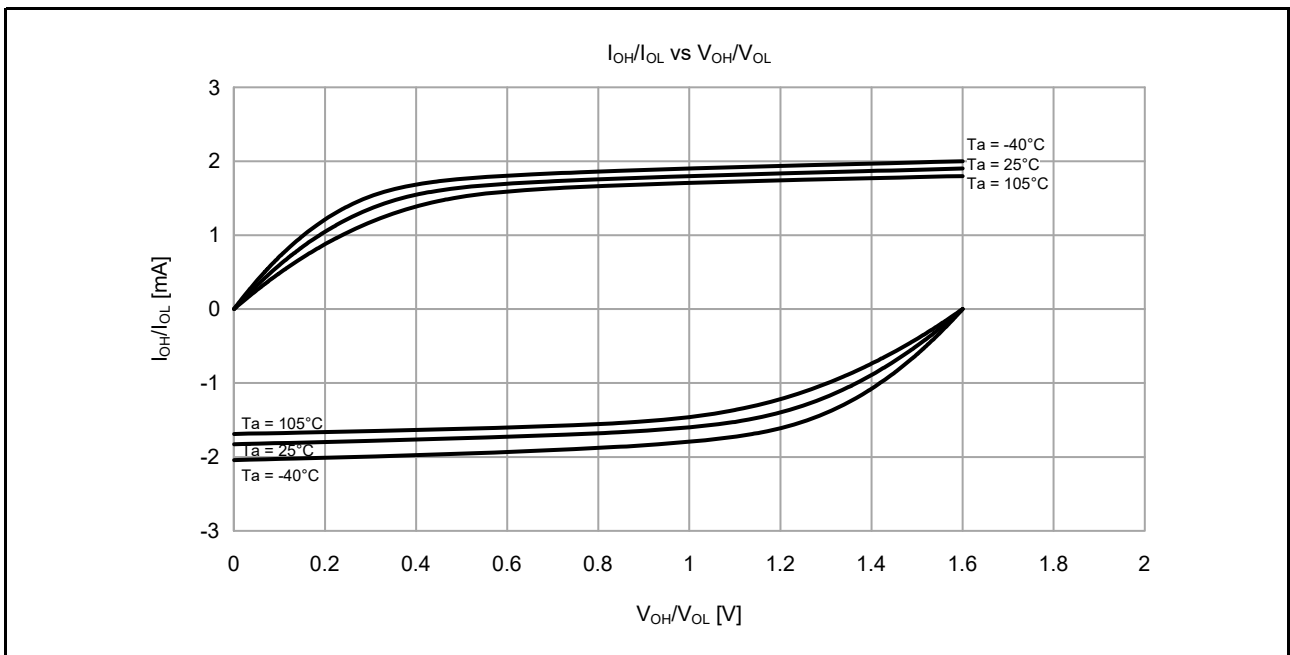


Figure 2.3 VOH/VOL and IOH/IOL temperature characteristics at VCC = 1.6 V when low drive output is selected (reference data)

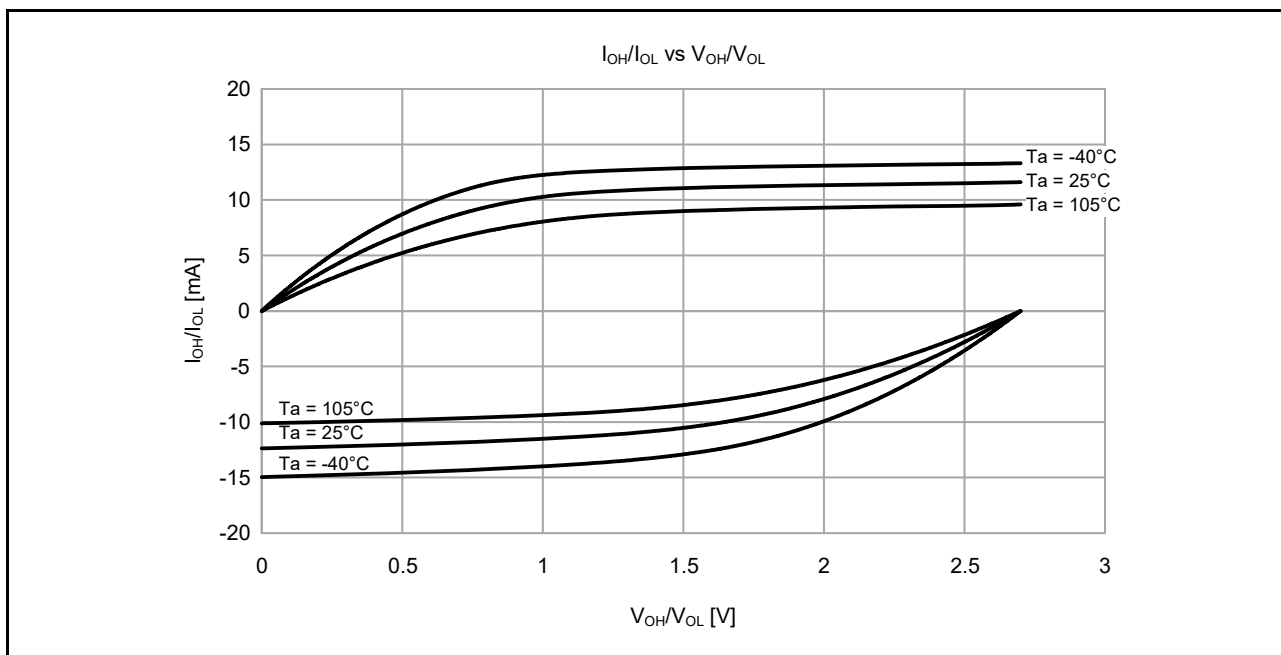


Figure 2.4 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 2.7$ V when low drive output is selected (reference data)

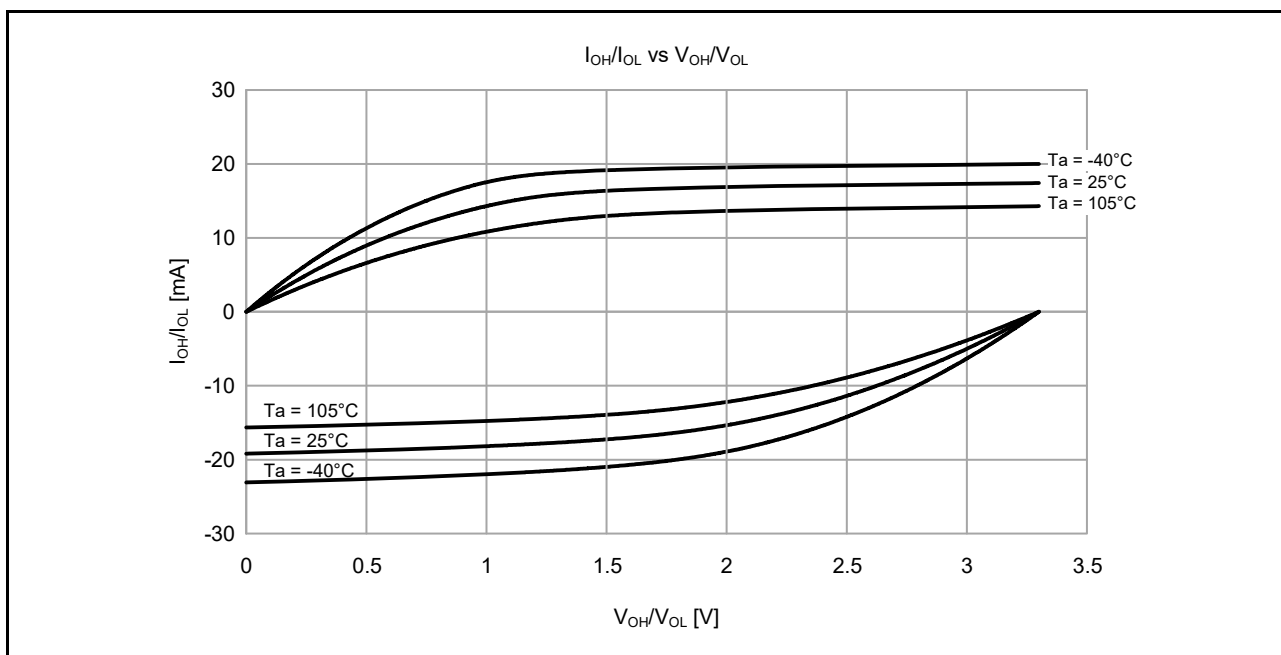


Figure 2.5 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 3.3$ V when low drive output is selected (reference data)

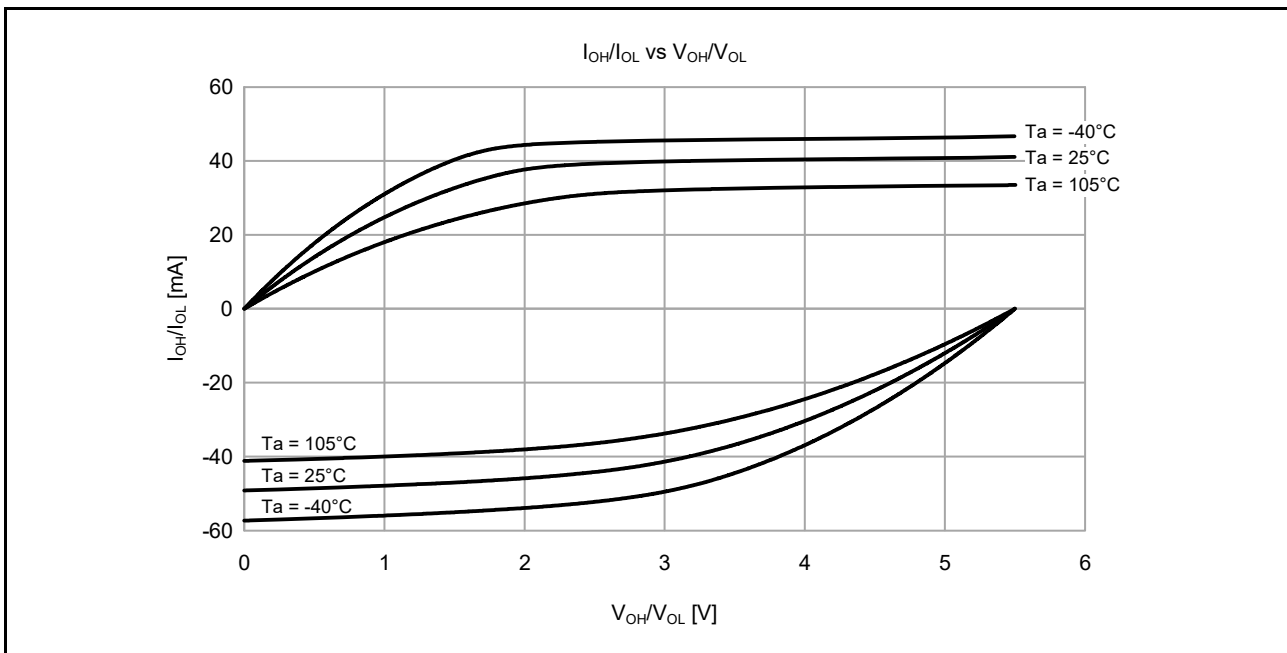


Figure 2.6 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 5.5\text{ V}$ when low drive output is selected (reference data)

2.2.6 I/O Pin Output Characteristics of Middle Drive Capacity

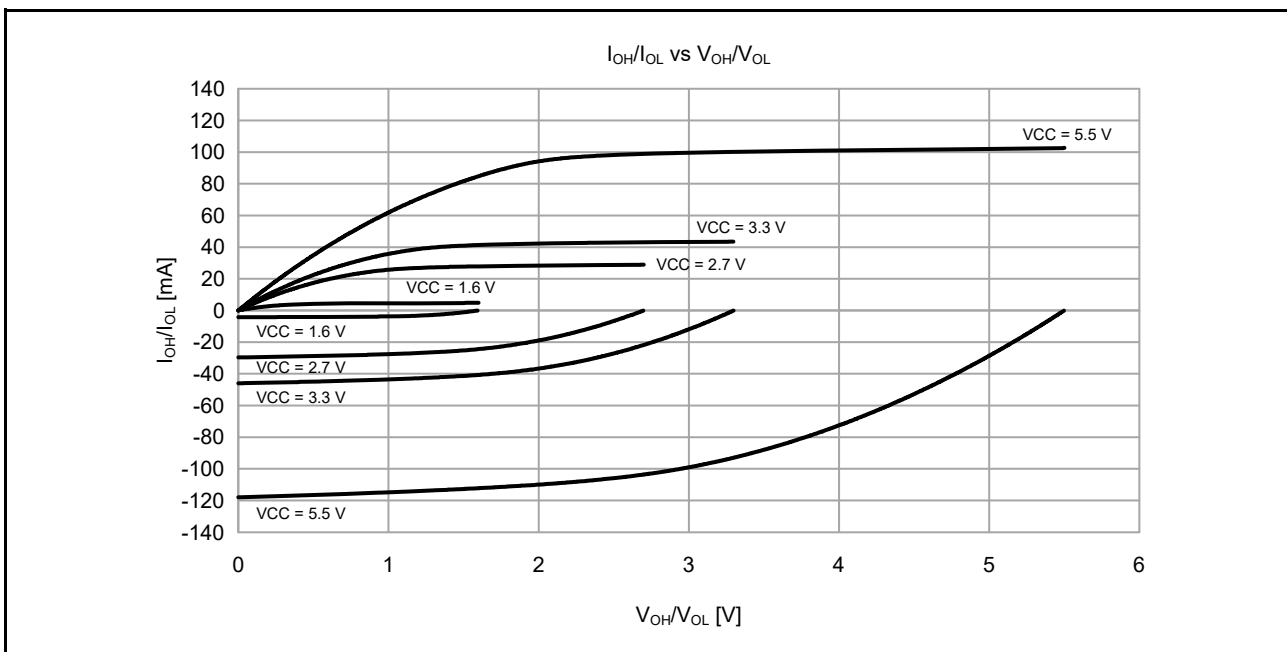


Figure 2.7 V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at $T_a = 25^\circ\text{C}$ when middle drive output is selected (reference data)

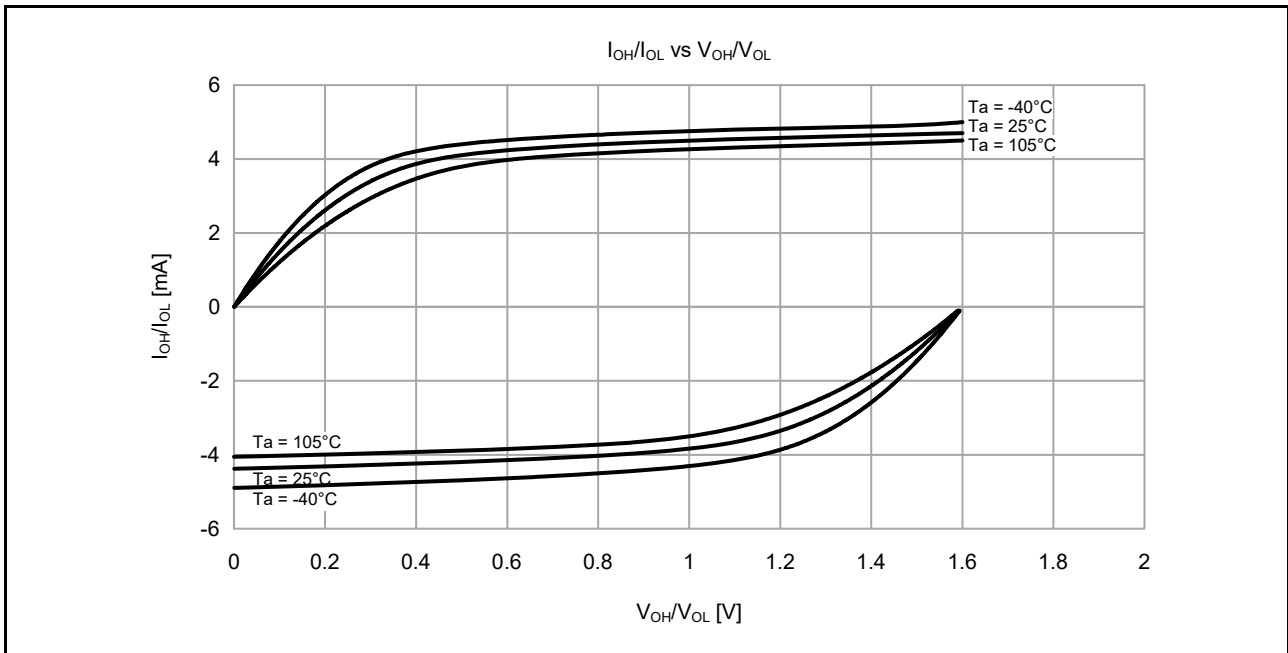


Figure 2.8 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 1.6$ V when middle drive output is selected (reference data)

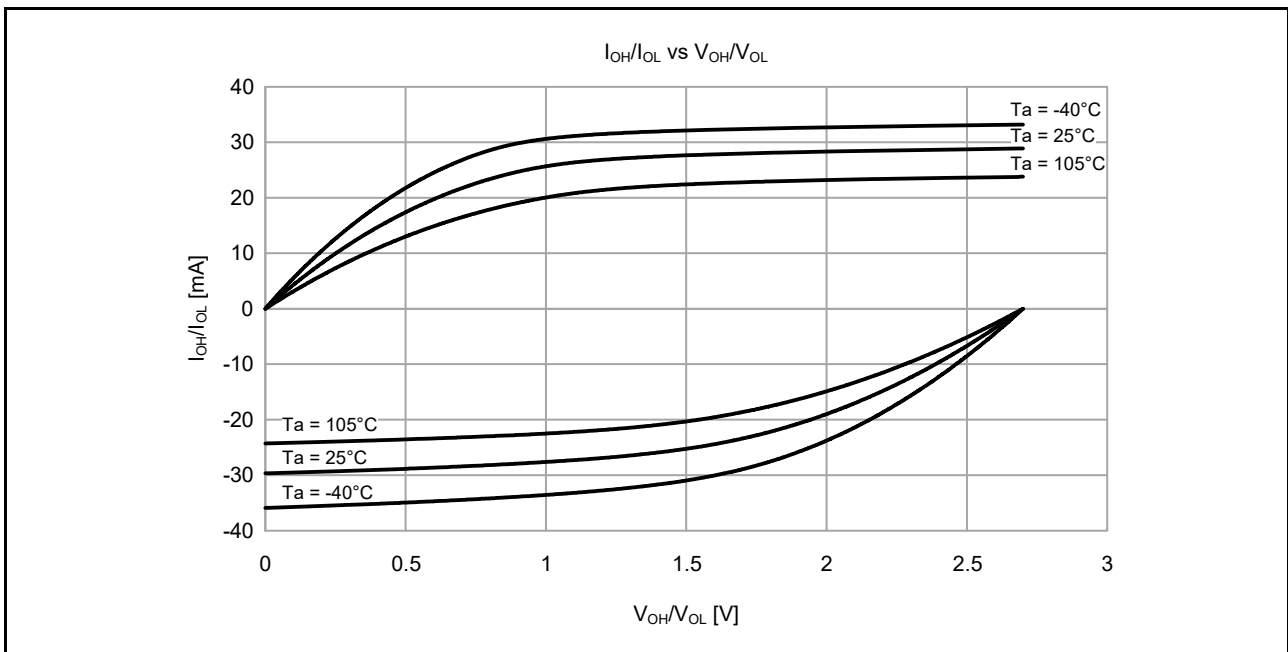


Figure 2.9 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 2.7$ V when middle drive output is selected (reference data)

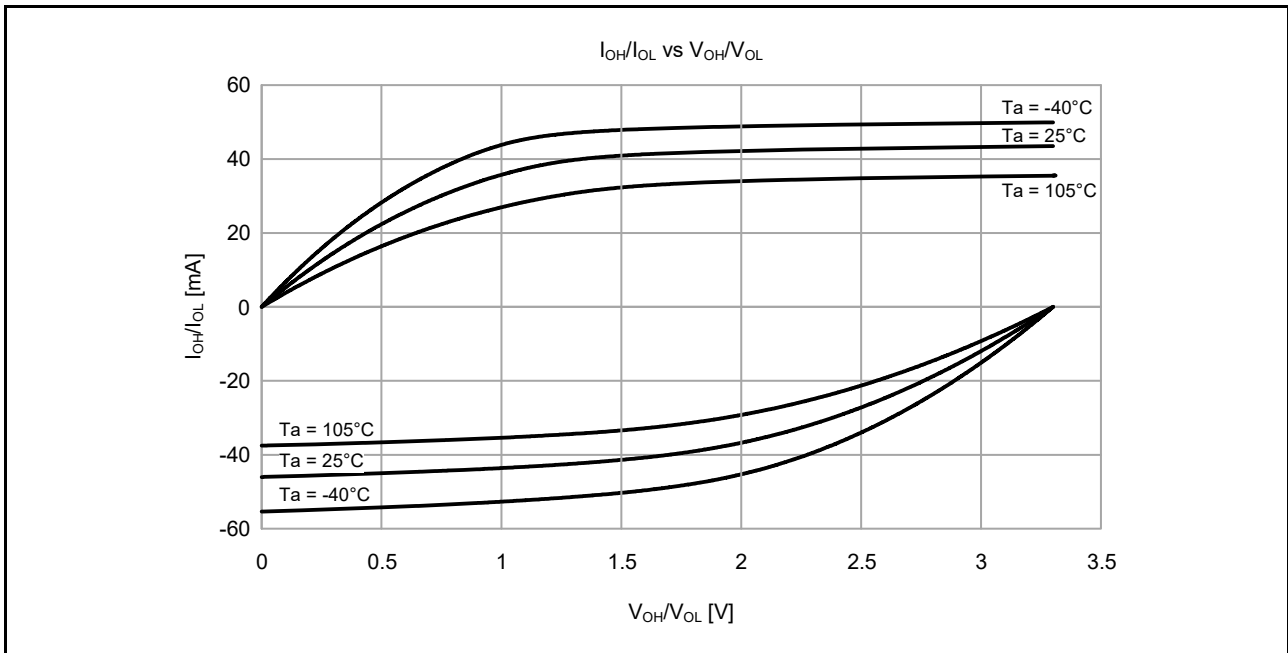


Figure 2.10 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 3.3$ V when middle drive output is selected (reference data)

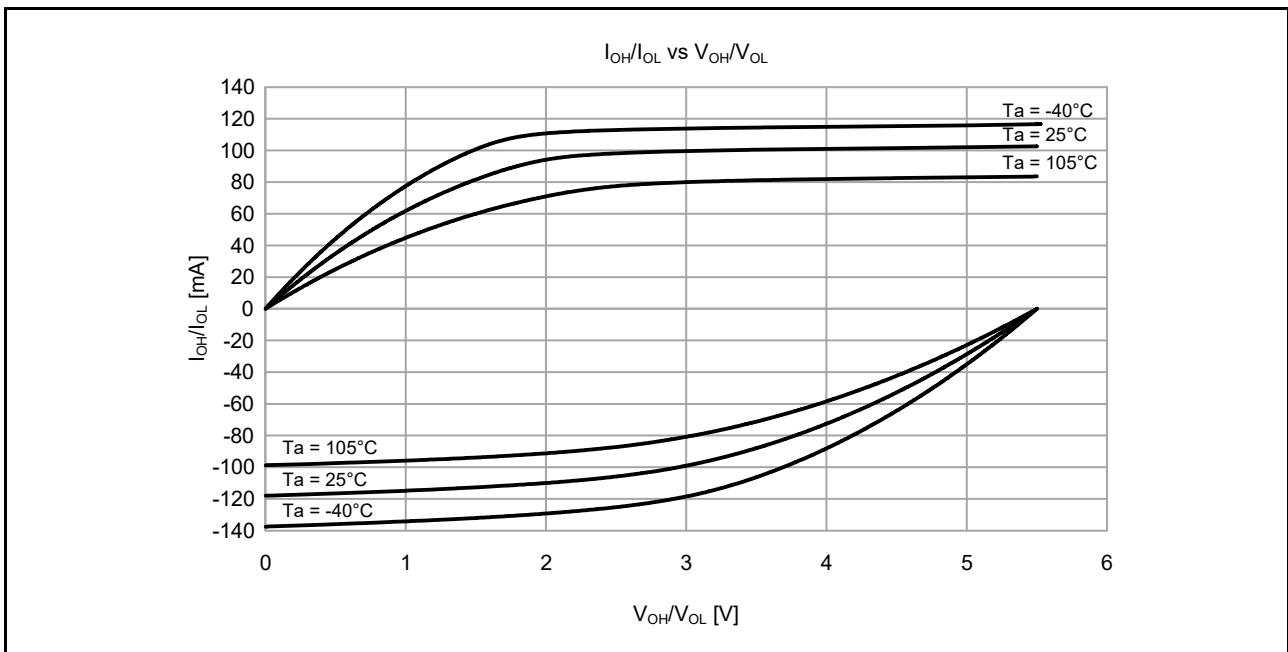


Figure 2.11 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 5.5$ V when middle drive output is selected (reference data)

2.2.7 P408, P409 I/O Pin Output Characteristics of Middle Drive Capacity

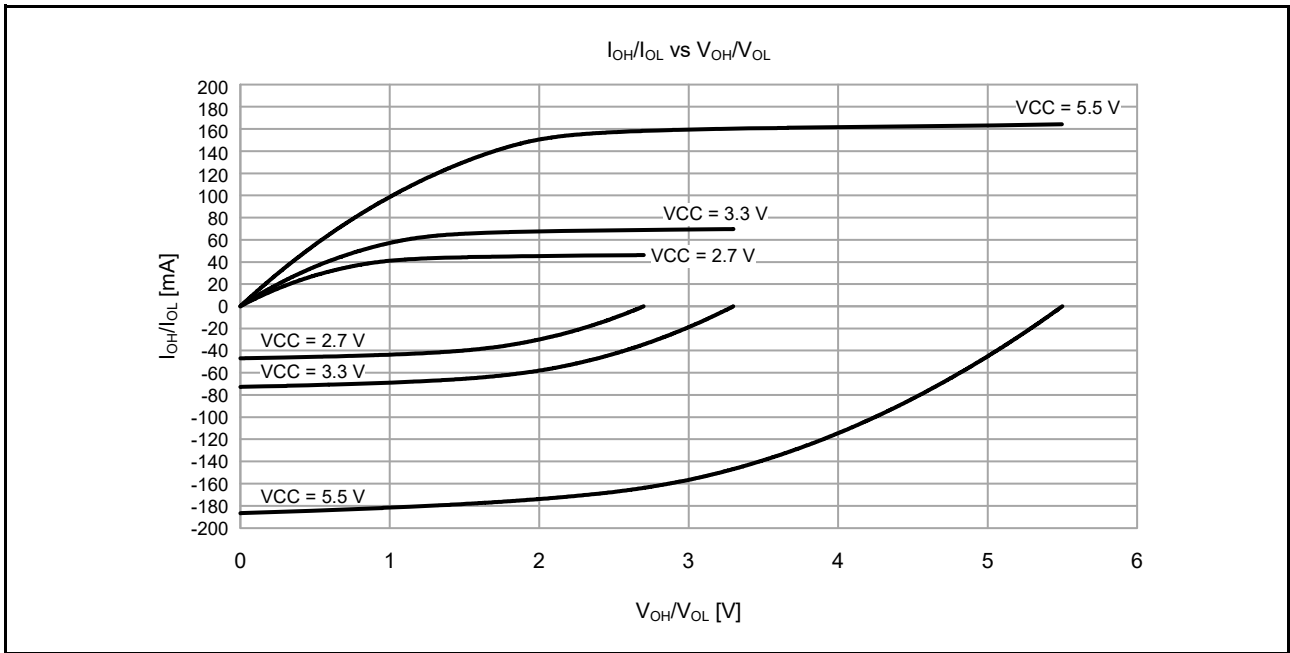


Figure 2.12 V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at $T_a = 25^\circ\text{C}$ when middle drive output is selected (reference data)

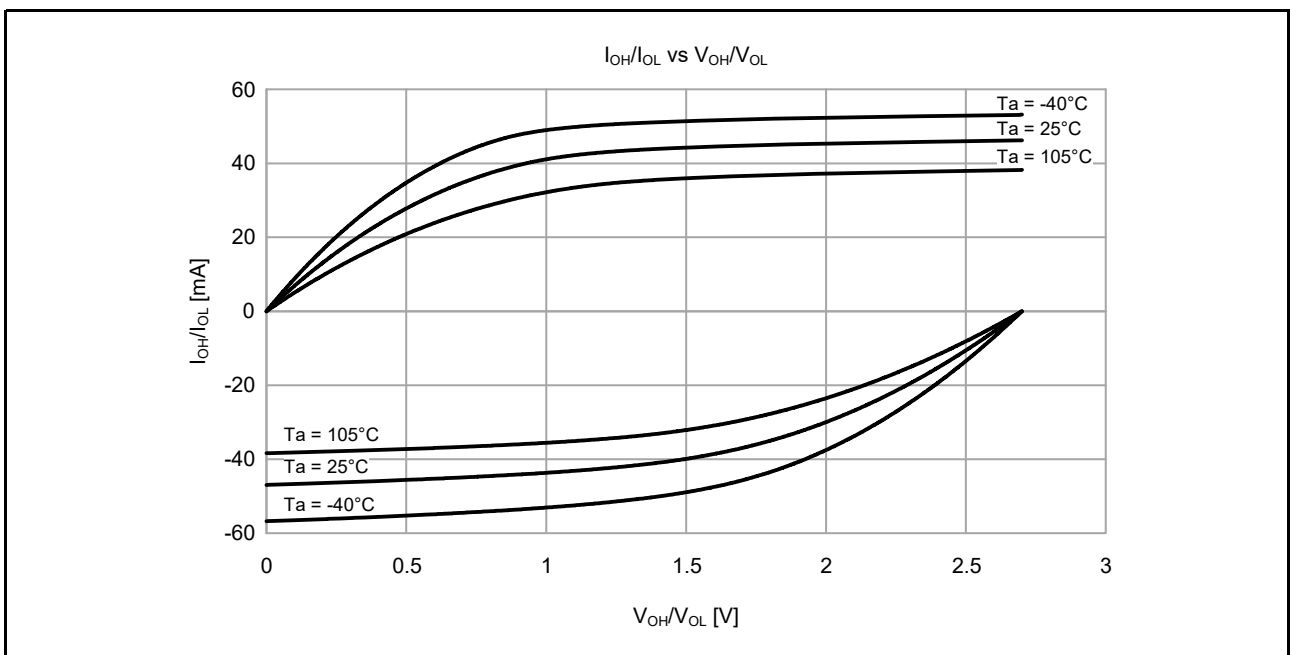


Figure 2.13 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 2.7\text{ V}$ when middle drive output is selected (reference data)

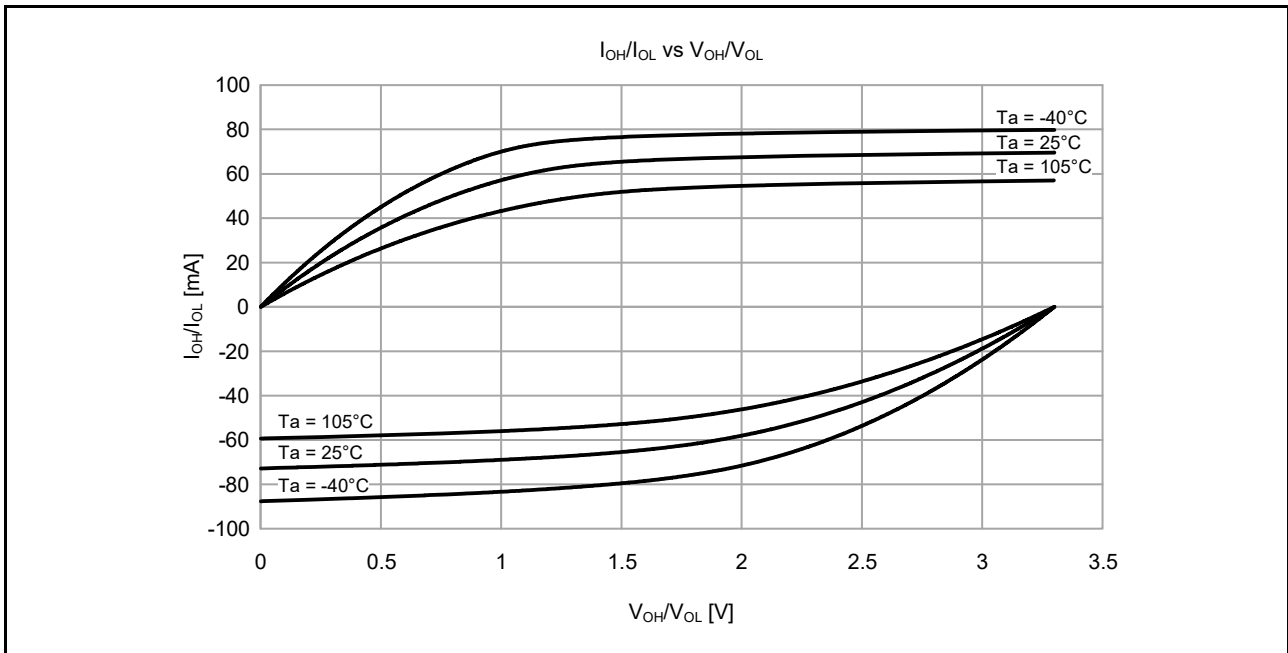


Figure 2.14 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 3.3$ V when middle drive output is selected (reference data)

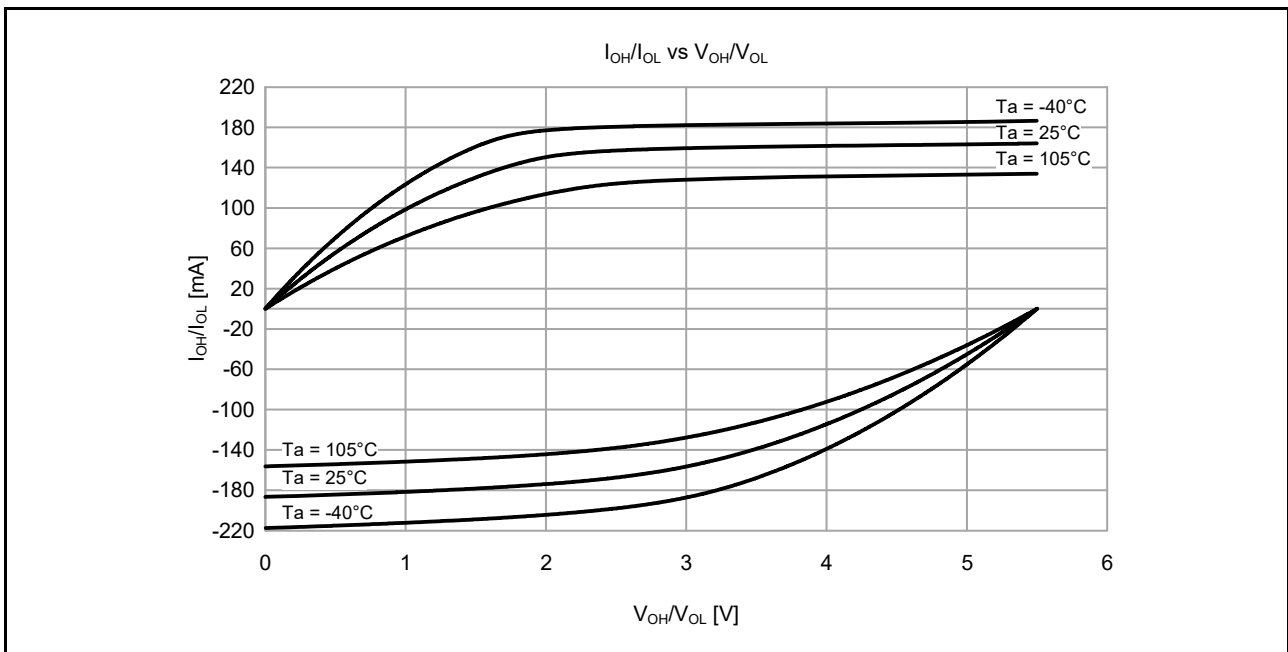


Figure 2.15 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at $V_{CC} = 5.5$ V when middle drive output is selected (reference data)

2.2.8 IIC I/O Pin Output Characteristics

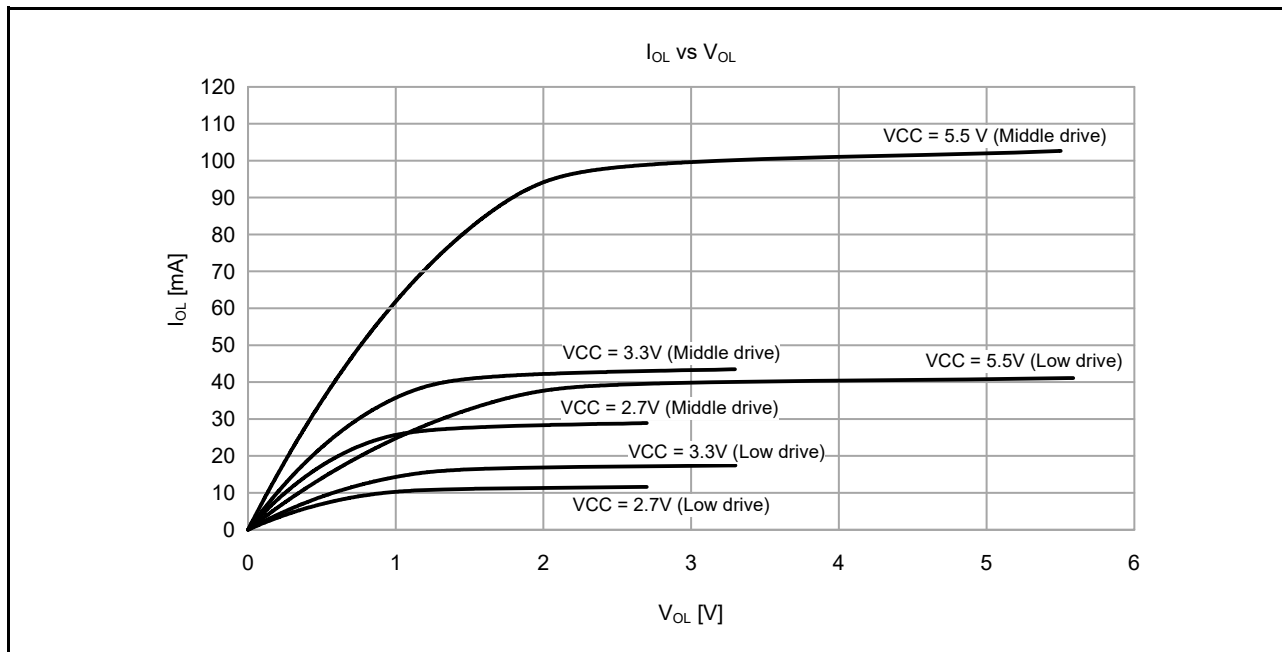


Figure 2.16 V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at Ta = 25°C

2.2.9 Operating and Standby Current

Table 2.11 Operating and standby current (1) (1 of 2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter					Symbol	Typ*10	Max	Unit	Test conditions						
Supply current*1	High-speed mode*2	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 48 MHz	I _{CC}	11.8	-	mA	*7						
				ICLK = 32 MHz		8.6	-								
				ICLK = 16 MHz		5.1	-								
				ICLK = 8 MHz		3.4	-								
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 48 MHz		18.6	-								
				ICLK = 32 MHz		12.7	-								
				ICLK = 16 MHz		7.2	-								
				ICLK = 8 MHz		4.5	-								
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 48 MHz		30.1	-			*9					
				ICLK = 32 MHz		23.2	-			*8					
				ICLK = 16 MHz		12.6	-								
				ICLK = 8 MHz		7.3	-								
		All peripheral clock enabled, code executing from SRAM*5	ICLK = 48 MHz	-	75.0	*9									
			Sleep mode				I _{CC}	mA	-	-					
			All peripheral clock disabled*5	ICLK = 48 MHz	6.4	-					*7				
				ICLK = 32 MHz	4.7	-									
		ICLK = 16 MHz		3.2	-										
		ICLK = 8 MHz		2.4	-										
		All peripheral clock enabled*5	ICLK = 48 MHz	24.7	-	*9									
			ICLK = 32 MHz	19.2	-	*8									
			ICLK = 16 MHz	10.7	-										
			ICLK = 8 MHz	6.4	-										
		Increase during BGO operation*6									2.5	-	-		
		Middle-speed mode*2	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 12 MHz	I _{CC}					mA	-	*7		
ICLK = 8 MHz	3.6				-										
ICLK = 1 MHz	3.0				-										
All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 12 MHz				5.2		-								
	ICLK = 8 MHz				4.0		-								
	ICLK = 1 MHz				1.6		-								
	All peripheral clock enabled, while (1) code executing from flash*5				ICLK = 12 MHz		9.4	-	*8						
ICLK = 8 MHz					6.9		-								
ICLK = 1 MHz					2.2		-								
All peripheral clock enabled, code executing from SRAM*5					ICLK = 12 MHz		-	30.0							
	Sleep mode				I _{CC}		mA	-	-						
	All peripheral clock disabled*5									ICLK = 12 MHz				2.2	-
				ICLK = 8 MHz		2.0				-					
ICLK = 1 MHz				1.3		-									
All peripheral clock enabled*5	ICLK = 12 MHz			7.9		-				*8					
	ICLK = 8 MHz			5.9		-									
	ICLK = 1 MHz			2.1		-									
Increase during BGO operation*6						2.5				-	-				

Table 2.11 Operating and standby current (1) (2 of 2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter				Symbol	Typ*10	Max	Unit	Test conditions	
Supply current*1	Low-speed mode*3	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 1 MHz	I _{CC}	0.5	-	mA	*7
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 1 MHz		0.7	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 1 MHz		1.5	-		*8
			All peripheral clock enabled, code executing from SRAM*5	ICLK = 1 MHz		-	3.2		
		Sleep mode	All peripheral clock disabled*5	ICLK = 1 MHz		0.4	-	*7	
			All peripheral clock enabled*5	ICLK = 1 MHz		1.3	-	*8	
	Low-voltage mode*3	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 4 MHz	I _{CC}	2.5	-	mA	*7
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 4 MHz		3.0	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 4 MHz		4.5	-		*8
			All peripheral clock enabled, code executing from SRAM*5	ICLK = 4 MHz		-	11.2		
		Sleep mode	All peripheral clock disabled*5	ICLK = 4 MHz		2.0	-	*7	
			All peripheral clock enabled*5	ICLK = 4 MHz		4.0	-	*8	
Subosc-speed mode*4	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 32.768 kHz	I _{CC}	13.5	-	μA	*8	
		All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 32.768 kHz		25.0	-			
		All peripheral clock enabled, code executing from SRAM*5	ICLK = 32.768 kHz		-	214.1			
	Sleep mode	All peripheral clock disabled*5	ICLK = 32.768 kHz		9.5	-			
		All peripheral clock enabled*5	ICLK = 32.768 kHz		21.0	-			

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.

Note 2. The clock source is HOCO.

Note 3. The clock source is MOCO.

Note 4. The clock source is the sub-clock oscillator.

Note 5. This does not include BGO operation.

Note 6. This is the increase for programming or erasure of the flash memory for data storage during program execution.

Note 7. FCLK, BCLK, PCLKA, PCLKB, PCLKC and PCLKD are set to divided by 64.

Note 8. FCLK, BCLK, PCLKA, PCLKB, PCLKC and PCLKD are the same frequency as that of ICLK.

Note 9. FCLK, BCLK, and PCLKB are set to divided by 2 and PCLKA, PCLKC and PCLKD are the same frequency as that of ICLK.

Note 10. VCC = 3.3 V.

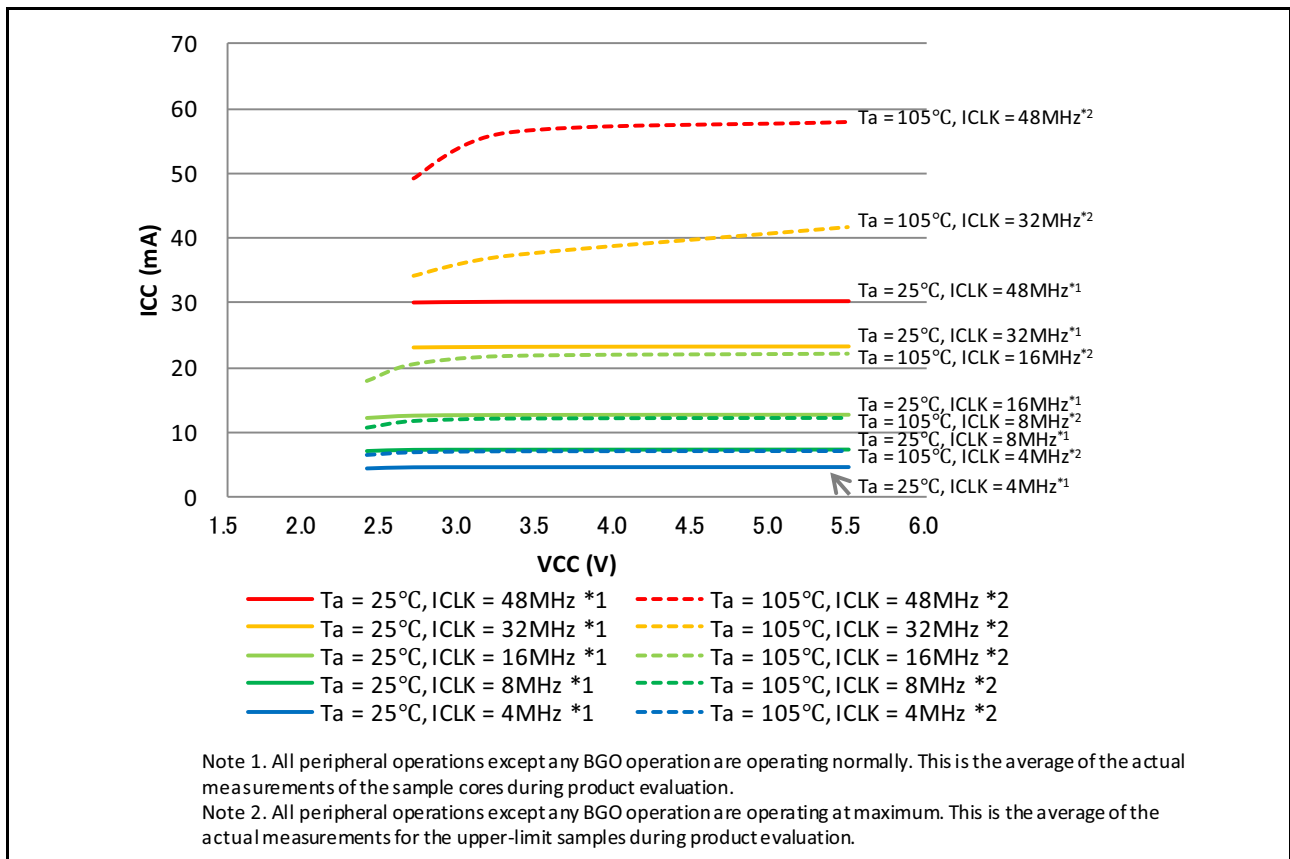


Figure 2.17 Voltage dependency in High-speed operating mode (reference data)

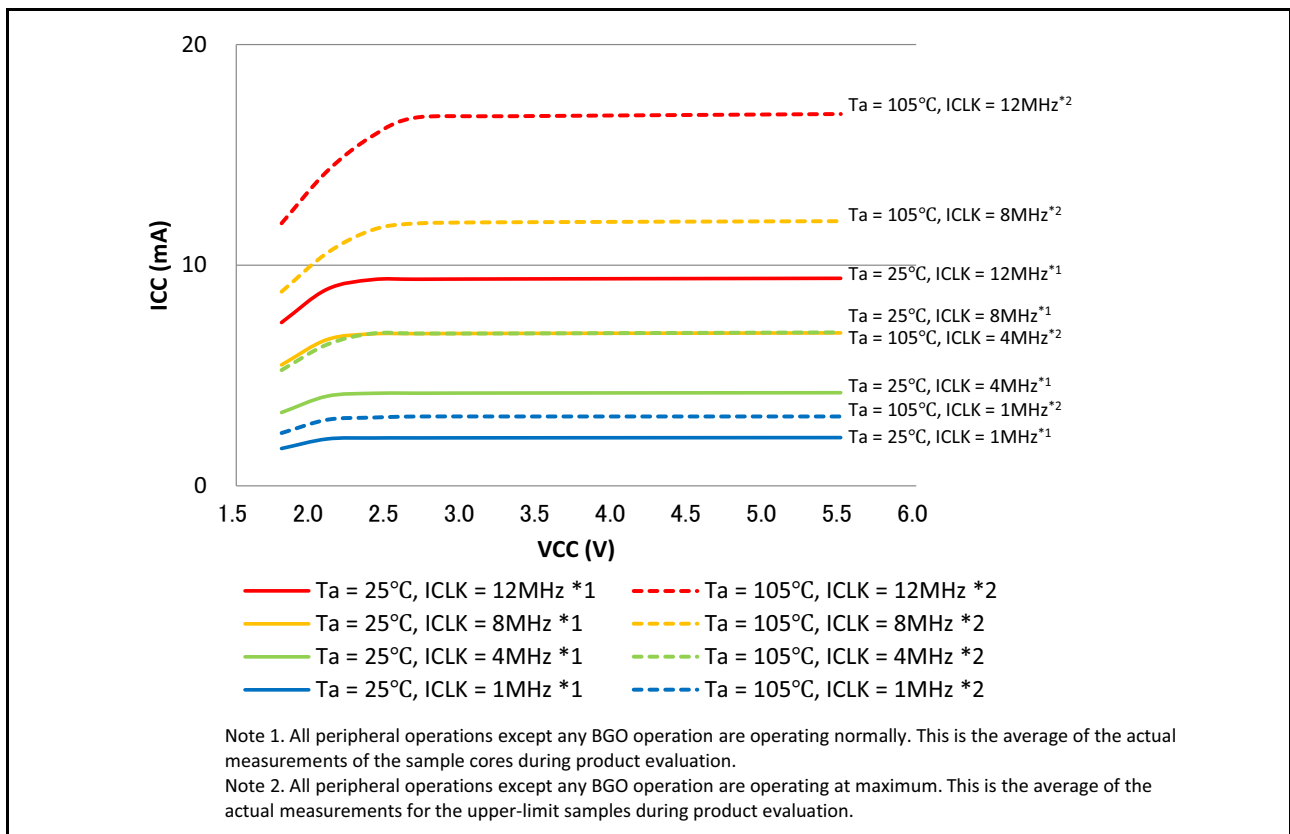


Figure 2.18 Voltage dependency in Middle-speed mode (reference data)

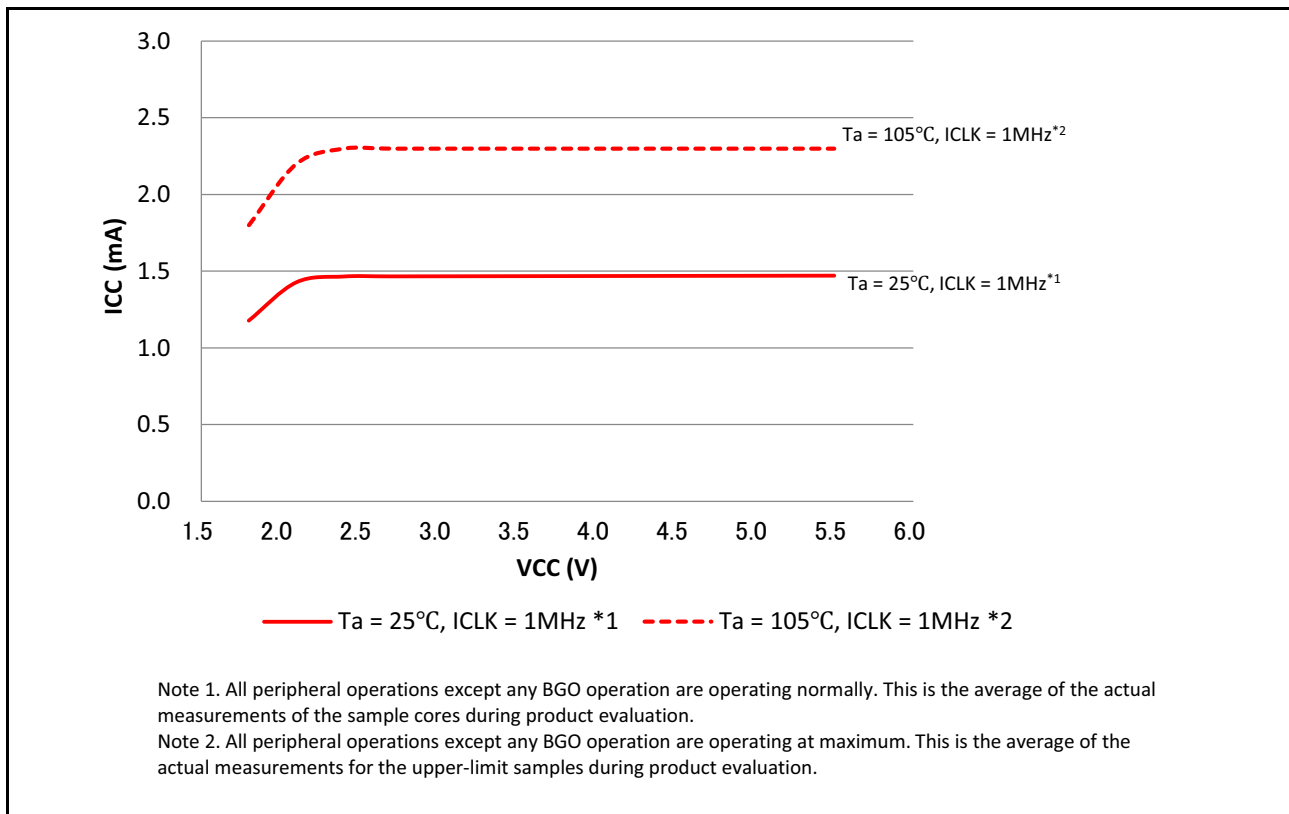


Figure 2.19 Voltage dependency in Low-speed mode (reference data)

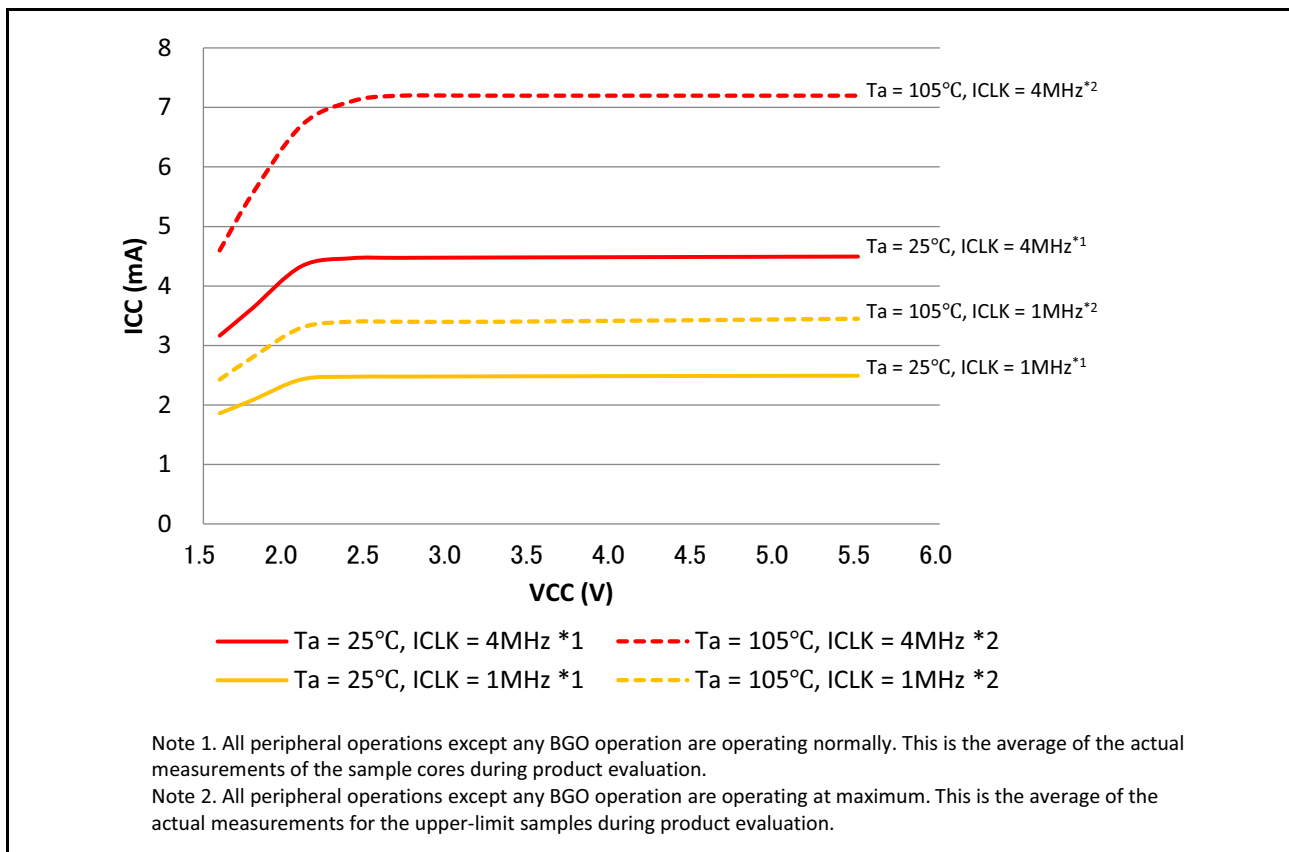


Figure 2.20 Voltage dependency in Low-voltage mode (reference data)

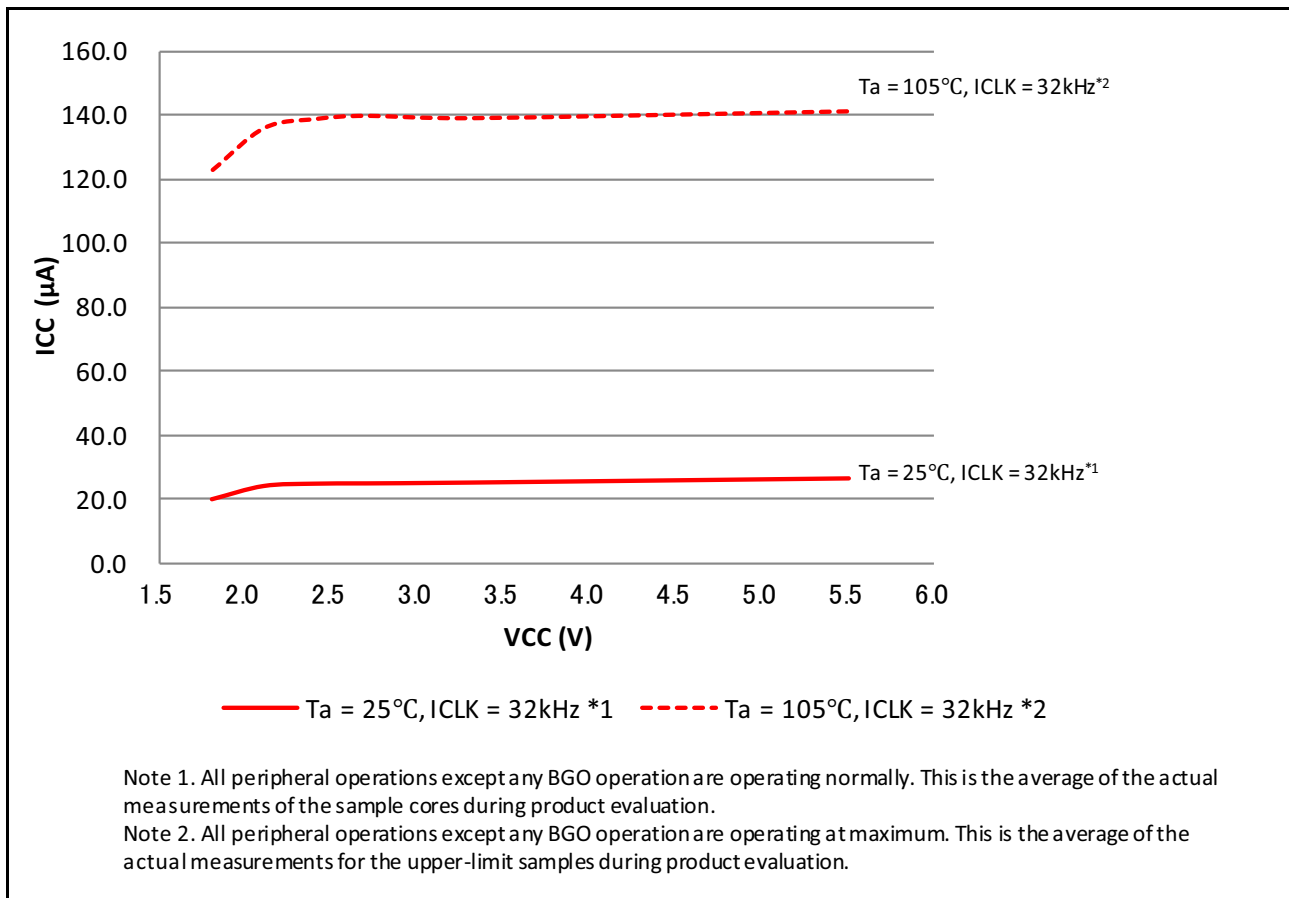


Figure 2.21 Voltage dependency in Subosc-speed mode (reference data)

Table 2.12 Operating and standby current (2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter		Symbol	Typ*4	Max	Unit	Test conditions	
Supply current*1	Software Standby mode*2	I _{CC}	T _a = 25°C	0.9	6.0	µA	PSMCR.PSMC[1:0] = 01b (48 KB SRAM on)
			T _a = 55°C	1.6	12.2		
			T _a = 85°C	4.8	27.1		
			T _a = 105°C	12.2	66.7		
			T _a = 25°C	1.1	7.5		PSMCR.PSMC[1:0] = 00b (All SRAM on)
			T _a = 55°C	2.2	17.0		
			T _a = 85°C	7.5	43.3		
			T _a = 105°C	19.6	105.9		
	Increment for RTC operation with low-speed on-chip oscillator*3			0.5	-		-
	Increment for RTC operation with sub-clock oscillator*3			0.5	-		SOMCR.SODRV[1:0] are 11b (Low power mode 3)
			1.6	-		SOMCR.SODRV[1:0] are 00b (Normal mode)	

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.

Note 2. The IWDT and LVD are not operating.

Note 3. Includes the current of sub-oscillation circuit or low-speed on-chip oscillator.

Note 4. VCC = 3.3 V.

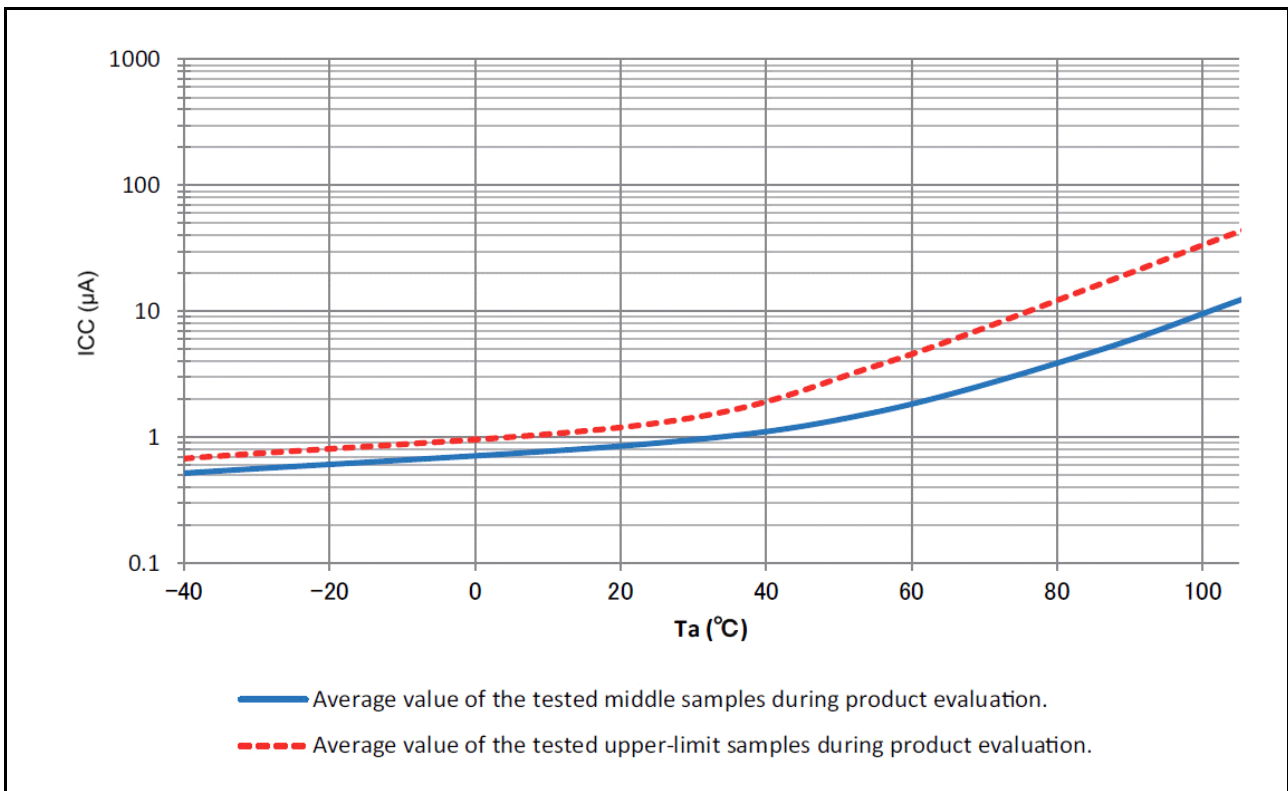


Figure 2.22 Temperature dependency in Software Standby mode 48 KB SRAM on (reference data)

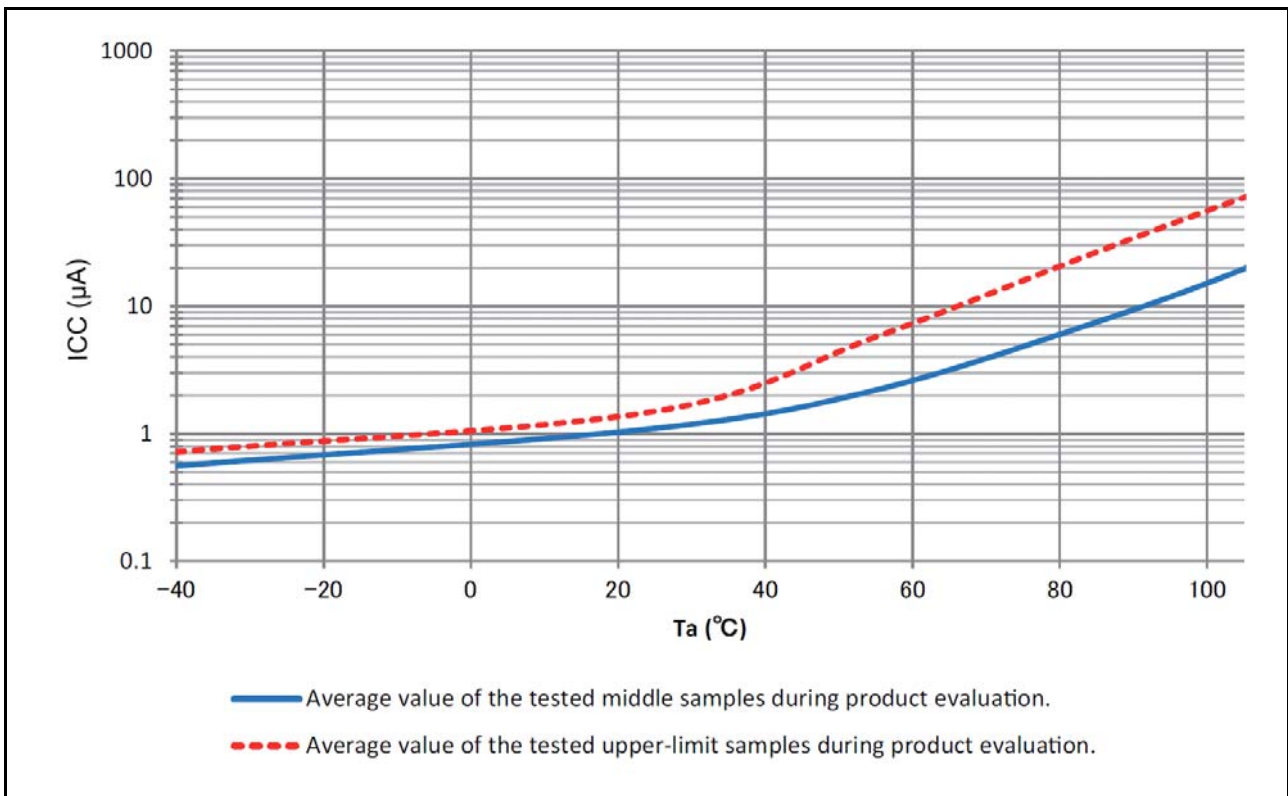


Figure 2.23 Temperature dependency in Software Standby mode all SRAM on (reference data)

Table 2.13 Operating and standby current (3)

Conditions: VCC = AVCC0 = 0V, VBATT = 1.6 to 3.6 V, VSS = AVSS0 = 0V

Parameter	Symbol	Typ	Max	Unit	Test conditions	
Supply current*1 RTC operation when VCC is off	I _{CC}	T _a = 25°C	1.1	-	µA	VBATT = 2.0 V SOMCR.SORDRV[1:0] = 11b (Low power mode 3)
		T _a = 55°C	1.2	-		
		T _a = 85°C	1.4	-		
		T _a = 105°C	1.6	-		
		T _a = 25°C	1.2	-		VBATT = 3.3 V SOMCR.SORDRV[1:0] = 11b (Low power mode 3)
		T _a = 55°C	1.3	-		
		T _a = 85°C	1.5	-		
		T _a = 105°C	1.7	-		
		T _a = 25°C	1.8	-		VBATT = 2.0 V SOMCR.SORDRV[1:0] = 00b (Normal mode)
		T _a = 55°C	2.1	-		
		T _a = 85°C	2.4	-		
		T _a = 105°C	2.7	-		
		T _a = 25°C	1.9	-		VBATT = 3.3 V SOMCR.SORDRV[1:0] = 00b (Normal mode)
		T _a = 55°C	2.2	-		
		T _a = 85°C	2.5	-		
		T _a = 105°C	2.8	-		

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.

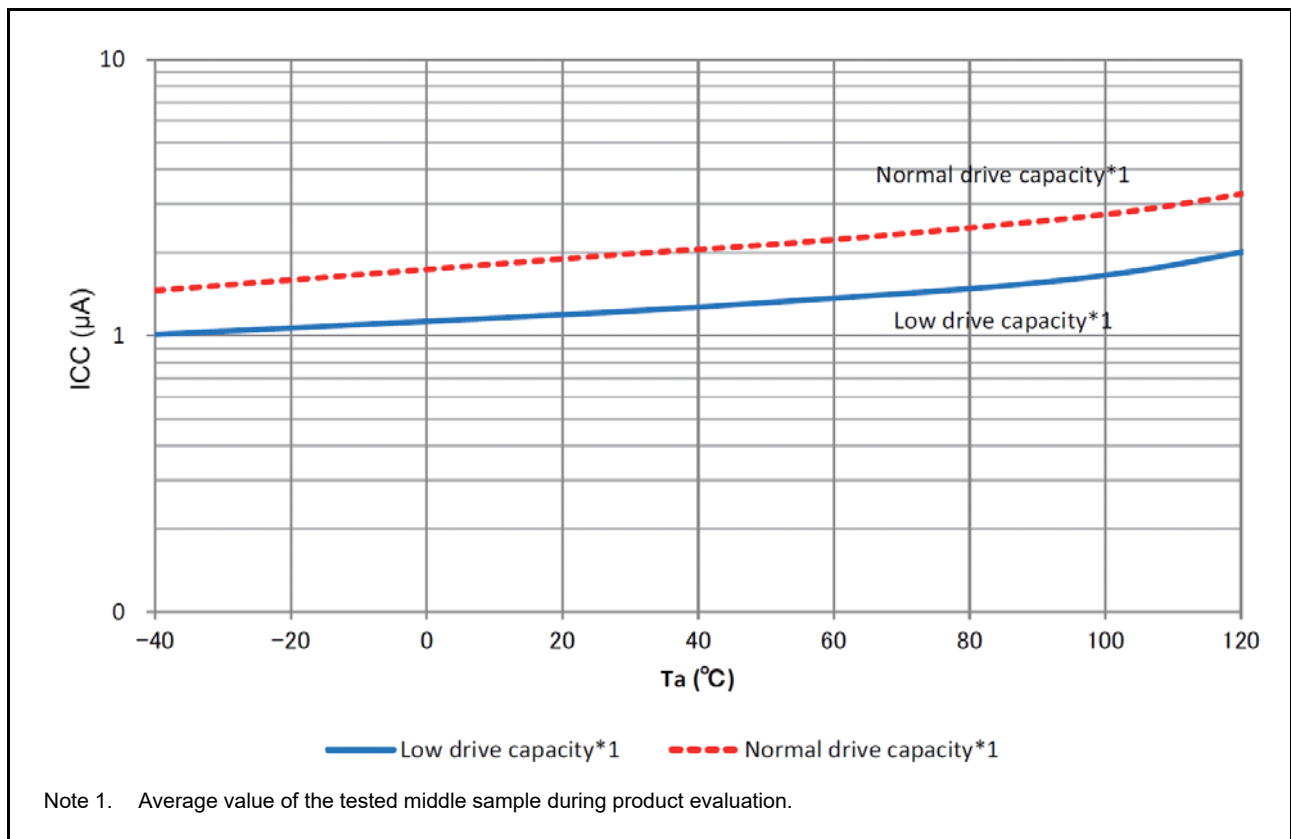


Figure 2.24 Temperature dependency of RTC operation with VCC off (reference data)

Table 2.14 Operating and standby current (4)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V, VREFH0 = 2.7 V to AVCC0

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
Analog power supply current	During A/D conversion (at high-speed conversion)		I _{AVCC}	-	-	3.0	mA	-
	During A/D conversion (at low power conversion)			-	-	1.0	mA	-
	During D/A conversion (per channel)*1			-	0.4	0.8	mA	-
	Waiting for A/D and D/A conversion (all units)*6			-	-	1.0	μA	-
Reference power supply current	During A/D conversion		I _{REFH0}	-	-	150	μA	-
	Waiting for A/D conversion (all units)			-	-	60	nA	-
	During D/A conversion		I _{REFH}	-	50	100	μA	-
	Waiting for D/A conversion (all units)			-	-	100	μA	-
Temperature sensor			I _{TNS}	-	75	-	μA	-
Low power Analog Comparator operating current	Window mode		I _{CMPLP}	-	15	-	μA	-
	Comparator High-speed mode			-	10	-	μA	-
	Comparator Low-speed mode			-	2	-	μA	-
High-Speed Analog Comparator operating current			I _{CMPHS}	-	70	100	μA	AVCC0 ≥ 2.7 V
Operational Amplifier operating current	Low power mode	1 unit operating	I _{AMP}	-	2.5	4.0	μA	-
		2 units operating		-	4.5	8.0	μA	-
		3 units operating		-	6.5	11.0	μA	-
		4 units operating		-	8.5	14.0	μA	-
	High-speed mode	1 unit operating		-	140	220	μA	-
		2 units operating		-	280	410	μA	-
		3 units operating		-	420	600	μA	-
		4 units operating		-	560	780	μA	-
LCD operating current	External resistance division method f _{LCD} = f _{SUB} = 128 Hz, 1/3 bias, and 4-time slice		I _{LCD1} *5	-	0.34	-	μA	-
	Internal voltage boosting method f _{LCD} = f _{SUB} = 128 Hz, 1/3 bias, and 4-time slice		I _{LCD2} *5	-	0.92	-	μA	-
	Capacitor split method f _{LCD} = f _{SUB} = 128 Hz, 1/3 bias, and 4-time slice		I _{LCD3} *5	-	0.19	-	μA	-
USB operating current	During USB communication operation under the following settings and conditions: • Host controller operation is set to Full-speed mode Bulk OUT transfer (64 bytes) × 1, bulk IN transfer (64 bytes) × 1 • Connect peripheral devices via a 1-meter USB cable from the USB port.		I _{USBH} *2	-	4.3 (VCC) 0.9 (VCC_USB)*4	-	mA	-
	During USB communication operation under the following settings and conditions: • Function controller operation is set to Full-speed mode Bulk OUT transfer (64 bytes) × 1, bulk IN transfer (64 bytes) × 1 • Connect the host device via a 1-meter USB cable from the USB port.		I _{USBF} *2	-	3.6 (VCC) 1.1 (VCC_USB)*4	-	mA	-
	During suspended state under the following setting and conditions: • Function controller operation is set to Full-speed mode (pull up the USB_DP pin) • Software standby mode • Connect the host device via a 1-meter USB cable from the USB port.		I _{SUSP} *3	-	0.35 (VCC) 170 (VCC_USB)*4	-	μA	-

Note 1. Includes the reference power supply current in the power supply current value for D/A conversion.

Note 2. Includes current consumed by the USBFS only.

Note 3. Includes current supplied from the pull-up resistor of the USB_DP pin to the pull-down resistor of the host device, in addition to the current consumed by the MCU during the suspended state.

Note 4. When VCC = VCC_USB = 3.3 V.

Note 5. Includes current flowing to the LCD controller only. Does not include current flowing through the LCD panel.

Note 6. When the MSTPCRD.MSTPD16 (14-Bit A/D Converter Module Stop bit) is in the module-stop state.

2.2.10 VCC Rise and Fall Gradient and Ripple Frequency

Table 2.15 Rise and fall gradient characteristics

Conditions: VCC = AVCC0 = 0 to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Power-on VCC rising gradient	Voltage monitor 0 reset disabled at startup	SrVCC	0.02	-	2	ms/V	-
	Voltage monitor 0 reset enabled at startup*1		0.02	-	-		
	SCI/USB Boot mode*2		0.02	-	2		

Note 1. When OFS1.LVDAS = 0.

Note 2. At boot mode, the reset from voltage monitor 0 is disabled regardless of the value of the OFS1.LVDAS bit.

Table 2.16 Rising and falling gradient and ripple frequency characteristics

Conditions: VCC = AVCC0 = VCC_USB = 1.6 to 5.5 V

The ripple voltage must meet the allowable ripple frequency $f_{r(VCC)}$ within the range between the VCC upper limit (5.5 V) and lower limit (1.6 V).

When VCC change exceeds VCC $\pm 10\%$, the allowable voltage change rising/falling gradient dt/dVCC must be met.

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Allowable ripple frequency	$f_{r(VCC)}$	-	-	10	kHz	Figure 2.25 $V_{r(VCC)} \leq VCC \times 0.2$
		-	-	1	MHz	Figure 2.25 $V_{r(VCC)} \leq VCC \times 0.08$
		-	-	10	MHz	Figure 2.25 $V_{r(VCC)} \leq VCC \times 0.06$
Allowable voltage change rising and falling gradient	dt/dVCC	1.0	-	-	ms/V	When VCC change exceeds VCC $\pm 10\%$

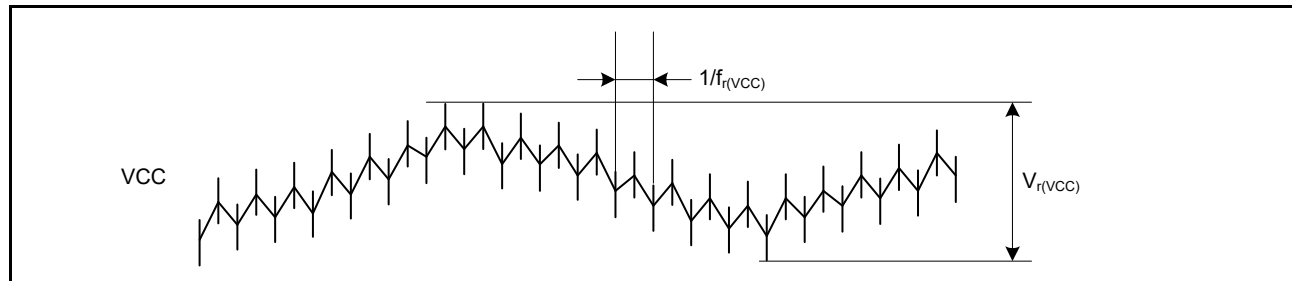


Figure 2.25 Ripple waveform

2.3 AC Characteristics

2.3.1 Frequency

Table 2.17 Operation frequency value in High-speed operating mode

Conditions: VCC = AVCC0 = 2.4 to 5.5 V

Parameter		Symbol	Min	Typ	Max*5	Unit	
Operation frequency	System clock (ICLK)*4	f	2.7 to 5.5 V	0.032768	-	48	MHz
			2.4 to 2.7 V	0.032768	-	16	
	FlashIF clock (FCLK)*1, *2, *4		2.7 to 5.5 V	0.032768	-	32	
			2.4 to 2.7 V	0.032768	-	16	
	Peripheral module clock (PCLKA)*4		2.7 to 5.5 V	-	-	48	
			2.4 to 2.7 V	-	-	16	
	Peripheral module clock (PCLKB)*4		2.7 to 5.5 V	-	-	32	
			2.4 to 2.7 V	-	-	16	
	Peripheral module clock (PCLKC)*3, *4		2.7 to 5.5 V	-	-	64	
			2.4 to 2.7 V	-	-	16	
	Peripheral module clock (PCLKD)*4		2.7 to 5.5 V	-	-	64	
			2.4 to 2.7 V	-	-	16	
	External bus clock (BCLK)*4		2.7 to 5.5 V	-	-	24	
			2.4 to 2.7 V	-	-	16	
	EBCLK pin output		2.7 to 5.5 V	-	-	12	
			2.4 to 2.7 V	-	-	8	

- Note 1. The lower-limit frequency of FCLK is 1 MHz while programming or erasing the flash memory. When using FCLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 2. The frequency accuracy of FCLK must be $\pm 3.5\%$ while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKC is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
- Note 4. See section 9, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK.
- Note 5. The maximum value of operation frequency does not include errors of the internal oscillator. The operation can be guaranteed with the errors of the internal oscillator. For details, on the range for the guaranteed operation, see [Table 2.22, Clock timing](#).

Table 2.18 Operation frequency value in Middle-speed mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter		Symbol	Min	Typ	Max ^{*5}	Unit	
Operation frequency	System clock (ICLK) ^{*4}	f	2.7 to 5.5 V	0.032768	-	12	MHz
			2.4 to 2.7 V	0.032768	-	12	
			1.8 to 2.4 V	0.032768	-	8	
	FlashIF clock (FCLK) ^{*1, *2, *4}		2.7 to 5.5 V	0.032768	-	12	
			2.4 to 2.7 V	0.032768	-	12	
			1.8 to 2.4 V	0.032768	-	8	
	Peripheral module clock (PCLKA) ^{*4}		2.7 to 5.5 V	-	-	12	
			2.4 to 2.7 V	-	-	12	
			1.8 to 2.4 V	-	-	8	
	Peripheral module clock (PCLKB) ^{*4}		2.7 to 5.5 V	-	-	12	
			2.4 to 2.7 V	-	-	12	
			1.8 to 2.4 V	-	-	8	
	Peripheral module clock (PCLKC) ^{*3, *4}		2.7 to 5.5 V	-	-	12	
			2.4 to 2.7 V	-	-	12	
			1.8 to 2.4 V	-	-	8	
	Peripheral module clock (PCLKD) ^{*4}		2.7 to 5.5 V	-	-	12	
			2.4 to 2.7 V	-	-	12	
			1.8 to 2.4 V	-	-	8	
	External bus clock (BCLK) ^{*4}		2.7 to 5.5 V	-	-	12	
			2.4 to 2.7 V	-	-	12	
			1.8 to 2.4 V	-	-	8	
EBCLK pin output	2.7 to 3.6 V	-	-	12			
	2.4 to 2.7 V	-	-	8			
	1.8 to 2.4 V	-	-	8			

- Note 1. The lower-limit frequency of FCLK is 1 MHz while programming or erasing the flash memory. When using FCLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 2. The frequency accuracy of FCLK must be $\pm 3.5\%$ while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKC is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
- Note 4. See section 9, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK.
- Note 5. The maximum value of operation frequency does not include errors of the internal oscillator. The operation can be guaranteed with the errors of the internal oscillator. For details on the range for the guaranteed operation, see [Table 2.22, Clock timing](#).

Table 2.19 Operation frequency value in Low-speed mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Typ	Max ^{*4}	Unit
Operation frequency	System clock (ICLK) ^{*3}	1.8 to 5.5 V	f	0.032768	-	1	MHz
	FlashIF clock (FCLK) ^{*1, *3}	1.8 to 5.5 V		0.032768	-	1	
	Peripheral module clock (PCLKA) ^{*3}	1.8 to 5.5 V		-	-	1	
	Peripheral module clock (PCLKB) ^{*3}	1.8 to 5.5 V		-	-	1	
	Peripheral module clock (PCLKC) ^{*2, *3}	1.8 to 5.5 V		-	-	1	
	Peripheral module clock (PCLKD) ^{*3}	1.8 to 5.5 V		-	-	1	
	External bus clock (BCLK) ^{*3}	1.8 to 5.5 V		-	-	1	
	EBCLK pin output	1.8 to 5.5 V		-	-	1	

Note 1. The lower-limit frequency of FCLK is 1 MHz while programming or erasing the flash memory.

Note 2. The lower-limit frequency of PCLKC is 1 MHz when the A/D converter is in use.

Note 3. See section 9, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK.

Note 4. The maximum value of operation frequency does not include errors of the internal oscillator. The operation can be guaranteed with the errors of the internal oscillator. For details on the range for the guaranteed operation, [Table 2.22, Clock timing](#).

Table 2.20 Operation frequency value in Low-voltage mode

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter			Symbol	Min	Typ	Max ^{*5}	Unit
Operation frequency	System clock (ICLK) ^{*4}	1.6 to 5.5 V	f	0.032768	-	4	MHz
	FlashIF clock (FCLK) ^{*1, *2, *4}	1.6 to 5.5 V		0.032768	-	4	
	Peripheral module clock (PCLKA) ^{*4}	1.6 to 5.5 V		-	-	4	
	Peripheral module clock (PCLKB) ^{*4}	1.6 to 5.5 V		-	-	4	
	Peripheral module clock (PCLKC) ^{*3, *4}	1.6 to 5.5 V		-	-	4	
	Peripheral module clock (PCLKD) ^{*4}	1.6 to 5.5 V		-	-	4	
	External bus clock (BCLK) ^{*4}	1.6 to 5.5 V		-	-	4	
	EBCLK pin output	1.8 to 5.5 V		-	-	4	
1.6 to 1.8 V		-	-	2			

Note 1. The lower-limit frequency of FCLK is 1 MHz while programming or erasing the flash memory. When using FCLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 2. The frequency accuracy of FCLK must be $\pm 3.5\%$ while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

Note 3. The lower-limit frequency of PCLKC is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-Bit A/D converter is in use.

Note 4. See section 9, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK.

Note 5. The maximum value of operation frequency does not include errors of the internal oscillator. The operation can be guaranteed with the errors of the internal oscillator. For details on the range for guaranteed operation, see [Table 2.22, Clock timing](#).

Table 2.21 Operation frequency value in Subosc-speed mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	
Operation frequency	System clock (ICLK)*3	f	1.8 to 5.5 V	27.8528	32.768	37.6832	kHz
	FlashIF clock (FCLK)*1, *3		1.8 to 5.5 V	27.8528	32.768	37.6832	
	Peripheral module clock (PCLKA)*3		1.8 to 5.5 V	-	-	37.6832	
	Peripheral module clock (PCLKB)*3		1.8 to 5.5 V	-	-	37.6832	
	Peripheral module clock (PCLKC)*2, *3		1.8 to 5.5 V	-	-	37.6832	
	Peripheral module clock (PCLKD)*3		1.8 to 5.5 V	-	-	37.6832	
	External bus clock (BCLK)*3		1.8 to 5.5 V	-	-	37.6832	
	EBCLK pin output		1.8 to 5.5 V	-	-	37.6832	

Note 1. Programming and erasing the flash memory is not possible.

Note 2. The 14-bit A/D converter cannot be used.

Note 3. See section 9, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK.

2.3.2 Clock Timing

Table 2.22 Clock timing (1 of 2)

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
EBCLK pin output cycle time	VCC = 2.7 V or above	t_{Bcyc}	83.3	-	-	ns	Figure 2.26
	VCC = 1.8 V or above		125	-	-		
	VCC = 1.6 V or above		500	-	-		
EBCLK pin output high pulse width	VCC = 2.7 V or above	t_{CH}	20	-	-	ns	
	VCC = 1.8 V or above		30	-	-		
	VCC = 1.6 V or above		150	-	-		
EBCLK pin output low pulse width	VCC = 2.7 V or above	t_{CL}	20	-	-	ns	
	VCC = 1.8 V or above		30	-	-		
	VCC = 1.6 V or above		150	-	-		
EBCLK pin output rise time	VCC = 2.7 V or above	t_{Cr}	-	-	15	ns	
	VCC = 2.4 V or above		-	-	25		
	VCC = 1.8 V or above		-	-	30		
	VCC = 1.6 V or above		-	-	50		
EBCLK pin output fall time	VCC = 2.7 V or above	t_{Cf}	-	-	15	ns	
	VCC = 2.4 V or above		-	-	25		
	VCC = 1.8 V or above		-	-	30		
	VCC = 1.6 V or above		-	-	50		
EXTAL external clock input cycle time		t_{Xcyc}	50	-	-	ns	Figure 2.27
EXTAL external clock input high pulse width		t_{XH}	20	-	-	ns	
EXTAL external clock input low pulse width		t_{XL}	20	-	-	ns	
EXTAL external clock rising time		t_{Xr}	-	-	5	ns	
EXTAL external clock falling time		t_{Xf}	-	-	5	ns	
EXTAL external clock input wait time*1		t_{EXWT}	0.3	-	-	μ s	
EXTAL external clock input frequency		f_{EXTAL}	-	-	20	MHz	2.4 \leq VCC \leq 5.5
			-	-	8		1.8 \leq VCC < 2.4
			-	-	1		1.6 \leq VCC < 1.8
Main clock oscillator oscillation frequency		f_{MAIN}	1	-	20	MHz	2.4 \leq VCC \leq 5.5
			1	-	8		1.8 \leq VCC < 2.4
			1	-	4		1.6 \leq VCC < 1.8
LOCO clock oscillation frequency		f_{LOCO}	27.8528	32.768	37.6832	kHz	-

Table 2.22 Clock timing (2 of 2)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions		
LOCO clock oscillation stabilization time	t_{LOCO}	-	-	100	μs	Figure 2.28		
IWDT-dedicated clock oscillation frequency	f_{ILOCO}	12.75	15	17.25	kHz	-		
MOCO clock oscillation frequency	f_{MOCO}	6.8	8	9.2	MHz	-		
MOCO clock oscillation stabilization time	t_{MOCO}	-	-	1	μs	-		
HOCO clock oscillation frequency	f_{HOCO24}	23.64	24	24.36	MHz	Ta = -40 to -20°C 1.8 ≤ VCC ≤ 5.5		
		22.68	24	25.32		Ta = -40 to 85°C 1.6 ≤ VCC < 1.8		
		23.76	24	24.24		Ta = -20 to 85°C 1.8 ≤ VCC ≤ 5.5		
		23.52	24	24.48		Ta = 85 to 105°C 2.4 ≤ VCC ≤ 5.5		
	f_{HOCO32}	31.52	32	32.48		Ta = -40 to -20°C 1.8 ≤ VCC ≤ 5.5		
		30.24	32	33.76		Ta = -40 to 85°C 1.6 ≤ VCC < 1.8		
		31.68	32	32.32		Ta = -20 to 85°C 1.8 ≤ VCC ≤ 5.5		
		31.36	32	32.64		Ta = 85 to 105°C 2.4 ≤ VCC ≤ 5.5		
	f_{HOCO48}^{*4}	47.28	48	48.72		Ta = -40 to -20°C 1.8 ≤ VCC ≤ 5.5		
		47.52	48	48.48		Ta = -20 to 85°C 1.8 ≤ VCC ≤ 5.5		
		47.04	48	48.96		Ta = 85 to 105°C 2.4 ≤ VCC ≤ 5.5		
	f_{HOCO64}^{*5}	63.04	64	64.96		Ta = -40 to -20°C 2.4 ≤ VCC ≤ 5.5		
		63.36	64	64.64		Ta = -20 to 85°C 2.4 ≤ VCC ≤ 5.5		
		62.72	64	65.28		Ta = 85 to 105°C 2.4 ≤ VCC ≤ 5.5		
	HOCO clock oscillation stabilization time ^{*6, *7}	Except Low-Voltage mode	t_{HOCO24}	-		-	μs	Figure 2.29
			t_{HOCO32}	-		-		
t_{HOCO48}			-	-				
t_{HOCO64}			-	-				
Low-Voltage mode		t_{HOCO24}	-	-				
		t_{HOCO32}	-	-				
		t_{HOCO48} t_{HOCO64}	-	-				
PLL input frequency ^{*2}	f_{PLLIN}	4	-	12.5	MHz	-		
PLL circuit oscillation frequency ^{*2}	f_{PLL}	24	-	64	MHz	-		
PLL clock oscillation stabilization time ^{*8}	t_{PLL}	-	-	55.5	μs	Figure 2.31		
PLL free-running oscillation frequency	f_{PLLFR}	-	8	-	MHz	-		
Sub-clock oscillator oscillation frequency	f_{SUB}	-	32.768	-	kHz	-		
Sub-clock oscillation stabilization time ^{*3}	t_{SUBOSC}	-	0.5	-	s	Figure 2.32		

Note 1. Time until the clock can be used after the main clock oscillator stop bit (MOSCCR.MOSTP) is set to 0 (operating) when the external clock is stable.

Note 2. The VCC range that the PLL can be used is 2.4 to 5.5 V.

Note 3. After changing the setting of the SOSCCR.SOSTP bit to start sub-clock oscillator operation, only start using the sub-clock oscillator after the sub-clock oscillation stabilization wait time elapsed. Use the oscillator wait time value recommended by the oscillator manufacturer.

Note 4. The 48-MHz HOCO can be used within a VCC range of 1.8 V to 5.5 V.

Note 5. The 64-MHz HOCO can be used within a VCC range of 2.4 V to 5.5 V.

Note 6. This is a characteristic when HOCOCCR.HCSTP bit is set to 0 (oscillation) in MOCO stop state.

When HOCOCCR.HCSTP bit is set to 0 (oscillation) during MOCO oscillation, this specification is shortened by 1 μs .

Note 7. Whether stabilization time has elapsed can be confirmed by OSCSF.HOCOSF.

Note 8. This is a characteristic when PLLCR.PLLSTP bit is set to 0 (operation) in MOCO stop state.

When PLLCR.PLLSTP bit is set to 0 (operation) during MOCO oscillation, this specification is shortened by 1 μs .

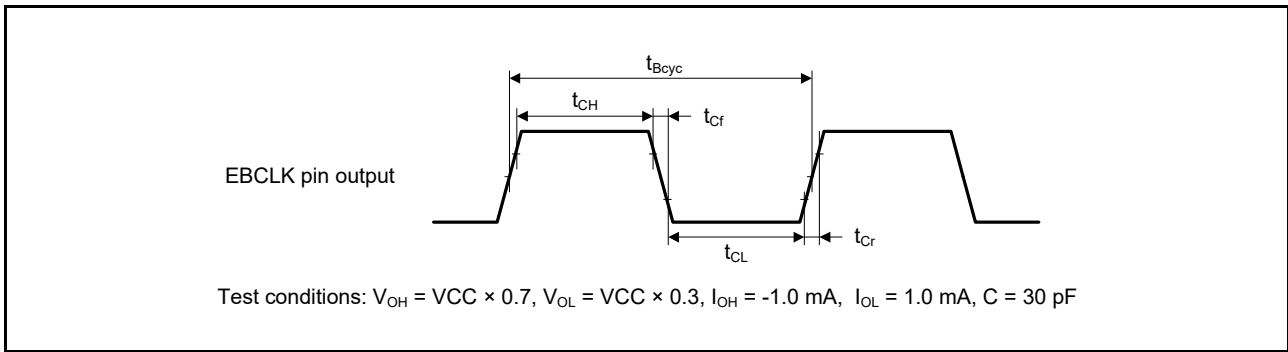


Figure 2.26 EBCLK pin output timing

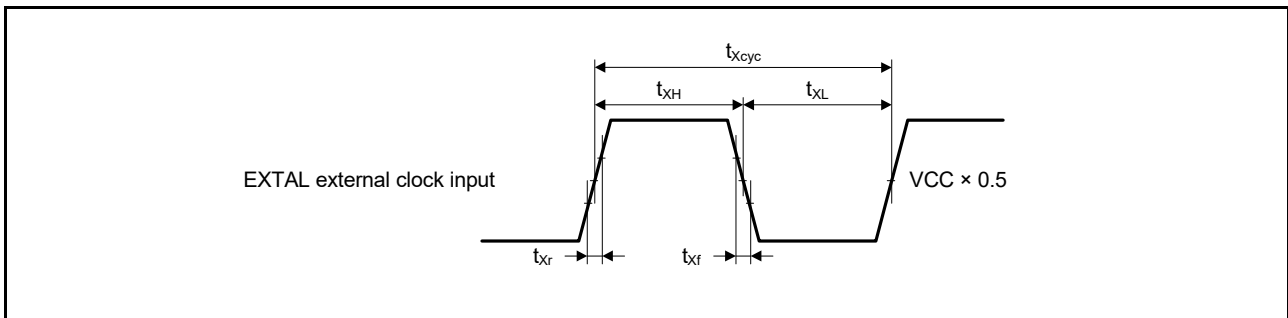


Figure 2.27 EXTAL external clock input timing

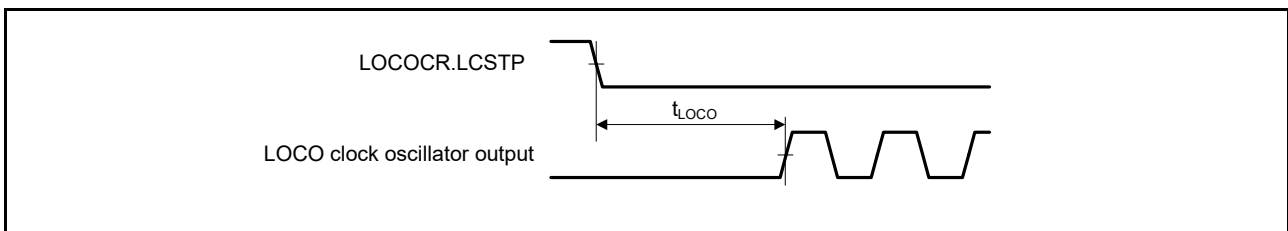


Figure 2.28 LOCO clock oscillation start timing

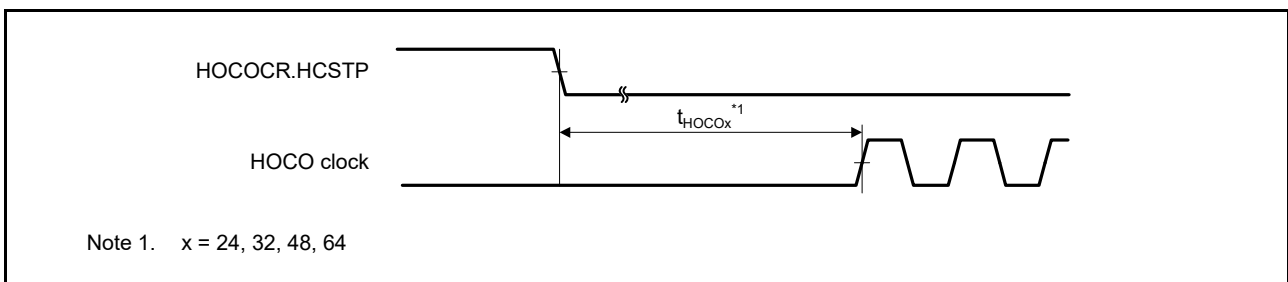


Figure 2.29 HOCO clock oscillation start timing (started by setting HOCOCR.HCSTP bit)

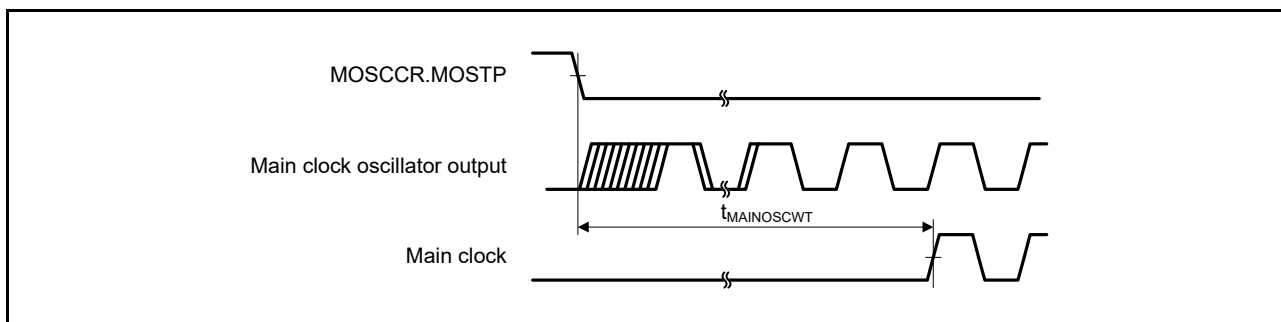


Figure 2.30 Main clock oscillation start timing

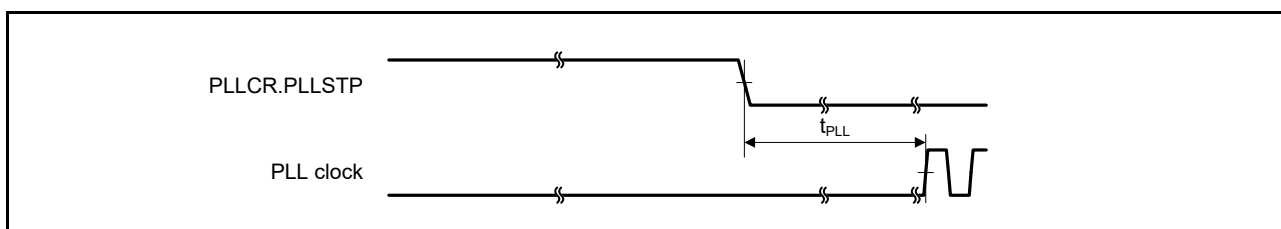


Figure 2.31 PLL clock oscillation start timing (PLL is operated after main clock oscillation has settled)

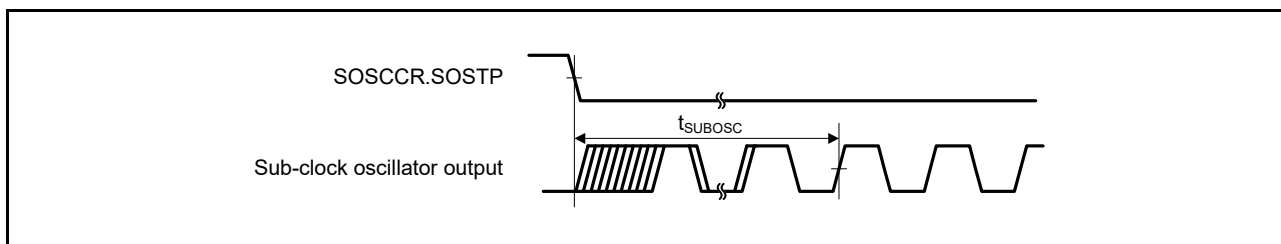


Figure 2.32 Sub-clock oscillation start timing

2.3.3 Reset Timing

Table 2.23 Reset timing

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
RES pulse width	At power-on	t_{RESWP}	3	-	-	ms	Figure 2.33
	Other than above	t_{RESW}	30	-	-	μ s	Figure 2.34
Wait time after RES cancellation (at power-on)	LVD0: enable*1	t_{RESWT}	-	0.7	-	ms	Figure 2.33
	LVD0: disable*2		-	0.3	-		
Wait time after RES cancellation (during powered-on state)	LVD0: enable*1	t_{RESWT2}	-	0.5	-	ms	Figure 2.34
	LVD0: disable*2		-	0.05	-		
Wait time after internal reset cancellation (Watchdog timer reset, SRAM parity error reset, SRAM ECC error reset, bus master MPU error reset, bus slave MPU error reset, stack pointer error reset, software reset)	LVD0: enable*1	t_{RESWT3}	-	0.6	-	ms	
	LVD0: disable*2		-	0.15	-		

Note 1. When OFS1.LVDAS = 0.

Note 2. When OFS1.LVDAS = 1.

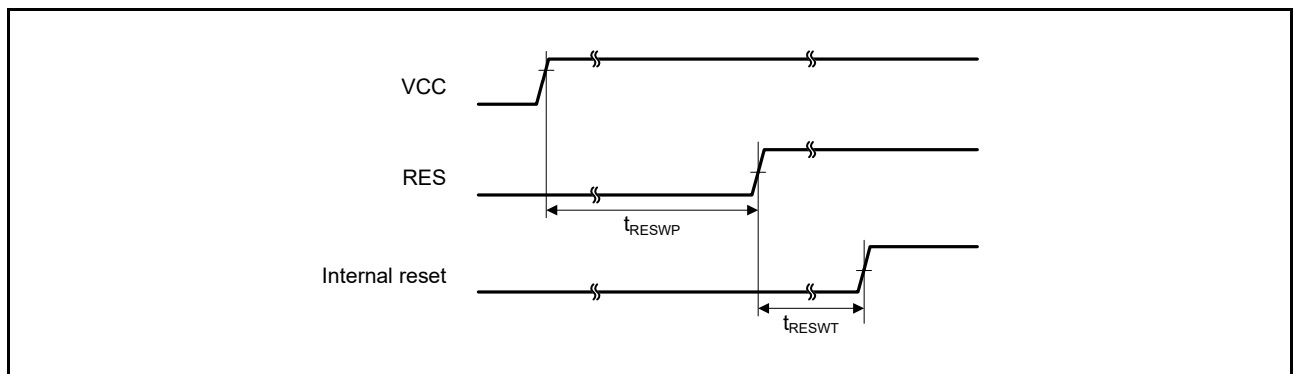


Figure 2.33 Reset input timing at power-on

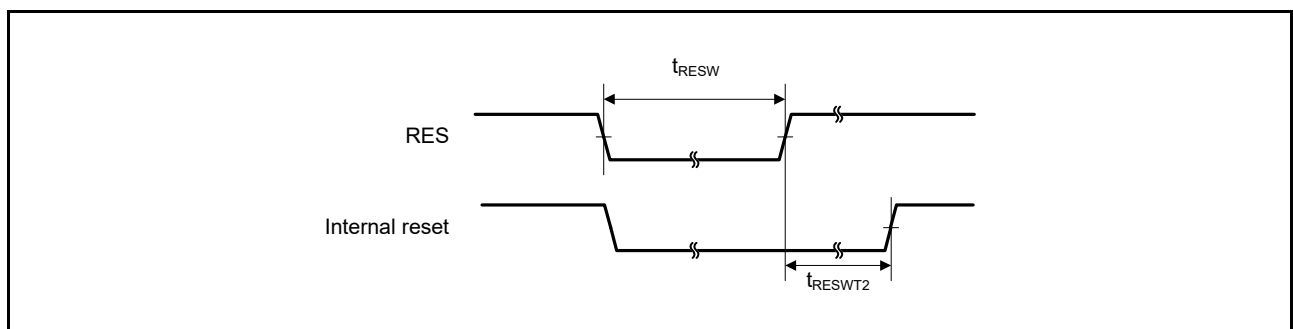


Figure 2.34 Reset input timing (1)

2.3.4 Wakeup Time

Table 2.24 Timing of recovery from Low power modes (1)

Parameter				Symbol	Min	Typ	Max	Unit	Test conditions	
Recovery time from Software Standby mode*1	High-speed mode	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator (20 MHz)*2	t _{SBYMC}	-	2	3	ms	Figure 2.35	
			System clock source is PLL (48 MHz) with Main clock oscillator*2	t _{SBYPC}	-	2	3	ms		
		External clock input to main clock oscillator	System clock source is main clock oscillator (20 MHz)*3	t _{SBYEX}	-	14	25	μs		
			System clock source is PLL (48 MHz) with Main clock oscillator*3	t _{SBYPE}	-	53	76	μs		
		System clock source is HOCO*4 (HOCO clock is 32 MHz)			t _{SBYHO}	-	43	52		μs
		System clock source is HOCO*4 (HOCO clock is 48 MHz)			t _{SBYHO}	-	44	52		μs
		System clock source is HOCO*5 (HOCO clock is 64 MHz)			t _{SBYHO}	-	82	110		μs
		System clock source is MOCO			t _{SBYMO}	-	16	25		μs

Note 1. The division ratio of ICK, BCK, FCK, and PCKx is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source.

Note 2. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h.

Note 3. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h.

Note 4. The HOCO Clock Wait Control Register (HOCOWTCR) is set to 05h.

Note 5. The HOCO Clock Wait Control Register (HOCOWTCR) is set to 06h.

Table 2.25 Timing of Recovery from Low power modes (2)

Parameter				Symbol	Min	Typ	Max	Unit	Test conditions	
Recovery time from Software Standby mode*1	Middle-speed mode	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator (12 MHz)*2	t _{SBYMC}	-	2	3	ms	Figure 2.35	
			System clock source is PLL (24 MHz) with Main clock oscillator*2	t _{SBYPC}	-	2	3	ms		
		External clock input to main clock oscillator	System clock source is main clock oscillator (12 MHz)*3	t _{SBYEX}	-	2.9	10	μs		
			System clock source is PLL (24 MHz) with Main clock oscillator*3	t _{SBYPE}	-	49	76	μs		
		System clock source is HOCO*4			t _{SBYHO}	-	38	50		μs
		System clock source is MOCO			t _{SBYMO}	-	3.5	5.5		μs

Note 1. The division ratio of ICK, BCK, FCK, and PCKx is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source.

Note 2. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h.

Note 3. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h.

Note 4. The system clock is 12 MHz.

Table 2.26 Timing of recovery from Low power modes (3)

Parameter				Symbol	Min	Typ	Max	Unit	Test conditions
Recovery time from Software Standby mode*1	Low-speed mode	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator (1 MHz)*2	t_{SBYMC}	-	2	3	ms	Figure 2.35
		External clock input to main clock oscillator	System clock source is main clock oscillator (1 MHz)*3	t_{SBYEX}	-	28	50	μ s	
		System clock source is MOCO		t_{SBYMO}	-	25	35	μ s	

Note 1. The division ratio of ICK, BCK, FCK, and PCKx is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source.

Note 2. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h.

Note 3. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h.

Table 2.27 Timing of recovery from Low power modes (4)

Parameter				Symbol	Min	Typ	Max	Unit	Test conditions
Recovery time from Software Standby mode*1	Low-voltage mode	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator (4 MHz)*2	t_{SBYMC}	-	2	3	ms	Figure 2.35
		External clock input to main clock oscillator	System clock source is main clock oscillator (4 MHz)*3	t_{SBYEX}	-	108	130	μ s	
		System clock source is HOCO		t_{SBYHO}	-	108	130	μ s	

Note 1. The division ratio of ICK, BCK, FCK, and PCKx is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source. When multiple oscillators are active, the recovery time can be determined by the following expression.

Note 2. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h.

Note 3. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h.

Table 2.28 Timing of recovery from Low power modes (5)

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
Recovery time from Software Standby mode*1	Subosc-speed mode	System clock source is sub-clock oscillator (32.768 kHz)	t_{SBYSC}	-	0.85	1	ms	Figure 2.35
		System clock source is LOCO (32.768 kHz)	t_{SBYLO}	-	0.85	1.2	ms	

Note 1. The sub-clock oscillator or LOCO itself continues to oscillate in Software Standby mode during Subosc-speed mode.

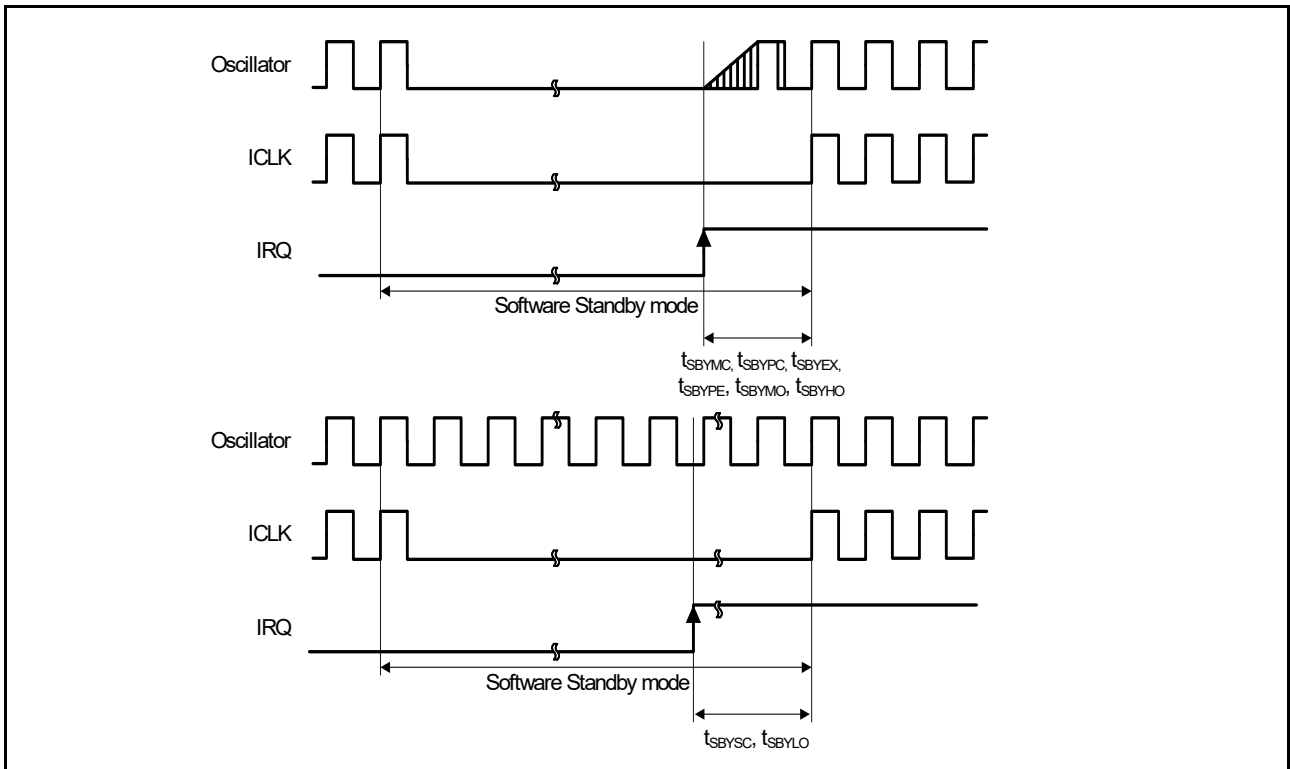


Figure 2.35 Software Standby mode cancellation timing

Table 2.29 Timing of recovery from Low power modes (6)

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Recovery time from Software Standby mode to Snooze mode	High-speed mode System clock source is HOCO	t_{SNZ}	-	36	45	μs	Figure 2.36
	Middle-speed mode System clock source is MOCO	t_{SNZ}	-	1.3	3.6	μs	
	Low-speed mode System clock source is MOCO	t_{SNZ}	-	10	13	μs	
	Low-voltage mode System clock source is HOCO	t_{SNZ}	-	87	110	μs	

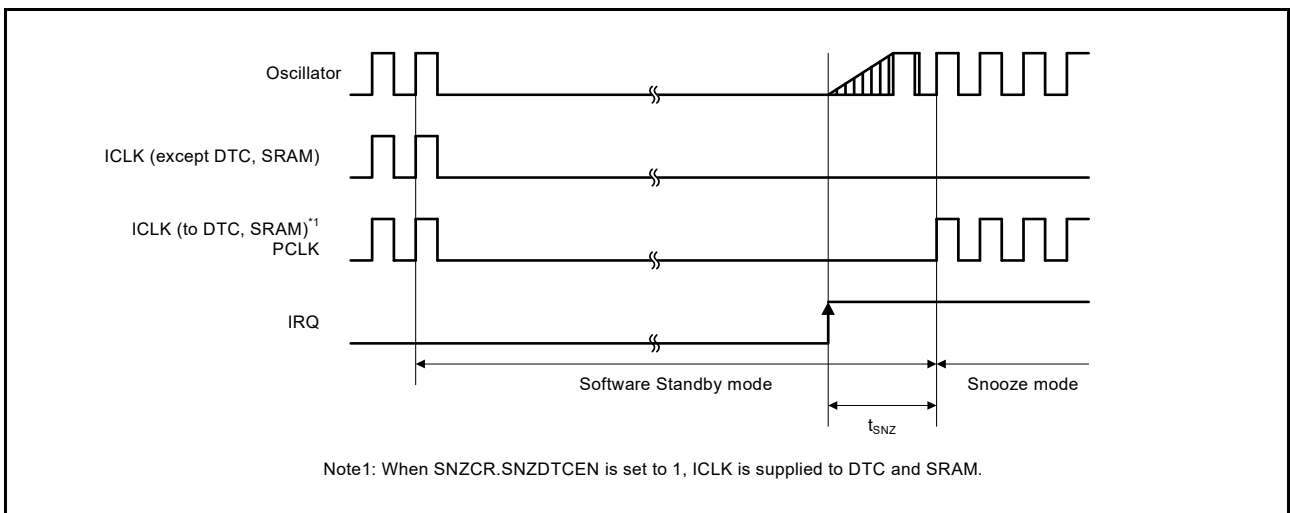


Figure 2.36 Recovery timing from Software Standby mode to Snooze mode

2.3.5 NMI and IRQ Noise Filter

Table 2.30 NMI and IRQ noise filter

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
NMI pulse width	t_{NMIW}	200	-	-	ns	NMI digital filter disabled	$t_{\text{Pcyc}} \times 2 \leq 200$ ns
		$t_{\text{Pcyc}} \times 2^{*1}$	-	-			$t_{\text{Pcyc}} \times 2 > 200$ ns
		200	-	-		NMI digital filter enabled	$t_{\text{NMICK}} \times 3 \leq 200$ ns
		$t_{\text{NMICK}} \times 3.5^{*2}$	-	-			$t_{\text{NMICK}} \times 3 > 200$ ns
IRQ pulse width	t_{IRQW}	200	-	-	ns	IRQ digital filter disabled	$t_{\text{Pcyc}} \times 2 \leq 200$ ns
		$t_{\text{Pcyc}} \times 2^{*1}$	-	-			$t_{\text{Pcyc}} \times 2 > 200$ ns
		200	-	-		IRQ digital filter enabled	$t_{\text{IRQCK}} \times 3 \leq 200$ ns
		$t_{\text{IRQCK}} \times 3.5^{*3}$	-	-			$t_{\text{IRQCK}} \times 3 > 200$ ns

Note: 200 ns minimum in Software Standby mode.

Note 1. t_{Pcyc} indicates the cycle of PCLKB.

Note 2. t_{NMICK} indicates the cycle of the NMI digital filter sampling clock.

Note 3. t_{IRQCK} indicates the cycle of the IRQ_i digital filter sampling clock (i = 0 to 15).

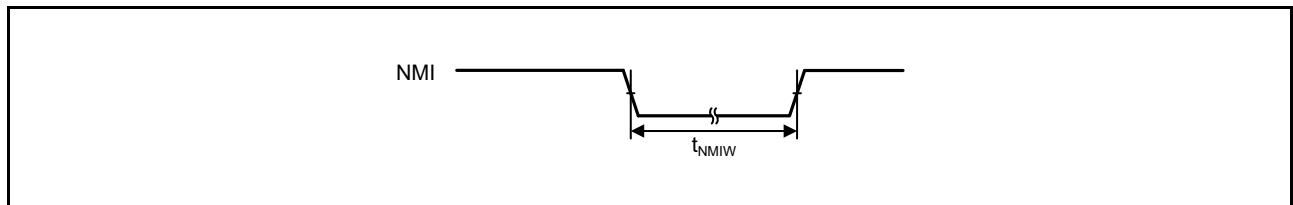


Figure 2.37 NMI interrupt input timing

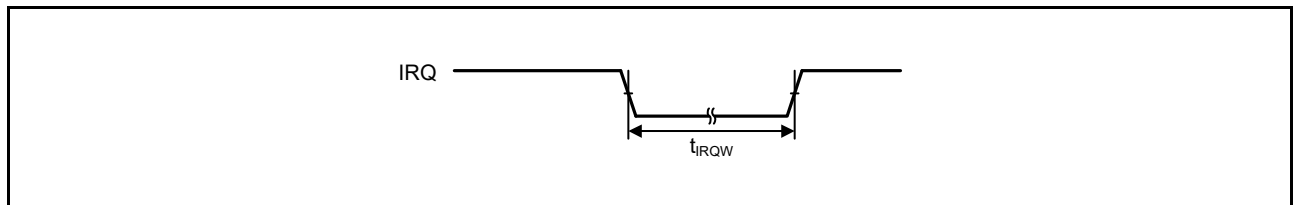


Figure 2.38 IRQ interrupt input timing

2.3.6 Bus Timing

Table 2.31 Bus timing (1)

Conditions: Low drive output is selected in the Port Drive Capability bit in PmnPFS register

VCC = AVCC0 = 2.7 to 5.5 V

Output load conditions: $V_{OH} = VCC \times 0.5$, $V_{OL} = VCC \times 0.5$, C = 30 pF

Parameter	Symbol	Min	Max	Unit	Test conditions
Address delay	t_{AD}	-	55	ns	Figure 2.39 to Figure 2.42
Byte control delay	t_{BCD}	-	55	ns	
CS delay	t_{CSD}	-	55	ns	
RD delay	t_{RSD}	-	55	ns	
Read data setup time	t_{RDS}	37	-	ns	
Read data hold time	t_{RDH}	0	-	ns	
WR delay	t_{WRD}	-	55	ns	
Write data delay	t_{WDD}	-	55	ns	
Write data hold time	t_{WDH}	0	-	ns	Figure 2.43
WAIT setup time	t_{WTS}	37	-	ns	
WAIT hold time	t_{WTH}	0	-	ns	

Table 2.32 Bus timing (2)

Conditions: Low drive output is selected in the Port Drive Capability bit in the PmnPFS register

VCC = AVCC0 = 2.4 to 2.7 V

Output load conditions: $V_{OH} = VCC \times 0.5$, $V_{OL} = VCC \times 0.5$, C = 30 pF

Parameter	Symbol	Min	Max	Unit	Test conditions
Address delay	t_{AD}	-	55	ns	Figure 2.39 to Figure 2.42
Byte control delay	t_{BCD}	-	55	ns	
CS delay	t_{CSD}	-	55	ns	
RD delay	t_{RSD}	-	55	ns	
Read data setup time	t_{RDS}	45	-	ns	
Read data hold time	t_{RDH}	0	-	ns	
WR delay	t_{WRD}	-	55	ns	
Write data delay	t_{WDD}	-	55	ns	
Write data hold time	t_{WDH}	0	-	ns	Figure 2.43
WAIT setup time	t_{WTS}	45	-	ns	
WAIT hold time	t_{WTH}	0	-	ns	

Table 2.33 Bus timing (3) (1 of 2)

Conditions: Low drive output is selected in the Port Drive Capability bit in the PmnPFS register

VCC = AVCC0 = 1.8 to 2.4 V

Output load conditions: $V_{OH} = VCC \times 0.5$, $V_{OL} = VCC \times 0.5$, C = 30 pF

Parameter	Symbol	Min	Max	Unit	Test conditions
Address delay	t_{AD}	-	90	ns	Figure 2.39 to Figure 2.42
Byte control delay	t_{BCD}	-	90	ns	
CS delay	t_{CSD}	-	90	ns	
RD delay	t_{RSD}	-	90	ns	
Read data setup time	t_{RDS}	70	-	ns	
Read data hold time	t_{RDH}	0	-	ns	
WR delay	t_{WRD}	-	90	ns	
Write data delay	t_{WDD}	-	90	ns	
Write data hold time	t_{WDH}	0	-	ns	

Table 2.33 Bus timing (3) (2 of 2)

Conditions: Low drive output is selected in the Port Drive Capability bit in the PmnPFS register

VCC = AVCC0 = 1.8 to 2.4 V

Output load conditions: $V_{OH} = VCC \times 0.5$, $V_{OL} = VCC \times 0.5$, $C = 30$ pF

Parameter	Symbol	Min	Max	Unit	Test conditions
WAIT setup time	t_{WTS}	70	-	ns	Figure 2.43
WAIT hold time	t_{WTH}	0	-	ns	

Table 2.34 Bus timing (4)

Conditions: Low drive output is selected in the Port Drive Capability bit in the PmnPFS register

VCC = AVCC0 = 1.6 to 1.8 V

Output load conditions: $V_{OH} = VCC \times 0.5$, $V_{OL} = VCC \times 0.5$, $C = 30$ pF

Parameter	Symbol	Min	Max	Unit	Test conditions
Address delay	t_{AD}	-	120	ns	Figure 2.39 to Figure 2.42
Byte control delay	t_{BCD}	-	120	ns	
CS delay	t_{CSD}	-	120	ns	
RD delay	t_{RSD}	-	120	ns	
Read data setup time	t_{RDS}	90	-	ns	
Read data hold time	t_{RDH}	0	-	ns	
WR delay	t_{WRD}	-	120	ns	
Write data delay	t_{WDD}	-	120	ns	
Write data hold time	t_{WDH}	0	-	ns	
WAIT setup time	t_{WTS}	90	-	ns	Figure 2.43
WAIT hold time	t_{WTH}	0	-	ns	

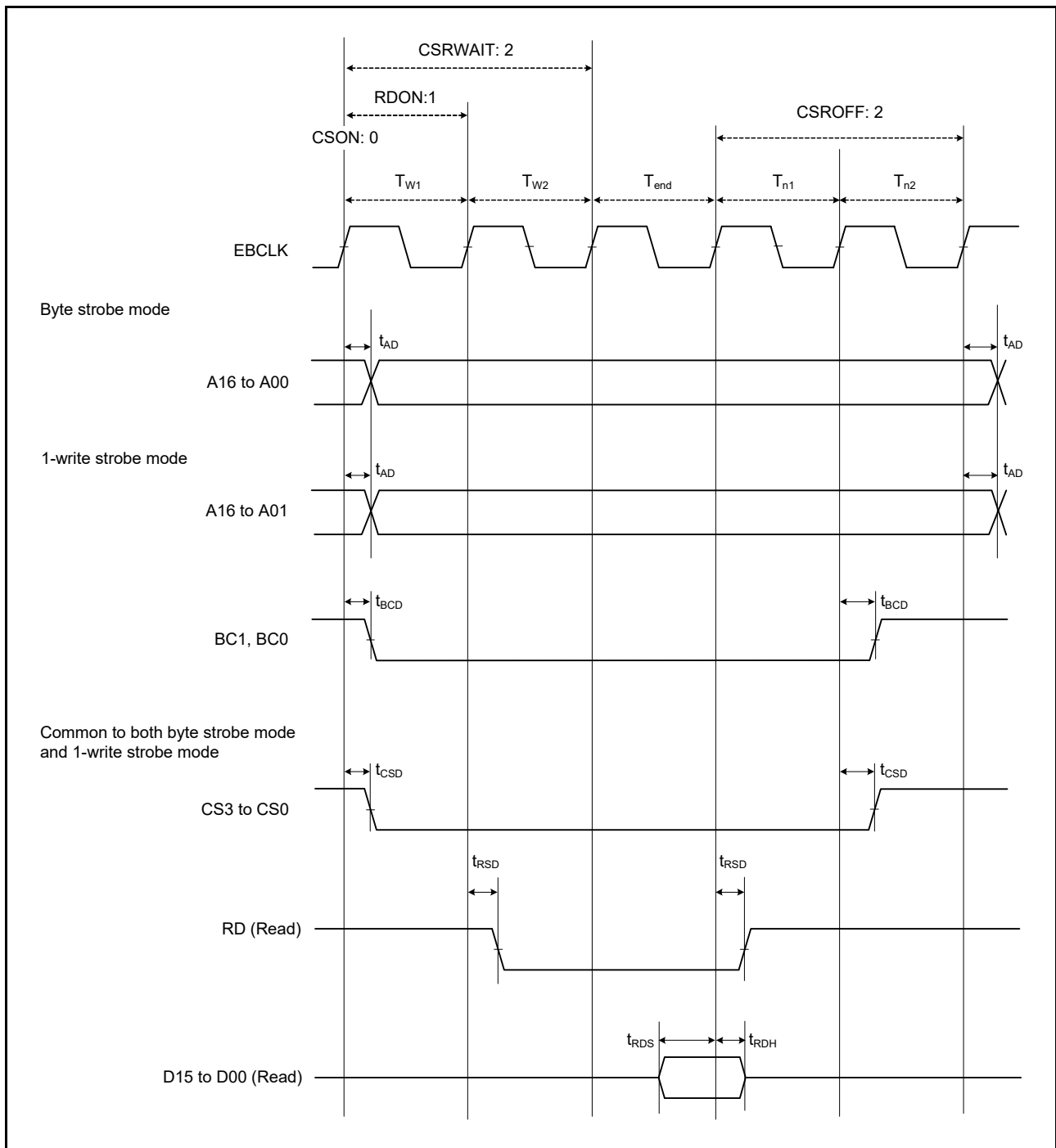


Figure 2.39 External bus timing/normal read cycle (bus clock synchronized)

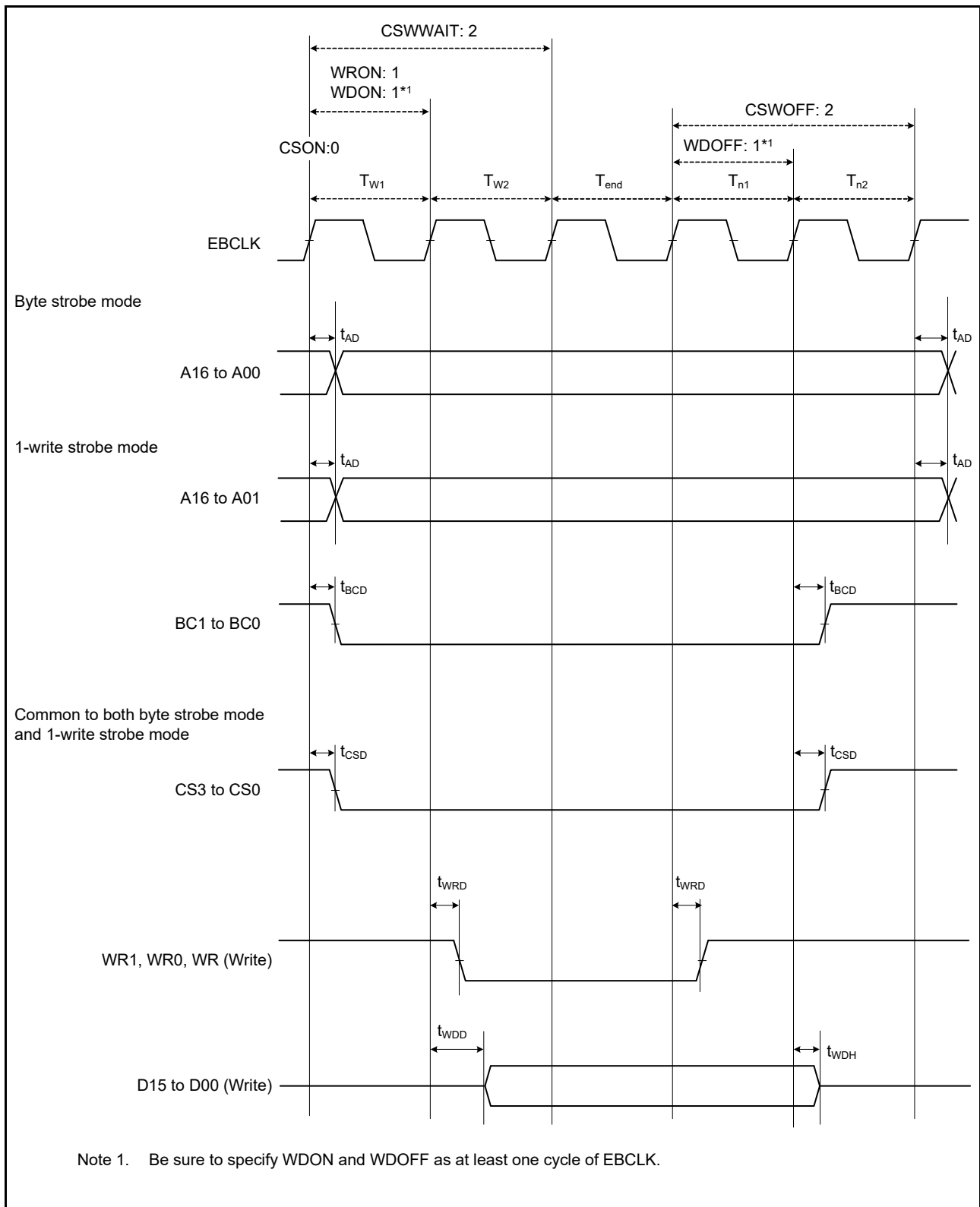


Figure 2.40 External bus timing/normal write cycle (bus clock synchronized)

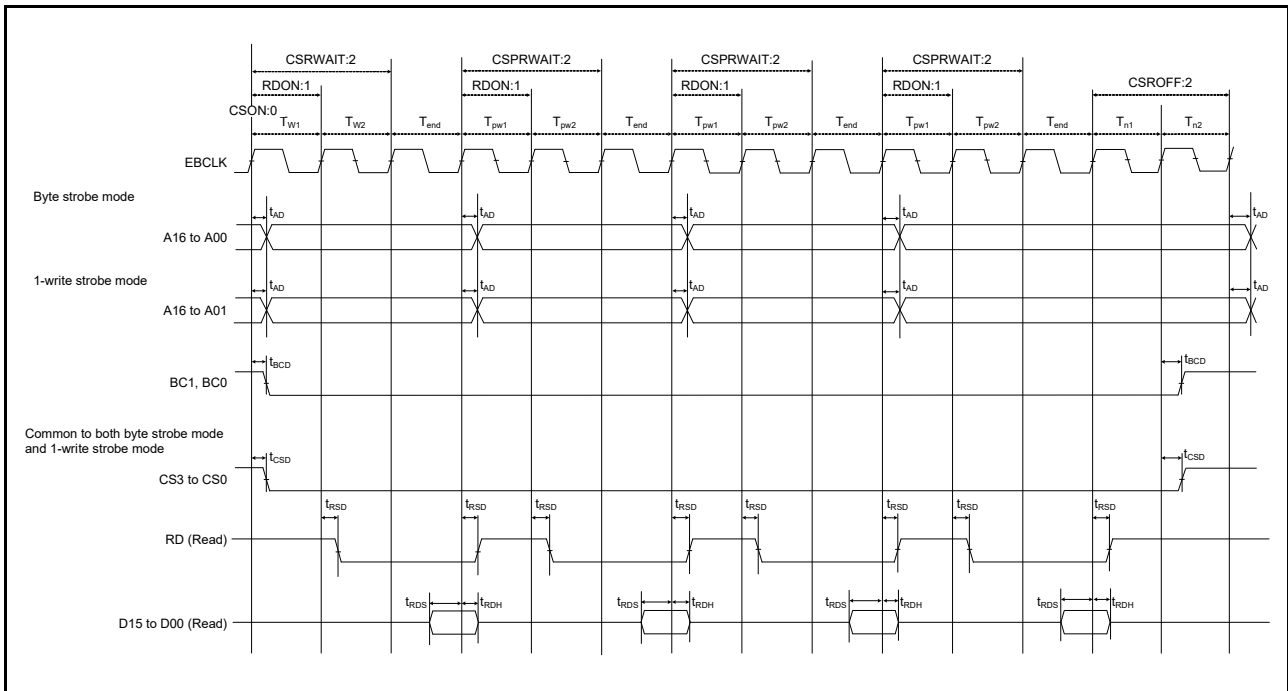
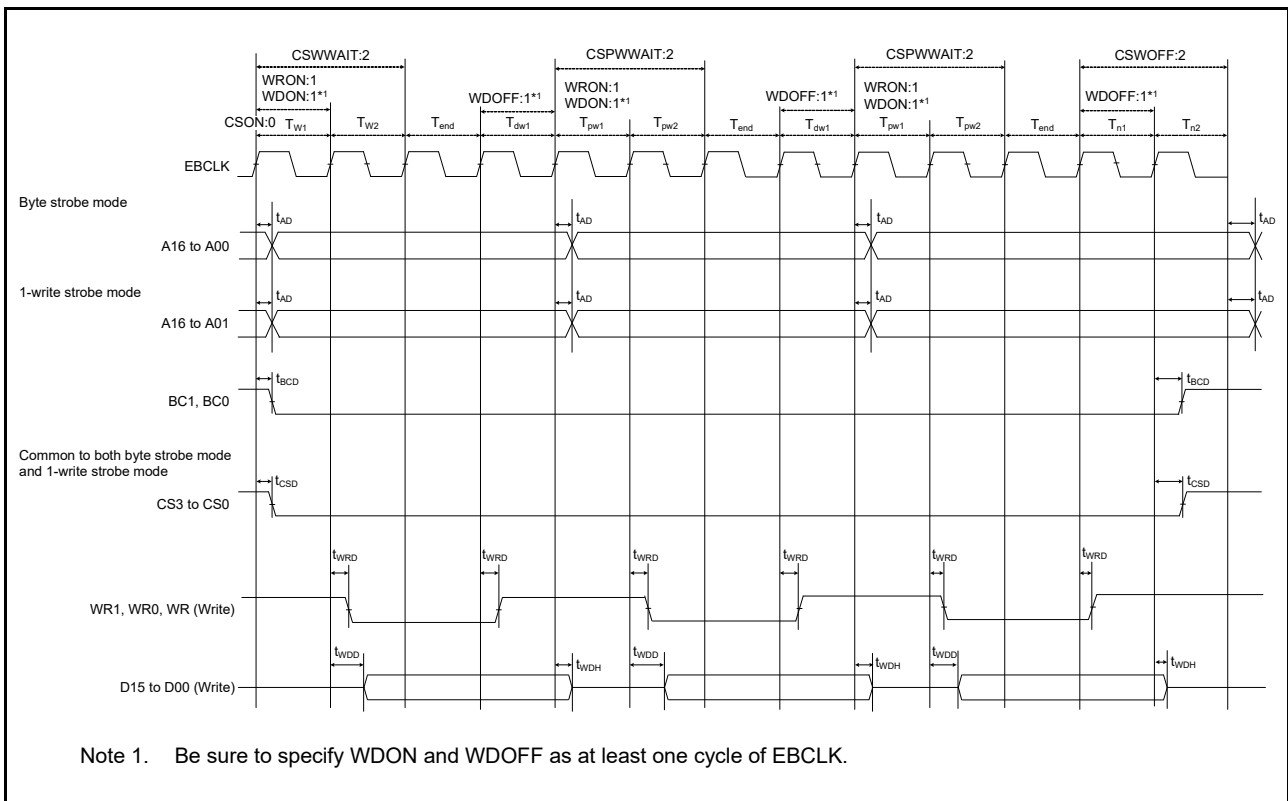


Figure 2.41 External bus timing/page read cycle (bus clock synchronized)



Note 1. Be sure to specify WDOFF and WDOFF as at least one cycle of EBCLK.

Figure 2.42 External bus timing/page write cycle (bus clock synchronized)

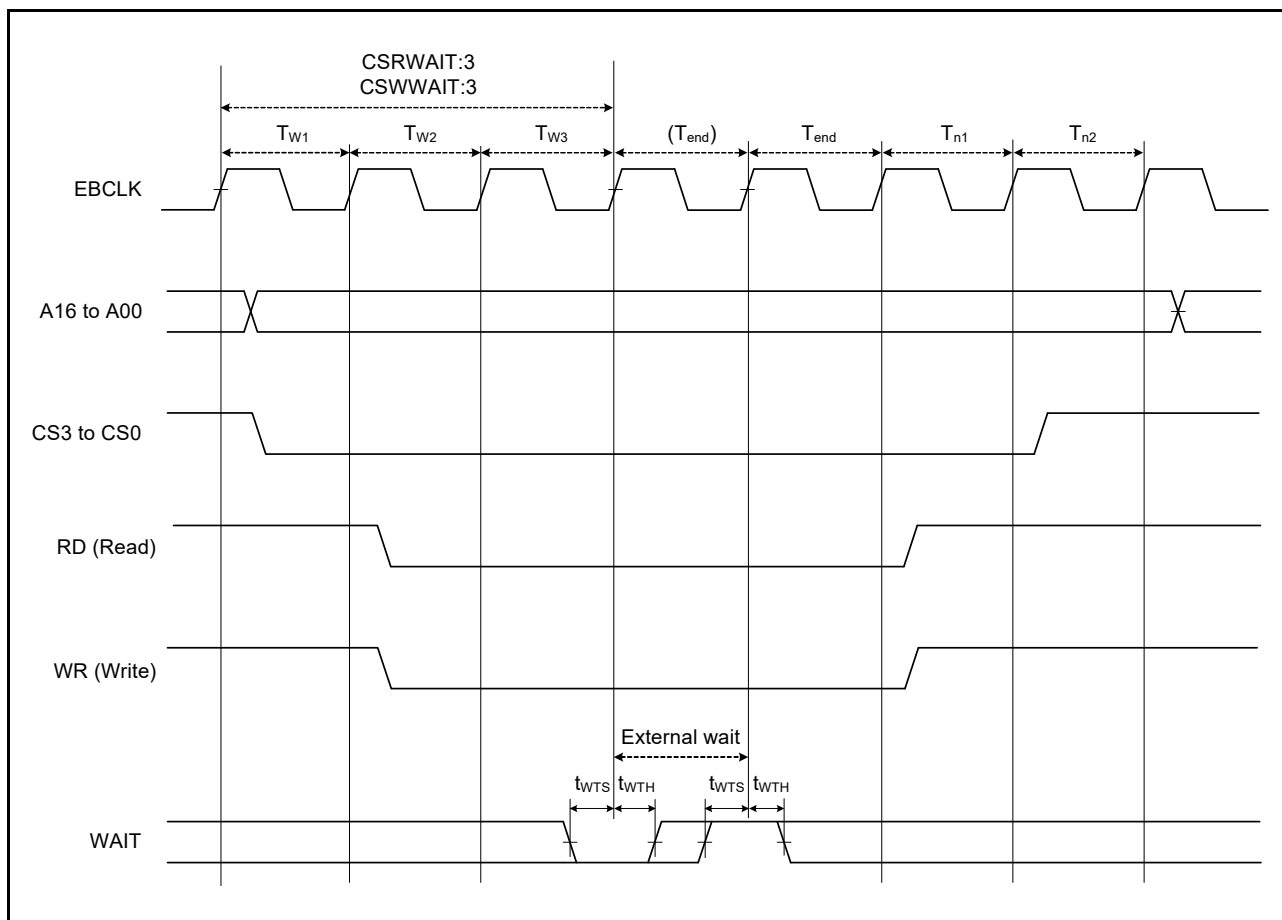


Figure 2.43 External bus timing/external wait control

2.3.7 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 Trigger Timing

Table 2.35 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 trigger timing

Parameter		Symbol	Min	Max	Unit	Test conditions	
I/O Ports	Input data pulse width	t_{PRW}	1.5	-	t_{Pcyc}	Figure 2.44	
	Input/Output data cycle (P002, P003, P004, P007)	t_{POcyc}	10	-	μs		
POEG	POEG input trigger pulse width	t_{POEW}	3	-	t_{Pcyc}	Figure 2.45	
GPT	Input capture pulse width	Single edge	t_{GTICW}	1.5	-	t_{PDcyc}	Figure 2.46
		Dual edge	2.5	-			
AGT	AGTIO, AGTEE input cycle	$2.7 V \leq VCC \leq 5.5 V$	t_{ACYC}^{*1}	250	-	ns	Figure 2.47
		$2.4 V \leq VCC < 2.7 V$		500	-	ns	
		$1.8 V \leq VCC < 2.4 V$		1000	-	ns	
		$1.6 V \leq VCC < 1.8 V$		2000	-	ns	
	AGTIO, AGTEE input high level width, low-level width	$2.7 V \leq VCC \leq 5.5 V$	t_{ACKWH} , t_{ACKWL}	100	-	ns	
		$2.4 V \leq VCC < 2.7 V$		200	-	ns	
		$1.8 V \leq VCC < 2.4 V$		400	-	ns	
		$1.6 V \leq VCC < 1.8 V$		800	-	ns	
	AGTIO, AGTO, AGTOA, AGTOB output cycle	$2.7 V \leq VCC \leq 5.5 V$	t_{ACYC2}	62.5	-	ns	
		$2.4 V \leq VCC < 2.7 V$		125	-	ns	
		$1.8 V \leq VCC < 2.4 V$		250	-	ns	
		$1.6 V \leq VCC < 1.8 V$		500	-	ns	
ADC14	14-bit A/D converter trigger input pulse width	t_{TRGW}	1.5	-	t_{Pcyc}	Figure 2.48	
KINT	KRn (n = 00 to 07) pulse width	t_{KR}	250	-	ns	Figure 2.49	

Note: t_{Pcyc} : PCLKB cycle, t_{PDcyc} : PCLKD cycle

Note 1. Constraints on AGTIO input: $t_{Pcyc} \times 2 (t_{Pcyc}: PCLKB \text{ cycle}) < t_{ACYC}$

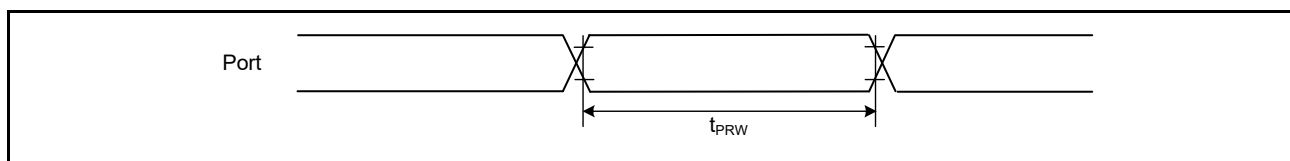


Figure 2.44 I/O ports input timing

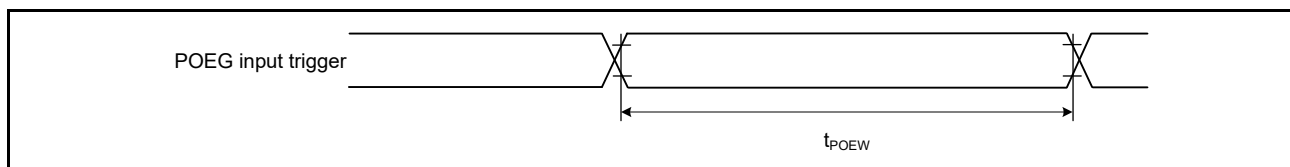


Figure 2.45 POEG input trigger timing

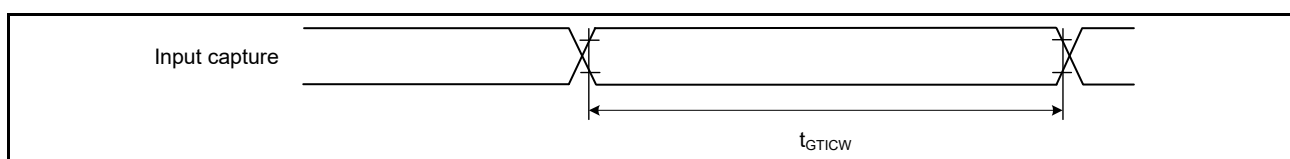


Figure 2.46 GPT input capture timing

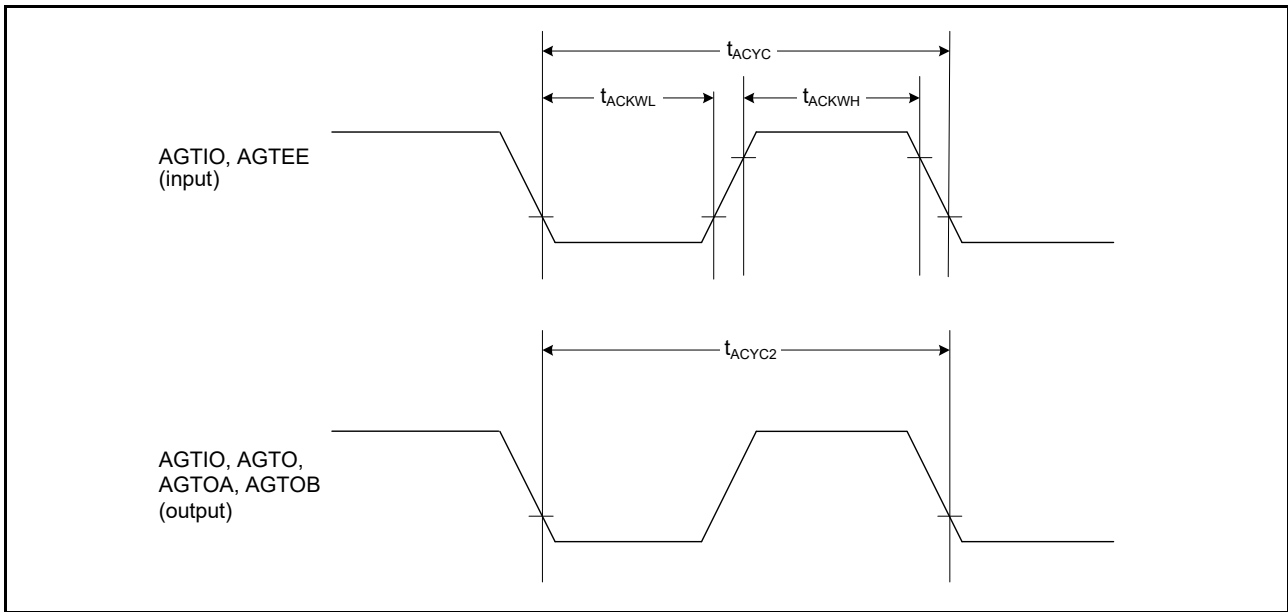


Figure 2.47 AGT I/O timing

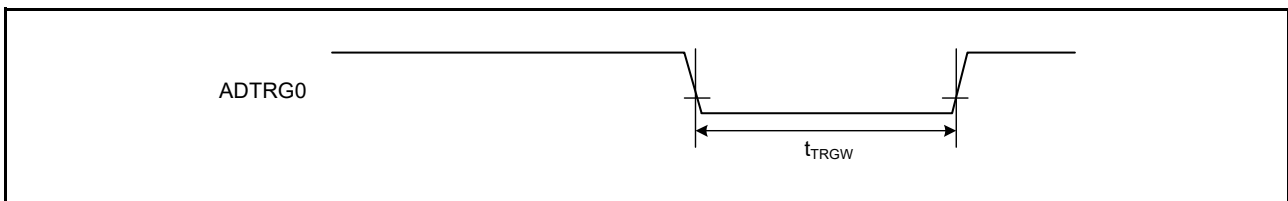


Figure 2.48 ADC14 trigger input timing

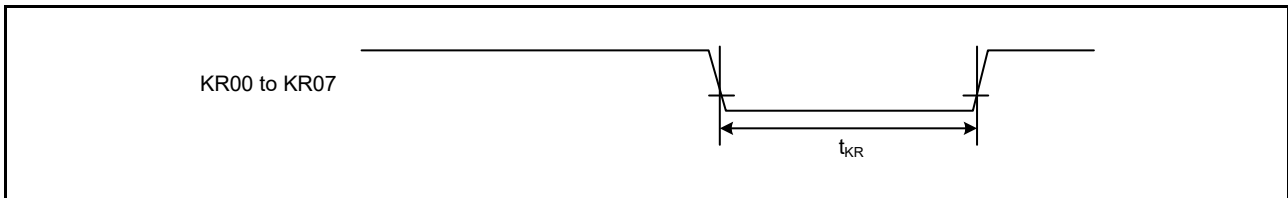


Figure 2.49 Key interrupt input timing

2.3.8 CAC Timing

Table 2.36 CAC timing

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
CAC	CACREF input pulse width	t_{CACREF}	$t_{PBcyc} \leq t_{cac}^*2$	$4.5 \times t_{cac} + 3 \times t_{PBcyc}$	-	-	ns
			$t_{PBcyc} > t_{cac}^*2$	$5 \times t_{cac} + 6.5 \times t_{PBcyc}$	-	-	ns

Note 1. t_{PBcyc} : PCLKB cycle.

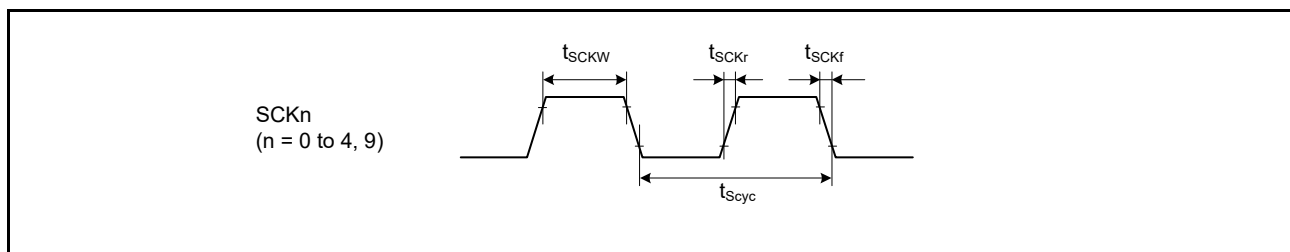
Note 2. t_{cac} : CAC count clock source cycle.

2.3.9 SCI Timing

Table 2.37 SCI timing (1)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter		Symbol	Min	Max	Unit*1	Test conditions		
SCI	Input clock cycle	Asynchronous	t_{Scyc}	4	-	t_{Pcyc}	Figure 2.50	
		Clock synchronous		6	-			
	Input clock pulse width		t_{SCKW}	0.4	0.6	t_{Scyc}		
	Input clock rise time		t_{SCKr}	-	20	ns		
	Input clock fall time		t_{SCKf}	-	20	ns		
	Output clock cycle	Asynchronous	t_{Scyc}	6	-	t_{Pcyc}		
		Clock synchronous		4	-			
	Output clock pulse width		t_{SCKW}	0.4	0.6	t_{Scyc}		
	Output clock rise time		t_{SCKr}	1.8 V or above	-	20		ns
				1.6 V or above	-	30		
	Output clock fall time		t_{SCKf}	1.8 V or above	-	20		ns
				1.6 V or above	-	30		
	Transmit data delay (master)	Clock synchronous	t_{TXD}	1.8 V or above	-	40		ns
				1.6 V or above	-	45		
Transmit data delay (slave)	Clock synchronous	t_{TXD}	2.7 V or above	-	55	ns		
			2.4 V or above	-	60			
			1.8 V or above	-	100			
			1.6 V or above	-	125			
Receive data setup time (master)	Clock synchronous	t_{RXS}	2.7 V or above	45	-	ns		
			2.4 V or above	55	-			
			1.8 V or above	90	-			
			1.6 V or above	105	-			
Receive data setup time (slave)	Clock synchronous	t_{RXS}	2.7 V or above	40	-	ns		
			1.6 V or above	45	-			
Receive data hold time (master)	Clock synchronous	t_{RXH}	5	-	ns			
Receive data hold time (slave)	Clock synchronous	t_{RXH}	40	-	ns			

Note 1. t_{Pcyc} : PCLKA cycle.**Figure 2.50 SCK clock input timing**

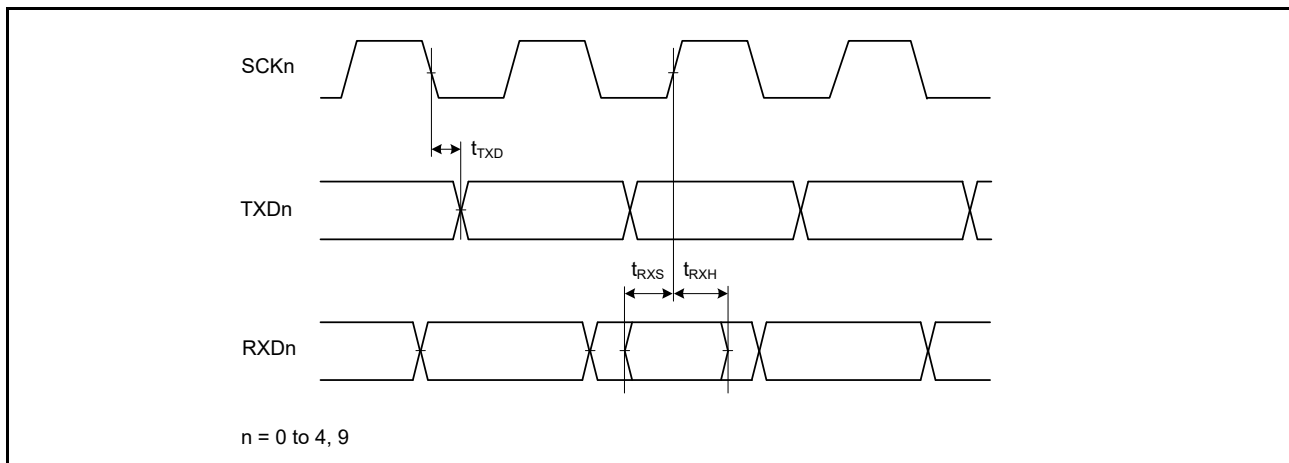


Figure 2.51 SCI input/output timing in clock synchronous mode

Table 2.38 SCI timing (2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter			Symbol	Min	Max	Unit	Test conditions		
Simple SPI	SCK clock cycle output (master)		t_{SPcyc}	4	65536	t_{Pcyc}	Figure 2.52		
	SCK clock cycle input (slave)			6	65536				
	SCK clock high pulse width		t_{SPCKWH}	0.4	0.6	t_{SPcyc}			
	SCK clock low pulse width		t_{SPCKWL}	0.4	0.6	t_{SPcyc}			
	SCK clock rise and fall time		t_{SPCKr} , t_{SPCKf}	1.8 V or above	-	20		ns	
				1.6 V or above	-	30			
	Data input setup time	Master	2.7 V or above	t_{SU}	45	-		ns	Figure 2.53 to Figure 2.56
			2.4 V or above		55	-			
			1.8 V or above		80	-			
			1.6 V or above		105	-			
Slave		2.7 V or above	40		-				
		1.6 V or above	45		-				
Data input hold time	Master		t_H	33.3	-	ns			
	Slave			40	-				
SS input setup time			t_{LEAD}	1	-	t_{SPcyc}			
SS input hold time			t_{LAG}	1	-	t_{SPcyc}			
Data output delay	Master	1.8 V or above	t_{OD}	-	40	ns			
		1.6 V or above		-	50				
	Slave	2.4 V or above		-	65				
		1.8 V or above		-	100				
		1.6 V or above		-	125				
Data output hold time	Master	2.7 V or above	t_{OH}	-10	-	ns			
		2.4 V or above		-20	-				
		1.8 V or above		-30	-				
		1.6 V or above		-40	-				
	Slave				-10		-		
	Data rise and fall time	Master		1.8 V or above	t_{Dr} , t_{Df}		-	20	ns
1.6 V or above			-	30					
Slave		1.8 V or above	-	20					
		1.6 V or above	-	30					
Slave access time			t_{SA}	-	10 (PCLKA > 32 MHz), 6 (PCLKA ≤ 32 MHz)	t_{Pcyc}	Figure 2.55 and Figure 2.56 PCLKB = PCLKA		
Slave output release time			t_{REL}	-	10 (PCLKA > 32 MHz), 6 (PCLKA ≤ 32 MHz)	t_{Pcyc}			

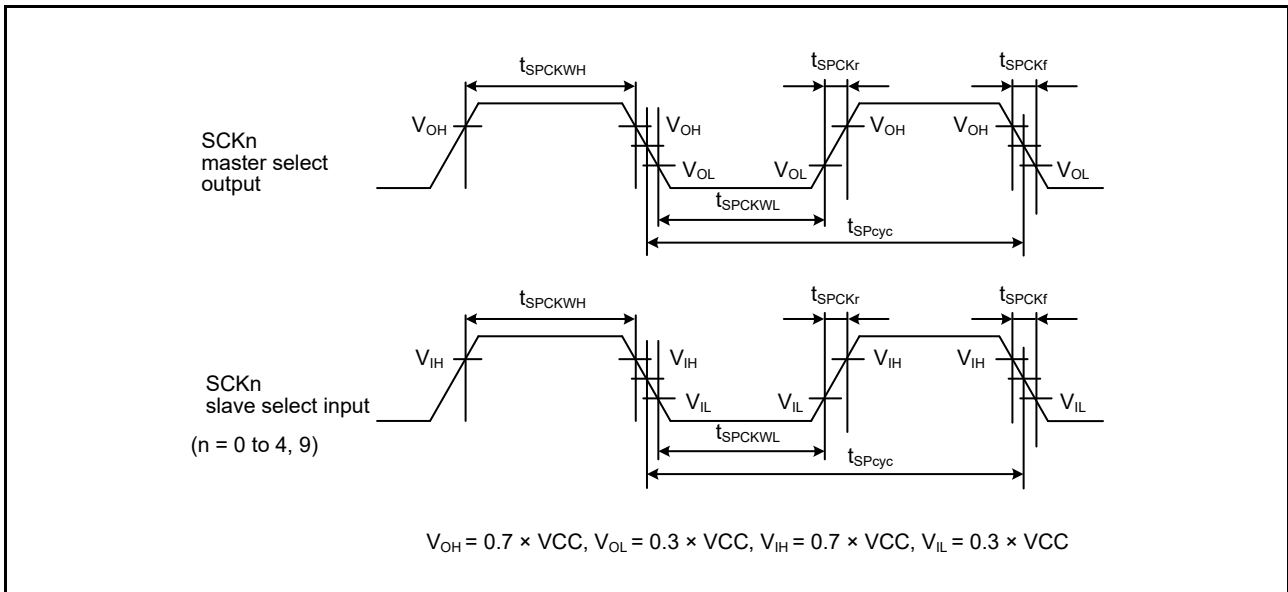


Figure 2.52 SCI simple SPI mode clock timing

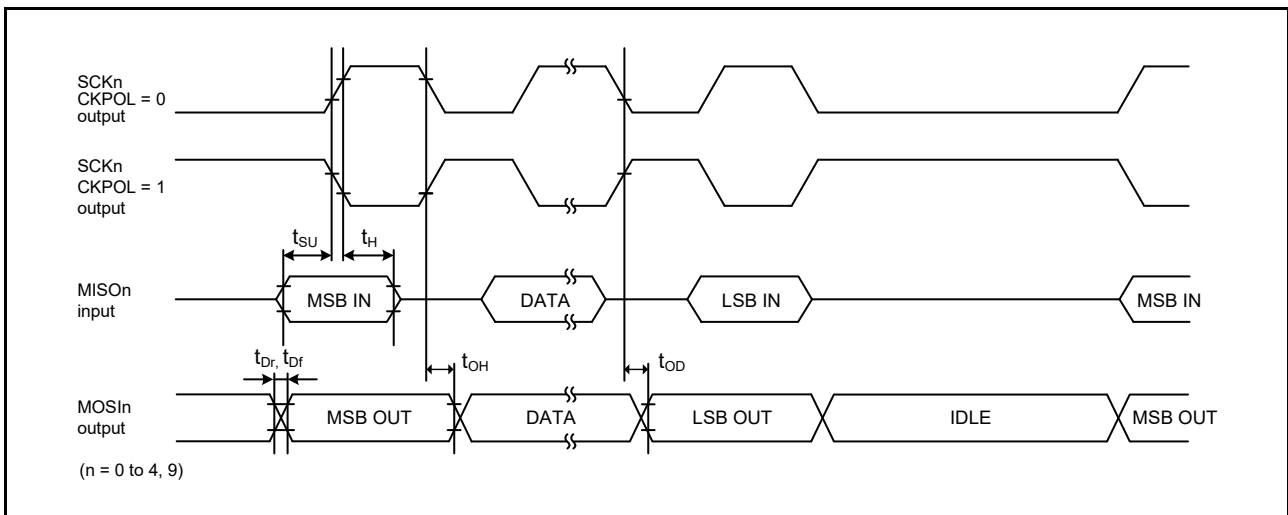


Figure 2.53 SCI simple SPI mode timing (master, CKPH = 1)

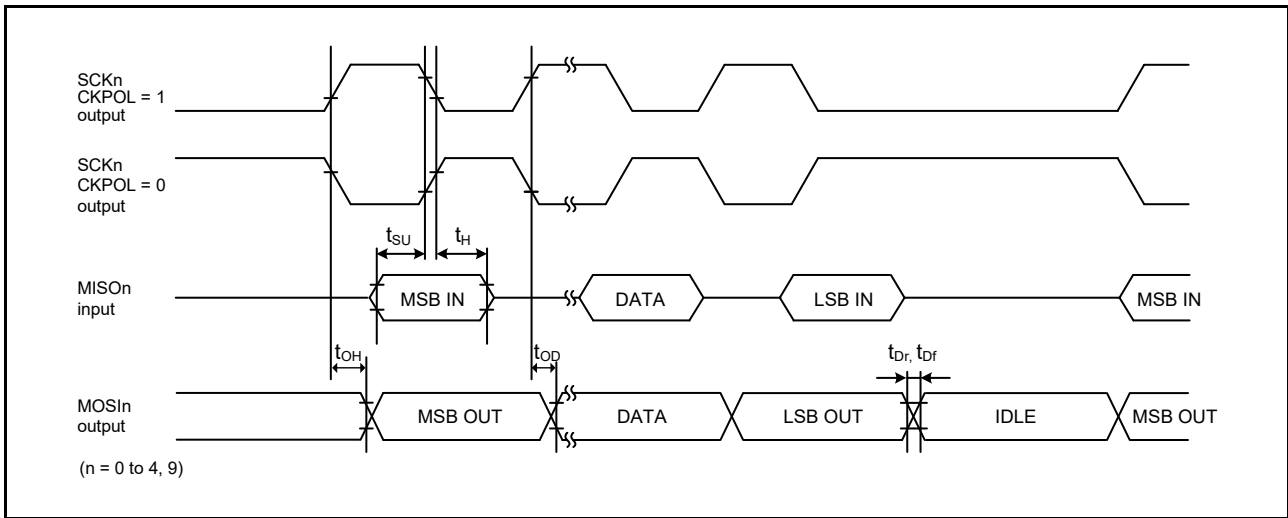


Figure 2.54 SCI simple SPI mode timing (master, CKPH = 0)

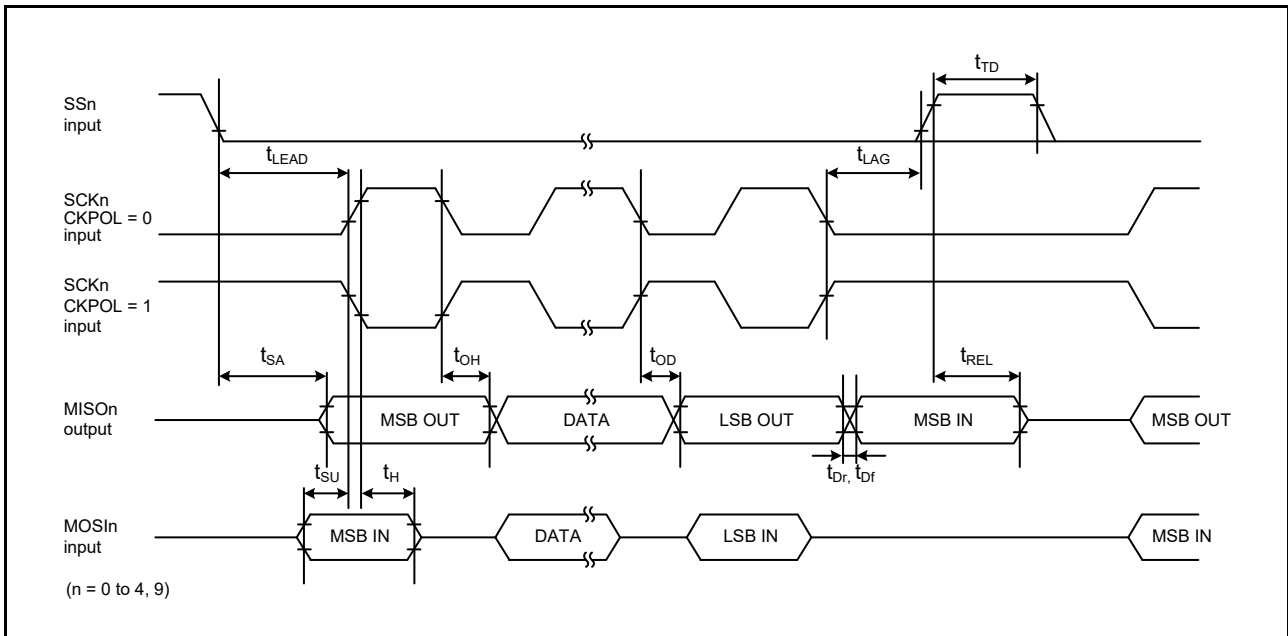


Figure 2.55 SCI simple SPI mode timing (slave, CKPH = 1)

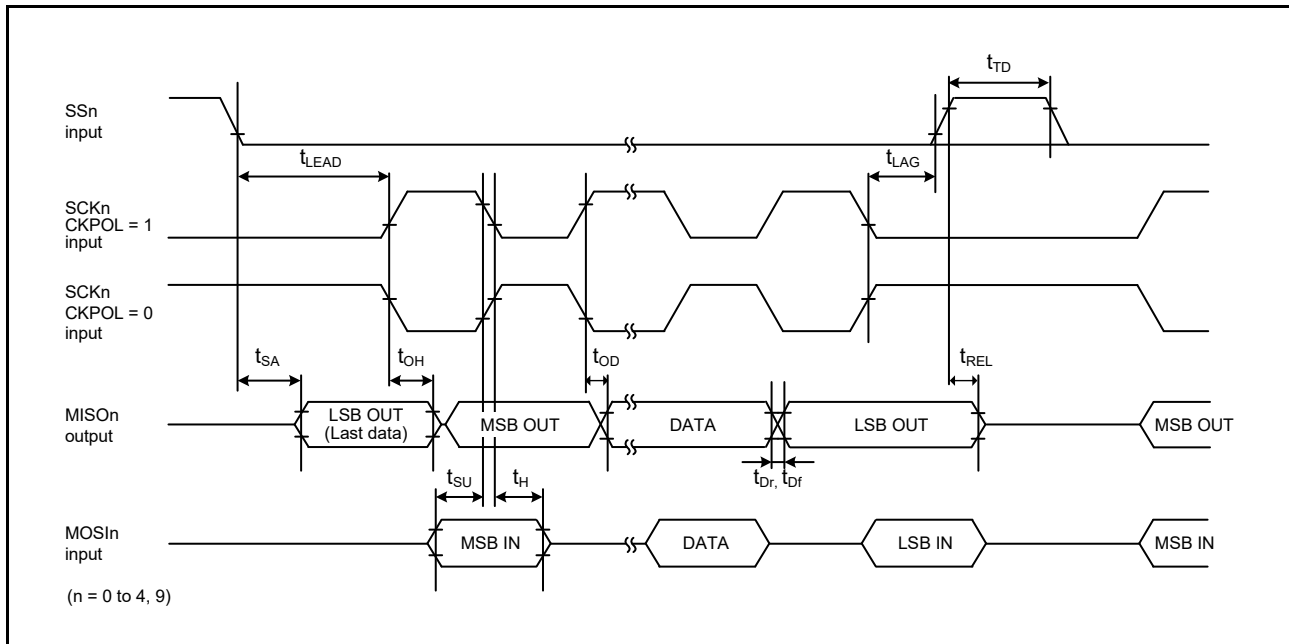


Figure 2.56 SCI simple SPI mode timing (slave, CKPH = 0)

Table 2.39 SCI timing (3)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter	Symbol	Min	Max	Unit	Test conditions	
Simple IIC (Standard mode)	SDA input rise time	t_{Sr}	-	1000	ns	Figure 2.57
	SDA input fall time	t_{Sf}	-	300	ns	
	SDA input spike pulse removal time	t_{SP}	0	$4 \times t_{IICcyc}$	ns	
	Data input setup time	t_{SDAS}	250	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b^{*2}	-	400	pF	
Simple IIC (Fast mode)*3	SDA input rise time	t_{Sr}	-	300	ns	Figure 2.57
	SDA input fall time	t_{Sf}	-	300	ns	
	SDA input spike pulse removal time	t_{SP}	0	$4 \times t_{IICcyc}$	ns	
	Data input setup time	t_{SDAS}	100	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b^{*2}	-	400	pF	

Note 1. t_{IICcyc} : Clock cycle selected in the SMR.CKS[1:0] bits.

Note 2. C_b indicates the total capacity of the bus line.

Note 3. Middle drive output is selected in the Port Drive Capability in the PmnPFS register

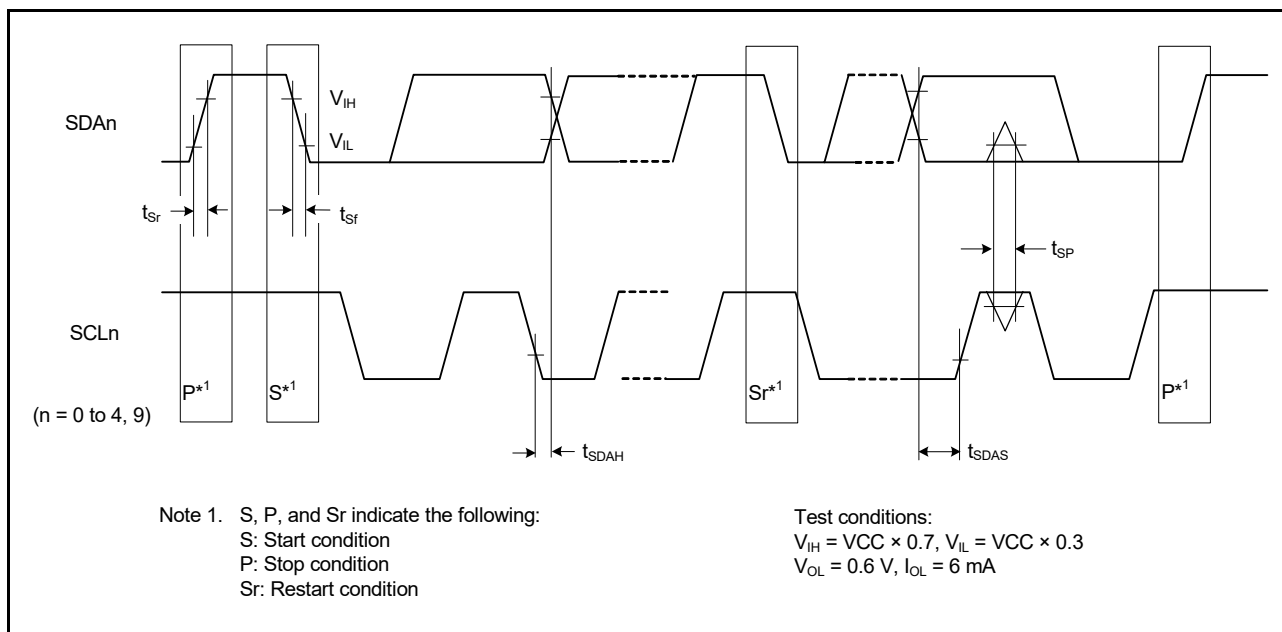


Figure 2.57 SCI simple IIC mode timing

2.3.10 SPI Timing

Table 2.40 SPI timing (1 of 2)

Conditions: Middle drive output is selected in the Port Drive Capability in the PmnPFS register

Parameter			Symbol	Min	Max	Unit*1	Test conditions	
SPI	RSPCK clock cycle	Master	t_{SPCyc}	2*4	4096	t_{Pcyc}	Figure 2.58 C = 30pF	
		Slave		6	4096			
	RSPCK clock high pulse width	Master	t_{SPCKWH}	$(t_{SPCyc} - t_{SPCKr} - t_{SPCKf}) / 2 - 3$	-	ns		
		Slave		$3 \times t_{Pcyc}$	-			
	RSPCK clock low pulse width	Master	t_{SPCKWL}	$(t_{SPCyc} - t_{SPCKr} - t_{SPCKf}) / 2 - 3$	-	ns		
		Slave		$3 \times t_{Pcyc}$	-			
	RSPCK clock rise and fall time	Output	2.7 V or above	t_{SPCKr} , t_{SPCKf}	-	10		ns
			2.4 V or above		-	15		
			1.8 V or above		-	20		
			1.6 V or above		-	30		
Input		-	1	μ s				
Data input setup time	Master	t_{SU}	10	-	ns	Figure 2.59 to Figure 2.64 C = 30pF		
	Slave		2.4 V or above	10			-	
			1.8 V or above	15			-	
			1.6 V or above	20			-	
Data input hold time	Master (RSPCK is PCLKA/2)	t_{HF}	0	-	ns			
	Master (RSPCK is other than above.)	t_H	t_{Pcyc}	-				
	Slave	t_H	20	-				
SSL setup time	Master	t_{LEAD}	$-30 + N \times t_{SPcyc}^{*2}$	-	ns			
	Slave		$6 \times t_{Pcyc}$	-	ns			
SSL hold time	Master	t_{LAG}	$-30 + N \times t_{SPcyc}^{*3}$	-	ns			
	Slave		$6 \times t_{Pcyc}$	-	ns			

Table 2.40 SPI timing (2 of 2)

Conditions: Middle drive output is selected in the Port Drive Capability in the PmnPFS register

Parameter			Symbol	Min	Max	Unit*1	Test conditions	
SPI	Data output delay	Master	2.7 V or above	t_{OD}	-	14	ns	Figure 2.59 to Figure 2.64 C = 30pF
			2.4 V or above		-	20		
			1.8 V or above		-	25		
			1.6 V or above		-	30		
		Slave	2.7 V or above		-	50		
			2.4 V or above		-	60		
			1.8 V or above		-	85		
			1.6 V or above		-	110		
Data output hold time	Master		t_{OH}	0	-	ns	Figure 2.63 and Figure 2.64 C = 30pF	
	Slave			0	-			
Successive transmission delay	Master		t_{TD}	$t_{SPcyc} + 2 \times t_{Pcyc}$	$8 \times t_{SPcyc} + 2 \times t_{Pcyc}$	ns		
	Slave			$6 \times t_{Pcyc}$	-			
MOSI and MISO rise and fall time	Output	2.7 V or above	t_{Dr}, t_{Df}	-	10	ns		
		2.4 V or above		-	15			
		1.8 V or above		-	20			
		1.6 V or above		-	30			
	Input			-	1		μs	
SSL rise and fall time	Output	2.7 V or above	t_{SSLr}, t_{SSLf}	-	10	ns		
		2.4 V or above		-	15			
		1.8 V or above		-	20			
		1.6 V or above		-	30			
	Input			-	1		μs	
Slave access time		2.4 V or above	t_{SA}	-	$2 \times t_{Pcyc} + 100$	ns	Figure 2.63 and Figure 2.64 C = 30pF	
		1.8 V or above		-	$2 \times t_{Pcyc} + 140$			
		1.6 V or above		-	$2 \times t_{Pcyc} + 180$			
Slave output release time		2.4 V or above	t_{REL}	-	$2 \times t_{Pcyc} + 100$	ns		
		1.8 V or above		-	$2 \times t_{Pcyc} + 140$			
		1.6 V or above		-	$2 \times t_{Pcyc} + 180$			

Note 1. t_{Pcyc} : PCLKA cycle.

Note 2. N is set as an integer from 1 to 8 by the SPCKD register.

Note 3. N is set as an integer from 1 to 8 by the SSLND register.

Note 4. The upper limit of RSPCK is 16 MHz.

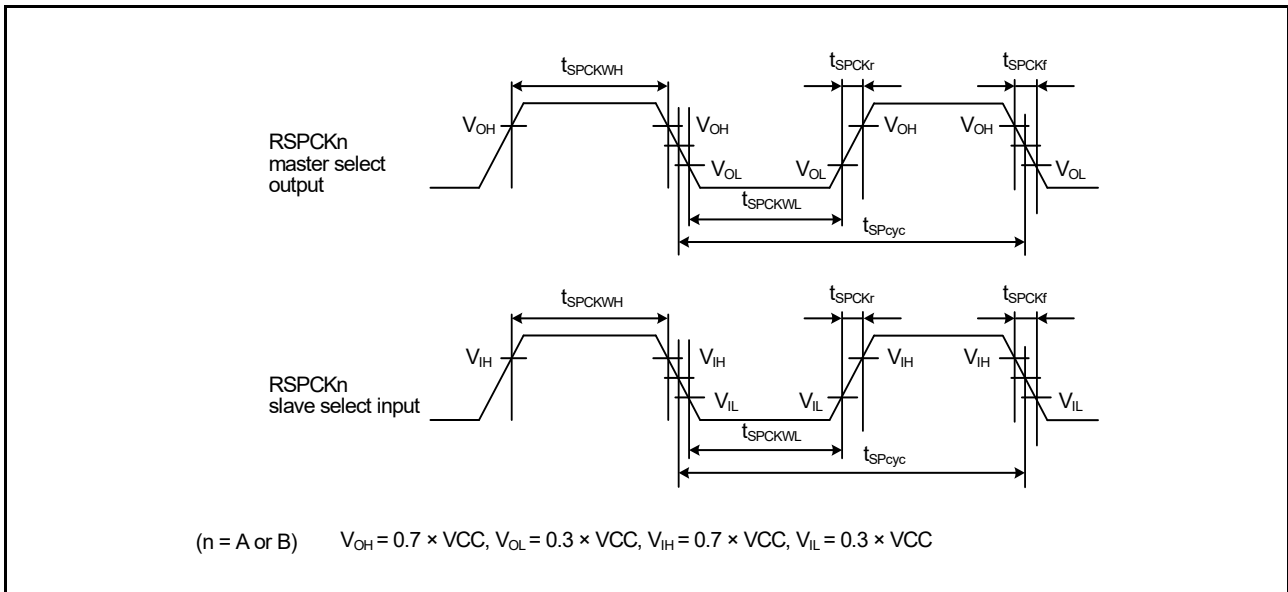


Figure 2.58 SPI clock timing

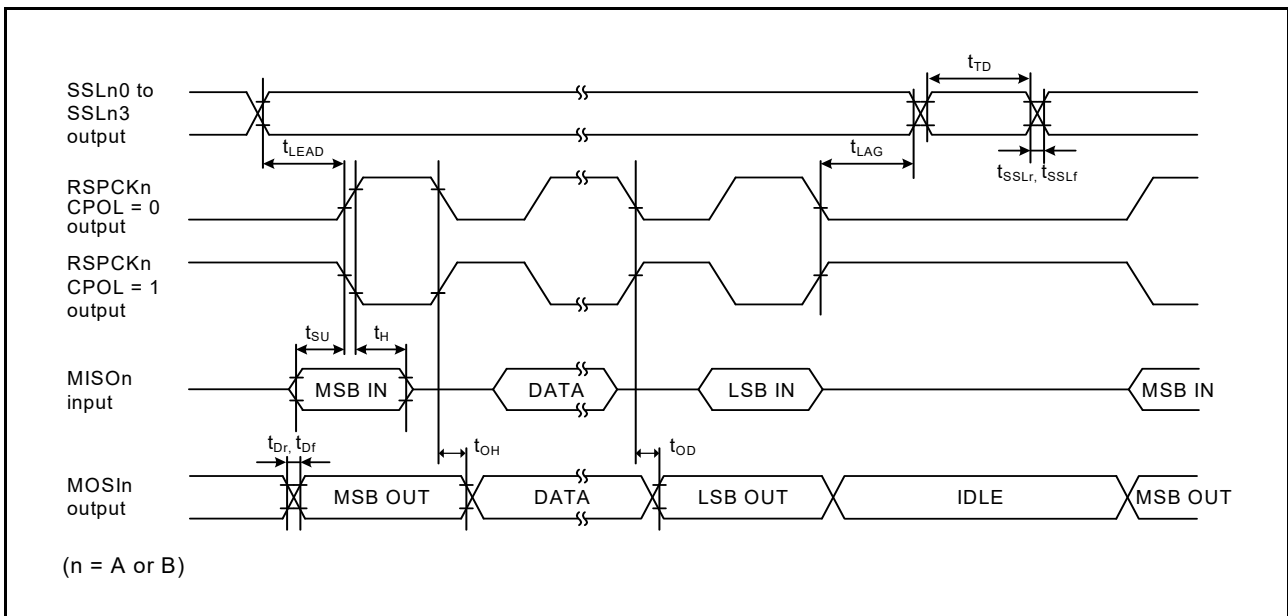


Figure 2.59 SPI timing (master, CPHA = 0) (bit rate: PCLKA division ratio is set to any value other than 1/2)

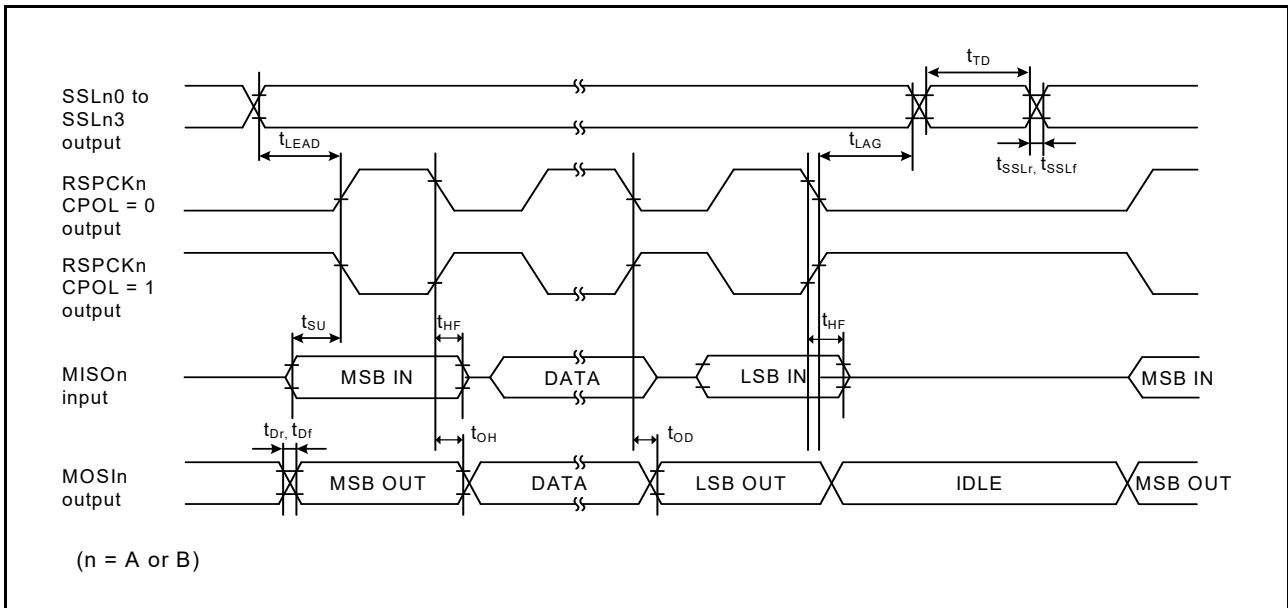


Figure 2.60 SPI timing (master, CPHA = 0) (bit rate: PCLKA division ratio is set to 1/2)

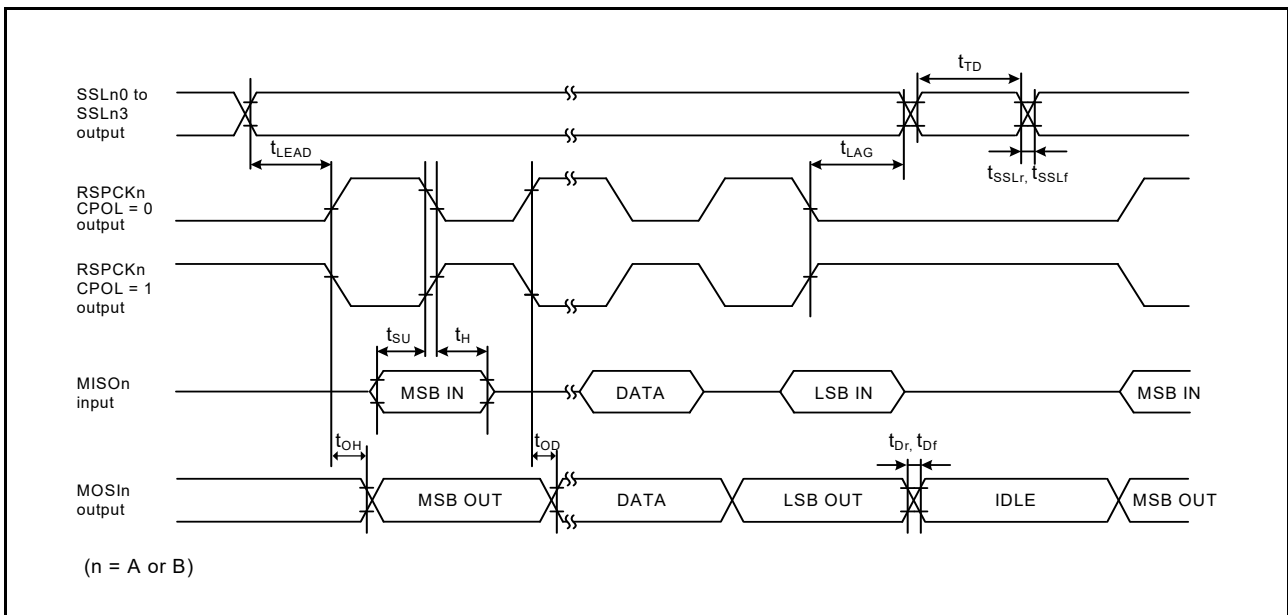


Figure 2.61 SPI timing (master, CPHA = 1) (bit rate: PCLKA division ratio is set to any value other than 1/2)

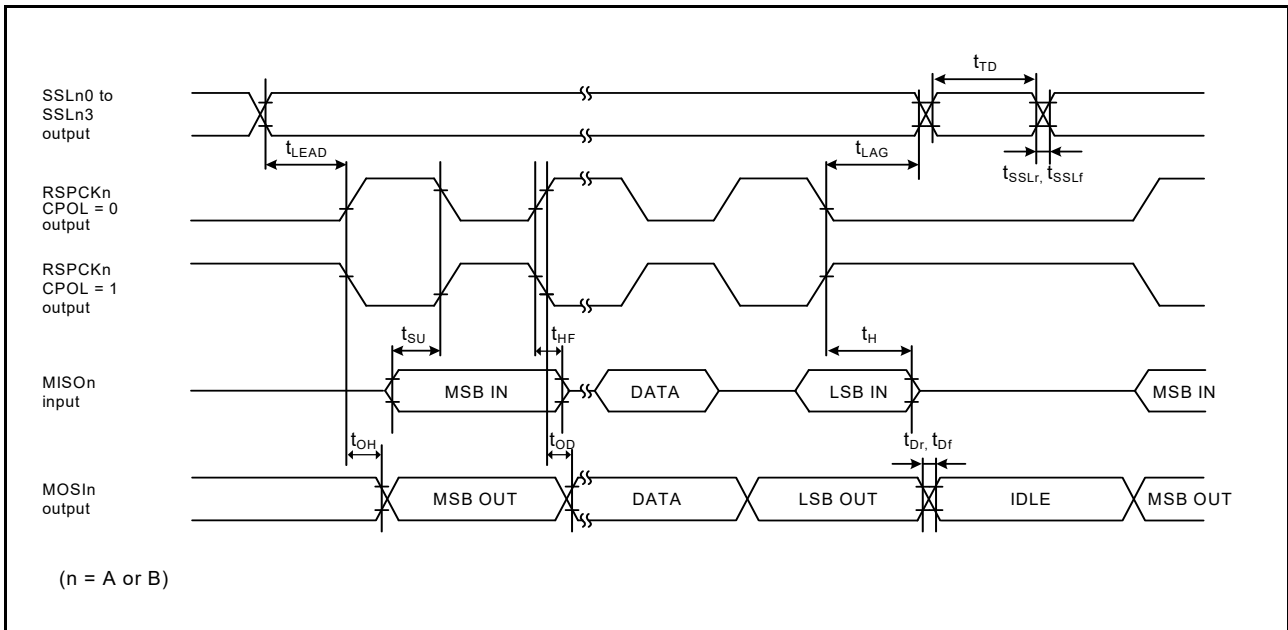


Figure 2.62 SPI timing (master, CPHA = 1) (bit rate: PCLKA division ratio is set to 1/2)

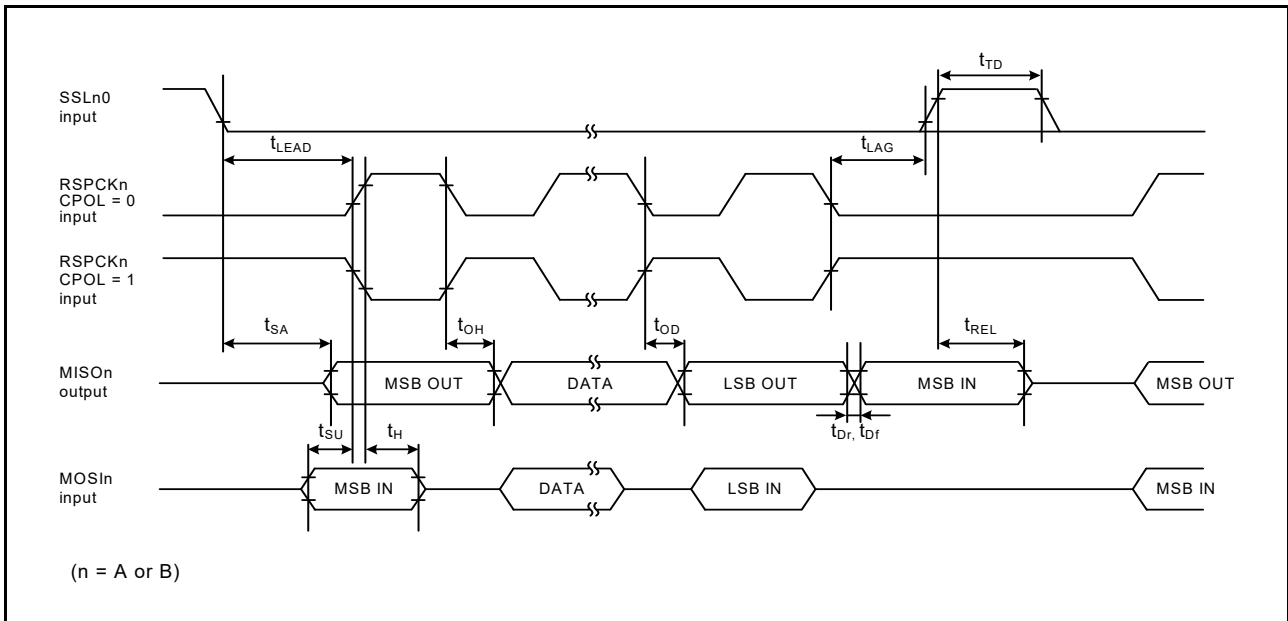


Figure 2.63 SPI timing (slave, CPHA = 0)

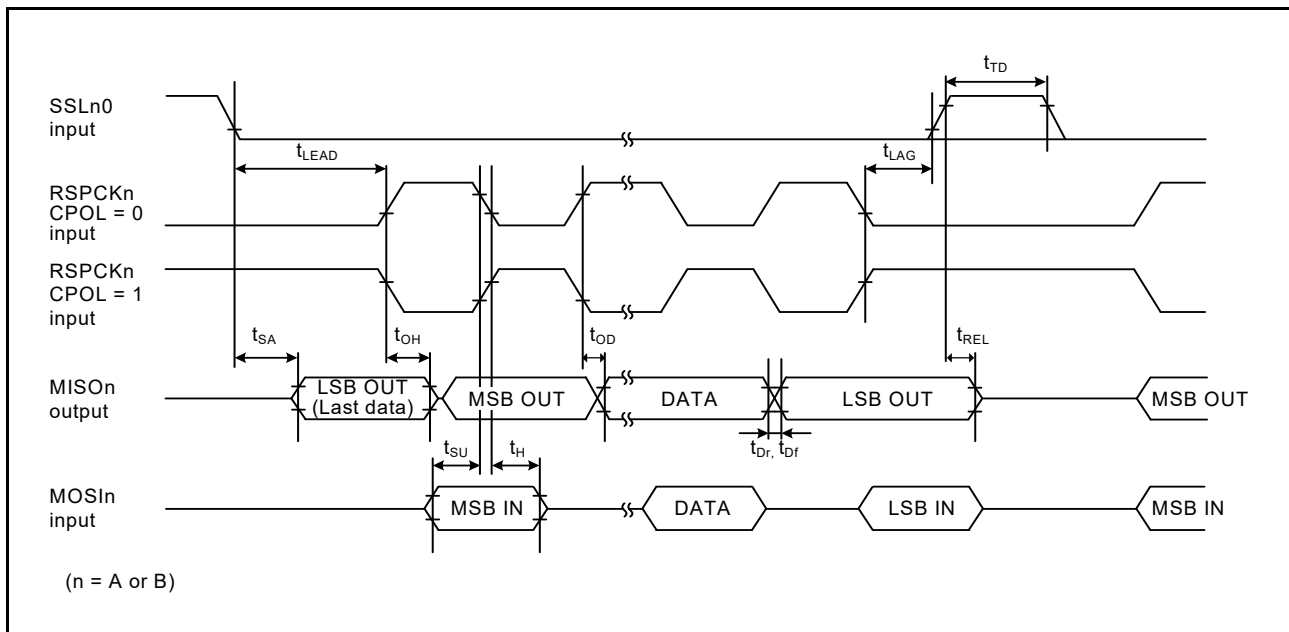


Figure 2.64 SPI timing (slave, CPHA = 1)

2.3.11 QSPI Timing

Table 2.41 QSPI timing

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Conditions: Middle drive output is selected in the Port Drive Capability bit in the PmnPFS register

Parameter		Symbol	Min	Max	Unit*1	Test conditions
QSPI	QSPCLK clock cycle	t_{QScyc}	2^4	48	t_{Pcyc}	Figure 2.65
	QSPCLK clock high-level pulse width	t_{QSWH}	$t_{QScyc} \times 0.4$	-	ns	
	QSPCLK clock low-level pulse width	t_{QSWL}	$t_{QScyc} \times 0.4$	-	ns	
Data input setup time	2.7 V or above 2.4 V or above 1.8 V or above	t_{SU}	40	-	ns	Figure 2.66
			40	-	ns	
			80	-	ns	
Data input hold time		t_{IH}	0	-	ns	
SSL setup time		t_{LEAD}	$(N + 0.5) \times t_{QScyc} - 15^*2$	$(N + 0.5) \times t_{QScyc} + 100^*2$	ns	
SSL hold time		t_{LAG}	$(N + 0.5) \times t_{QScyc} - 15^*3$	$(N + 0.5) \times t_{QScyc} + 100^*3$	ns	
Data output delay	2.7 V or above	t_{OD}	-	14	ns	
	2.4 V or above		-	20		
	1.8 V or above		-	30		
Data output hold time	2.7 V or above	t_{OH}	-3.3	-	ns	
	1.8 V or above		-10	-		
Successive transmission delay		t_{TD}	1	16	t_{QScyc}	

Note 1. t_{Pcyc} : PCLKA cycle.

Note 2. N is set to 0 or 1 in SFMSLD.

Note 3. N is set to 0 or 1 in SFMSHD.

Note 4. The upper limit of QSPCLK is 16 MHz.

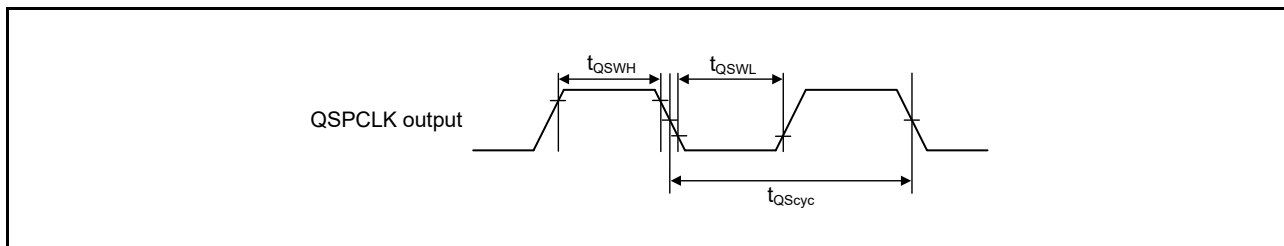


Figure 2.65 QSPI clock timing

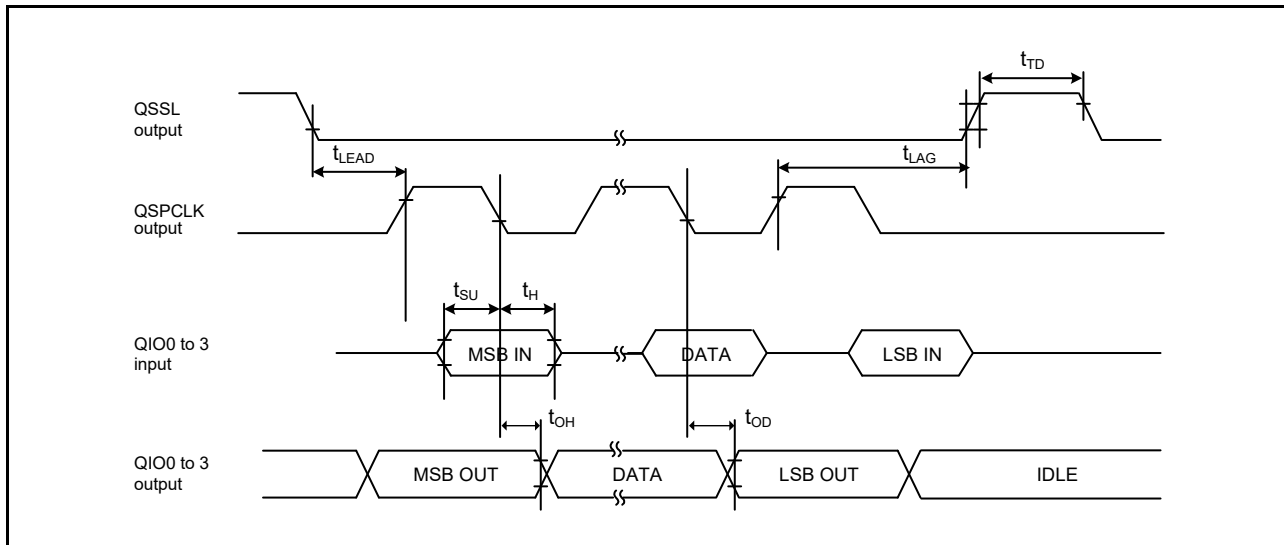


Figure 2.66 Transfer/receive timing

2.3.12 IIC Timing

Table 2.42 IIC timing

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter		Symbol	Min*1	Max	Unit	Test conditions
IIC (standard mode, SMBus)	SCL input cycle time	t_{SCL}	$6 (12) \times t_{IICcyc} + 1300$	-	ns	Figure 2.67
	SCL input high pulse width	t_{SCLH}	$3 (6) \times t_{IICcyc} + 300$	-	ns	
	SCL input low pulse width	t_{SCLL}	$3 (6) \times t_{IICcyc} + 300$	-	ns	
	SCL, SDA input rise time	t_{Sr}	-	1000	ns	
	SCL, SDA input fall time	t_{Sf}	-	300	ns	
	SCL, SDA input spike pulse removal time	t_{SP}	0	$1 (4) \times t_{IICcyc}$	ns	
	SDA input bus free time (When wakeup function is disabled)	t_{BUF}	$3 (6) \times t_{IICcyc} + 300$	-	ns	
	SDA input bus free time (When wakeup function is enabled)	t_{BUF}	$3 (6) \times t_{IICcyc} + 4 \times t_{Pcyc} + 300$	-	ns	
	START condition input hold time (When wakeup function is disabled)	t_{STAH}	$t_{IICcyc} + 300$	-	ns	
	START condition input hold time (When wakeup function is enabled)	t_{STAH}	$1 (5) \times t_{IICcyc} + t_{Pcyc} + 300$	-	ns	
	Repeated START condition input setup time	t_{STAS}	1000	-	ns	
	STOP condition input setup time	t_{STOS}	1000	-	ns	
	Data input setup time	t_{SDAS}	$t_{IICcyc} + 50$	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b	-	400	pF	
IIC (Fast mode)*2	SCL input cycle time	t_{SCL}	$6 (12) \times t_{IICcyc} + 600$	-	ns	Figure 2.67
	SCL input high pulse width	t_{SCLH}	$3 (6) \times t_{IICcyc} + 300$	-	ns	
	SCL input low pulse width	t_{SCLL}	$3 (6) \times t_{IICcyc} + 300$	-	ns	
	SCL, SDA input rise time	t_{Sr}	-	300	ns	
	SCL, SDA input fall time	t_{Sf}	-	300	ns	
	SCL, SDA input spike pulse removal time	t_{SP}	0	$1 (4) \times t_{IICcyc}$	ns	
	SDA input bus free time (When wakeup function is disabled)	t_{BUF}	$3 (6) \times t_{IICcyc} + 300$	-	ns	
	SDA input bus free time (When wakeup function is enabled)	t_{BUF}	$3 (6) \times t_{IICcyc} + 4 \times t_{Pcyc} + 300$	-	ns	
	START condition input hold time (When wakeup function is disabled)	t_{STAH}	$t_{IICcyc} + 300$	-	ns	
	START condition input hold time (When wakeup function is enabled)	t_{STAH}	$1(5) \times t_{IICcyc} + t_{Pcyc} + 300$	-	ns	
	Repeated START condition input setup time	t_{STAS}	300	-	ns	
	STOP condition input setup time	t_{STOS}	300	-	ns	
	Data input setup time	t_{SDAS}	$t_{IICcyc} + 50$	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b	-	400	pF	

Note: t_{IICcyc} : IIC internal reference clock (IIC ϕ) cycle, t_{Pcyc} : PCLKB cycle

Note 1. The value in parentheses apply when ICMR3.NF[1:0] is set to 11b while the digital filter is enabled with ICFER.NFE set to 1.

Note 2. Middle drive output is selected in the Port Drive Capability bit in the PmnPFS register.

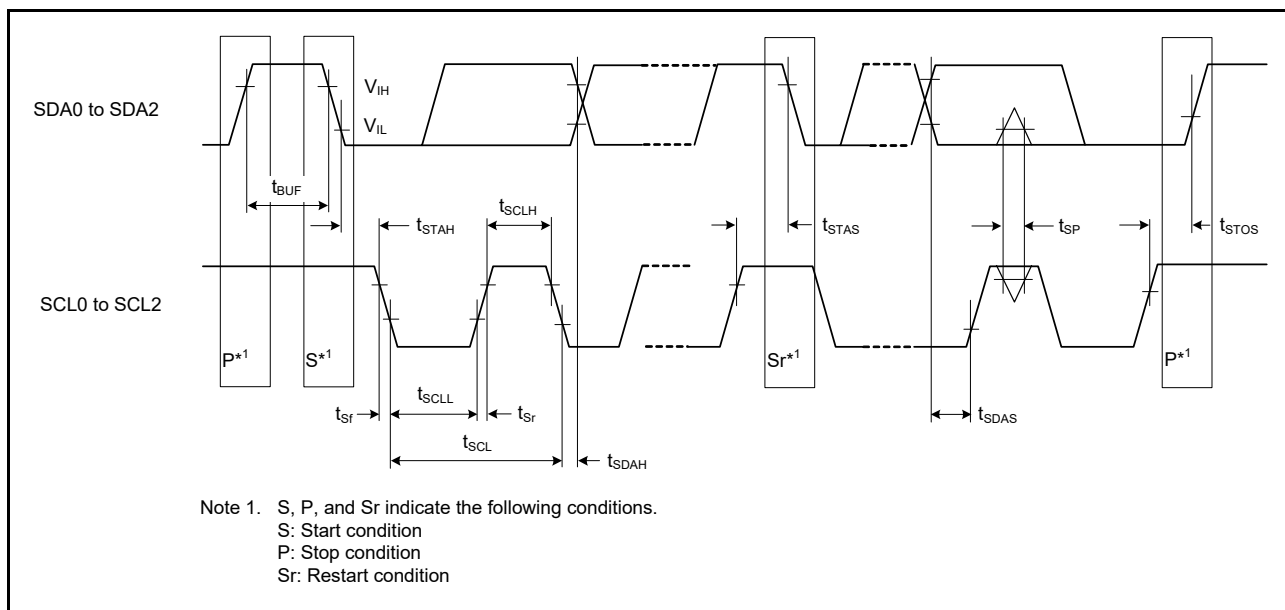


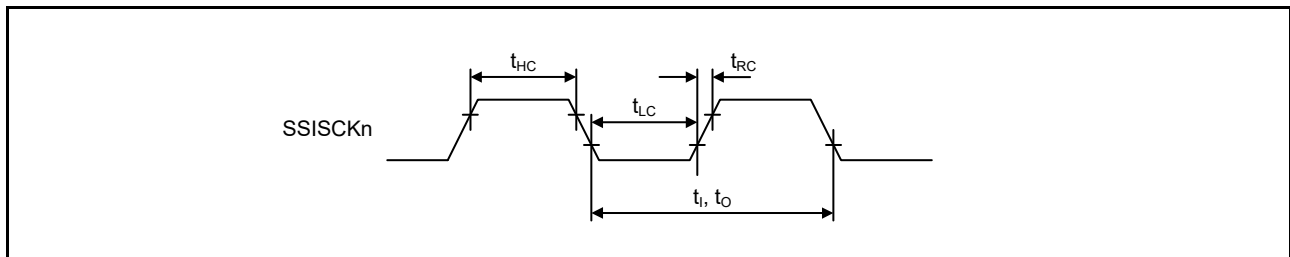
Figure 2.67 I2C bus interface input/output timing

2.3.13 SSI Timing

Table 2.43 SSI timing

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter		Symbol	Min	Max	Unit	Test conditions
SSI	AUDIO_CLK input frequency	t_{AUDIO}	2.7 V or above	25	MHz	-
			1.6 V or above	4		
Output clock period		t_{O}	250	-	ns	Figure 2.68
Input clock period		t_{I}	250	-	ns	
Clock high pulse width	1.8 V or above	t_{HC}	100	-	ns	
	1.6 V or above		200	-		
Clock low pulse width	1.8 V or above	t_{LC}	100	-	ns	
	1.6 V or above		200	-		
Clock rise time		t_{RC}	-	25	ns	
Data delay	2.7 V or above	t_{DTR}	-	65	ns	Figure 2.69, Figure 2.70
	1.8 V or above		-	105		
	1.6 V or above		-	140		
Set-up time	2.7 V or above	t_{SR}	65	-	ns	
	1.8 V or above		90	-		
	1.6 V or above		140	-		
Hold time		t_{HTR}	40	-	ns	
SSIDATA output delay from WS change time	1.8 V or above	T_{DTRW}	-	105	ns	Figure 2.71
	1.6 V or above		-	140		

**Figure 2.68 SSI clock input/output timing**

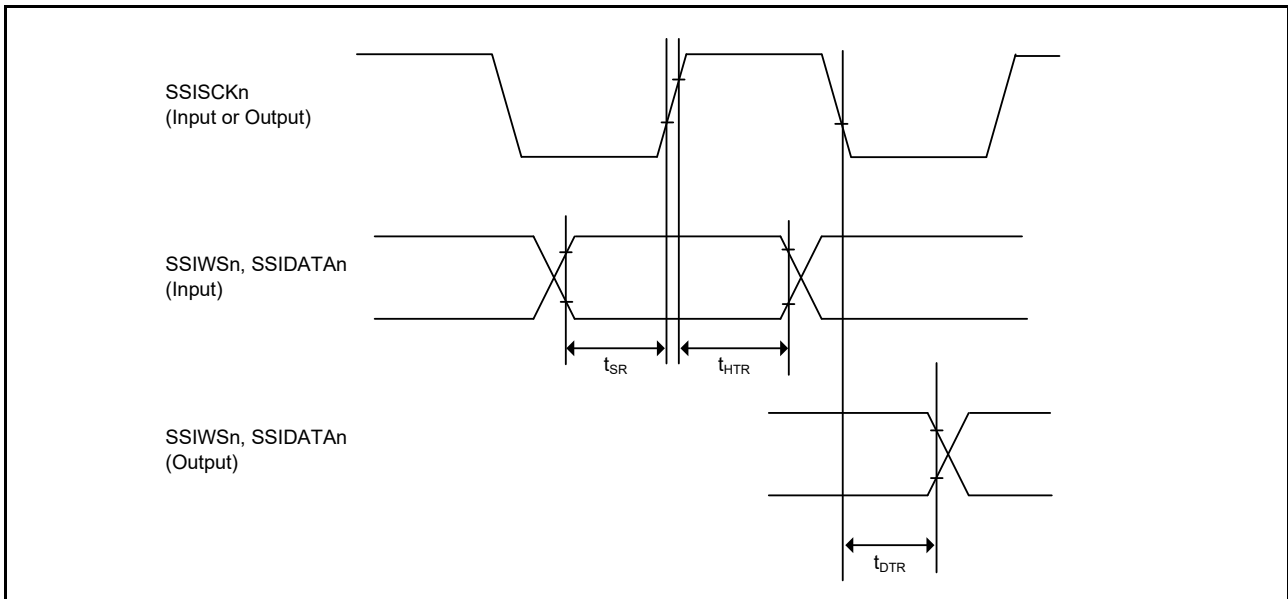


Figure 2.69 SSI data transmit/receive timing (SSICR.SCKP = 0)

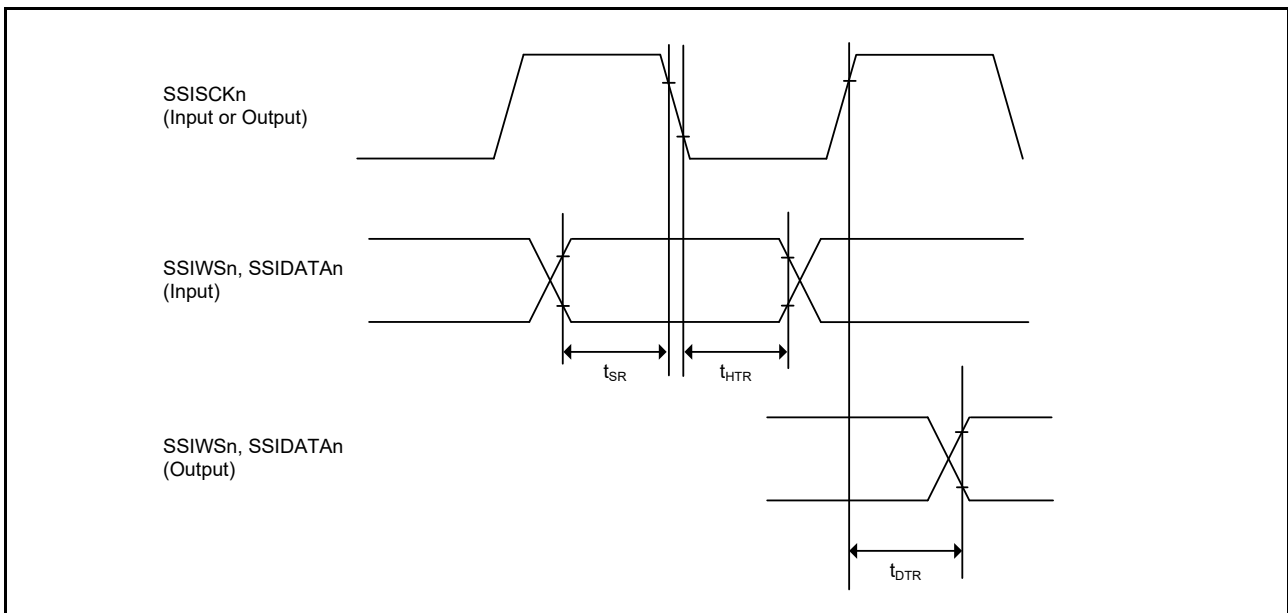


Figure 2.70 SSI data transmit/receive timing (SSICR.SCKP = 1)

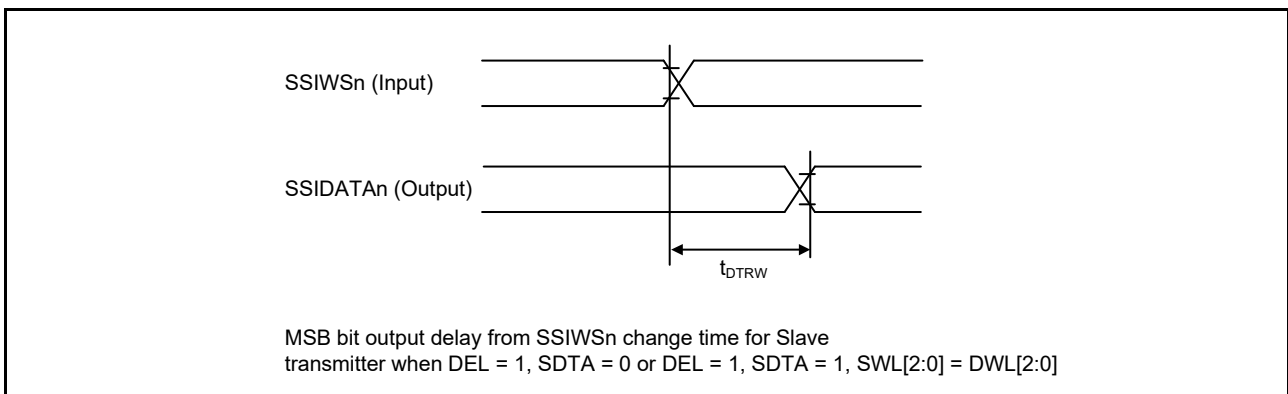


Figure 2.71 SSI data output delay from SSIWSn change time

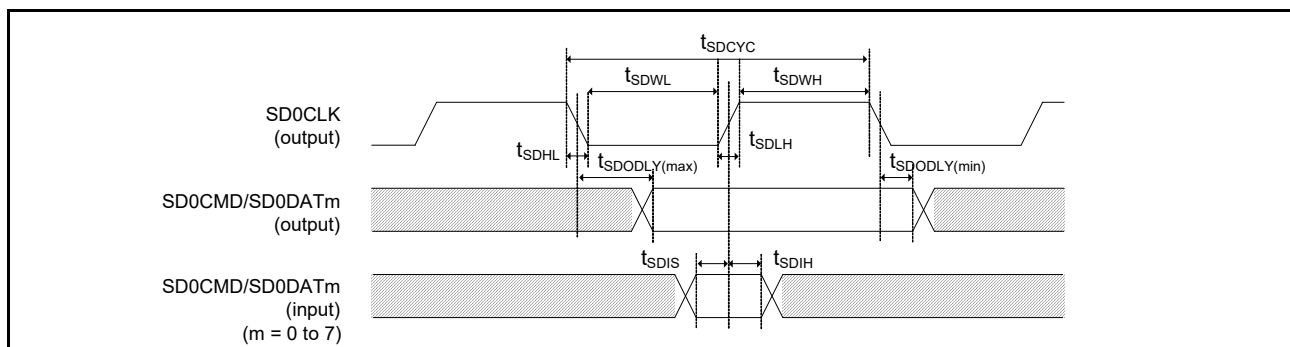
2.3.14 SD/MMC Host Interface Timing

Table 2.44 SD/MMC host interface signal timing

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Conditions: Middle drive output is selected in the Port Drive Capability in PmnPFS register

Parameter	Symbol	Min	Max	Unit	Test conditions
SDCLK clock cycle	t_{SDCYC}	62.5	-	ns	Figure 2.72
SDCLK clock high-level pulse width	t_{SDWH}	18.25	-	ns	
SDCLK clock low-level pulse width	t_{SDWL}	18.25	-	ns	
SDCLK clock rising time	t_{SDLH}	-	10	ns	
SDCLK clock falling time	t_{SDHL}	-	10	ns	
SDCMD/SDDAT output data delay	t_{SDODLY}	-18.25	18.25	ns	
SDCMD/SDDAT input data setup	t_{SDIS}	9.25	-	ns	
SDCMD/SDDAT input data hold	t_{SDIH}	23.25	-	ns	

**Figure 2.72 SD/MMC host interface signal timing**

2.3.15 CLKOUT Timing

Table 2.45 CLKOUT timing

Parameter		Symbol	Min	Max	Unit*1	Test conditions	
CLKOUT	CLKOUT pin output cycle*1	VCC = 2.7 V or above	t_{Cyc}	62.5	-	ns	Figure 2.73
		VCC = 1.8 V or above		125	-		
		VCC = 1.6 V or above		250	-		
CLKOUT	CLKOUT pin high pulse width*2	VCC = 2.7 V or above	t_{CH}	15	-	ns	
		VCC = 1.8 V or above		30	-		
		VCC = 1.6 V or above		150	-		
CLKOUT	CLKOUT pin low pulse width*2	VCC = 2.7 V or above	t_{CL}	15	-	ns	
		VCC = 1.8 V or above		30	-		
		VCC = 1.6 V or above		150	-		
CLKOUT	CLKOUT pin output rise time	VCC = 2.7 V or above	t_{Cr}	-	12	ns	
		VCC = 1.8 V or above		-	25		
		VCC = 1.6 V or above		-	50		
CLKOUT	CLKOUT pin output fall time	VCC = 2.7 V or above	t_{Cf}	-	12	ns	
		VCC = 1.8 V or above		-	25		
		VCC = 1.6 V or above		-	50		

Note 1. When the EXTAL external clock input or an oscillator is used with division by 1 (the CKOCR.CKOSSEL[2:0] bits are 011b and the CKOCR.CKODIV[2:0] bits are 000b) to output from CLKOUT, the above should be satisfied with an input duty cycle of 45 to 55%.

Note 2. When the MOCO is selected as the clock output source (the CKOCR.CKOSSEL[2:0] bits are 001b), set the clock output division ratio selection to be divided by 2 (the CKOCR.CKODIV[2:0] bits are 001b).

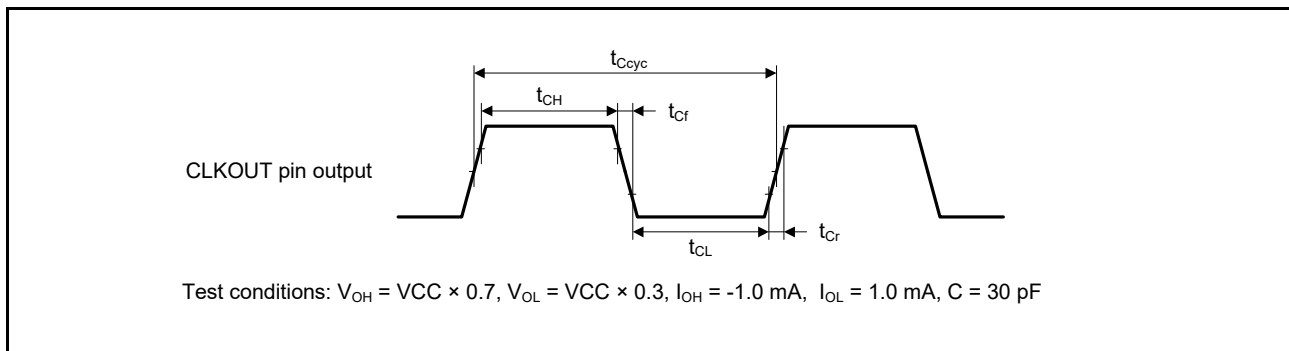


Figure 2.73 CLKOUT output timing

2.4 USB Characteristics

2.4.1 USBFS Timing

Table 2.46 USB characteristics

Conditions: $VCC = AVCC0 = VCC_{USB} = 3.0 \text{ to } 3.6 \text{ V}$

Parameter		Symbol	Min	Max	Unit	Test conditions	
Input characteristics	Input high level voltage	V_{IH}	2.0	-	V	-	
	Input low level voltage	V_{IL}	-	0.8	V	-	
	Differential input sensitivity	V_{DI}	0.2	-	V	$ USB_{DP} - USB_{DM} $	
	Differential common mode range	V_{CM}	0.8	2.5	V	-	
Output characteristics	Output high level voltage	V_{OH}	2.8	VCC_{USB}	V	$I_{OH} = -200 \mu\text{A}$	
	Output low level voltage	V_{OL}	0.0	0.3	V	$I_{OL} = 2 \text{ mA}$	
	Cross-over voltage	V_{CRS}	1.3	2.0	V	Figure 2.74, Figure 2.75, Figure 2.76	
	Rise time	FS	t_r	4	20		ns
		LS		75	300		
	Fall time	FS	t_f	4	20		ns
		LS		75	300		
	Rise/fall time ratio	FS	t_r/t_f	90	111.11		%
LS			80	125			
Output resistance	Z_{DRV}	28	44	Ω	(Adjusting the resistance of external elements is not necessary.)		
VBUS characteristics	VBUS input voltage	V_{IH}	$VCC \times 0.8$	-	V	-	
		V_{IL}	-	$VCC \times 0.2$	V	-	
Pull-up, pull-down	Pull-down resistor	R_{PD}	14.25	24.80	k Ω	-	
	Pull-up resistor	R_{PUI}	0.9	1.575	k Ω	During idle state	
		R_{PUA}	1.425	3.09	k Ω	During reception	
Battery Charging Specification version 1.2	D + sink current	I_{DP_SINK}	25	175	μA	-	
	D - sink current	I_{DM_SINK}	25	175	μA	-	
	DCD source current	I_{DP_SRC}	7	13	μA	-	
	Data detection voltage	V_{DAT_REF}	0.25	0.4	V	-	
	D + source voltage	V_{DP_SRC}	0.5	0.7	V	Output current = 250 μA	
	D - source voltage	V_{DM_SRC}	0.5	0.7	V	Output current = 250 μA	

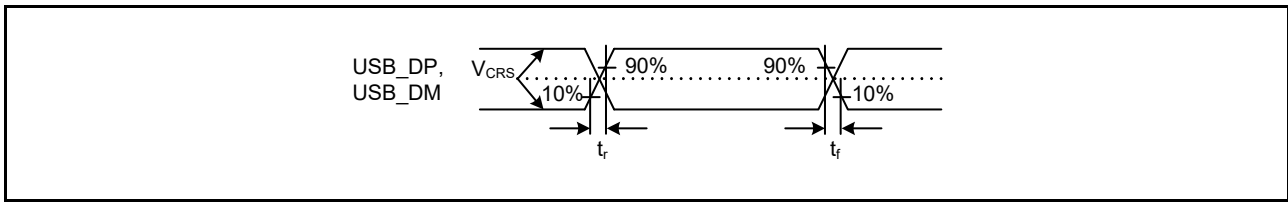


Figure 2.74 USB_DP and USB_DM output timing

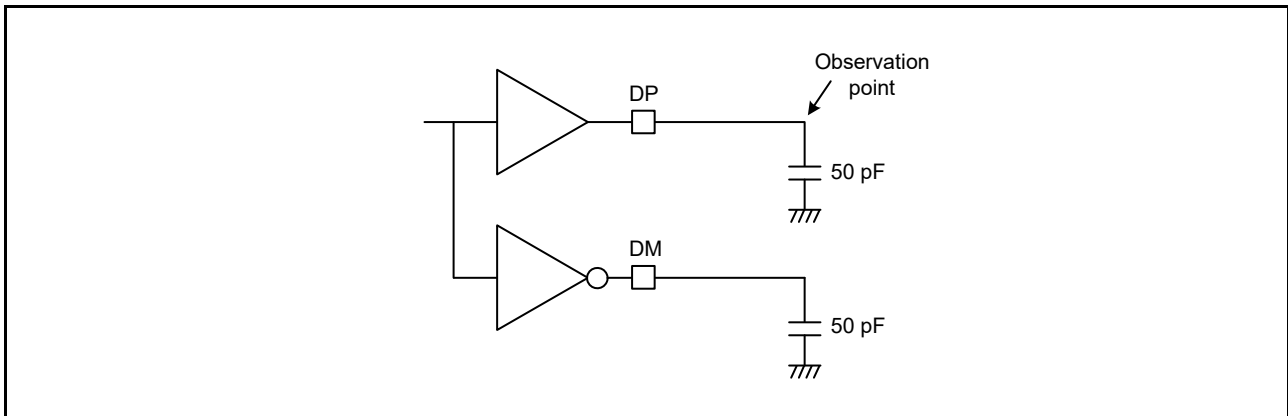


Figure 2.75 Test circuit for Full-Speed (FS) connection

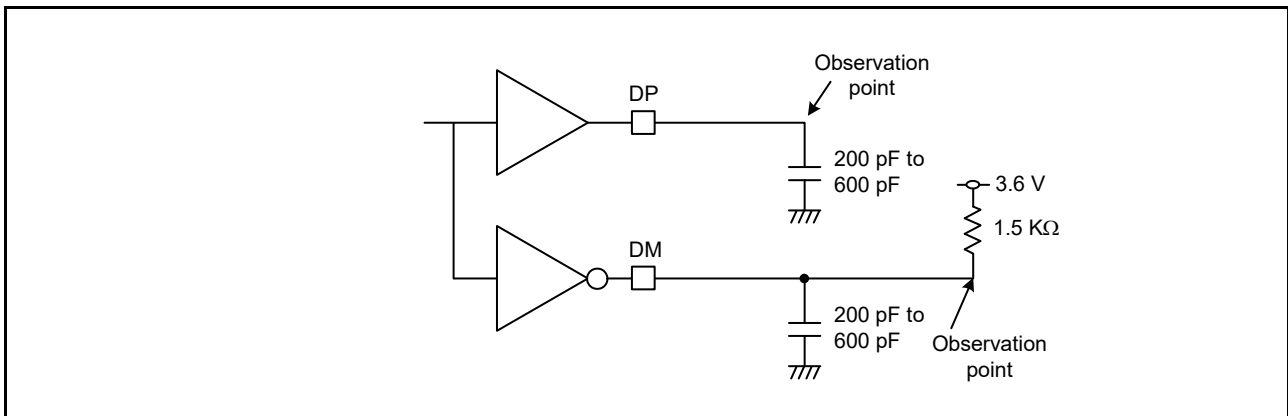


Figure 2.76 Test circuit for Low-Speed (LS) connection

2.4.2 USB External Supply

Table 2.47 USB regulator

Parameter	Min	Typ	Max	Unit	Test conditions	
VCC_USB supply current	VCC_USB_LDO ≥ 3.8V	-	-	50	mA	-
	VCC_USB_LDO ≥ 4.5V	-	-	100	mA	-
VCC_USB supply voltage	3.0	-	3.6	V	-	

2.5 ADC14 Characteristics

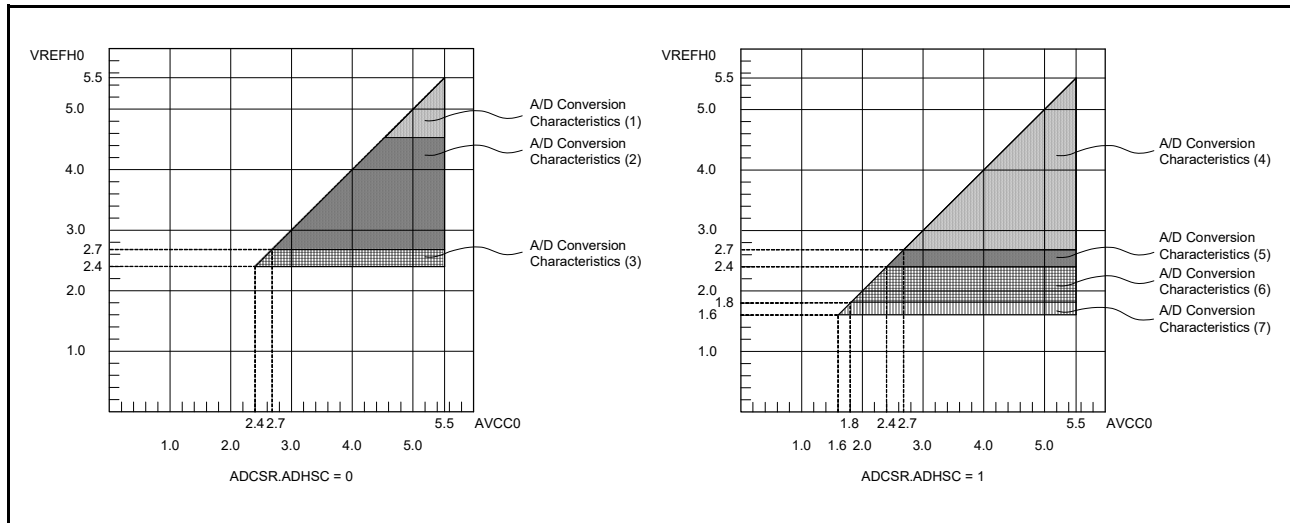


Figure 2.77 AVCC0 to VREFH0 voltage range

Table 2.48 A/D conversion characteristics (1) in High-speed A/D conversion mode (1 of 2)

Conditions: $V_{CC} = AV_{CC0} = 4.5$ to 5.5 V, $V_{REFH0} = 4.5$ to 5.5 V, $V_{SS} = AV_{SS0} = V_{REFL0} = 0$ V
Reference voltage range applied to the V_{REFH0} and V_{REFL0} .

Parameter	Min	Typ	Max	Unit	Test conditions	
Frequency	1	-	64	MHz	-	
Analog input capacitance*2	Cs	-	8 (reference data)	pF	High-precision channel	
		-	9 (reference data)	pF	Normal-precision channel	
Analog input resistance	Rs	-	2.5 (reference data)	kΩ	High-precision channel	
		-	6.7 (reference data)	kΩ	Normal-precision channel	
Analog input voltage range	Ain	0	VREFH0	V	-	
12-bit mode						
Resolution	-	-	12	Bit	-	
Conversion time*1 (Operation at PCLKC = 64 MHz)	Permissible signal source impedance Max. = 0.3 kΩ	0.70	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.13	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error	-	±0.5	±4.5	LSB	High-precision channel	
			±6.0	LSB	Other than above	
Full-scale error	-	±0.75	±4.5	LSB	High-precision channel	
			±6.0	LSB	Other than above	
Quantization error	-	±0.5	-	LSB	-	
Absolute accuracy	-	±1.25	±5.0	LSB	High-precision channel	
			±8.0	LSB	Other than above	
DNL differential nonlinearity error	-	±1.0	-	LSB	-	
INL integral nonlinearity error	-	±1.0	±3.0	LSB	-	
14-bit mode						
Resolution	-	-	14	Bit	-	

Table 2.48 A/D conversion characteristics (1) in High-speed A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 4.5 to 5.5 V, VREFH0 = 4.5 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test conditions
Conversion time*1 (Operation at PCLKC = 64 MHz)	Permissible signal source impedance Max. = 0.3 kΩ	0.80	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.22	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error		-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see [section 2.2.4, I/O V_{OH}, V_{OL}, and Other Characteristics](#).

Table 2.49 A/D conversion characteristics (2) in High-speed A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test conditions
Frequency		1	-	48	MHz	-
Analog input capacitance*2	Cs	-	-	8 (reference data)	pF	High-precision channel
		-	-	9 (reference data)	pF	Normal-precision channel
Analog input resistance	Rs	-	-	2.5 (reference data)	kΩ	High-precision channel
		-	-	6.7 (reference data)	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution		-	-	12	Bit	-
Conversion time*1 (Operation at PCLKC = 48 MHz)	Permissible signal source impedance Max. = 0.3 kΩ	0.94	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.50	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error		-	±0.5	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		-	±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-

Table 2.49 A/D conversion characteristics (2) in High-speed A/D conversion mode (2 of 2)

Conditions: $V_{CC} = AV_{CC0} = 2.7$ to 5.5 V, $V_{REFH0} = 2.7$ to 5.5 V, $V_{SS} = AV_{SS0} = V_{REFL0} = 0$ V
Reference voltage range applied to the V_{REFH0} and V_{REFL0} .

Parameter	Min	Typ	Max	Unit	Test conditions	
INL integral nonlinearity error	-	± 1.0	± 3.0	LSB	-	
14-bit mode						
Resolution	-	-	14	Bit	-	
Conversion time*1 (Operation at PCLKC = 48 MHz)	Permissible signal source impedance Max. = 0.3 k Ω	1.06	-	-	μ s	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.63	-	-	μ s	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error	-	± 2.0	± 18	LSB	High-precision channel	
			± 24.0	LSB	Other than above	
Full-scale error	-	± 3.0	± 18	LSB	High-precision channel	
			± 24.0	LSB	Other than above	
Quantization error	-	± 0.5	-	LSB	-	
Absolute accuracy	-	± 5.0	± 20	LSB	High-precision channel	
			± 32.0	LSB	Other than above	
DNL differential nonlinearity error	-	± 4.0	-	LSB	-	
INL integral nonlinearity error	-	± 4.0	± 12.0	LSB	-	

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see [section 2.2.4, I/O \$V_{OH}\$, \$V_{OL}\$, and Other Characteristics](#).

Table 2.50 A/D conversion characteristics (3) in High-speed A/D conversion mode (1 of 2)

Conditions: $V_{CC} = AV_{CC0} = 2.4$ to 5.5 V, $V_{REFH0} = 2.4$ to 5.5 V, $V_{SS} = AV_{SS0} = V_{REFL0} = 0$ V
Reference voltage range applied to the V_{REFH0} and V_{REFL0} .

Parameter	Min	Typ	Max	Unit	Test conditions	
Frequency	1	-	32	MHz	-	
Analog input capacitance*2	Cs	-	8 (reference data)	pF	High-precision channel	
			9 (reference data)	pF	Normal-precision channel	
Analog input resistance	Rs	-	2.5 (reference data)	k Ω	High-precision channel	
			6.7 (reference data)	k Ω	Normal-precision channel	
Analog input voltage range	Ain	0	V_{REFH0}	V	-	
12-bit mode						
Resolution	-	-	12	Bit	-	
Conversion time*1 (Operation at PCLKC = 32 MHz)	Permissible signal source impedance Max. = 1.3 k Ω	1.41	-	-	μ s	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		2.25	-	-	μ s	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error	-	± 0.5	± 4.5	LSB	High-precision channel	
			± 6.0	LSB	Other than above	
Full-scale error	-	± 0.75	± 4.5	LSB	High-precision channel	
			± 6.0	LSB	Other than above	
Quantization error	-	± 0.5	-	LSB	-	
Absolute accuracy	-	± 1.25	± 5.0	LSB	High-precision channel	
			± 8.0	LSB	Other than above	

Table 2.50 A/D conversion characteristics (3) in High-speed A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter	Min	Typ	Max	Unit	Test conditions	
DNL differential nonlinearity error	-	±1.0	-	LSB	-	
INL integral nonlinearity error	-	±1.0	±3.0	LSB	-	
14-bit mode						
Resolution	-	-	14	Bit	-	
Conversion time*1 (Operation at PCLKC = 32 MHz)	Permissible signal source impedance Max. = 1.3 kΩ	1.59	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		2.44	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error	-	±2.0	±18	LSB	High-precision channel	
			±24.0	LSB	Other than above	
Full-scale error	-	±3.0	±18	LSB	High-precision channel	
			±24.0	LSB	Other than above	
Quantization error	-	±0.5	-	LSB	-	
Absolute accuracy	-	±5.0	±20	LSB	High-precision channel	
			±32.0	LSB	Other than above	
DNL differential nonlinearity error	-	±4.0	-	LSB	-	
INL integral nonlinearity error	-	±4.0	±12.0	LSB	-	

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see [section 2.2.4, I/O V_{OH}, V_{OL}, and Other Characteristics](#).

Table 2.51 A/D conversion characteristics (4) in Low-power A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter	Min	Typ	Max	Unit	Test conditions	
Frequency	1	-	24	MHz	-	
Analog input capacitance*2	Cs	-	-	8 (reference data)	pF	High-precision channel
		-	-	9 (reference data)	pF	Normal-precision channel
Analog input resistance	Rs	-	-	2.5 (reference data)	kΩ	High-precision channel
		-	-	6.7 (reference data)	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution	-	-	12	Bit	-	
Conversion time*1 (Operation at PCLKC = 24 MHz)	Permissible signal source impedance Max. = 1.1 kΩ	2.25	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
		3.38	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error	-	±0.5	±4.5	LSB	High-precision channel	
			±6.0	LSB	Other than above	
Full-scale error	-	±0.75	±4.5	LSB	High-precision channel	
			±6.0	LSB	Other than above	
Quantization error	-	±0.5	-	LSB	-	

Table 2.51 A/D conversion characteristics (4) in Low-power A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test conditions
Absolute accuracy			±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-
14-bit mode						
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKC = 24 MHz)	Permissible signal source impedance Max. = 1.1 kΩ	2.50	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
					μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error			±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error			±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy			±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH}, V_{OL}, and Other Characteristics.

Table 2.52 A/D conversion characteristics (5) in Low-power A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test conditions
Frequency		1	-	16	MHz	-
Analog input capacitance*2	Cs			8 (reference)	pF	High-precision channel
				9 (reference)	pF	Normal-precision channel
Analog input resistance	Rs			2.5 (reference)	kΩ	High-precision channel
				6.7 (reference)	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution		-	-	12	Bit	-
Conversion time*1 (Operation at PCLKC = 16 MHz)	Permissible signal source impedance Max. = 2.2 kΩ	3.38	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
					μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error			±0.5	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error			±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above

Table 2.52 A/D conversion characteristics (5) in Low-power A/D conversion mode (2 of 2)

Conditions: $V_{CC} = AV_{CC0} = 2.4$ to 5.5 V, $V_{REFH0} = 2.4$ to 5.5 V, $V_{SS} = AV_{SS0} = V_{REFL0} = 0$ V
Reference voltage range applied to the V_{REFH0} and V_{REFL0} .

Parameter		Min	Typ	Max	Unit	Test conditions
Quantization error		-	± 0.5	-	LSB	-
Absolute accuracy		-	± 1.25	± 5.0	LSB	High-precision channel
				± 8.0	LSB	Other than above
DNL differential nonlinearity error		-	± 1.0	-	LSB	-
INL integral nonlinearity error		-	± 1.0	± 3.0	LSB	-
14-bit mode						
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKC = 16 MHz)	Permissible signal source impedance Max. = 2.2 k Ω	3.75	-	-	μ s	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
				5.44	-	μ s
Offset error		-	± 2.0	± 18	LSB	High-precision channel
				± 24.0	LSB	Other than above
Full-scale error		-	± 3.0	± 18	LSB	High-precision channel
				± 24.0	LSB	Other than above
Quantization error		-	± 0.5	-	LSB	-
Absolute accuracy		-	± 5.0	± 20	LSB	High-precision channel
				± 32.0	LSB	Other than above
DNL differential nonlinearity error		-	± 4.0	-	LSB	-
INL integral nonlinearity error		-	± 4.0	± 12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH} , V_{OL} , and Other Characteristics.

Table 2.53 A/D conversion characteristics (6) in Low-power A/D conversion mode (1 of 2)

Conditions: $V_{CC} = AV_{CC0} = 1.8$ to 5.5 V ($AV_{CC0} = V_{CC}$ when $V_{CC} < 2.0$ V), $V_{REFH0} = 1.8$ to 5.5 V, $V_{SS} = AV_{SS0} = V_{REFL0} = 0$ V
Reference voltage range applied to the V_{REFH0} and V_{REFL0} .

Parameter		Min	Typ	Max	Unit	Test conditions
Frequency		1	-	8	MHz	-
Analog input capacitance*2	C_s	-	-	8 (reference data)	pF	High-precision channel
				9 (reference data)	pF	Normal-precision channel
Analog input resistance	R_s	-	-	3.8 (reference data)	k Ω	High-precision channel
				8.2 (reference data)	k Ω	Normal-precision channel
Analog input voltage range	A_{in}	0	-	V_{REFH0}	V	-
12-bit mode						
Resolution		-	-	12	Bit	-
Conversion time*1 (Operation at PCLKC = 8 MHz)	Permissible signal source impedance Max. = 5 k Ω	6.75	-	-	μ s	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
				10.13	-	μ s
Offset error		-	± 1.0	± 7.5	LSB	High-precision channel
				± 10.0	LSB	Other than above

Table 2.53 A/D conversion characteristics (6) in Low-power A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.8 to 5.5 V, VSS = AVSS0 = VREFL0 = 0 V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test conditions
Full-scale error		-	±1.5	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±3.0	±8.0	LSB	High-precision channel
				±12.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-
14-bit mode						
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKC = 8 MHz)	Permissible signal source impedance Max. = 5 kΩ	7.50	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
					μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±4.0	±30.0	LSB	High-precision channel
				±40.0	LSB	Other than above
Full-scale error		-	±6.0	±30.0	LSB	High-precision channel
				±40.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±12.0	±32.0	LSB	High-precision channel
				±48.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see [section 2.2.4, I/O V_{OH}, V_{OL}, and Other Characteristics](#).

Table 2.54 A/D conversion characteristics (7) in Low-power A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.6 to 5.5 V, VSS = AVSS0 = VREFL0 = 0
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test conditions
Frequency		1	-	4	MHz	-
Analog input capacitance*2	Cs	-	-	8 (reference data)	pF	High-precision channel
				9 (reference data)	pF	Normal-precision channel
Analog input resistance	Rs	-	-	13.1 (reference data)	kΩ	High-precision channel
				14.3 (reference data)	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution		-	-	12	Bit	-
Conversion time*1 (Operation at PCLKC = 4 MHz)	Permissible signal source impedance Max. = 9.9 kΩ	13.5	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
					μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h

Table 2.54 A/D conversion characteristics (7) in Low-power A/D conversion mode (2 of 2)

Conditions: $V_{CC} = AV_{CC0} = 1.6$ to 5.5 V ($AV_{CC0} = V_{CC}$ when $V_{CC} < 2.0$ V), $V_{REFH0} = 1.6$ to 5.5 V, $V_{SS} = AV_{SS0} = V_{REFL0} = 0$
Reference voltage range applied to the V_{REFH0} and V_{REFL0} .

Parameter	Min	Typ	Max	Unit	Test conditions	
Offset error	-	± 1.0	± 7.5	LSB	High-precision channel	
			± 10.0	LSB	Other than above	
Full-scale error	-	± 1.5	± 7.5	LSB	High-precision channel	
			± 10.0	LSB	Other than above	
Quantization error	-	± 0.5	-	LSB	-	
Absolute accuracy	-	± 3.0	± 8.0	LSB	High-precision channel	
			± 12.0	LSB	Other than above	
DNL differential nonlinearity error	-	± 1.0	-	LSB	-	
INL integral nonlinearity error	-	± 1.0	± 3.0	LSB	-	
14-bit mode						
Resolution	-	-	14	Bit	-	
Conversion time*1 (Operation at PCLKC = 4 MHz)	Permissible signal source impedance Max. = 9.9 k Ω	15.0	-	-	μ s	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
		21.75	-	-	μ s	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error	-	± 4.0	± 30.0	LSB	High-precision channel	
			± 40.0	LSB	Other than above	
Full-scale error	-	± 6.0	± 30.0	LSB	High-precision channel	
			± 40.0	LSB	Other than above	
Quantization error	-	± 0.5	-	LSB	-	
Absolute accuracy	-	± 12.0	± 32.0	LSB	High-precision channel	
			± 48.0	LSB	Other than above	
DNL differential nonlinearity error	-	± 4.0	-	LSB	-	
INL integral nonlinearity error	-	± 4.0	± 12.0	LSB	-	

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH} , V_{OL} , and Other Characteristics.

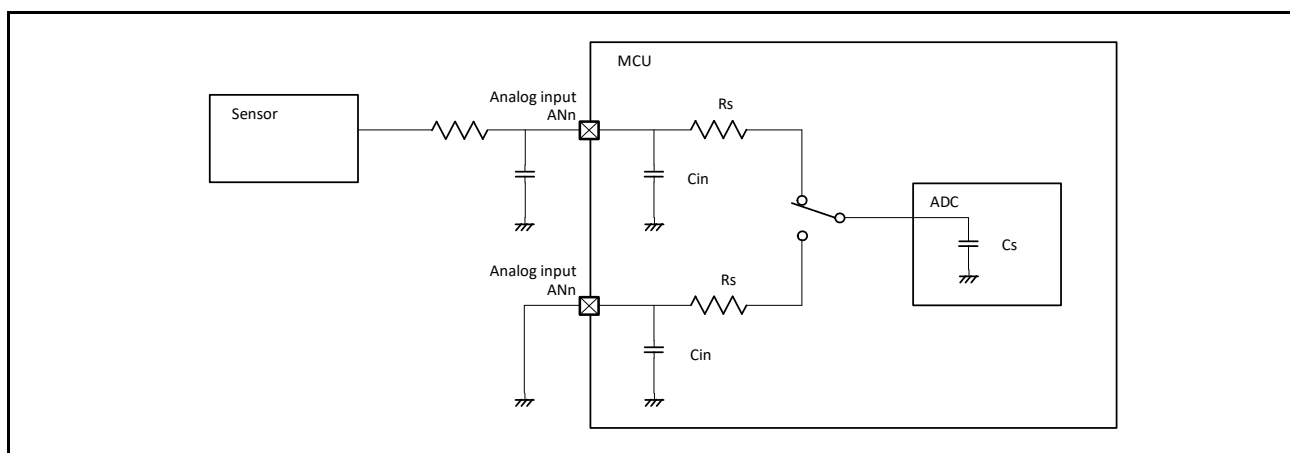
**Figure 2.78 Equivalent circuit for analog input**

Table 2.55 14-Bit A/D converter channel classification

Classification	Channel	Conditions	Remarks
High-precision channel	AN000 to AN015	AVCC0 = 1.6 to 5.5 V	Pins AN000 to AN015 cannot be used as general I/O, IRQ8, IRQ9 inputs, and TS transmission, when the A/D converter is in use
Normal-precision channel	AN016 to AN027		
Internal reference voltage input channel	Internal reference voltage	AVCC0 = 2.0 to 5.5 V	-
Temperature sensor input channel	Temperature sensor output	AVCC0 = 2.0 to 5.5 V	-

Table 2.56 A/D internal reference voltage characteristics

Conditions: VCC = AVCC0 = VREFH0 = 2.0 to 5.5 V*1

Parameter	Min	Typ	Max	Unit	Test conditions
Internal reference voltage input channel*2	1.36	1.43	1.50	V	-
Frequency*3	1	-	2	MHz	-
Sampling time*4	5.0	-	-	μs	-

Note 1. The internal reference voltage cannot be selected for input channels when AVCC0 < 2.0 V.

Note 2. The 14-bit A/D internal reference voltage indicates the voltage when the internal reference voltage is input to the 14-bit A/D converter.

Note 3. This is a parameter for ADC14 when the internal reference voltage is used as the high-potential reference voltage.

Note 4. This is a parameter for ADC14 when the internal reference voltage is selected for an analog input channel in ADC14.

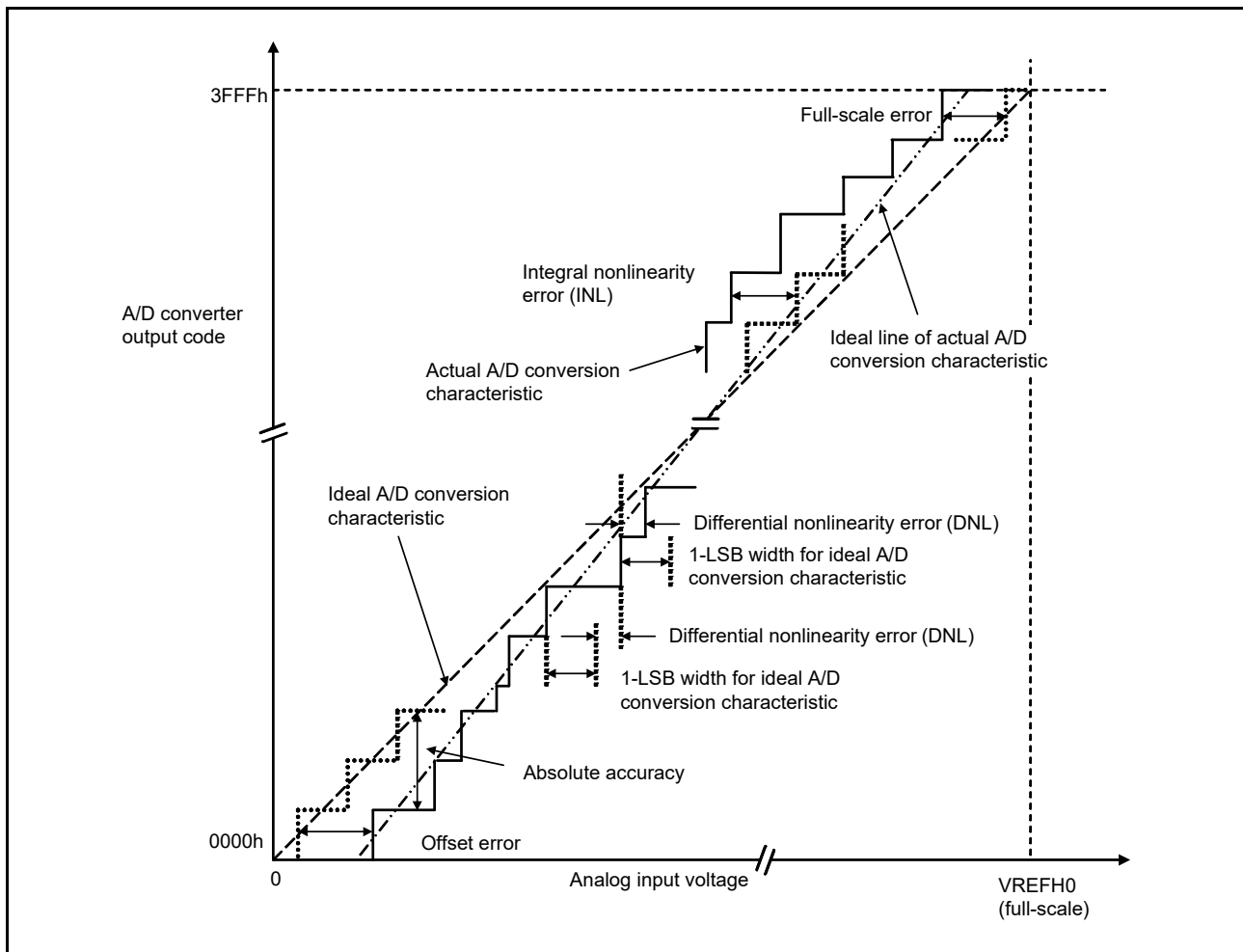


Figure 2.79 Illustration of 14-bit A/D converter characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as the analog input voltage. For example, if 12-bit resolution is used and the reference voltage $V_{REFH0} = 3.072$ V, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, 1.5 mV are used as the analog input voltages. If analog input voltage is 6 mV, an absolute accuracy of ± 5 LSB means that the actual A/D conversion result is in the range of 003h to 00Dh, though an output code of 008h can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB width based on the ideal A/D conversion characteristics and the width of the actually output code.

Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.

2.6 DAC12 Characteristics

Table 2.57 D/A conversion characteristics (1)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Reference voltage = VREFH or VREFL selected

Parameter	Min	Typ	Max	Unit	Test conditions
Resolution	-	-	12	bit	-
Resistive load	30	-	-	kΩ	-
Capacitive load	-	-	50	pF	-
Output voltage range	0.35	-	AVCC0 – 0.47	V	-
DNL differential nonlinearity error	-	±0.5	±1.0	LSB	-
INL integral nonlinearity error	-	±2.0	±8.0	LSB	-
Offset error	-	-	±20	mV	-
Full-scale error	-	-	±20	mV	-
Output impedance	-	5	-	Ω	-
Conversion time	-	-	30	μs	-

Table 2.58 D/A conversion characteristics (2)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Reference voltage = AVCC0 or AVSS0 selected

Parameter	Min	Typ	Max	Unit	Test conditions
Resolution	-	-	12	bit	-
Resistive load	30	-	-	kΩ	-
Capacitive load	-	-	50	pF	-
Output voltage range	0.35	-	AVCC0 – 0.47	V	-
DNL differential nonlinearity error	-	±0.5	±2.0	LSB	-
INL integral nonlinearity error	-	±2.0	±8.0	LSB	-
Offset error	-	-	±30	mV	-
Full-scale error	-	-	±30	mV	-
Output impedance	-	5	-	Ω	-
Conversion time	-	-	30	μs	-

Table 2.59 D/A conversion characteristics (3)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Reference voltage = internal reference voltage selected

Parameter	Min	Typ	Max	Unit	Test conditions
Resolution	-	-	12	bit	-
Internal reference voltage (Vbgr)	1.36	1.43	1.50	V	-
Resistive load	30	-	-	kΩ	-
Capacitive load	-	-	50	pF	-
Output voltage range	0.35	-	Vbgr	V	-
DNL differential nonlinearity error	-	±2.0	±16.0	LSB	-
INL integral nonlinearity error	-	±8.0	±16.0	LSB	-
Offset error	-	-	±30	mV	-
Output impedance	-	5	-	Ω	-
Conversion time	-	-	30	μs	-

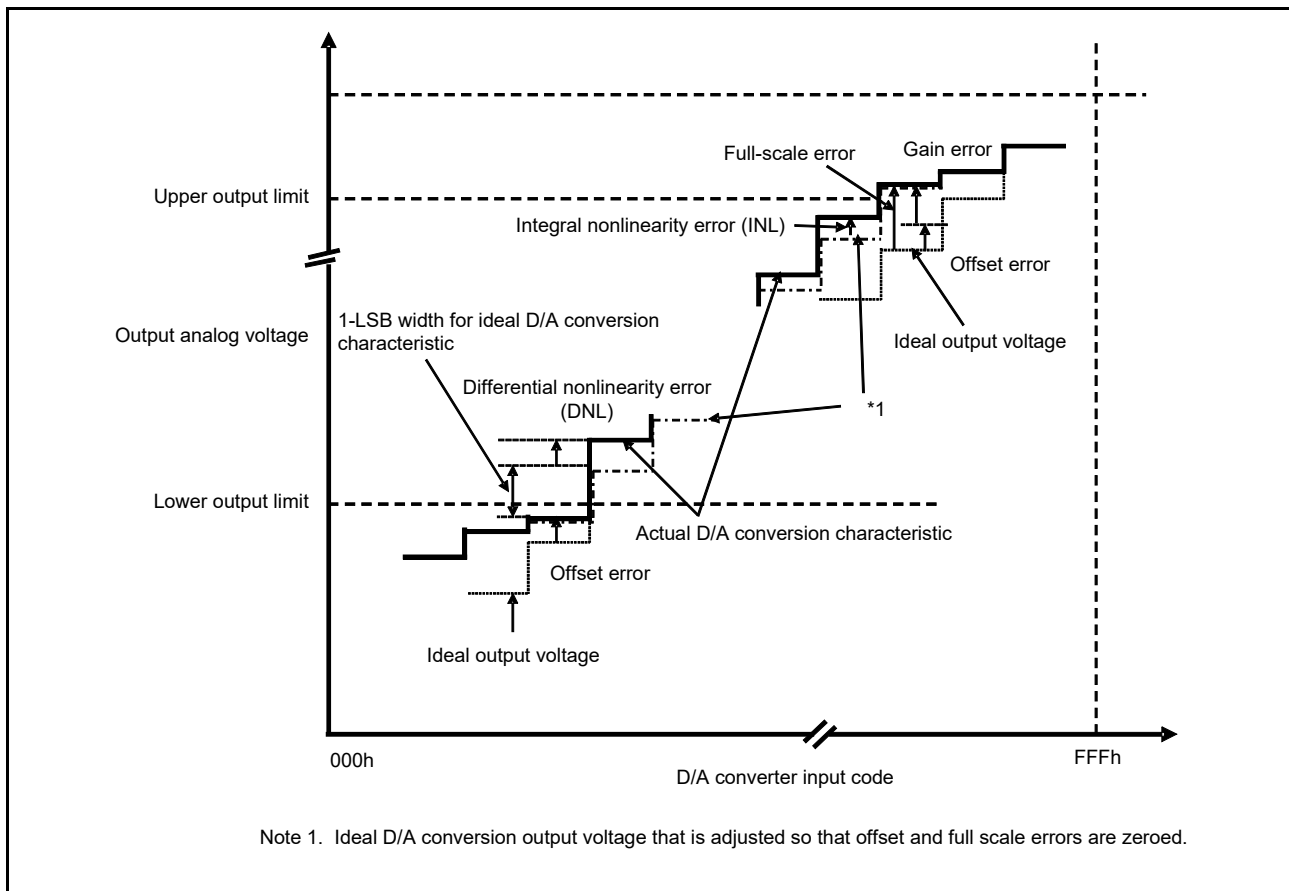


Figure 2.80 Illustration of D/A converter characteristic terms

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal output voltage based on the ideal conversion characteristic when the measured offset and full-scale errors are zeroed, and the actual output voltage.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB voltage width based on the ideal D/A conversion characteristics and the width of the actual output voltage.

Offset error

Offset error is the difference between the highest actual output voltage that falls below the lower output limit and the ideal output voltage based on the input code.

Full-scale error

Full-scale error is the difference between the lowest actual output voltage that exceeds the upper output limit and the ideal output voltage based on the input code.

2.7 TSN Characteristics

Table 2.60 TSN characteristics

Conditions: VCC = AVCC0 = 2.0 to 5.5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Relative accuracy	-	-	±1.5	-	°C	2.4 V or above
	-	-	±2.0	-	°C	Below 2.4 V
Temperature slope	-	-	-3.65	-	mV/°C	-
Output voltage (at 25°C)	-	-	1.05	-	V	VCC = 3.3 V
Temperature sensor start time	t _{START}	-	-	5	µs	-
Sampling time	-	5	-	-	µs	-

2.8 OSC Stop Detect Characteristics

Table 2.61 Oscillation stop detection circuit characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Detection time	t _{dr}	-	-	1	ms	Figure 2.81

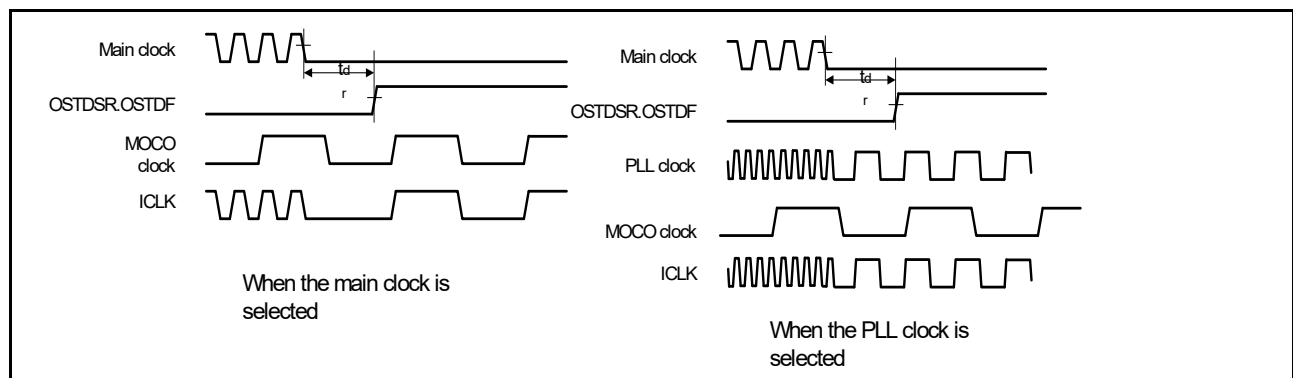


Figure 2.81 Oscillation stop detection timing

2.9 POR and LVD Characteristics

Table 2.62 Power-on reset circuit and voltage detection circuit characteristics (1)

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Voltage detection level*1	Power-on reset (POR)	V_{POR}	1.27	1.42	1.57	V	Figure 2.82, Figure 2.83
	Voltage detection circuit (LVD0)*2	V_{det0_0}	3.68	3.85	4.00	V	Figure 2.84 At falling edge VCC
		V_{det0_1}	2.68	2.85	2.96		
		V_{det0_2}	2.38	2.53	2.64		
		V_{det0_3}	1.78	1.90	2.02		
		V_{det0_4}	1.60	1.69	1.82		
	Voltage detection circuit (LVD1)*3	V_{det1_0}	4.13	4.29	4.45	V	Figure 2.85 At falling edge VCC
		V_{det1_1}	3.98	4.16	4.30		
		V_{det1_2}	3.86	4.03	4.18		
		V_{det1_3}	3.68	3.86	4.00		
		V_{det1_4}	2.98	3.10	3.22		
		V_{det1_5}	2.89	3.00	3.11		
		V_{det1_6}	2.79	2.90	3.01		
		V_{det1_7}	2.68	2.79	2.90		
		V_{det1_8}	2.58	2.68	2.78		
		V_{det1_9}	2.48	2.58	2.68		
		V_{det1_A}	2.38	2.48	2.58		
		V_{det1_B}	2.10	2.20	2.30		
		V_{det1_C}	1.84	1.96	2.05		
		V_{det1_D}	1.74	1.86	1.95		
V_{det1_E}	1.63	1.75	1.84				
V_{det1_F}	1.60	1.65	1.73				
Voltage detection circuit (LVD2)*4	V_{det2_0}	4.11	4.31	4.48	V	Figure 2.86 At falling edge VCC	
	V_{det2_1}	3.97	4.17	4.34			
	V_{det2_2}	3.83	4.03	4.20			
	V_{det2_3}	3.64	3.84	4.01			

Note 1. These characteristics apply when noise is not superimposed on the power supply. When a setting causes this voltage detection level to overlap with that of the voltage detection circuit, it cannot be specified whether LVD1 or LVD2 is used for voltage detection.

Note 2. # in the symbol $V_{det0_#}$ denotes the value of the OFS1.VDSEL1[2:0] bits.

Note 3. # in the symbol $V_{det1_#}$ denotes the value of the LVDLVLR.LVD1LVL[4:0] bits.

Note 4. # in the symbol $V_{det2_#}$ denotes the value of the LVDLVLR.LVD2LVL[2:0] bits.

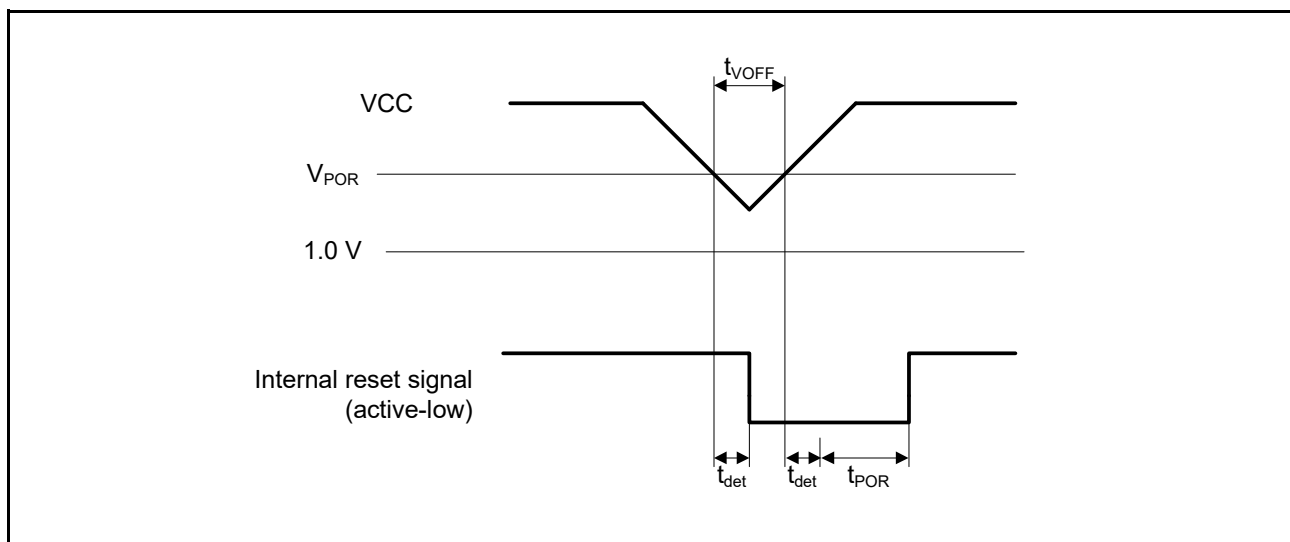
Table 2.63 Power-on reset circuit and voltage detection circuit characteristics (2)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
Wait time after power-on reset cancellation	LVD0:enable	t_{POR}	-	1.7	-	ms	-
	LVD0:disable	t_{POR}	-	1.3	-	ms	-
Wait time after voltage monitor 0,1,2 reset cancellation	LVD0:enable*1	$t_{LVD0,1,2}$	-	0.6	-	ms	-
	LVD0:disable*2	$t_{LVD1,2}$	-	0.2	-	ms	-
Response delay*3	t_{det}	-	-	350	μ s	Figure 2.82, Figure 2.83	
Minimum VCC down time	t_{VOFF}	450	-	-	μ s	Figure 2.82, VCC = 1.0 V or above	
Power-on reset enable time	t_W (POR)	1	-	-	ms	Figure 2.83, VCC = below 1.0 V	
LVD operation stabilization time (after LVD is enabled)	T_d (E-A)	-	-	300	μ s	Figure 2.85, Figure 2.86	
Hysteresis width (POR)	V_{PORH}	-	110	-	mV	-	
Hysteresis width (LVD0, LVD1 and LVD2)	V_{LVH}	-	60	-	mV	LVD0 selected	
		-	100	-	mV	V_{det1_0} to V_{det1_2} selected.	
		-	60	-	mV	V_{det1_3} to V_{det1_g} selected.	
		-	50	-	mV	V_{det1_A} or V_{det1_B} selected.	
		-	40	-	mV	V_{det1_C} or V_{det1_F} selected.	
		-	60	-	mV	LVD2 selected	

Note 1. When OFS1.LVDAS = 0.

Note 2. When OFS1.LVDAS = 1.

Note 3. The minimum VCC down time indicates the time when VCC is below the minimum value of voltage detection levels V_{POR} , V_{det0} , V_{det1} , and V_{det2} for the POR/LVD.

**Figure 2.82 Voltage detection reset timing**

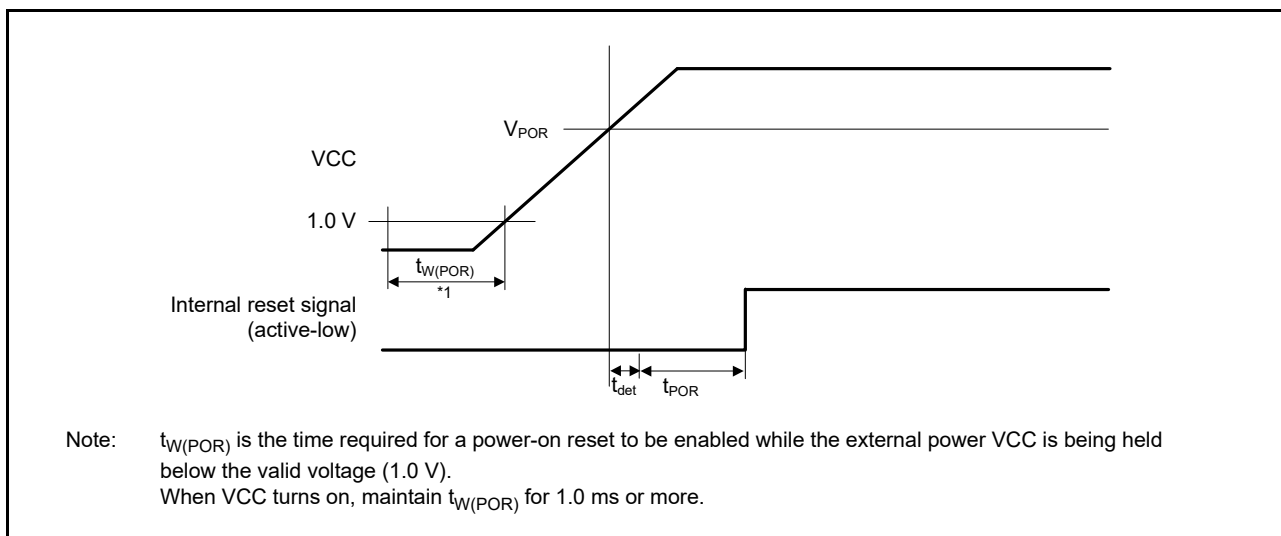


Figure 2.83 Power-on reset timing

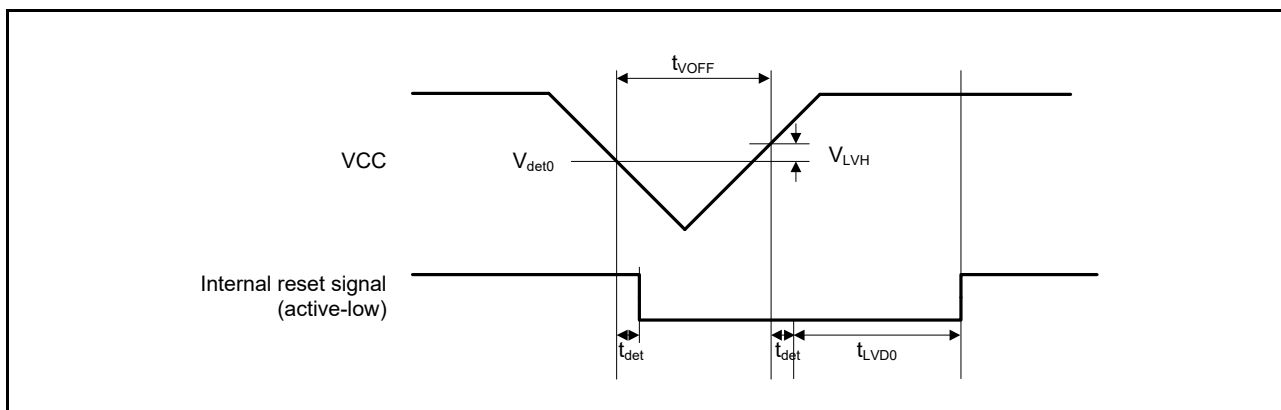


Figure 2.84 Voltage detection circuit timing (V_{det0})

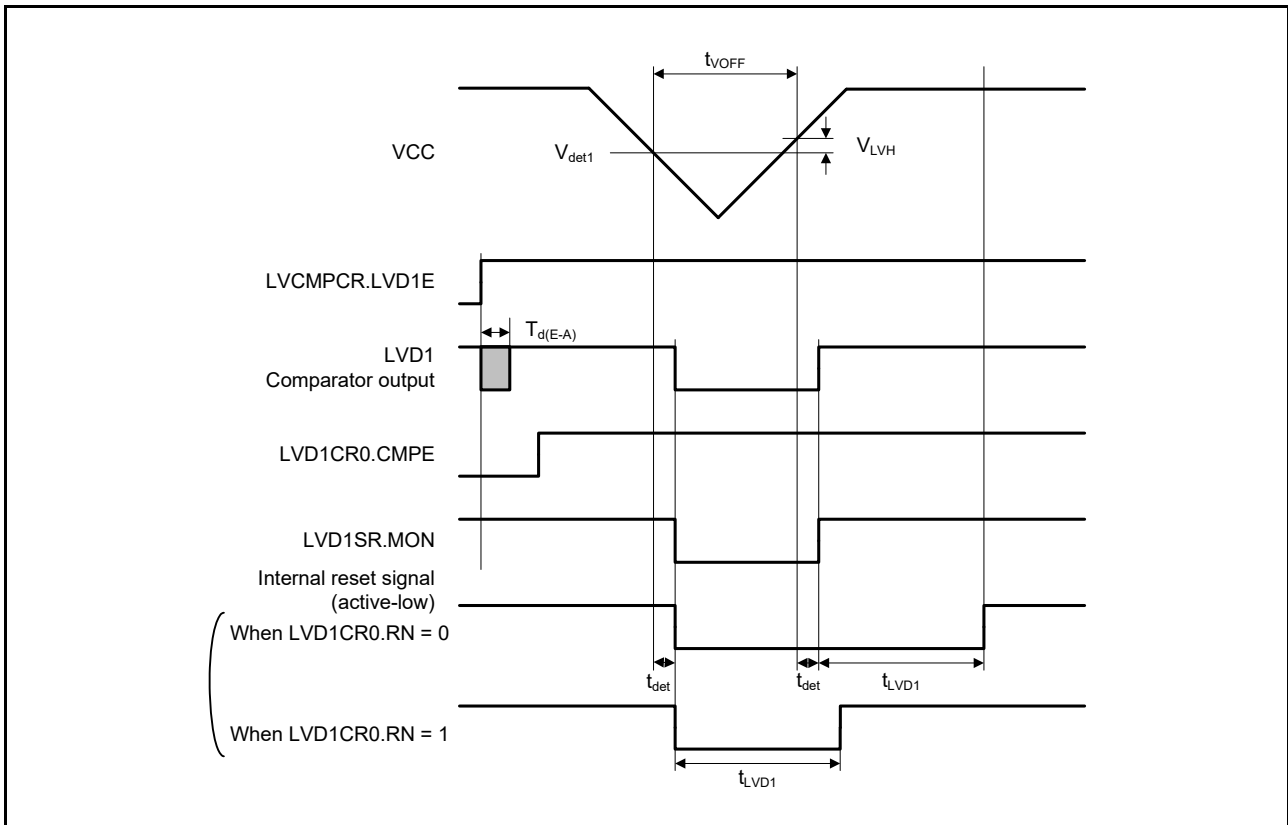


Figure 2.85 Voltage detection circuit timing (V_{det1})

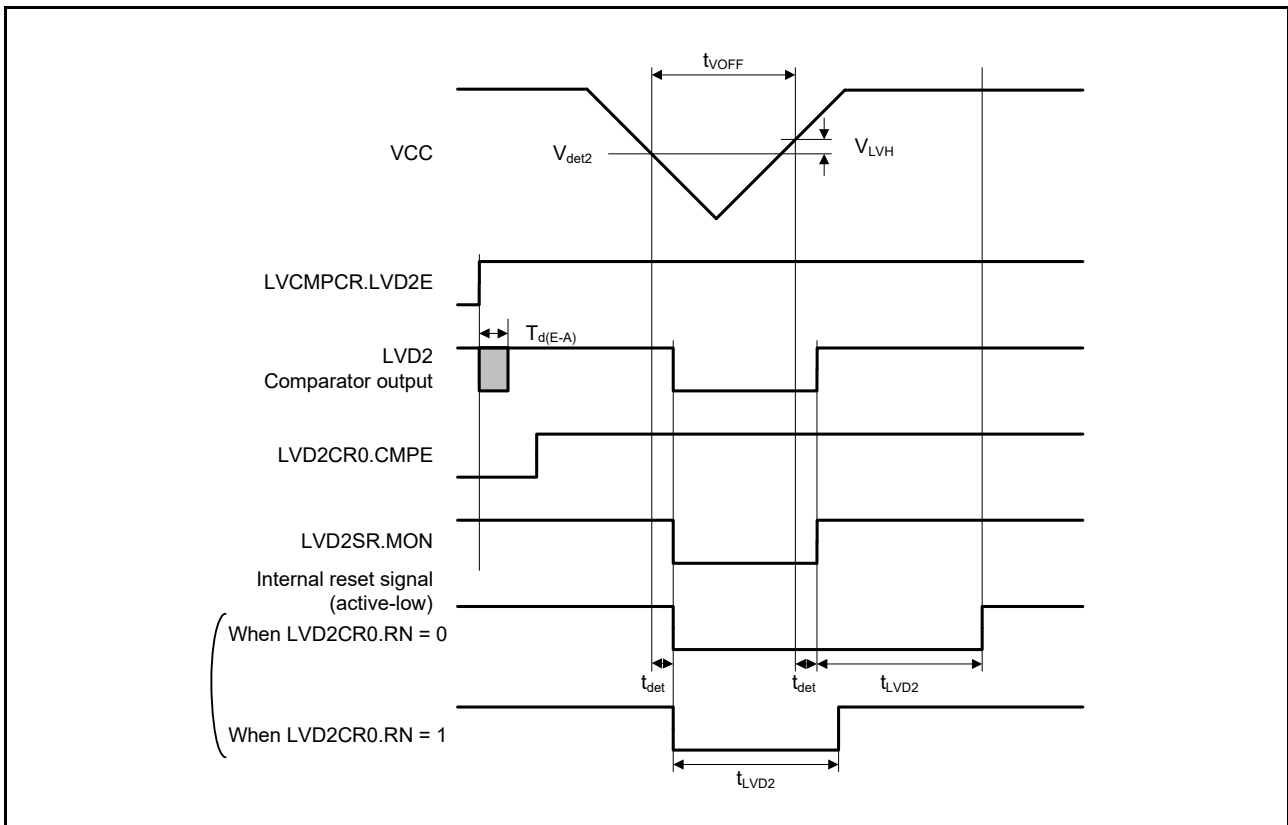


Figure 2.86 Voltage detection circuit timing (V_{det2})

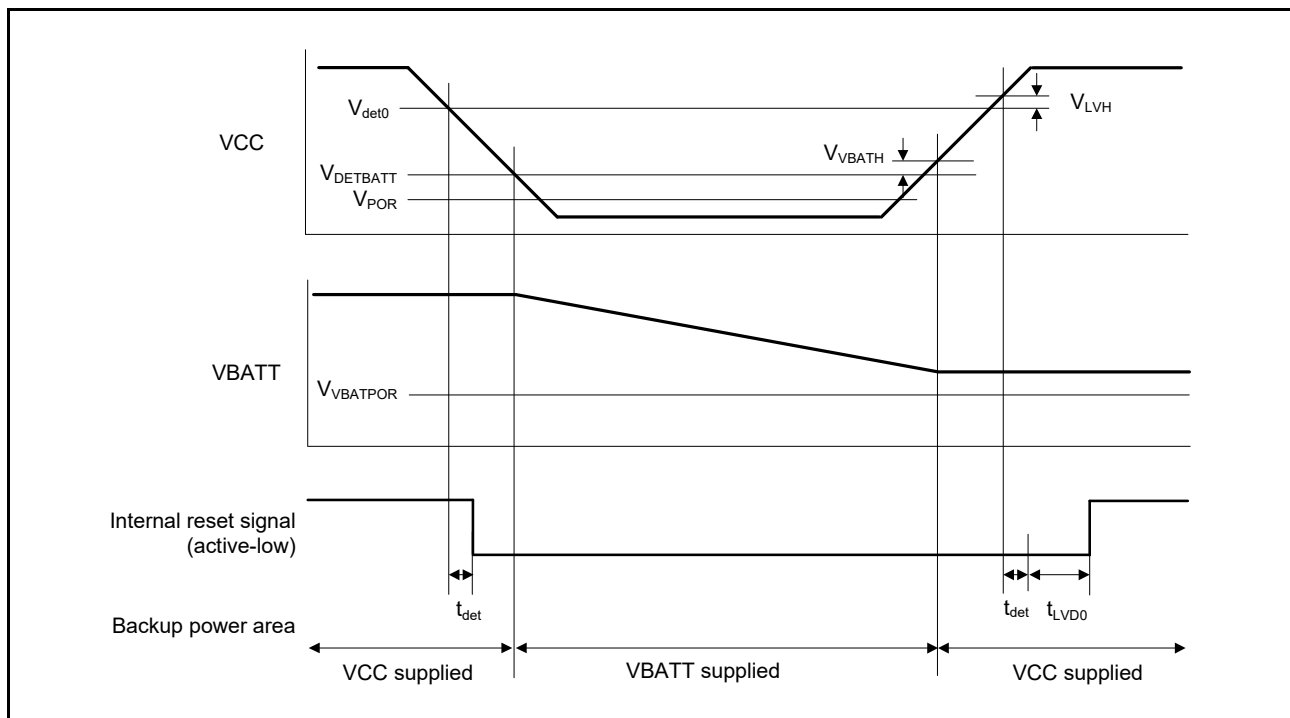
2.10 Battery Backup Function Characteristics

Table 2.64 Battery Backup Function Characteristics

Conditions: VCC = AVCC0 = 1.6V to 5.5V, VBATT = 1.6 to 3.6 V, VSS = AVSS0 = 0V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
Voltage level for switching to battery backup (falling)	$V_{DET\ BATT}$	1.99	2.09	2.19	V	Figure 2.87, Figure 2.88	
Hysteresis width for switching to battery back up	$V_{VBAT\ TH}$	-	100	-	mV		
VCC-off period for starting power supply switching	$t_{OFF\ BATT}$	300	-	-	μs	-	
Voltage detection level VBATT_Power-on reset (VBATT_POR)	$V_{VBAT\ POR}$	1.30	1.40	1.50	V	Figure 2.87, Figure 2.88	
Wait time after VBATT_POR reset time cancellation	$t_{VBAT\ POR}$	-	-	3	mS	-	
Level for detection of voltage drop on the VBATT pin (falling)	VBTLVDLVL[1:0] = 10b	$V_{DET\ BAT\ LVD}$	2.11	2.2	2.29	V	Figure 2.89
	VBTLVDLVL[1:0] = 11b		1.92	2	2.08	V	
Hysteresis width for VBATT pin LVD	$V_{VBAT\ LVD\ TH}$	-	50	-	mV		
VBATT pin LVD operation stabilization time	t_{d_vbat}	-	-	300	μs	Figure 2.89	
VBATT pin LVD response delay time	t_{det_vbat}	-	-	350	μs		
Allowable voltage change rising/falling gradient	$dt/dVCC$	1.0	-	-	ms/V	-	
VCC voltage level for access to the VBATT backup registers	$V_{_BKBATT}$	1.8	-	-	V	-	

Note: The VCC-off period for starting power supply switching indicates the period in which VCC is below the minimum value of the voltage level for switching to battery backup ($V_{DET\ BATT}$).

**Figure 2.87 Power supply switching and LVD0 reset Timing**

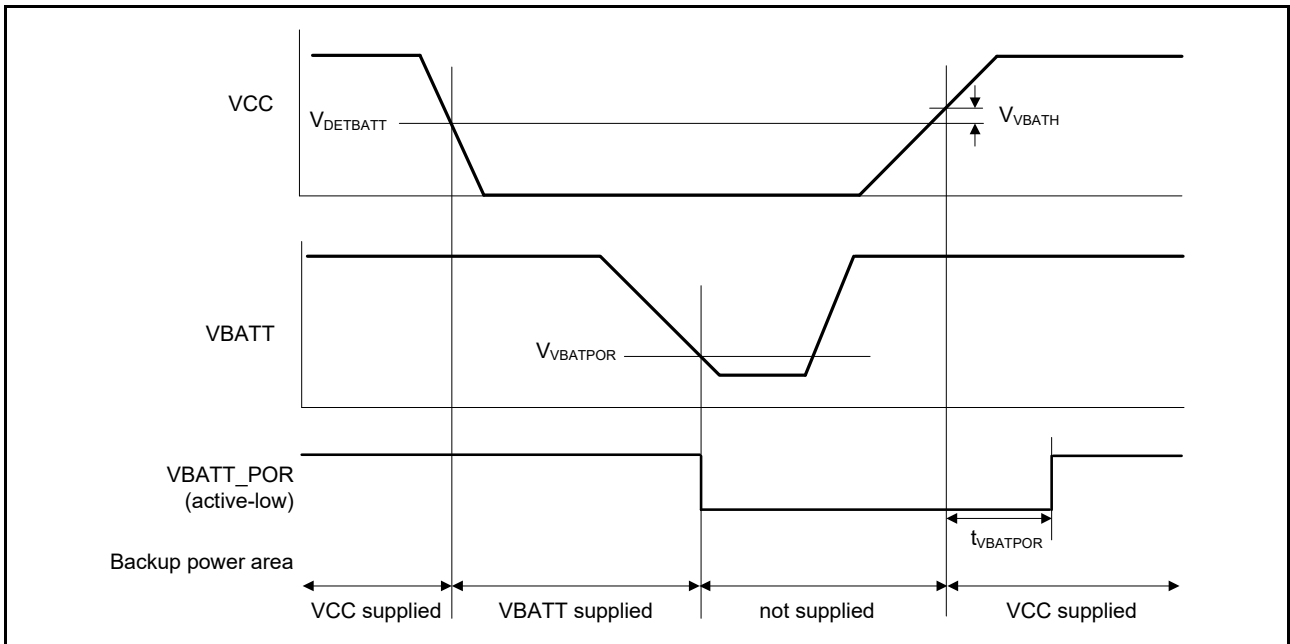


Figure 2.88 VBATT_POR reset timing

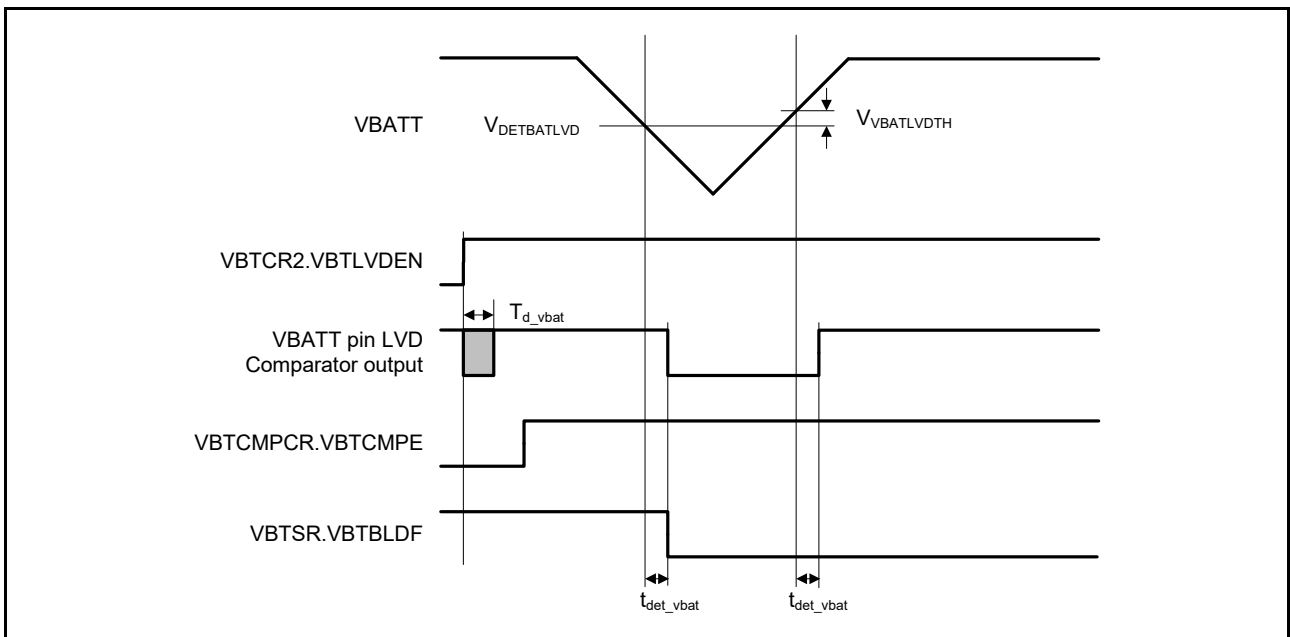


Figure 2.89 VBATT pin voltage detection circuit timing

Table 2.65 VBATT-I/O characteristics

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
VBATWIO n/I/O output characteristics (n = 0 to 2)	VCC > V _{DET} BATT	VCC = 4.0 to 5.5 V	V _{OH}	VCC - 0.8	-	-	V	I _{OH} = -200 μA
			V _{OL}	-	-	0.8		I _{OL} = 200 μA
		VCC = 2.7 to 4.0 V	V _{OH}	VCC - 0.5	-	-		I _{OH} = -100 μA
			V _{OL}	-	-	0.5		I _{OL} = 100 μA
		VCC = V _{DET} BATT to 2.7 V	V _{OH}	VCC - 0.3	-	-		I _{OH} = -50 μA
			V _{OL}	-	-	0.3		I _{OL} = 50 μA
	VCC < V _{DET} BATT	VBATT = 2.7 to 3.6 V	V _{OH}	V _{BATT} - 0.5	-	-		I _{OH} = -100 μA
			V _{OL}	-	-	0.5		I _{OL} = 100 μA
		VBATT = 1.6 to 2.7 V	V _{OH}	V _{BATT} - 0.3	-	-		I _{OH} = -50 μA
			V _{OL}	-	-	0.3		I _{OL} = 50 μA

2.11 CTSU Characteristics

Table 2.66 CTSU characteristics

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
External capacitance connected to TSCAP pin	C _{tscap}	9	10	11	nF	-
TS pin capacitive load	C _{base}	-	-	50	pF	-
Permissible output high current	ΣI _{oH}	-	-	-24	mA	When the mutual capacitance method is applied

2.12 Segment LCD Controller/Driver Characteristics

2.12.1 Resistance Division Method

[Static Display Mode]

Table 2.67 Resistance division method LCD characteristics (1)

Conditions: VL4 ≤ VCC ≤ 5.5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
LCD drive voltage	V _{L4}	2.0	-	VCC	V	-

[1/2 Bias Method, 1/4 Bias Method]

Table 2.68 Resistance division method LCD characteristics (2)

Conditions: VL4 ≤ VCC ≤ 5.5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
LCD drive voltage	V _{L4}	2.7	-	VCC	V	-

[1/3 Bias Method]

Table 2.69 Resistance division method LCD characteristics (3)

Conditions: VL4 ≤ VCC ≤ 5.5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
LCD drive voltage	V _{L4}	2.5	-	VCC	V	-

2.12.2 Internal Voltage Boosting Method

[1/3 Bias Method]

Table 2.70 Internal voltage boosting method LCD characteristics

Conditions: VCC = AVCC0 = 1.8 V to 5.5 V

Parameter	Symbol	Conditions		Min	Typ	Max	Unit	Test conditions
LCD output voltage variation range	V _{L1}	C1 to C4*1 = 0.47 μF	VLCD = 04h	0.90	1.0	1.08	V	-
			VLCD = 05h	0.95	1.05	1.13	V	-
			VLCD = 06h	1.00	1.10	1.18	V	-
			VLCD = 07h	1.05	1.15	1.23	V	-
			VLCD = 08h	1.10	1.20	1.28	V	-
			VLCD = 09h	1.15	1.25	1.33	V	-
			VLCD = 0Ah	1.20	1.30	1.38	V	-
			VLCD = 0Bh	1.25	1.35	1.43	V	-
			VLCD = 0Ch	1.30	1.40	1.48	V	-
			VLCD = 0Dh	1.35	1.45	1.53	V	-
			VLCD = 0Eh	1.40	1.50	1.58	V	-
			VLCD = 0Fh	1.45	1.55	1.63	V	-
			VLCD = 10h	1.50	1.60	1.68	V	-
			VLCD = 11h	1.55	1.65	1.73	V	-
VLCD = 12h	1.60	1.70	1.78	V	-			
VLCD = 13h	1.65	1.75	1.83	V	-			
Doubler output voltage	V _{L2}	C1 to C4*1 = 0.47 μF		$2 \times V_{L1} - 0.1$	$2 \times V_{L1}$	$2 \times V_{L1}$	V	-
Tripler output voltage	V _{L4}	C1 to C4*1 = 0.47 μF		$3 \times V_{L1} - 0.15$	$3 \times V_{L1}$	$3 \times V_{L1}$	V	-
Reference voltage setup time*2	t _{VL1S}			5	-	-	ms	Figure 2.90
LCD output voltage variation range*3	t _{VLWT}	C1 to C4*1 = 0.47 μF		500	-	-	ms	

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between VL1 and GND

C3: A capacitor connected between VL2 and GND

C4: A capacitor connected between VL4 and GND

C1 = C2 = C3 = C4 = 0.47 μF ±30%

Note 2. This is the time required to wait from when the reference voltage is specified using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET[1:0] bits in the LCDM0 register to 01b) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

[1/4 Bias Method]

Table 2.71 Internal voltage boosting method LCD characteristics

Conditions: VCC = AVCC0 = 1.8 V to 5.5 V

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	Test conditions	
LCD output voltage variation range	V _{L1}	C1 to C5*1 = 0.47 μF	VLCD = 04h	0.90	1.0	1.08	V	-
			VLCD = 05h	0.95	1.05	1.13	V	-
			VLCD = 06h	1.00	1.10	1.18	V	-
			VLCD = 07h	1.05	1.15	1.23	V	-
			VLCD = 08h	1.10	1.20	1.28	V	-
			VLCD = 09h	1.15	1.25	1.33	V	-
			VLCD = 0Ah	1.20	1.30	1.38	V	-
			VLCD = 0Bh	1.25	1.35	1.43	V	-
		VLCD = 0Ch	1.30	1.40	1.48	V	-	
Doubler output voltage	V _{L2}	C1 to C5*1 = 0.47 μF	2V _{L1} - 0.08	2V _{L1}	2V _{L1}	V	-	
Tripler output voltage	V _{L3}	C1 to C5*1 = 0.47 μF	3V _{L1} - 0.12	3V _{L1}	3V _{L1}	V	-	
Quadruply output voltage	V _{L4} *4	C1 to C5*1 = 0.47 μF	4V _{L1} - 0.16	4V _{L1}	4V _{L1}	V	-	
Reference voltage setup time*2	t _{VL1S}		5	-	-	ms	Figure 2.90	
LCD output voltage variation range*3	t _{VLWT}	C1 to C5*1 = 0.47 μF	500	-	-	ms		

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between VL1 and GND

C3: A capacitor connected between VL2 and GND

C4: A capacitor connected between VL3 and GND

C5: A capacitor connected between VL4 and GND

C1 = C2 = C3 = C4 = C5 = 0.47 μF ± 30%

Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits in the LCDM0 register to 01b) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

Note 4. V_{L4} must be 5.5 V or lower.

2.12.3 Capacitor Split Method

[1/3 Bias Method]

Table 2.72 Internal voltage boosting method LCD characteristics

Conditions: VCC = AVCC0 = 2.2 V to 5.5 V

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	Test conditions
VL4 voltage*1	V_{L4}	C1 to C4 = 0.47 μF *2	-	VCC	-	V	-
VL2 voltage*1	V_{L2}	C1 to C4 = 0.47 μF *2	$2/3 \times V_{L4} - 0.07$	$2/3 \times V_{L4}$	$2/3 \times V_{L4} + 0.07$	V	-
VL1 voltage*1	V_{L1}	C1 to C4 = 0.47 μF *2	$1/3 \times V_{L4} - 0.08$	$1/3 \times V_{L4}$	$1/3 \times V_{L4} + 0.08$	V	-
Capacitor split wait time*1	t_{WAIT}		100	-	-	ms	Figure 2.90

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between VL1 and GND

C3: A capacitor connected between VL2 and GND

C4: A capacitor connected between VL4 and GND

C1 = C2 = C3 = C4 = 0.47 $\mu\text{F} \pm 30\%$

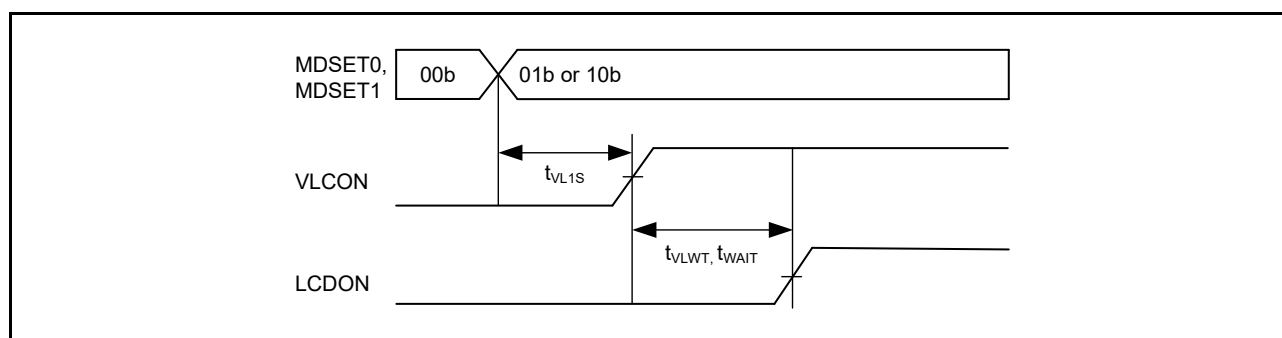


Figure 2.90 LCD reference voltage setup time, voltage boosting wait time, and capacitor split wait time

2.13 Comparator Characteristics

Table 2.73 ACMPHS characteristics

Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VSS = AVSS0 = 0 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input offset voltage	V _{IOCOMP}	-	±5	±40	mV	-
Input voltage range	V _{ICMP}	0	-	AVCC0	V	-
Internal reference voltage	-	1.36	1.44	1.50	V	-
Input signal cycle	t _{PCMP}	10	-	-	µs	-
Output delay time	t _d	-	50	100	ns	Input amplitude ± 100 mV
Stabilization wait time during input channel switching*1	t _{WAIT}	300	-	-	ns	Input amplitude ± 100 mV
Operation stabilization wait time*2	t _{CMP}	1	-	-	µs	3.3 V ≤ AVCC0 ≤ 5.5 V
		3	-	-	µs	2.7 V ≤ AVCC0 < 3.3 V

Note 1. Period of time from when the comparator input channel is switched until the comparator is switched to output.

Note 2. Period of time from when the comparator operation is enabled (CMPCTL.HCMPON = 1) until the comparator satisfies the DC/AC characteristics.

Table 2.74 ACMPPLP characteristics

Conditions: VCC = AVCC0 = 1.8 to 5.5 V, VSS = AVSS0 = 0 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
Reference voltage range	VREF	0	-	VCC -1.4	V	-	
Input voltage range	V _I	0	-	VCC	V	-	
Internal reference voltage	-	1.36	1.44	1.50	V	-	
Output delay	High-speed mode	T _d	-	-	1.2	µs	VCC = 3.0 Slew rate of input signal > 50 mV/µs
	Low-speed mode		-	-	5	µs	
	Window mode		-	-	2	µs	
Offset voltage	High-speed mode	-	-	-	50	mV	-
	Low-speed mode	-	-	-	40	mV	-
	Window mode	-	-	-	60	mV	-
Internal reference voltage for window mode	VRFH	-	0.76 × VCC	-	V	-	
	VRFL	-	0.24 × VCC	-	V	-	
Operation stabilization wait time	T _{cmp}	100	-	-	µs	-	

2.14 OPAMP Characteristics

Table 2.75 OPAMP characteristicsConditions: $1.8\text{ V} \leq AVCC0 = VCC \leq 5.5\text{ V}$, $VSS = AVSS0 = 0\text{ V}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Common mode input range	Vicm1	Low power mode	0.2	-	$AVCC0 - 0.5$	V	
	Vicm2	High-speed mode	0.3	-	$AVCC0 - 0.6$	V	
Output voltage range	Vo1	Low power mode	0.1	-	$AVCC0 - 0.1$	V	
	Vo2	High-speed mode	0.1	-	$AVCC0 - 0.1$	V	
Input offset voltage	Vioff	3σ	-10	-	10	mV	
Open gain	Av		60	120	-	dB	
Gain-bandwidth (GB) product	GBW1	Low power mode	-	0.04	-	MHz	
	GBW2	High-speed mode	-	1.7	-	MHz	
Phase margin	PM	CL = 20 pF	50	-	-	deg	
Gain margin	GM	CL = 20 pF	10	-	-	dB	
Equivalent input noise	Vnoise1	f = 1 kHz	Low power mode	-	230	-	$\text{nV}/\sqrt{\text{Hz}}$
	Vnoise2	f = 10 kHz		-	200	-	$\text{nV}/\sqrt{\text{Hz}}$
	Vnoise3	f = 1 kHz	High-speed mode	-	90	-	$\text{nV}/\sqrt{\text{Hz}}$
	Vnoise4	f = 2 kHz		-	70	-	$\text{nV}/\sqrt{\text{Hz}}$
Power supply reduction ratio	PSRR		-	90	-	dB	
Common mode signal reduction ratio	CMRR		-	90	-	dB	
Stabilization wait time	Tstd1	CL = 20 pF Only operational amplifier is activated *1	Low power mode	650	-	-	μs
	Tstd2		High-speed mode	13	-	-	μs
	Tstd3	CL = 20 pF Operational amplifier and reference current circuit are activated simultaneously	Low power mode	650	-	-	μs
	Tstd4		High-speed mode	13	-	-	μs
Settling time	Tset1	CL = 20 pF	Low power mode	-	-	750	μs
	Tset2		High-speed mode	-	-	13	μs
Slew rate	Tslew1	CL = 20 pF	Low power mode	-	0.02	-	$\text{V}/\mu\text{s}$
	Tslew2		High-speed mode	-	1.1	-	$\text{V}/\mu\text{s}$
Load current	Iload1	Low power mode	-100	-	100	μA	
	Iload2	High-speed mode	-100	-	100	μA	
Load capacitance	CL		-	-	20	pF	

Note 1. When the operational amplifier reference current circuit is activated in advance.

2.15 Flash Memory Characteristics

2.15.1 Code Flash Memory Characteristics

Table 2.76 Code flash characteristics (1)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Reprogramming/erasure cycle*1	N _{PEC}	1000	-	-	Times	-
Data hold time	After 1000 times of N _{PEC}	t _{DRP}	20*2, *3	-	Year	T _a = +85°C

Note 1. The reprogram/erase cycle is the number of erasure for each block. When the reprogram/erase cycle is n times (n = 1,000), erasing can be performed n times for each block. For instance, when 8-byte programming is performed 256 times for different addresses in 2-KB blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited).

Note 2. Characteristic when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. This result is obtained from reliability testing.

Table 2.77 Code flash characteristics (2)

High-speed operating mode

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter	Symbol	FCLK = 1 MHz			FCLK = 32 MHz			Unit	
		Min	Typ	Max	Min	Typ	Max		
Programming time	8-byte	t _{P8}	-	116	998	-	54	506	μs
Erasure time	2-KB	t _{E2K}	-	9.03	287	-	5.67	222	ms
Blank check time	8-byte	t _{BC8}	-	-	56.8	-	-	16.6	μs
	2-KB	t _{BC2K}	-	-	1899	-	-	140	μs
Erase suspended time		t _{SED}	-	-	22.5	-	-	10.7	μs
Startup area switching setting time		t _{SAS}	-	21.7	585	-	12.1	447	ms
Access window time		t _{AWS}	-	21.7	585	-	12.1	447	ms
OCD/serial programmer ID setting time		t _{OSIS}	-	21.7	585	-	12.1	447	ms
Flash memory mode transition wait time 1		t _{DIS}	2	-	-	2	-	-	μs
Flash memory mode transition wait time 2		t _{MS}	5	-	-	5	-	-	μs

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be ±3.5%. Confirm the frequency accuracy of the clock source.

Table 2.78 Code flash characteristics (3)

Middle-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V, Ta = -40 to +85°C

Parameter	Symbol	FCLK = 1 MHz			FCLK = 8 MHz			Unit	
		Min	Typ	Max	Min	Typ	Max		
Programming time	8-byte	t _{P8}	-	157	1411	-	101	966	μs
Erase time	2-KB	t _{E2K}	-	9.10	289	-	6.10	228	ms
Blank check time	8-byte	t _{BC8}	-	-	87.7	-	-	52.5	μs
	2-KB	t _{BC2K}	-	-	1930	-	-	414	μs
Erase suspended time		t _{SED}	-	-	32.7	-	-	21.6	μs
Startup area switching setting time		t _{SAS}	-	22.5	592	-	14.0	464	ms
Access window time		t _{AWS}	-	22.5	592	-	14.0	464	ms
OCD/serial programmer ID setting time		t _{OSIS}	-	22.5	592	-	14.0	464	ms
Flash memory mode transition wait time 1		t _{DIS}	2	-	-	2	-	-	μs
Flash memory mode transition wait time 2		t _{MS}	720	-	-	720	-	-	ns

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be ±3.5%. Confirm the frequency accuracy of the clock source.

2.15.2 Data Flash Memory Characteristics

Table 2.79 Data flash characteristics (1)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
Reprogramming/erase cycle*1	N _{DPEC}	100,000	1,000,000	-	Times	-	
Data hold time	After 10000 times of N _{DPEC}	t _{DDRP}	20*2, *3	-	-	Year	Ta = +85°C
	After 100000 times of N _{DPEC}		5*2, *3	-	-	Year	
	After 1000000 times of N _{DPEC}		-	1*2, *3	-	-	Year

Note 1. The reprogram/erase cycle is the number of erasure for each block. When the reprogram/erase cycle is n times (n = 100,000), erasing can be performed n times for each block. For instance, when 1-byte programming is performed 1,000 times for different addresses in 1-byte blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited).

Note 2. Characteristics when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. These results are obtained from reliability testing.

Table 2.80 Data flash characteristics (2)

High-speed operating mode

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter	Symbol	FCLK = 4 MHz			FCLK = 32 MHz			Unit	
		Min	Typ	Max	Min	Typ	Max		
Programming time	1-byte	t _{DP1}	-	52.4	463	-	42.1	387	μs
Erase time	1-KB	t _{DE1K}	-	8.98	286	-	6.42	237	ms
Blank check time	1-byte	t _{DBC1}	-	-	24.3	-	-	16.6	μs
	1-KB	t _{DBC1K}	-	-	1872	-	-	512	μs
Suspended time during erasing		t _{DSED}	-	-	13.0	-	-	10.7	μs
Data flash STOP recovery time		t _{DSTOP}	5	-	-	5	-	-	μs

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note 2. The lower-limit frequency of FCLK is 1 MHz during programming or erasing the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 3. The frequency accuracy of FCLK must be ±3.5%. Confirm the frequency accuracy of the clock source.

Table 2.81 Data flash characteristics (3)

Middle-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V, Ta = -40 to +85°C

Parameter	Symbol	FCLK = 4 MHz			FCLK = 8 MHz			Unit	
		Min	Typ	Max	Min	Typ	Max		
Programming time	1-byte	t _{DP1}	-	94.7	886	-	89.3	849	μs
Erase time	1-KB	t _{DE1K}	-	9.59	299	-	8.29	273	ms
Blank check time	1-byte	t _{DBC1}	-	-	56.2	-	-	52.5	μs
	1-KB	t _{DBC1K}	-	-	2.17	-	-	1.51	ms
Suspended time during erasing		t _{DSER}	-	-	23.0	-	-	21.7	μs
Data flash STOP recovery time		t _{DSTOP}	720	-	-	720	-	-	ns

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note 2. The lower-limit frequency of FCLK is 1 MHz during programming or erasing the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 3. The frequency accuracy of FCLK must be ±3.5%. Confirm the frequency accuracy of the clock source.

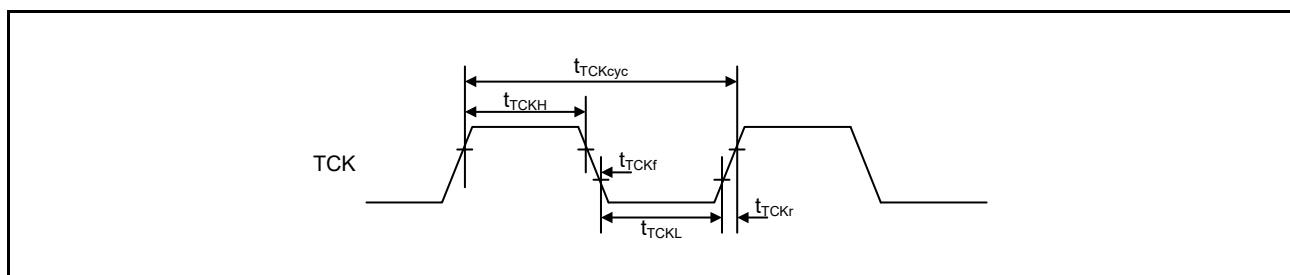
2.16 Boundary Scan

Table 2.82 Boundary scan

Conditions: VCC = AVCC0 = 2.4 to 5.5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
TCK clock cycle time	t _{TCKcyc}	100	-	-	ns	Figure 2.91
TCK clock high pulse width	t _{TCKH}	45	-	-	ns	
TCK clock low pulse width	t _{TCKL}	45	-	-	ns	
TCK clock rise time	t _{TCKr}	-	-	5	ns	
TCK clock fall time	t _{TCKf}	-	-	5	ns	
TMS setup time	t _{TMSS}	20	-	-	ns	Figure 2.92
TMS hold time	t _{TMSH}	20	-	-	ns	
TDI setup time	t _{TDIS}	20	-	-	ns	
TDI hold time	t _{TDIH}	20	-	-	ns	
TDO data delay	t _{TDOD}	-	-	70	ns	Figure 2.93
Boundary Scan circuit start up time*1	t _{BSSTUP}	t _{RESWP}	-	-	-	

Note 1. Boundary scan does not function until Power-On-Reset becomes negative.

**Figure 2.91 Boundary scan TCK timing**

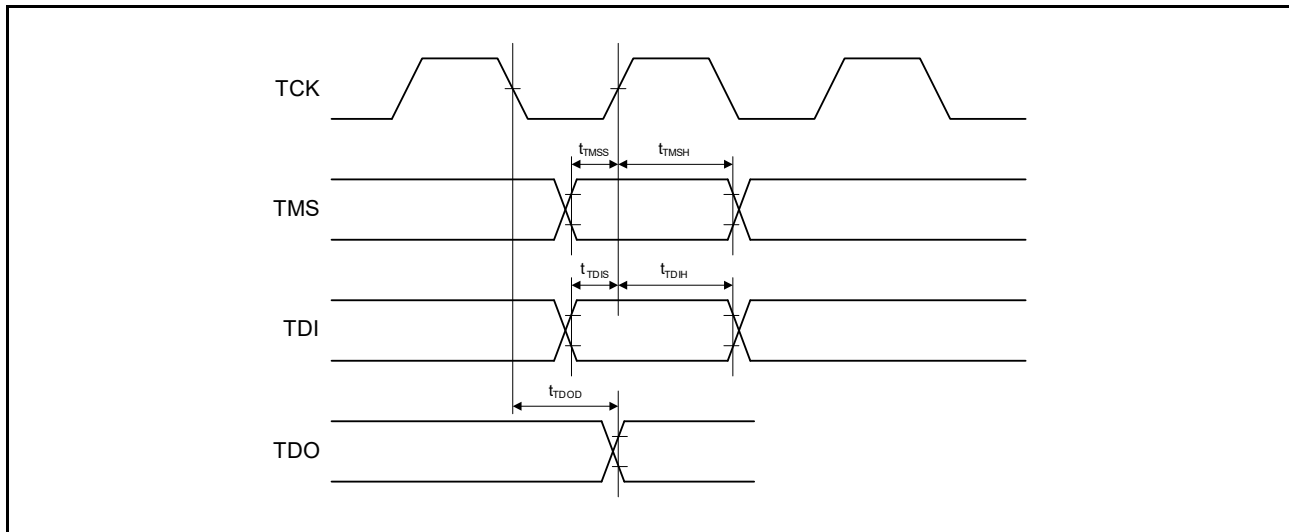


Figure 2.92 Boundary scan input/output timing

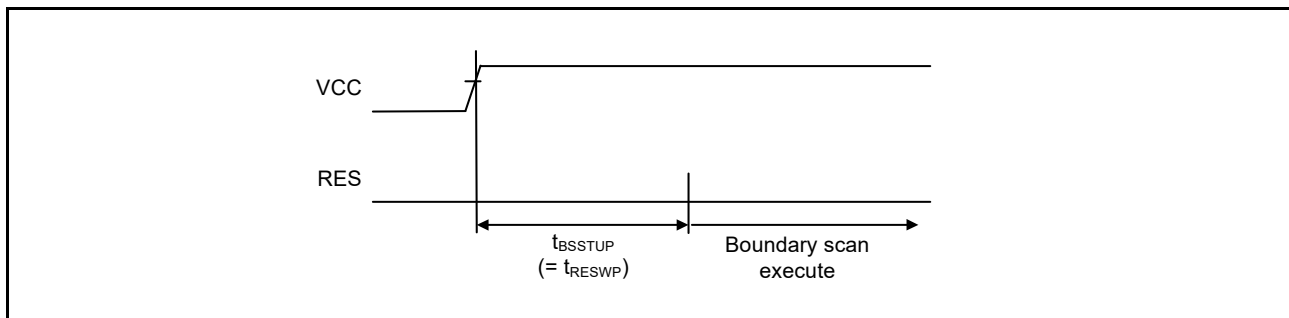


Figure 2.93 Boundary scan circuit start up timing

2.17 Joint Test Action Group (JTAG)

Table 2.83 JTAG (Debug) characteristics (1)

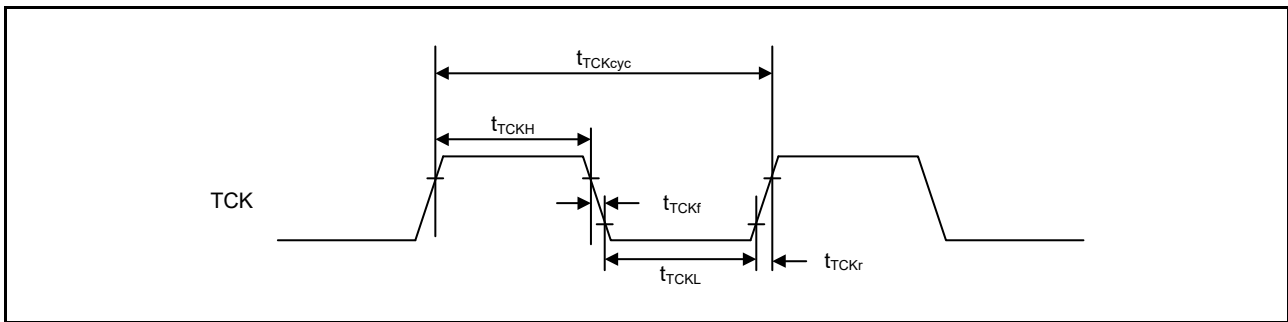
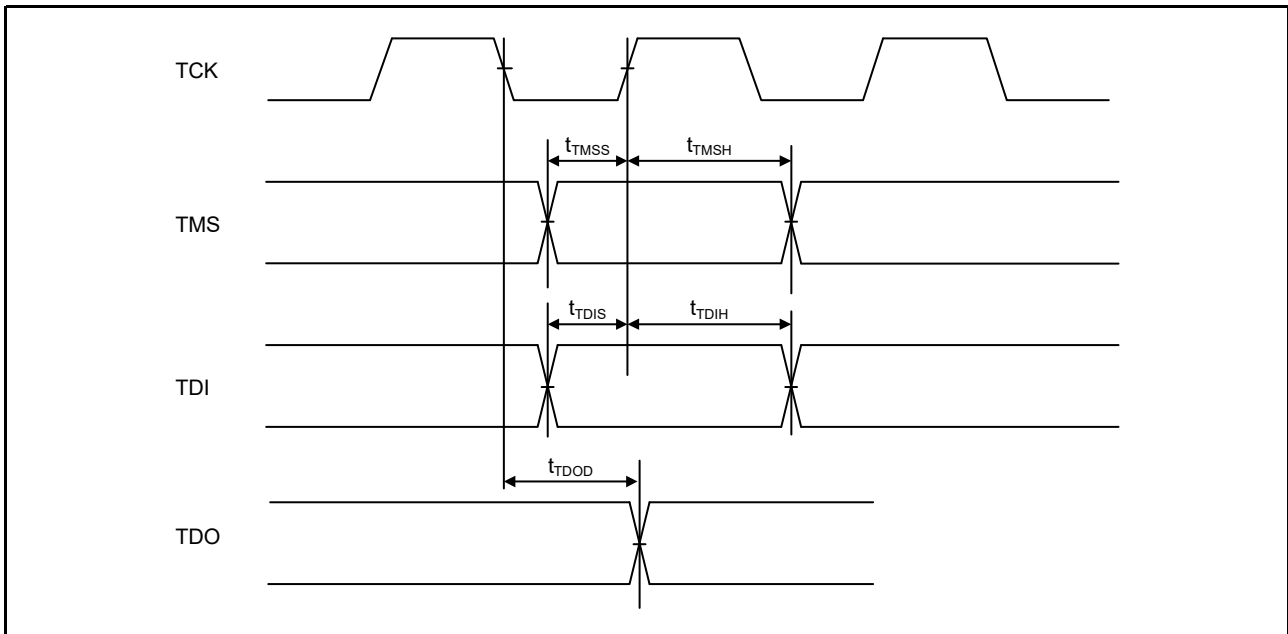
Conditions: VCC = AVCC0 = 2.4 to 5.5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
TCK clock cycle time	t_{TCKcyc}	80	-	-	ns	Figure 2.94
TCK clock high pulse width	t_{TCKH}	35	-	-	ns	
TCK clock low pulse width	t_{TCKL}	35	-	-	ns	
TCK clock rise time	t_{TCKr}	-	-	5	ns	
TCK clock fall time	t_{TCKf}	-	-	5	ns	
TMS setup time	t_{TMSS}	16	-	-	ns	Figure 2.95
TMS hold time	t_{TMSh}	16	-	-	ns	
TDI setup time	t_{TDIS}	16	-	-	ns	
TDI hold time	t_{TDIH}	16	-	-	ns	
TDO data delay time	t_{TDOD}	-	-	70	ns	

Table 2.84 JTAG (Debug) characteristics (2)

Conditions: VCC = AVCC0 = 1.6 to 2.4 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
TCK clock cycle time	t_{TCKcyc}	250	-	-	ns	Figure 2.94
TCK clock high pulse width	t_{TCKH}	120	-	-	ns	
TCK clock low pulse width	t_{TCKL}	120	-	-	ns	
TCK clock rise time	t_{TCKr}	-	-	5	ns	
TCK clock fall time	t_{TCKf}	-	-	5	ns	
TMS setup time	t_{TMSS}	50	-	-	ns	Figure 2.95
TMS hold time	t_{TMSh}	50	-	-	ns	
TDI setup time	t_{TDis}	50	-	-	ns	
TDI hold time	t_{TDIH}	50	-	-	ns	
TDO data delay time	t_{TDOD}	-	-	150	ns	

**Figure 2.94 JTAG TCK timing****Figure 2.95 JTAG input/output timing**

2.17.1 Serial Wire Debug (SWD)

Table 2.85 SWD characteristics (1)

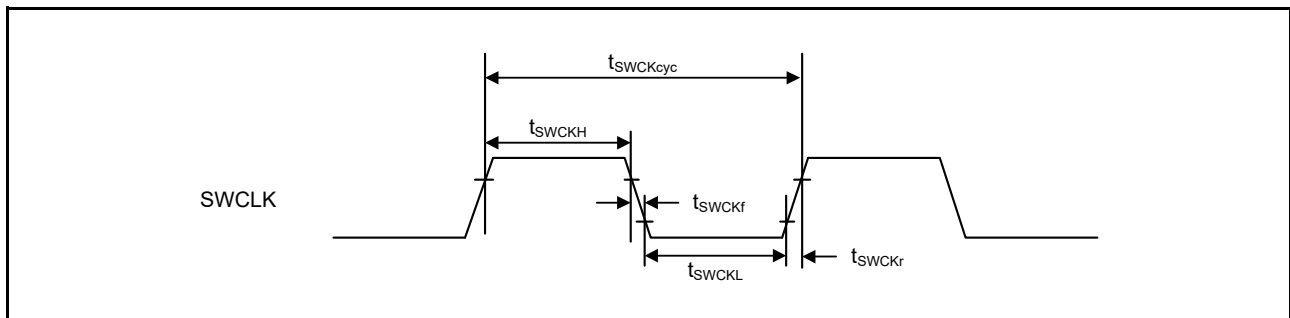
Conditions: VCC = AVCC0 = 2.4 to 5.5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
SWCLK clock cycle time	t_{SWCKcyc}	80	-	-	ns	Figure 2.96
SWCLK clock high pulse width	t_{SWCKH}	35	-	-	ns	
SWCLK clock low pulse width	t_{SWCKL}	35	-	-	ns	
SWCLK clock rise time	t_{SWCKr}	-	-	5	ns	
SWCLK clock fall time	t_{SWCKf}	-	-	5	ns	
SWDIO setup time	t_{SWDS}	16	-	-	ns	Figure 2.97
SWDIO hold time	t_{SWDH}	16	-	-	ns	
SWDIO data delay time	t_{SWDD}	2	-	70	ns	

Table 2.86 SWD characteristics (2)

Conditions: VCC = AVCC0 = 1.6 to 2.4 V

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
SWCLK clock cycle time	t_{SWCKcyc}	250	-	-	ns	Figure 2.96
SWCLK clock high pulse width	t_{SWCKH}	120	-	-	ns	
SWCLK clock low pulse width	t_{SWCKL}	120	-	-	ns	
SWCLK clock rise time	t_{SWCKr}	-	-	5	ns	
SWCLK clock fall time	t_{SWCKf}	-	-	5	ns	
SWDIO setup time	t_{SWDS}	50	-	-	ns	Figure 2.97
SWDIO hold time	t_{SWDH}	50	-	-	ns	
SWDIO data delay time	t_{SWDD}	2	-	150	ns	

**Figure 2.96 SWD SWCLK timing**

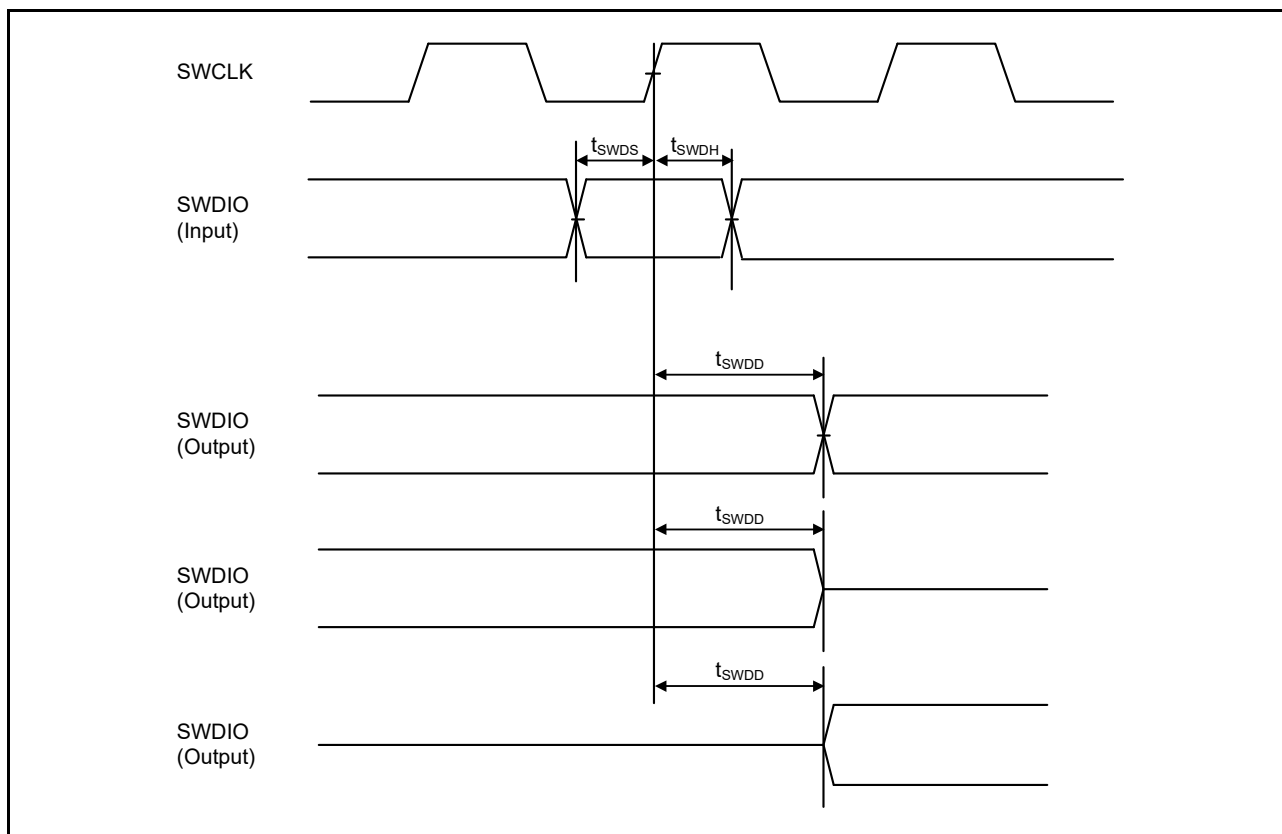


Figure 2.97 SWD input/output timing

Appendix 1. Package Dimensions

Information on the latest version of the package dimensions or mountings is displayed in “Packages” on the Renesas Electronics Corporation website.

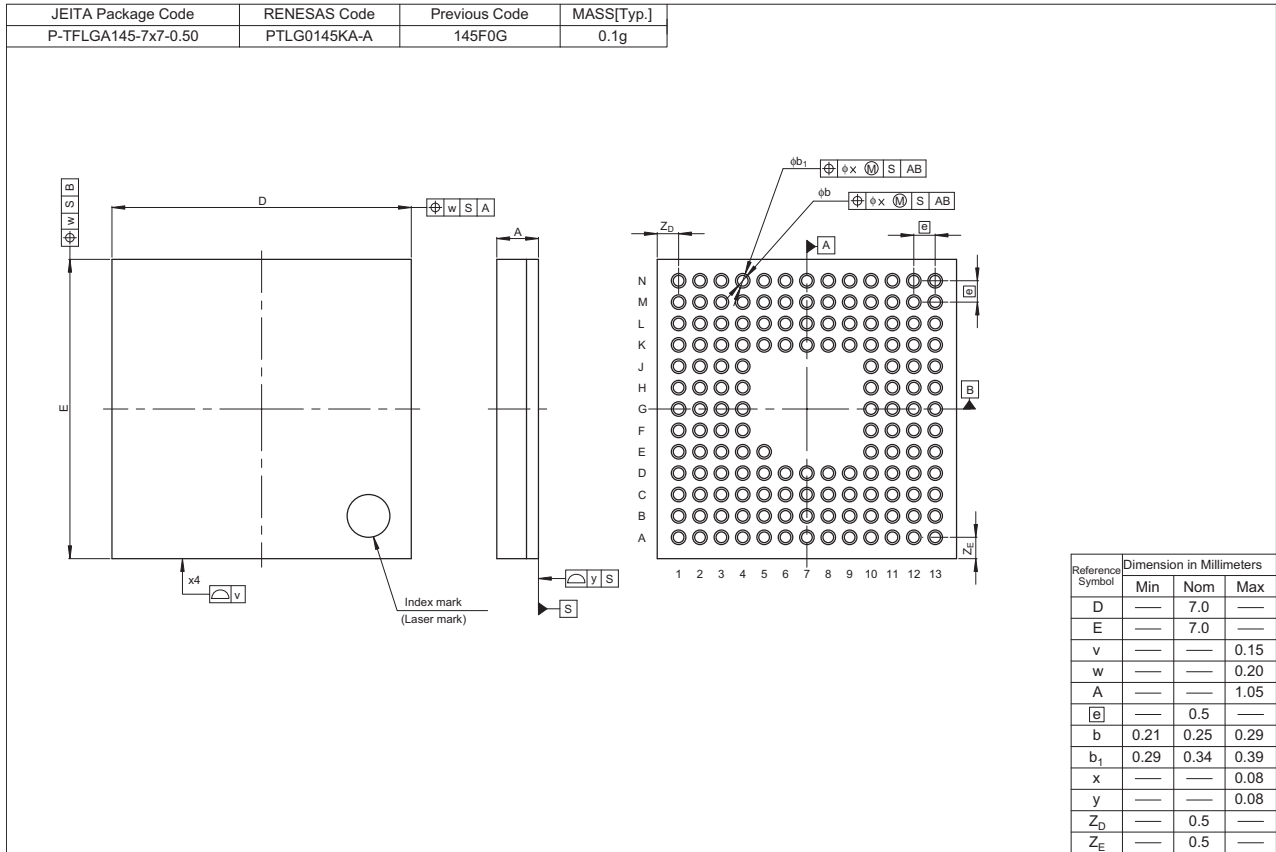
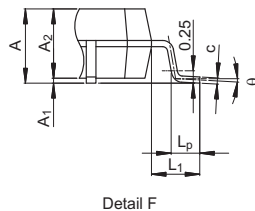
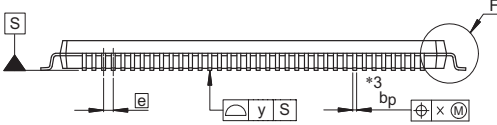
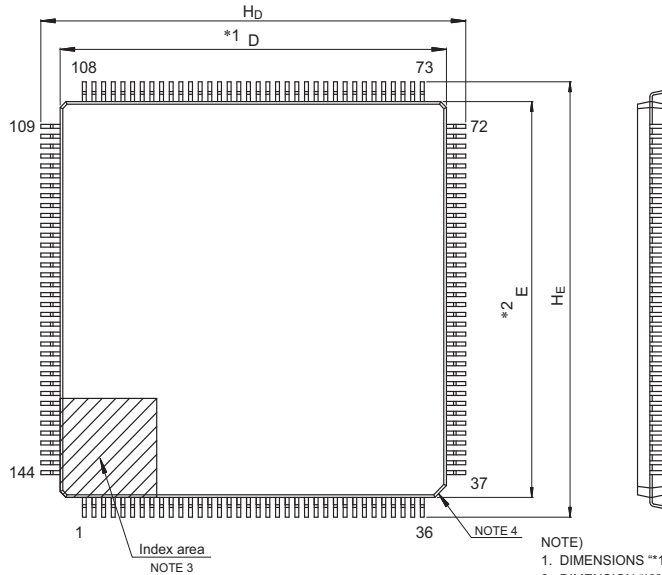


Figure 1.1 LGA 145-pin

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP144-20x20-0.50	PLQP0144KA-B	—	1.2

Unit: mm



- NOTE)
1. DIMENSIONS **1* AND **2* DO NOT INCLUDE MOLD FLASH.
 2. DIMENSION **3* DOES NOT INCLUDE TRIM OFFSET.
 3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
 4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

Reference Symbol	Dimensions in millimeters		
	Min	Nom	Max
D	19.9	20.0	20.1
E	19.9	20.0	20.1
A ₂	—	1.4	—
H _D	21.8	22.0	22.2
H _E	21.8	22.0	22.2
A	—	—	1.7
A ₁	0.05	—	0.15
b _p	0.17	0.20	0.27
c	0.09	—	0.20
θ	0°	3.5°	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.10
L _p	0.45	0.6	0.75
L ₁	—	1.0	—

Figure 1.2 LQFP 144-pin

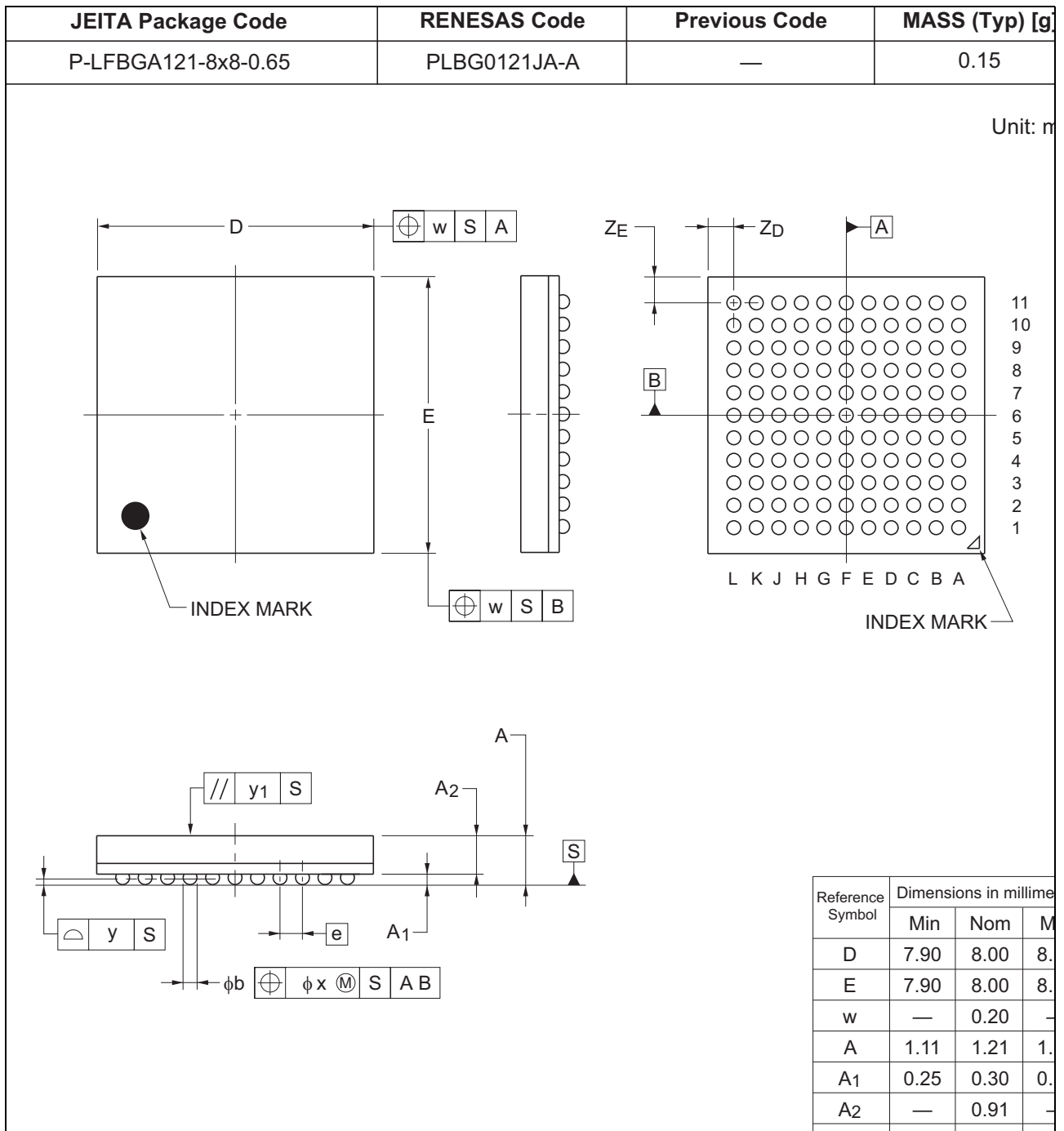


Figure 1.3 BGA 121-pin

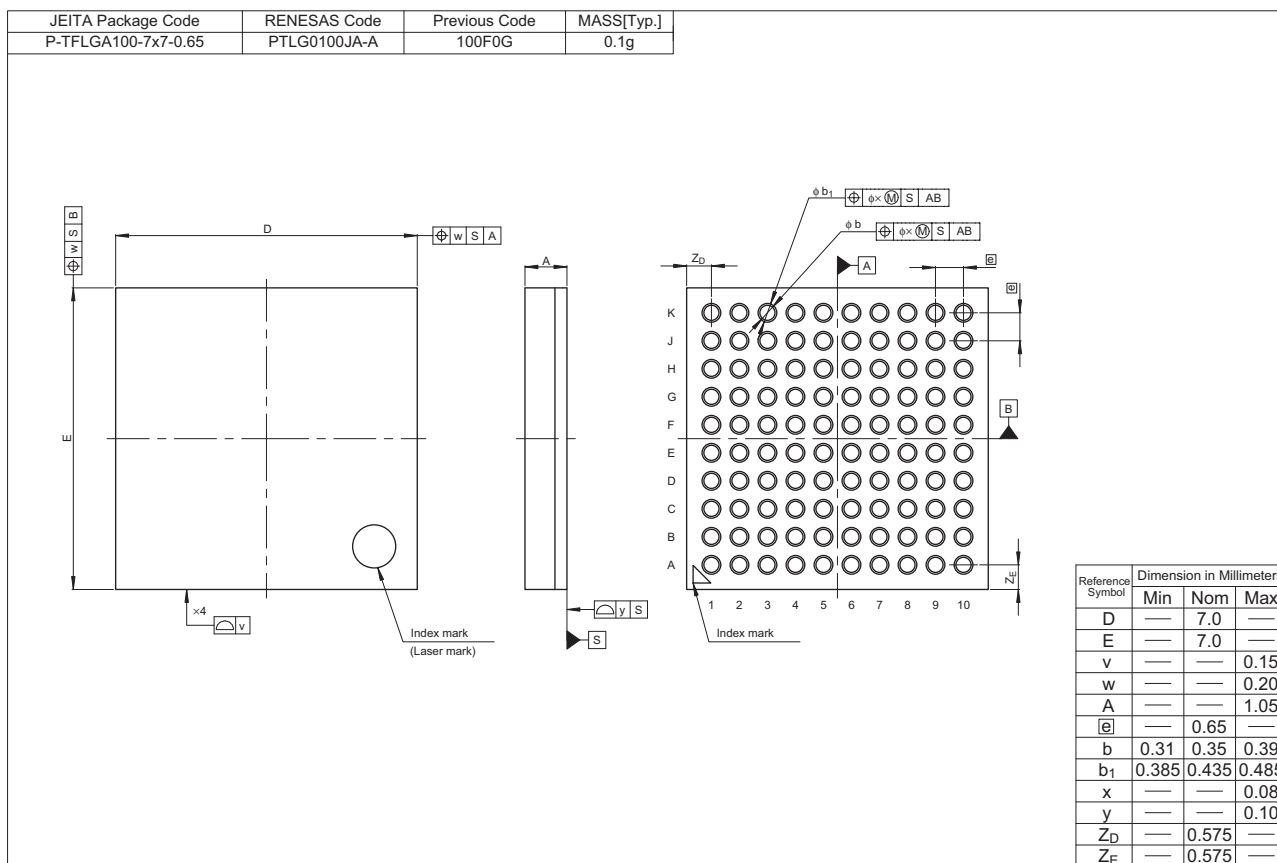
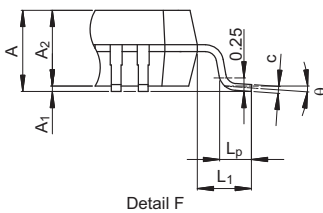
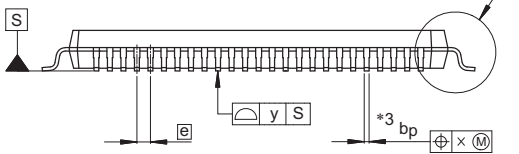
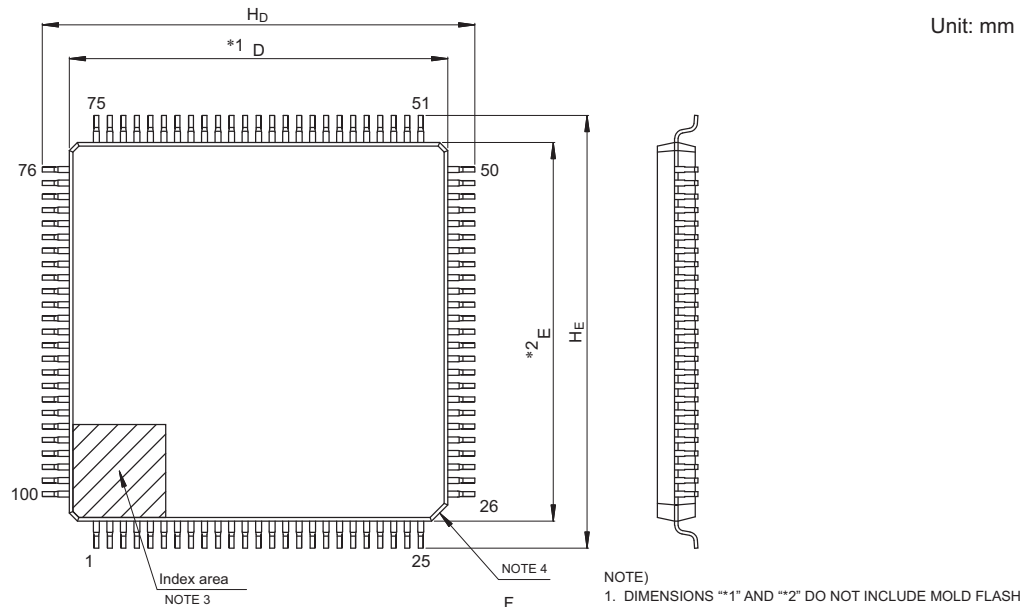


Figure 1.4 LGA 100-pin

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP100-14x14-0.50	PLQP0100KB-B	—	0.6



- NOTE)
1. DIMENSIONS **1* AND **2* DO NOT INCLUDE MOLD FLASH.
 2. DIMENSION **3* DOES NOT INCLUDE TRIM OFFSET.
 3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
 4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

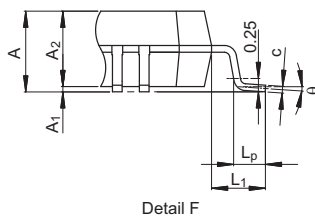
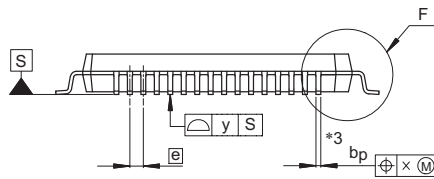
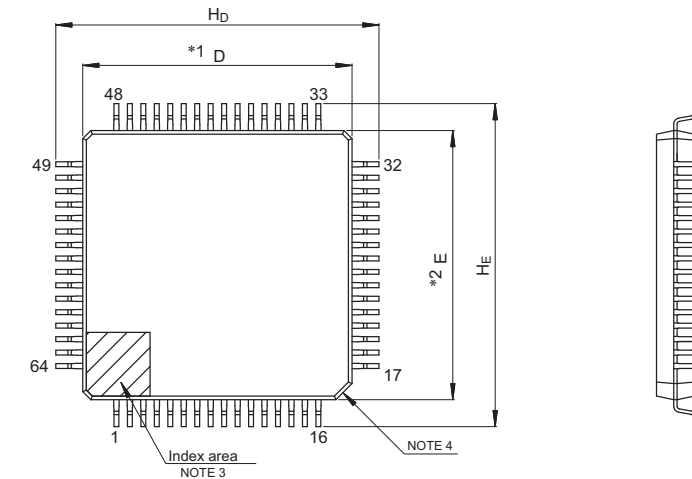
Reference Symbol	Dimensions in millimeters		
	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A ₂	—	1.4	—
H _D	15.8	16.0	16.2
H _E	15.8	16.0	16.2
A	—	—	1.7
A ₁	0.05	—	0.15
b _p	0.15	0.20	0.27
c	0.09	—	0.20
θ	0°	3.5°	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
L _p	0.45	0.6	0.75
L ₁	—	1.0	—

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Figure 1.5 LQFP 100-pin

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP64-10x10-0.50	PLQP0064KB-C	—	0.3

Unit: mm



NOTE)

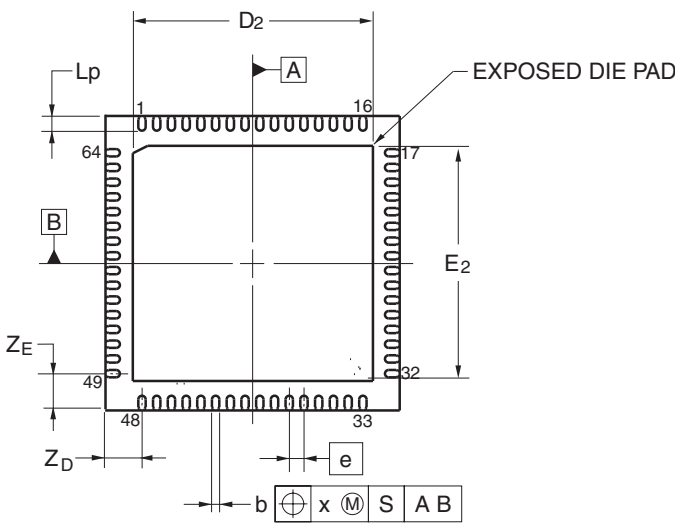
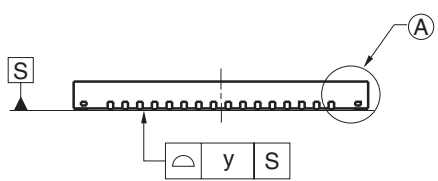
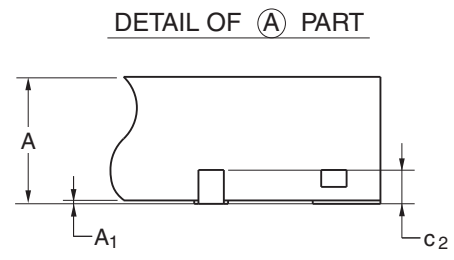
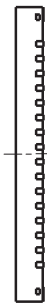
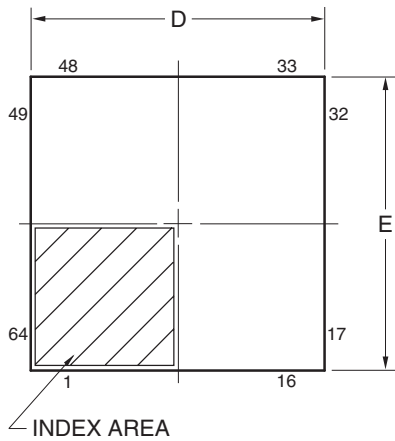
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.
3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

Reference Symbol	Dimensions in millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A ₂	—	1.4	—
H _D	11.8	12.0	12.2
H _E	11.8	12.0	12.2
A	—	—	1.7
A ₁	0.05	—	0.15
b _p	0.15	0.20	0.27
c	0.09	—	0.20
θ	0°	3.5°	8°
[e]	—	0.5	—
x	—	—	0.08
y	—	—	0.08
L _p	0.45	0.6	0.75
L ₁	—	1.0	—

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Figure 1.6 LQFP 64-pin

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN64-8x8-0.40	PWQN0064LA-A	P64K8-40-9B5-3	0.16



Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	7.95	8.00	8.05
E	7.95	8.00	8.05
A	—	—	0.80
A ₁	0.00	—	—
b	0.17	0.20	0.23
e	—	0.40	—
L _p	0.30	0.40	0.50
x	—	—	0.05
y	—	—	0.05
Z _D	—	1.00	—
Z _E	—	1.00	—
c ₂	0.15	0.20	0.25
D ₂	—	6.50	—
E ₂	—	6.50	—

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Figure 1.7 QFN 64-pin

Rev.	Date	Summary
1.00	Feb 23, 2016	1st release
1.30	Feb 7, 2018	2nd release
1.40	Oct 29, 2018	3rd release

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Synergy Hardware	renesassynergy.com/hardware
Microcontrollers	renesassynergy.com/mcus
MCU glossary	renesassynergy.com/mcuglossary
Parametric search	renesassynergy.com/parametric
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S3A7 Microcontroller Group Datasheet

Publication Date: Rev.1.40 Oct 29, 2018

Published by: Renesas Electronics Corporation

General Precautions

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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(Rev.4.0-1 November 2017)



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